ISSN 0022-0248

JOURNAL OF CRYSTAL GROWTH

VOLUME 140

MASTER INDEX

Volumes 131–140

EDITORS:

M. SCHIEBER (Principal Editor), Hebrew University

R.S. FEIGELSON, Stanford University

D.T.J. HURLE, University of Bristol

R. KERN, Université Aix–Marseille

T. NISHINAGA, University of Tokyo

G.B. STRINGFELLOW, University of Utah

Last Issue of this Volume

CO-FOUNDERS: N. CABRERA, B. CHALMERS, F.C. FRANK
ADVISOR: R.A. LAUDISE

North-Holland

JCRGAE 131–140 (MI) 467–536 (1994)

EDITORIAL BOARD

M. SCHIEBER (Principal Editor)
Dept. Materials Science,
School Appl. Sci. & Technol.
Hebrew University, Jerusalem 91904, Israel
Telefax: +972-2-666 804

R. KERN
CRMC^2, CNRS, Campus Luminy, Case 913
F-13288 Marseille Cedex 9, France
Telefax: +33-91-418 916

R.S. FEIGELSON
Ctr. Materials Res., 105 McCullough Bldg.
Stanford Univ., Stanford, CA 94305-4045, USA
Telefax: +1-415-723 3044

T. NISHINAGA
Dept. Electronic Engineering, University of Tokyo
7-3-1, Hongo, Bunkyo-ku, Tokyo 113, Japan
Telefax: +81-3-5684-3974

D.T.J. HURLE
H.H. Wills Physics Laboratory
Univ. Bristol, Tyndall Avenue
Bristol BS8 1TL, UK

G.B. STRINGFELLOW
Dept. Materials Science, 304 EMRO
University of Utah
Salt Lake City, UT 84112, USA
Telefax: +1-801-581 4816

ASSOCIATE EDITORS

Y. BANDO (*Superconductivity*)
Lab. of Solid State Chemistry
Inst. for Chemical Research, Kyoto Univ.
Uji, Kyoto-fu 611, Japan
Telefax: +81-774-33 5089

A. BARONNET (*Industrial, Biological and Molecular Crystals*)
CRMC^2, CNRS, Campus Luminy, Case 913
F-13288 Marseille Cedex 9, France
Telefax: +33-91-418 916

K.W. BENZ (*Microgravity, Electronic Materials*)
Kristallographisches Inst., Universität
Hebelstr. 25, D-79104 Freiburg, Germany
Telefax: +49-761-203 4369

G.M. BLOM (*Liquid Phase Epitaxy*)
Philips Laboratories, 345 Scarborough Road
Briarcliff Manor, NY 10510, USA
Telefax: +1-914-945 6375

A.A. CHERNOV (*Kinetics of Crystallization*)
Inst. Crystallography, Acad. of Sciences
Leninskii Prosp., Moscow 117 333, Russian Fed.
Telefax: +7-095-135 1011

J. CHIKAWA (*Perfection of Crystals*)
Faculty of Science, Himeji Inst. Technology
Harima Garden City, Kamigori-chyo
Hyogo 678-12, Japan

A.Y. CHO (*Molecular Beam Epitaxy*)
Room 1C-323, AT&T Bell Laboratories
Murray Hill, NJ 07974-2070, USA
Telefax: +1-908-582 2043

B. COCKAYNE (*Review Articles, IOCG News*)
DRA Malvern, St. Andrews Road,
Great Malvern, Worcs. WR14 3PS, UK
Telefax: +44-684-894 540

S.R. CORIELL (*Theory*)
A153 Materials
Natl. Inst. of Standards & Technol.
Gaithersburgh, MD 20899-0001, USA

D. ELWELL (*Priority Communications, Superconductivity*)
Hughes Aircraft Company
P.O. Box H, M/S A2408, 500 Superior Avenue
New Port Beach, CA 92658-8908, USA
Telefax: +1-714-759 2868

M.E. GLICKSMAN (*Solidification*)
School of Engineering, Mater. Eng. Dept.
Rensselaer Polytechnic Inst.
Troy, NY 12180-3590, USA
Telefax: +1-518-276 8854

M.A.G. HALLIWELL (*X-ray Diffraction*)
Philips Analytical X-ray, Lelyweg 1
7602 EA Almelo, Netherlands

K.A. JACKSON (*Theory*)
Arizona Materials Laboratory
4715 E Fort Lowell Road, Tucson, AZ 85712, USA

E. KALDIS (*Chemical Transport*)
Institut für Festkörperphysik, ETH
Hönggerberg, CH-8093 Zürich, Switzerland
Telefax: +41-1-371 5989

S. KIMURA (*Oxide Crystals*)
National Inst. Res. Inorg. Materials
1-1 Namiki, Tsukuba, Ibaraki 305, Japan
Telefax: +81-298-52 7449

T.F. KUECH (*Thin Films and Electronic and Optical Devices*)
Dept. Chemical Engineering
Univ. Wisconsin-Madison
Madison, WI 53706, USA
Telefax: +1-608-262 5434

H. KUKIMOTO (*Thin Films, Epitaxy*)
Imaging Science & Eng. Lab.
Tokyo Inst. of Technology
4259 Nagatsuda, Midori-ku
Yokohama 227, Japan
Telefax: +81-45-921-1492

A. McPHERSON (*Protein Growth*)
Dept. Biochemistry, Univ. of California
Riverside, CA 92521, USA
Telefax: +1-909-787 3790

J.B. MULLIN (*Semiconductors*)
EMC, "The Hoo", Brockhill Road
West Malvern, Worcs. WR14 4DL, UK
Telefax: +44-684-575 591

K. PLOOG (*Molecular Beam Epitaxy*)
Paul-Drude-Inst. für Festkörperelektronik
Hausvogteiplatz 5–7, D-10117 Berlin, Germany
Telefax: +49-30-203 77201

F. ROSENBERGER (*Vapor Growth, Fluid Dynamics*)
Center for Microgravity and Materials Research
Univ. Alabama, Huntsville, AL 35899, USA
Telefax: +1-205-895 6791

R.W. ROUSSEAU (*Solution Growth, Industrial Crystallization*)
School of Chemical Engineering
Georgia Institute of Technology
Atlanta, GA 30332-0100, USA
Telefax: +1-404-894 2866

K. SATO (*Biocrystallization and Organic Crystals*)
Fac. Applied Biological Science
Hiroshima Univ.
Higashi-Hiroshima 724, Japan
Telefax: +81-824-227 062

L.F. SCHNEEMEYER (*Superconductivity, Oxides, Novel Materials*)
Room 1A-363, AT&T Bell Laboratories
Murray Hill, NJ 07974-2070, USA
Telefax: +1-908-582 2521

D.W. SHAW (*Semiconductors, Epitaxy, Devices*)
Texas Instruments Inc., P.O. Box 655936, MS 147
Dallas, TX 75265, USA
Telefax: +1-214-995 5539

I. SUNAGAWA (*Morphology and Minerals*)
3-54-2 Kashiwa-cho, Tachikawa-shi
Tokyo 190, Japan
Telefax: +81-425-35 3637

T. SUREK (*Materials for Energy Conversion and Photovoltaics*)
National Renewable Energy Lab.
1617 Cole Blvd., Golden, CO 80401, USA
Telefax: +1-303-231 1030

G. VAN TENDELOO (*Electron Microscopy, Fullerenes, Superconductivity*)
University of Antwerp, RUCA
Groenenborgerlaan 171
B-2020 Antwerp, Belgium
Telefax: +32-3-2180 217

A.F. WITT (*Semiconductor Crystals*)
Dept. of Metallurgy & Materials Science
Massachusetts Institute of Technology
Cambridge, MA 02139, USA
Telefax: +1-617-253 5827

Technical Editors: F.Y. Verploegh Chassé and J. Hanraads, Elsevier/North-Holland, P.O. Box 103, 1000 AC Amsterdam, Netherlands,
Telefax: +31-20-5862 775

Elsevier Science B.V.: All rights reserved. No part of this publication may be reproduced, stored in a retrieval system or transmitted in any form or by any means, electronic, mechanical, photocopying, recording or otherwise, without the written permission of the publisher, Elsevier Science B.V., P.O. Box 103, 1000 AC Amsterdam, Netherlands.

Special regulations for authors – Upon acceptance of an article by the journal, the author(s) will be asked to transfer copyright of the article to the publisher. This transfer will ensure the widest possible dissemination of information.

Special regulations for readers in the USA – This journal has been registered with the Copyright Clearance Center, Inc. Consent is given for copying of articles for personal or internal use, or for the personal use of specific clients. This consent is given on the condition that the copier pays through the Center the per-copy fee stated in the code on the first page of each article for copying beyond that permitted by Sections 107 or 108 of the US Copyright Law. The appropriate fee should be forwarded with a copy of the first page of the article to the Copyright Clearance Center, Inc., 27 Congress Street, Salem, MA 01970, USA. If no code appears in an article, the author has not given broad consent to copy and permission to copy must be obtained directly from the author. The fee indicated on the first page of an article in this issue will apply retroactively to all articles published in the journal, regardless of the year of publication. This consent does not extend to other kinds of copying, such as for general distribution, resale, advertising and promotion purposes, or for creating new collective works. Special written permission must be obtained from the publisher for such copying.

No responsibility is assumed by the Publisher for any injury and/or damage to persons or property as a matter of products liability, negligence or otherwise, or from any use or operation of any methods, products, instructions or ideas contained in the material herein. Although all advertising material is expected to conform to ethical standards, inclusion in this publication does not constitute a guarantee or endorsement of the quality or value of such product or of the claims made of it by its manufacturer.

US mailing notice – Journal of Crystal Growth (ISSN 0022-0248) is published semimonthly except monthly in January, February, June, July and November by Elsevier Science, Molenwerf 1, P.O. Box 211, 1000 AE Amsterdam, Netherlands. Annual subscription price in the USA is US $4822 (valid in North, Central and South America only), including air speed delivery. Second class postage paid at Jamaica NY 11431.

USA POSTMASTERS: Send address changes to Journal of Crystal Growth, Publications Expediting, Inc., 200 Meacham Avenue, Elmont NY 11003. Airfreight and mailing in the USA by Publications Expediting.

PRINTED IN THE NETHERLANDS

ELSEVIER

Journal of Crystal Growth 140 (1994) 467–519

JOURNAL OF CRYSTAL GROWTH

Author index to volumes 131–140

Abbona, F., F. Christensson, M. Franchini Angela and H.E. Lundager Madsen, Crystal habit and growth conditions of brushite, $CaHPO_4 \cdot 2H_2O$ 131 (1993) 331
Abe, K., see Ono 135 (1994) 359
Abe, S., see Mori 133 (1993) 80
Abe, T., see Sasaki 136 (1994) 162
Abe, Y., see Haga 132 (1993) 575
Abernathy, C.R., F. Ren, S.J. Pearton, P.W. Wisk, D.A. Bohling, G.T. Muhr, A.C. Jones, M. Stavola and D.M. Kozuch, The impact of impurity incorporation on heterojunction bipolar transistors grown by metalorganic molecular beam epitaxy 136 (1994) 11
Abernathy, C.R., see Bohling 136 (1994) 118
Abounadi, A., see Bouchara 138 (1994) 121
Abousahl, S., C. Loos-Neskovic and M. Fedoroff, Mechanism of the preparation of insoluble compounds by local growth in aqueous solution 137 (1994) 569
Abramof, E., W. Faschinger, H. Sitter and A. Pesek, Short period CdTe(ZnTe)/MnTe superlattices: growth and characterization 135 (1994) 447
Achtziger, N., see Rüb 138 (1994) 285
Adamski, J.A., see Bliss 137 (1994) 145
Affrossman, S., see Fisher 138 (1994) 86
Agahi, F., C.R. Lutz, Jr. and K.M. Lau, Improvement of gas-switching abruptness for atmospheric pressure organometallic vapor phase epitaxy 139 (1994) 344
Agarwal, M.K., see Arora 131 (1993) 268
Ager III, J.W., see Wolk 138 (1994) 1071
Aggarwal, M.D., W.S. Wang, J. Choi, J.C. Cochrane and Z.Y. Wang, Morphology and formation of the color core of $Bi_{12}SiO_{20}$ crystals grown by the Czochralski method 137 (1994) 132
Agranat, A., see Hofmeister 131 (1993) 486
Agrawal, N., see Reier 135 (1994) 463
Agrinskaya, N.V., Low temperature variable range hopping conductivity in doped CdTe crystals 138 (1994) 493
Ai, Z.P., see Wang 139 (1994) 86
Aidun, D.K., see Shen 132 (1993) 250
Aidun, D.K., see Shen 132 (1993) 351
Aindow, M., T.T. Cheng, N.J. Mason, T.-Y. Seong and P.J. Walker, Geometry and interface structure of island nuclei for GaSb buffer layers grown on (001) GaAs by metalorganic vapour phase epitaxy 133 (1993) 168
Aindow, M., see Cheng 135 (1994) 409
Ainger, F.W., see Erdei 139 (1994) 54
Akasaki, I., see Detchprohm 137 (1994) 170
Akinaga, F., see Kato 138 (1994) 373
Akita, N., see Suzuki 138 (1994) 199
Akitsu, T., see Matsumoto 138 (1994) 403
Akram, S. and I. Bhat, Organometallic vapor phase epitaxial growth of p-type ZnSe using phenylhydrazine as the dopant source 138 (1994) 105
Akram, S., see Bhat 138 (1994) 127
Al-Bassam, A.A.I. and A.M. Al-Dhafiri, Crystallographic and optical absorption characterization of CdS_xSe_{1-x} alloys for $0 < x < 1$ 134 (1993) 63
Al-Bassam, A.A.I., A.A. Al-Juffali and A.M. Al-Dhafiri, Structure and lattice parameters of cadmium sulphide selenide (CdS_xSe_{1-x}) mixed crystals 135 (1994) 476
Albers, C., see Zimmermann 131 (1993) 276
Alberts, V., Influence of initial growth parameters on the structural and optical properties of GaAs on (001) Si 140 (1994) 299
Al-Dhafiri, A.M., see Al-Bassam 134 (1993) 63
Al-Dhafiri, A.M., see Al-Bassam 135 (1994) 476
Aldinger, F., see Seher 137 (1994) 452
Alex, V., see Uecher 137 (1994) 278
Alexandre, F., D. Zerguine, P. Launay, J.L. Benchimol, M. Berz, B. Sermage, D. Komatitsch and M. Juhel, Quasi-planar GaAs heterojunction bipolar transistor device entirely grown by chemical beam epitaxy 136 (1994) 235
Alexiev, D., K.S.A. Butcher, M. Edmondson and T.L. Tansley, Thermal annealing of liquid phase epitaxial gallium arsenide 135 (1994) 367
Alexiev, D., see Butcher 140 (1994) 9

Al-Juffali, A.A., see Al-Bassam 135 (1994) 476

Allègre, J., G. Arnaud, H. Mathieu, P. Lefebvre, W. Granier and L. Boudes, Absorption properties of CdS nanocrystals in glasses; evidence of both weak and strong confinement regimes 138 (1994) 998

Allen, J.W., see Zheng 138 (1994) 477

Allen, J.W., see Zheng 138 (1994) 504

Allen, L.H., see Zhou 134 (1993) 167

Ammann, N., see Gleitsmann 138 (1994) 324

Anan, T., see Li 135 (1994) 78

Anandan, M., see Bagai 139 (1994) 259

Ananth, R., see Lee 132 (1993) 226

Anbukumar, S., see Ravi 133 (1993) 212

Anbukumar, S., see Ravi 137 (1994) 598

Anderson, M., see Piffault 135 (1994) 11

Anderson, P.L., A. Erbil, C.R. Nelson, G.S. Tompa and K. Moy, A high-speed, rotating-disc metalorganic chemical vapor deposition system for the growth of (Hg,Cd)Te and related alloys 135 (1994) 383

Andersson, T.G., see Wang 135 (1994) 455

Andreeta, J.P., see Prokofiev 137 (1994) 528

Andreeta, M.R.B., see Prokofiev 137 (1994) 528

Andrews, R.N., see Beske 137 (1994) 102

Andrews, R.N., see Price 137 (1994) 201

Anestiev, L., On the solute redistribution at thermally activated phase transition processes. I. Theory 140 (1994) 167

Anestiev, L., On the solute redistribution at thermally activated phase transition processes. II. Applications 140 (1994) 175

Angert, N., L. Kaplun, M. Tseitlin, E. Yashchin and M. Roth, Growth and domain structure of potassium titanyl phosphate crystals pulled from high-temperature solutions 137 (1994) 116

Anselmetti, D., see Schlom 137 (1994) 259

Anselmo, A., V. Prasad, J. Koziol and K.P. Gupta, Numerical and experimental study of a solid pellet feed continuous Czochralski growth process for silicon single crystals 131 (1993) 247

Anselmo, A., V. Prasad, J. Koziol and K.P. Gupta, Oscillatory convection in low aspect ratio Czochralski melts 134 (1993) 116

Antolini, A., see Rigo 136 (1994) 293

Anzai, Y., S. Kimura, T. Sawada, T. Rudolph and K. Shigematsu, Measurement of density, viscosity and surface tension of molten lithium niobate 134 (1993) 227

Anzai, Y., K. Terashima and S. Kimura, Physical properties of molten lithium tetraborate 134 (1993) 235

Anzai, Y., see Imoto 135 (1994) 279

Anzai, Y., see Shigematsu 137 (1994) 509

Aoki, S., see Sazaki 139 (1994) 95

Aoki, Y., see Sakaki 133 (1993) 329

Aota, J., see Quon 134 (1993) 266

Aoudia, A., see Rzepka 138 (1994) 244

Aoyagi, Y., see Zhang 136 (1994) 200

Aoyama, T., T. Ikarashi, K. Miyanaga and T. Tatsumi, Facet formation mechanism of silicon selective epitaxial layer by Si ultrahigh vacuum chemical vapor deposition 136 (1994) 349

Arai, Y., see Ono 132 (1993) 297

Arai, Y., see Ono 135 (1994) 359

Arai, Y., see Ono 137 (1994) 427

Araki, H., see Kanie 138 (1994) 145

Araujo, D., see Rudra 136 (1994) 173

Arends, J., see Christoffersen 137 (1994) 545

Arikawa, Y., see Beske 137 (1994) 102

Arita, M., N. Suzuki and I. Nishida, Smoke particles of ytterbium and its oxides 132 (1993) 71

Arkenbout, G., see Lin 133 (1993) 322

Armas, B., see Rodríguez-Clemente 133 (1993) 59

Armington, A.F., see Harris 137 (1994) 128

Armington, A.F., see Bliss 137 (1994) 145

Armstrong, J.V., see Sun 132 (1993) 592

Arnaud, G., see Allègre 138 (1994) 998

Arnold, E., see DeLucas 135 (1994) 183

Arnold, E., see Schall 135 (1994) 548

Arnold, S., see Na 139 (1994) 104

Arora, S.K., D.H. Patel and M.K. Agarwal, Vapour growth of SnS_2 single crystals 131 (1993) 268

Artemyev, M.V., see Gurin 138 (1994) 993

Arterton, B.W., J.W. Brightwell, B. Ray and I.V.F. Viney, Formation and optical properties of homogeneous solid solutions of $Ca_{1-x}Sr_xS:Ce$ 138 (1994) 1051

Arterton, B.W., see Viney 138 (1994) 1055

Asahi, H., see Okuno 136 (1994) 83

Asahi, H., see Marx 136 (1994) 204

Asahi, H., see Liu 136 (1994) 250

Asahi, H., M. Enokida, K. Asami, J.H. Kim, T. Watanabe, R.K. Soni and S. Gonda, Gas source molecular beam epitaxy growth of GaP/AlP short period superlattices 136 (1994) 268

Asahi, H., see Kim 136 (1994) 310

Asami, K., see Asahi 136 (1994) 268

Asami, K., see Kim 136 (1994) 310

Asano, T., see Fujita 138 (1994) 737

Ashenford, D.E., see Dhese 138 (1994) 443

Ashenford, D.E., see Wolverson 138 (1994) 656

Ashenford, D.E., see Sawicki 138 (1994) 900

Ashizawa, Y., see Naritsuka 131 (1993) 186

Aspar, B., see Rodríguez-Clemente 133 (1993) 59

Astles, M.G., see Cheng 135 (1994) 409

Astles, M.G., see Fisher 138 (1994) 86

Ataka, M., see Niimura 137 (1994) 671

Atherton, L.J., see Brandon 132 (1993) 261

Auld, J., see Jones 135 (1994) 285

Aulombard, R.L., see Cloitre 133 (1993) 101
Aulombard, R.L., see Bouchara 138 (1994) 121
Aulombard, R.L., see Frandon 138 (1994) 513
Aulombard, R.L., see Gil 138 (1994) 868
Ausloos, M., see Cloots 135 (1994) 496
Austin, J.C., see Doran 138 (1994) 826
Austin, J.C., see Hughes 138 (1994) 1040
Averous, M., see Bouchara 138 (1994) 121
Avramov, V.G., see Bikov 140 (1994) 100
Ayers, J.E., The measurement of threading dislocation densities in semiconductor crystals by X-ray diffraction 135 (1994) 71
Azema, N., see Rodríguez-Clemente 133 (1993) 59
Azoulay, M., M. Sinvani, M. Mizrachi and H. Feldstein, Stripe structure CdTe–CdZnTe–CdTe in a bulk single crystal 137 (1994) 208
Azoulay, M., see George 137 (1994) 299
Azoulay, M., see Biao 138 (1994) 219
Azoulay, M., M.A. George, A. Burger, W.E. Collins and E. Silberman, Interface morphology studies of liquid phase epitaxy grown HgCdTe films by atomic force microscopy 138 (1994) 517

Babić-Ivančić, V., see Škrtić 133 (1993) 189
Bacher, G., see Tönnies 138 (1994) 362
Bacher, G., see Illing 138 (1994) 638
Bacher, G., F. Daiminger, A. Forchel, A. Waag, Th. Litz and G. Landwehr, Many body effects in transient luminescence spectra of a homogeneous electron–hole plasma in CdTe/CdMnTe quantum wells 138 (1994) 856
Baek, S.J., J.S. Chang, E.S. Choi and H.H. Lee, Axial dopant distribution and its control in bulk crystal growth 131 (1993) 481
Baetzold, R.C. and J. Mir, A computational model for growth of (100) $SrTiO_3$ and (001) $YBa_2Cu_3O_7$ oxide films 135 (1994) 145
Bagai, R.K., R.D.S. Yadava, B.S. Sundersheshu, G.L. Seth, M. Anandan and W.N. Borle, A study on contaminations during bulk growth of CdTe crystals 139 (1994) 259
Bahir, G., see Maayan 135 (1994) 23
Bähr, G., see Möller 131 (1993) 165
Bailly, F., see Cohen-Solal 138 (1994) 68
Baker, E.S., see DeLucas 135 (1994) 183
Balakrishnan, K. and P. Ramasamy, Study of anomalous electrical behaviour of molybdenum ditelluride single crystals 137 (1994) 309
Balk, P., see Werner 136 (1994) 322
Balk, P., see Werner 136 (1994) 338
Balkanski, M., see Le 135 (1994) 1
Ballman, A.A., see Cheng 132 (1993) 280
Balokrys, S.P., see Oseledchik 135 (1994) 373
Balzuweit, K., A. Hovestad, H. Meekes and J.L. de Boer, The temperature and composition dependence of the modulation wave vector of incommensurate calaverite 131 (1993) 518
Balzuweit, K. and W.J.P. van Enckevort, Surface studies on the five-fold facets of Al–Cu–Fe quasicrystals 135 (1994) 297
Bamberger, C.E., and O.C. Kopp, Acicular crystals of sodium tungsten bronzes 131 (1993) 473
Bangert, U., A.J. Harvey, V.A. Wilkinson, C. Dieker, J.M. Jowett, A.D. Smith, S.D. Perrin and C.J. Gibbins, Evidence for strain relaxation via composition fluctuations in strained quaternary/quaternary and quaternary/ternary multiple quantum well structures 132 (1993) 231
Barbé, M., see Cohen-Solal 138 (1994) 68
Barber, R., see Suderena Rao 136 (1994) 179
Barnett, S.A., see Hultman 135 (1994) 309
Barnett, S.A., see Choi 137 (1994) 381
Barrett, D.L., see Hobgood 137 (1994) 181
Barrette, P., B. Michel and E. Stander, On the reproduction of ice from a common seed 131 (1993) 153
Barthou, C., see Zeinert 138 (1994) 1023
Basmaji, P., see Lubyshev 132 (1993) 533
Bassani, F., K. Kheng, M. Mamor, R.T. Cox, N. Magnea, K. Saminadayar and S. Tatarenko, Electron-gas screening of the piezoelectric fields in indium-doped (211) $CdTe/Cd_{1-x}Zn_xTe$ quantum wells 138 (1994) 607
Batra, A.K., see Zhang 137 (1994) 141
Baubinas, R., see Vaitkus 138 (1994) 545
Baucom, K.C., see Biefeld 133 (1993) 38
Baucom, K.C., see Biefeld 135 (1994) 401
Baucom, K.C., see Biefeld 137 (1994) 231
Baude, P.F., see DePuydt 138 (1994) 667
Bauer, G., see Fromherz 138 (1994) 580
Bauer, G., see Giebultowicz 138 (1994) 877
Bäuerle, D., see Wang 139 (1994) 86
Bäume, P., F. Kubacki and J. Gutowski, Characterization of impurities in II–VI semiconductors by time-resolved lineshape analysis of donor–acceptor pair spectra 138 (1994) 266
Bauser, E., see Weishart 131 (1993) 17
Bauser, E., see Marek 134 (1993) 14
Bauser, E., see Weishart 137 (1994) 335
Baxter, C.S., W.M. Stobbs, R.F. Broom and J.P. Reithmaier, Observation of a novel form of ordering in $Al_{0.5}In_{0.5}As$ and $(Ga, Al)_{0.5}In_{0.5}As$ 131 (1993) 410
Beam III, E.A., H.F. Chau, T.S. Henderson, W. Liu and A.C. Seabaugh, The use of organometallic group-V sources for the metalorganic molecular beam epitaxy growth of $In_{0.48}Ga_{0.52}P/GaAs$ and $In_{0.53}Ga_{0.47}As/InP$ heterojunction bipolar device structures 136 (1994) 1

Beanland, R., see Sun 132 (1993) 592
Beaumont, B., see Taylor 132 (1993) 61
Becker, Ch., see Tönnies 138 (1994) 362
Becker, C.R., see Waag 131 (1993) 607
Becker, C.R., see Schikora 138 (1994) 8
Becker, C.R., see Einfeldt 138 (1994) 471
Becla, P., see Ji 138 (1994) 187
Becla, P., see Feng 138 (1994) 239
Bednorz, J.G., see Schlom 137 (1994) 259
Behet, M., B. Stoll and K. Heime, Comparative study on the low pressure metalorganic vapor phase epitaxial growth of InSb on GaAs with trimethylantimony and triethylantimony as Sb precursors 135 (1994) 434
Behr, T., see Ruppert 138 (1994) 48
Behr, T., see Hommel 138 (1994) 331
Behr, T., see Hommel 138 (1994) 1076
Behringer, M., see Einfeldt 138 (1994) 471
Belas, E., P. Höschl, R. Grill, J. Franc, P. Moravec, K. Lischka, H. Sitter and A. Toth, Ultrafast diffusion of Hg in $Hg_{1-x}Cd_xTe$ ($x \approx 0.21$) 138 (1994) 940
Belas, E., see Höschl 138 (1994) 956
Ben Hadid, H., see Kaddeche 135 (1994) 341
Benaissa, M., J. Werckmann, J.L. Hutchison, E. Peschiera, J. Guille and M.J. Ledoux, High-resolution transmission electron microscopy study on SiC grown from SiO and C^*: crystal growth and structural characterization 131 (1993) 5
Benalloul, P., see Zeinert 138 (1994) 1023
Benchimol, J.L., see Alexandre 136 (1994) 235
Bennema, P., see Lin 133 (1993) 322
Bennema, P., see Liu 135 (1994) 209
Bennema, P., see Liu 139 (1994) 179
Benoit, J., see Zeinert 138 (1994) 1023
Benyon, B., see Sudersena Rao 136 (1994) 179
Benz II, R.G., see Maruyama 137 (1994) 435
Benz, K.W., see Weishart 131 (1993) 17
Benz, K.W., see Zimmermann 131 (1993) 276
Benz, K.W., see Eckstein 131 (1993) 453
Benz, K.W., see Cröll 137 (1994) 95
Benz, K.W., see Salk 138 (1994) 161
Benz, K.W., see Fiederle 138 (1994) 529
Benz, K.W., see Novák 139 (1994) 206
Berger, H., see Bickmann 131 (1993) 133
Berger, H., see Szczerbakow 139 (1994) 172
Berglund, K.A., see Dunuwila 137 (1994) 561
Berlouis, L.E.A., see Fisher 138 (1994) 86
Bertram, D., W. Stolz and E.O. Göbel, Direct growth of (AlGa)As/GaAs quantum wires by metalorganic vapour phase epitaxy 132 (1993) 179
Berz, M., see Alexandre 136 (1994) 235
Beserman, R., see Maayan 135 (1994) 23
Beske, S.A., Y. Arikawa, R.N. Andrews and W. Lundblad, Chemical compatibility studies of GaAs and CdZnTe with the alloys WC-103 and TZM 137 (1994) 102
Bettahi, A. and J. Marfaing, Early stage of microstructure formation in thick superconducting $YBa_2Cu_3O_{7-\delta}$ films; dependence on the sintering conditions and the substrate type 135 (1994) 487
Betzel, C., see Hennig 135 (1994) 513
Beyersdorfer, V., see Hommel 138 (1994) 331
Beyersdorfer, V., see Hommel 138 (1994) 1076
Bhalla, A., see Erdei 139 (1994) 54
Bhargava, R.N., see Gallagher 138 (1994) 970
Bhat, H.L., see Venkataramanan 140 (1994) 336
Bhat, I., see Wang 138 (1994) 43
Bhat, I., see Akram 138 (1994) 105
Bhat, I. and S. Akram, Atomic layer epitaxial growth studies of ZnSe using dimethylzinc and hydrogen selenide 138 (1994) 127
Bhat, R., see Caneau 132 (1993) 364
Bhattacharjee, A.K., Orbital exchange in diluted magnetic semiconductors 138 (1994) 895
Bhattacharya, P.K., see Chen 136 (1994) 50
Bhattacharya, P.K., see Munns 136 (1994) 166
Bhihe, C.K., P.A. Mataga, J.W. Hutchinson, S. Rajendran and J.P. Kalejs, Residual stresses in crystal growth 137 (1994) 86
Biao, Y., see George 137 (1994) 299
Biao, Y., M. Azoulay, M.A. George, A. Burger, W.E. Collins, E. Silberman, C.-H. Su, M.E. Volz, F.R. Szofran and D.C. Gillies, Photoluminescence of vapor and solution grown ZnTe single crystals 138 (1994) 219
Bickmann, K., J. Hauck, P. Möck and H. Berger, Monoclinic deformation and tilting of epitaxial CdTe films on GaAs at 25–400°C 131 (1993) 133
Bicknell-Tassius, R.N., W.M. Theis, T. Cole, K.T. Higa and T.J. Groshens, Metalorganic molecular beam epitaxy doping of II–VI compound semiconductors 138 (1994) 425
Biefeld, R.M., K.C. Baucom, S.R. Kurtz and D.M. Follsteadt, The growth of $InP_{1-x}Sb_x$ by metalorganic chemical vapor deposition 133 (1993) 38
Biefeld, R.M. and K.C. Baucom, Substrate orientation and surface morphology improvements for InSb grown by metalorganic chemical vapor deposition 135 (1994) 401
Biefeld, R.M., K.C. Baucom and S.R. Kurtz, The growth of $InAs_{1-x}Sb_x/InAs$ strained-layer superlattices by metalorganic chemical vapor deposition 137 (1994) 231
Bierlein, J.D., see Cheng 132 (1993) 280
Bierlein, J.D., see Cheng 132 (1993) 289
Bierlein, J.D., see Cheng 137 (1994) 107
Biernath, T., see Erb 132 (1993) 389
Bikov, A.Z., V.G. Avramov, S.B. Damianova

and S.D. Stoichkov, Adsorption of Fe^{3+} ions on the (001) face of a triglycine sulphate crystal; in situ investigation 140 (1994) 100
Bilger, G., see Hommel 138 (1994) 331
Bilger, G., see Waag 138 (1994) 437
Bill, J., see Seher 137 (1994) 452
Billia, B., see Jamgotchian 134 (1993) 181
Billia, B., see Minari 140 (1994) 264
Bishop, S.P., see DeLucas 135 (1994) 183
Björqvist, M., see Vaitkus 138 (1994) 545
Blanton, T.N., see Wernberg 131 (1993) 176
Blatter, A. and C. Ortiz, Crystallization study of glassy Te–Se–I thin films 139 (1994) 120
Bliss, D.F., M. Harris, J. Horrigan, W.M. Higgins, A.F. Armington and J.A. Adamski, Synthesis and growth processes for zinc germanium diphosphide 137 (1994) 145
Bocchi, C., C. Ferrari, P. Franzosi, A. Bosacchi and S. Franchi, Accurate determination of lattice mismatch in the epitaxial AlAs/GaAs system by high-resolution X-ray diffraction 132 (1993) 427
Bocchi, C., C. Ferrari, P. Franzosi, A. Bosacchi and S. Franchi, Accurate determination of lattice mismatch in the epitaxial AlAs/GaAs system by high-resolution X-ray diffraction (E) 137 (1994) 680
Bodin, C., see Legras 138 (1994) 585
Bogdanov, S.V., see Klingshirn 138 (1994) 786
Bogdanov, S.V., see Woggon 138 (1994) 976
Bogonin, I.A., see Joshkin 132 (1993) 209
Bohling, D.A., see Abernathy 136 (1994) 11
Bohling, D.A., C.R. Abernathy and K.F. Jensen, Chemical/surface mechanistic considerations in the design of novel precursors for metalorganic molecular beam epitaxy 136 (1994) 118
Boistelle, R., see Vessler 135 (1994) 505
Boisvert, R.F., see Coriell 140 (1994) 139
Bole, V., see Maček 132 (1993) 99
Bonard, J.M., see Rudra 136 (1994) 173
Boney, C., see Ren 138 (1994) 455
Boney, C., see Eason 138 (1994) 703
Booker, G.R., see Philips 140 (1994) 249
Boone, J.L., G. Cantwell, W.C. Harsch, J.E. Thomas and B.A. Foreman, Electrical and crystallographic characterization of CdTe grown by the vapor transport method 139 (1994) 27
Boring, P., see Gil 138 (1994) 868
Borle, W.N., see Bagai 139 (1994) 259
Bornside, D.E., see Zhou 137 (1994) 26
Borshchevsky, A. and J.-P. Fleurial, Ru_2Ge_3: crystal growth and some properties 137 (1994) 283
Bosacchi, A., see Bocchi 132 (1993) 427
Bosacchi, A., see Bocchi 137 (1994) 680
Bouchara, D., A. Abounadi, M. Di Blasio, N. Briot, T. Cloitre, O. Briot, B. Gil, J. Calas, M. Averous and R.L. Aulombard, Contamination effects from tellurium in ZnS–ZnSe superlattices 138 (1994) 121
Boudes, L., see Allègre 138 (1994) 998
Boué, F., F. Lefaucheux, M.C. Robert and I. Rosenman, Small angle neutron scattering study of lysozyme solutions 133 (1993) 246
Bourée, J.E., see Qu'Hen 138 (1994) 1079
Bourkiza, M., see Nacer 137 (1994) 91
Boutz, M.M.R. and C.F. Woensdregt, Theoretical growth forms of natural garnets 134 (1993) 325
Bove, P., K. Ono, K. Joshin, H. Tanaka, K. Kasai and J. Komeno, Chemical beam epitaxy selectively-regrown n^+-GaAs layer on metalorganic chemical vapor deposition grown GaInP/GaInAs/GaAs pseudomorphic high electron mobility transistor structure 136 (1994) 261
Bowen, P., see Rubattel 135 (1994) 135
Bowersox, K.D., see DeLucas 135 (1994) 183
Bowman, L.E., see Cook 131 (1993) 395
Boyer, A., see Mzerd 140 (1994) 365
Boyn, R., see Zimmermann 131 (1993) 276
Brandon, S., J.J. Derby, L.J. Atherton, D.H. Roberts and R.L. Vital, Three-dimensional heat transfer effects during the growth of $LiCaAlF_6$ in a modified Bridgman furnace 132 (1993) 261
Brandt, C.D., see Hobgood 137 (1994) 181
Brandt, G.B., see Singh 137 (1994) 155
Braunstein, G., see Wernberg 140 (1994) 57
Bray, T.L., see DeLucas 135 (1994) 183
Brémond, G., see Rzepka 138 (1994) 244
Bressler, P.R. and H.-E. Gumlich, Mn-3d derived partial density of states at the interface of epitaxially grown zinc-blende MnTe on CdTe(100) 138 (1994) 1028
Bridenbaugh, P.M., see Laudise 140 (1994) 51
Brightwell, J.W., see Arterton 138 (1994) 1051
Brightwell, J.W., see Viney 138 (1994) 1055
Brinkman, A.W., see Jones 138 (1994) 274
Brinkman, A.W., see Brown 138 (1994) 538
Brinkman, A.W., see Funaki 139 (1994) 211
Brion, H.G., C. Mewes, I. Hahn and U. Schäufele, Infrared contrast of inclusions in CdTe 134 (1993) 281
Briones, F., see Mazuelas 131 (1993) 465
Briot, N., see Cloitre 133 (1993) 101
Briot, N., see Bouchara 138 (1994) 121
Briot, N., see Frandon 138 (1994) 513
Briot, N., see Gil 138 (1994) 868
Briot, O., see Cloitre 133 (1993) 101
Briot, O., see Bouchara 138 (1994) 121
Briot, O., see Frandon 138 (1994) 513
Briot, O., see Gil 138 (1994) 868
Brokman, A., see Vilenkin 131 (1993) 239

Broom, R.F., see Baxter 131 (1993) 419
Broser, I., see Krause 138 (1994) 75
Broser, I., see Hoffmann 138 (1994) 379
Broser, I., B. Lummer, R. Heitz and A. Hoffmann, Degenerate four-wave mixing at bound excitons in II–VI semiconductors 138 (1994) 809
Broser, I., see Fricke 138 (1994) 815
Broser, I., see Presser 138 (1994) 820
Broser, I., see Hoffmann 138 (1994) 1073
Brown, C.M., F. Novin and D.L. Purich, Calcium oxalate crystal morphology: influence of phospholipid micelles with compositions based on each leaflet of the erythrocyte membrane 135 (1994) 523
Brown, P.D., Y.Y. Loginov, J.T. Mullins, K. Durose, A.W. Brinkman and C.J. Humphreys, Transmission electron microscopy investigations of II–VI/GaAs heterostructures 138 (1994) 538
Brown, P.W., see Graham 132 (1993) 215
Brown, R.A., see Kinney 132 (1993) 551
Brown, R.A., D. Maroudas and T. Sinno, Modelling point defect dynamics in the crystal growth of silicon 137 (1994) 12
Brown, R.A., see Zhou 137 (1994) 26
Brown, W.E., see Marković 135 (1994) 533
Brückner, F.-U. and K. Schwerdtfeger, Single crystal growth with the Czochralski method involving rotational electromagnetic stirring of the melt 139 (1994) 351
Brummell, M.A., see Sawicki 138 (1994) 900
Brunthaler, G., see Lang 138 (1994) 81
Brunthaler, G., M. Lang, A. Forstner, C. Giftge, D. Schikora, S. Ferreira, H. Sitter and K. Lischka, Deep blue and UV photoluminescence from ZnS/CdS superlattices and quantum wells 138 (1994) 559
Brunthaler, G., see Ferreira 140 (1994) 282
Brush, L.N., G.B. McFadden and S.R. Coriell, The effect of crystalline anisotropy on pattern formation in laser-melted thin silicon films 137 (1994) 355
Brush, L.N., see Coriell 140 (1994) 139
Bublik, V., see Charniy 135 (1994) 302
Bublik, V.T., A.K. Tkalich and M.L. Shupegin, Clusters of native point defects and high-coercive state in films of Ca,Ge-substituted magnetic garnet 140 (1994) 84
Buchegger, C., see Rothfritz 136 (1994) 225
Bucher, E., see Kloc 131 (1993) 448
Bucher, E., see Oglesby 137 (1994) 289
Buda, B., M. Dahl, N. von Truchsess and A. Waag, Polar magneto-optic Kerr effect in (Cd,Mn)Te/CdTe superlattices 138 (1994) 652
Bugg, C.E., see DeLucas 135 (1994) 183
Buhl, H. and R. Weiss, Carbon fibre spring for high-temperature application 131 (1993) 470
Bullough, T.J., see Sun 132 (1993) 592
Bullough, T.J., see Joyce 135 (1994) 31
Burger, A., see George 137 (1994) 299
Burger, A., see Biao 138 (1994) 219
Burger, A., see Azoulay 138 (1994) 517
Burk, A.A., see Hobgood 137 (1994) 181
Busch, M.C., see Rzepka 138 (1994) 244
Butcher, K.S.A., see Alexiev 135 (1994) 367
Butcher, K.S.A., D. Alexiev and T.L. Tansley, Lithium compensation of GaAs 140 (1994) 9
Button, C.C., see Roberts 135 (1994) 365
Butzke, S., see Werner 136 (1994) 322
Butzke, S., see Werner 136 (1994) 338
Bykov, A.B. and L.N. Demianets, Crystal growth and characterization of RE-substituted Bi–Sr–Ca–Cu–O superconductors (RE = Y, Er, Yb) 139 (1994) 81
Byrne, E.K., see Karlicek, Jr. 131 (1993) 204

Cacciatore, C., see Rigo 136 (1994) 293
Cadoret, R., see Piffault 135 (1994) 11
Cai, Q.Y., see Zhang 132 (1993) 200
Calabrese, J., see Cheng 132 (1993) 280
Calas, J., see Bouchara 138 (1994) 121
Calhoun, L.C., C.M. Rouleau, M.H. Jeon and R.M. Park, p-Type ZnSe:N grown by molecular beam epitaxy: evidence of non-radiative recombination centers in moderately to heavily doped material 138 (1994) 352
Camel, D., see Favier 140 (1994) 237
Campbell, S.A., see Knutson 140 (1994) 191
Campbell, T.A. and J.N. Koster, Visualization of liquid–solid interface morphologies in gallium subject to natural convection 140 (1994) 414
Caneau, C., R. Bhat, C.C. Chang, K. Kash and M.A. Koza, Selective organometallic vapor phase epitaxy of Ga and In compounds: a comparison of TMIn and TEGa versus TMIn and TMGa 132 (1993) 364
Cantwell, G., see Boone 139 (1994) 27
Capper, P., see Hastings 138 (1994) 917
Carlin, J.F., A. Rudra and M. Ilegems, Quantitative study of the incorporation of group III elements in chemical beam epitaxy of GaInAsP alloys 131 (1993) 387
Carlin, J.F., see Rudra 136 (1994) 278
Carlin, J.F., see Gailhanou 140 (1994) 205
Caroli, B., C. Caroli and L. Ramirez-Piscina, Initial front transients in directional solidification of thin samples of dilute alloys 132 (1993) 377
Caroli, C., see Caroli 132 (1993) 377
Carr, R.W., see Knutson 140 (1994) 191
Carroll II, L.B., see Dunuwila 137 (1994) 561

Carson, M., see DeLucas 135 (1994) 183
Carter, D., see DeLucas 135 (1994) 183
Carvalho, J.F., see Prokofiev 137 (1994) 528
Casagrande, L.G., D.J. Larson, Jr., D. Di Marzio, J. Wu and M. Dudley, The growth and comparison of large-diameter vertical Bridgman CdZnTe and CdTe 137 (1994) 195
Catana, A., see Guilloux-Viry 132 (1993) 396
Cavenett, B.C., see Prior 138 (1994) 94
Cavenett, B.C., see Mullins 138 (1994) 357
Cavenett, B.C., see Wang 138 (1994) 647
Cavenett, B.C., see Kawakami 138 (1994) 759
Cerva, H., see Hommel 138 (1994) 1076
Červeň, I., T. Lacko, I. Novotný, V. Tvarožek and M. Harvanka, Texture of obliquely sputtered ZnO thin films 131 (1993) 546
Chadi, D.J., Acceptor and donor states of impurities in wide band gap II–VI semiconductors 138 (1994) 295
Chai, W.P., Y.S. Gu, M. Li, Z.H. Mai, Q.Z. Li, L. Yuan and S.J. Pang, Orientation influence of cubic boron nitride crystal facets on the epitaxial growth of diamond film by microwave plasma chemical vapor deposition 135 (1994) 639
Chait, A., see Korpela 137 (1994) 623
Chang, C.C., see Caneau 132 (1993) 364
Chang, C.-M., see Lin 137 (1994) 400
Chang, J.S., see Baek 131 (1993) 481
Chang, S.K., see Lee 138 (1994) 136
Chani, V.I., K. Shimamura, K. Inoue, T. Fukuda and K. Sugiyama, Synthesis and search for equilibrium compositions of borates with the huntite structure 132 (1993) 173
Chani, V.I., K. Inoue, K. Shimamura, K. Sugiyama and T. Fukuda, Segregation coefficients in β-Ga_2O_3 : Cr crystals grown from a Ba_2O_3 based flux 132 (1993) 335
Chani, V.I., K. Shimamura, K. Inoue and T. Fukuda, Huntite-borate crystallization in stoichiometric melts 133 (1993) 181
Chao, C.H., G. Popovici, E.J. Charlson, E.M. Charlson, J.M. Meese and M.A. Prelas, Smooth diamond films grown by hot filament chemical vapor deposition on positively biased silicon substrates 140 (1994) 454
Charles, J.B., see Dhas 137 (1994) 295
Charlson, E.J., see Chao 140 (1994) 454
Charlson, E.M., see Chao 140 (1994) 454
Charniy, L. and V. Bublik, The influence of GaAs crystal composition on the features of matrix microdefects 135 (1994) 302
Chatchaturov, A., see Polity 131 (1993) 271
Chau, H.F. see Beam 136 (1994) 1
Chebotaev, N.M., see Fischer 132 (1993) 444
Chehab, S., see Quon 134 (1993) 266
Chen, Chuangtian, see Mei 132 (1993) 609
Chen, C.P., see Kou 137 (1994) 663
Chen, E.-H., see Wu 139 (1994) 251
Chen, F., see Kaito 140 (1994) 123
Chen, F., see Lu 140 (1994) 182
Chen, Guang, see Tu 135 (1994) 636
Chen, H.L., see Quon 134 (1993) 266
Chen, K.M., see Rao 139 (1994) 190
Chen, L.C., see Yang 138 (1994) 629
Chen Lizue, see Hao 135 (1994) 370
Chen, S.D., L. Lin, X.Z. He, Z.Y. Xu, C.P. Luo and J.Z. Xu, High-resolution photoluminescence studies of (211) CdTe grown on (211)B GaAs substrate 140 (1994) 287
Chen, W., J. Gaines, C. Ponzoni, D. Olego, P.S. Mangat, P. Soukiassian and A. Kahn, Reduction of the Au/p-ZnSe(100) Schottky barrier height using a thin Se interlayer 138 (1994) 1078
Chen, W.L., G.O. Munns, L. Davis, P.K. Bhattacharya and G.I. Haddad, The growth of resonant tunneling hot electron transistors using chemical beam epitaxy 136 (1994) 50
Chen, W.L., see Munns 136 (1994) 166
Chen, W.Q., see Wang 135 (1994) 455
Chen Xianqiu, see Xu 130 (1993) 337
Chen Xianqiu, see Xu 133 (1993) 267
Chen, Y.F., see Rao 139 (1994) 190
Chen, Y.K., R. Kapre, W.T. Tsang, A. Tate, D.A. Humphrey and L. Fan, Carbon-doped InGaP/GaAs/InGaP double heterojunction bipolar transistors with a very low $1/f$ noise corner frequency of 108 kHz grown by chemical beam epitaxy 136 (1994) 221
Chen, Y.-P., J.D. Reed, S.S. O'Keefe, W.J. Schaff and L.F. Eastman, Fabrication and characterization of InGaAs/GaAs strained quantum wires grown by molecular beam epitaxy 134 (1993) 162
Chen Yufei, see Hao 135 (1994) 370
Chen Yufei, see Hao 140 (1994) 441
Cheng, H., see Zhang 138 (1994) 310
Cheng, H., see DePuydt 138 (1994) 667
Cheng, H.M., see Zhang 132 (1993) 200
Cheng, L.K., E.M. McCarron III, J. Calabrese, J.D. Bierlein and A.A. Ballman, Development of the nonlinear optical crystal $CsTiOAsO_4$. I. Structural stability 132 (1993) 280
Cheng, L.K., L.T. Cheng, F.C. Zumsteg, J.D. Bierlein and J. Galperin, Development of the nonlinear optical crystal $CsTiOAsO_4$. II. Crystal growth and characterization 132 (1993) 289
Cheng, L.K., L.T. Cheng, J. Galperin, P.A. Morris Hotsenpiller and J.D. Bierlein, Crystal growth and characterization of $KTiOPO_4$ isomorphs from the self-fluxes 137 (1994) 107
Cheng, L.T., see Cheng 132 (1993) 289

Cheng, L.T., see Cheng 137 (1994) 107
Cheng, T.T., see Aindow 133 (1993) 168
Cheng, T.T., M. Aindow, I.P. Jones, J.E. Hails, D.J. Williams and M.G. Astles, The influence of substrate surface preparation on the microstructure of CdTe grown on (001) GaAs by metalorganic chemical vapour deposition 135 (1994) 409
Cheng, V.K.W., A Monte Carlo study of moving steps during crystal growth and dissolution 134 (1993) 369
Cherkaoui, K., see Rzepka 138 (1994) 244
Chernov, A.A., S.R. Coriell and B.T. Murray, Morphological stability of a vicinal face induced by step flow 132 (1993) 405
Chevrier, V., see Fontaine 139 (1994) 67
Chew, A., see Smith 134 (1993) 140
Chew, A., see Roberts 135 (1994) 365
Chiang, J.D., see Li 137 (1994) 421
Chiang, T.Y., E.H. Liu and T.R. Yew, Low temperature GaAs epitaxial growth on Si(100) by molecular beam epitaxy and the post-growth rapid thermal annealing 135 (1994) 469
Chiareli, A.O.P., H.E. Huppert and M.G. Worster, Segregation and flow during the solidification of alloys 139 (1994) 134
Chichibu, S., S. Shirakata, A. Iwai, S. Matsumoto, H. Higuchi and S. Isomura, $CuAlSe_2$ chalcopyrite epitaxial layers grown by low-pressure metalorganic chemical vapor deposition 131 (1993) 551
Chichibu, S., S. Shirakata, A. Ogawa, R. Sudo, M. Uchida, Y. Harada, T. Wakiyama, M. Shishikura, S. Matsumoto and S. Isomura, Growth of $Cu(Al_xGa_{1-x})SSe$ pentenary alloy crystals by iodine chemical vapor transport method 140 (1994) 388
Chien, F.-R., S.R. Nutt, W.S. Yoo, T. Kimoto and H. Matsunami, Interface structures of epitaxial β-SiC on α-SiC substrates 137 (1994) 175
Chin, C.C., T. Morishita and T. Sugimoto, The influence of the surface roughness of the substrates on the surface morphology of $YBa_2Cu_3O_{7-x}$ thin films 132 (1994) 82
Chin, T.P., see Tu 136 (1994) 191
Chiu, C.T., see Huang 134 (1993) 29
Chiu, K., see Shin 132 (1993) 371
Chiu, T.H., see Tsang 135 (1994) 377
Chiu, T.H., M.D. Williams, F.G. Storz and J.F. Ferguson, Chemical beam epitaxial growth of InGaAs using a new precursor tri-isopropylgallium 136 (1994) 148
Chiu, T.H., see Cunningham 136 (1994) 282
Choi, C.-H. and S.A. Barnett, Morphology and crystalline perfection of InAs films on Si(100) 137 (1994) 381
Choi, C.S., see Moon 138 (1994) 944
Choi, E.S., see Baek 131 (1993) 481
Choi, I.H., see Kwak 138 (1994) 950
Choi, J., see Aggarwal 137 (1994) 132
Chong, T.C., see Zeng 140 (1994) 148
Chow-Chong, P., see Sudersena Rao 136 (1994) 179
Choyke, W.J., see Hobgood 137 (1994) 181
Christensson, F., see Abbona 131 (1993) 331
Christoffersen, J., M.R. Christoffersen, J. Arends and M. Höök, Effects of aluminium(III) and fluoride on the demineralization of bovine enamel powder and hydroxyapatite; in vitro kinetic studies showing synergistic inhibition 137 (1994) 545
Christoffersen, M.R., see Christoffersen 137 (1994) 545
Christov, M. and G.K. Kirov, The ratio of dissolving surface area/growing surface area in the hydrothermal growth of quartz 131 (1993) 560
Chung, C., see Jain 138 (1994) 709
Chung, C.H., see Hwang 138 (1994) 131
Chung, C.H., see Lee 138 (1994) 136
Chung, C.K., see Yao 138 (1994) 290
Chung, H.T., see Yi 132 (1993) 451
Chung, I.H., see Hwang 138 (1994) 131
Chung, S.J., see Park 134 (1993) 43
Churchill, L.E., see Ren 138 (1994) 455
Churchill, L.E., see Eason 138 (1994) 703
Cibert, J., see Legras 138 (1994) 585
Cihlář, A., see Nitsch 131 (1993) 612
Clancy, L.L., see DeLucas 135 (1994) 183
Clark, Jr., A.D., see DeLucas 135 (1994) 183
Clark, J.C., see Jones 138 (1994) 274
Clark, S.A., see Piffault 135 (1994) 11
Clarke, R.C., see Hobgood 137 (1994) 181
Cloitre, T., N. Briot, O. Briot, B. Gil and R.L. Aulombard, Low pressure metalorganic vapour-phase epitaxy growth of ZnTe using triethylamine dimethyl zinc adduct 133 (1993) 101
Cloitre, T., see Bouchara 138 (1994) 121
Cloitre, T., see Gil 138 (1994) 868
Cloots, R., S. Stassen, A. Rulmont, P.A. Godelaine, P. Diko, P.H. Duvigneaud and M. Ausloos, Crystallization process in Pb-free or Pb-doped $Bi_{2-x}Pb_xSr_2Ca_2Cu_3O_{10-y}$ glass system 135 (1994) 496
Clydesdale, G., K.J. Roberts and R. Docherty, Modelling the morphology of molecular crystals in the presence of disruptive tailor-made additives 135 (1994) 331
Coblentz, D.L., see Karlicek, Jr. 131 (1993) 204
Cochrane, J.C., see Aggarwal 137 (1994) 132
Cockayne, B., see Dhese 138 (1994) 140
Cody, A.M. and R.D. Cody, Calcium oxalate trihydrate phase control by structurally-specific carboxylic acids 135 (1994) 235
Cody, R.D., see Cody 135 (1994) 235

Cohen, R.M., see Huang 134 (1993) 29
Cohen-Solal, G., F. Bailly and M. Barbé, Critical thickness in heteroepitaxial growth of zinc-blende semiconductor compounds 138 (1994) 68
Cole, T., see Bicknell-Tassius 138 (1994) 425
Cole-Hamilton, D.J., see Hoare 137 (1994) 347
Coleman, C.C. and E. Yamada, Optimization of the vapor reaction growth of single crystal FeI_2 132 (1993) 129
Collins, W.E., see George 137 (1994) 299
Collins, W.E., see Biao 138 (1994) 219
Collins, W.E., see Azoulay 138 (1994) 517
Combescure, C., see Rodríguez-Clemente 133 (1993) 59
Conte, A., see Rajavel 140 (1994) 327
Conte-Matos, A., see Maruyama 137 (1994) 435
Cook, A.P., L.E. Bowman and A.P. Wade, Study of $KBr/Pb(NO_3)_2$ growth and crystal morphologies by acoustic emission and photomicrographic techniques 131 (1993) 395
Cook, Jr., J.W., see Vaudo 138 (1994) 430
Cook, Jr., J.W., see Ren 138 (1994) 455
Cook, Jr., J.W., see Eason 138 (1994) 703
Cook, P.F., see DeLucas 135 (1994) 183
Coquerel, G., see Petit 137 (1994) 585
Coriasso, C., see Rigo 136 (1994) 293
Coriell, S.R., see Chernov 132 (1993) 405
Coriell, S.R., see Brush 137 (1994) 355
Coriell, S.R., R.F. Boisvert, G.B. McFadden, L.N. Brush and J.J. Favier, Morphological stability of a binary alloy during directional solidification: initial transient 140 (1994) 139
Cormier, J.E., see Harris 137 (1994) 128
Coronado, C.A., see Lu 138 (1994) 1
Coulter, Y., see Pettit 139 (1994) 302
Cox, R.T., see Bassani 138 (1994) 607
Cox, R.T., see Davies 138 (1994) 661
Critchlow, G.W., see Jones 135 (1994) 285
Cröll, A., P. Dold and K.W. Benz, Segregation in Si floating-zone crystals grown under microgravity and in a magnetic field 137 (1994) 95
Cross, L.E., see Erdei 139 (1994) 54
Cui, J., see Zhang 136 (1994) 200
Cullis, A.G., see Mullins 138 (1994) 357
Cundiff, S.T., see Hellmann 138 (1994) 791
Cuniot, M., see Rzepka 138 (1994) 244
Cunningham, J.E., M.B. Santos, K.W. Goossen, T.H. Chiu, M.D. Williams, W. Jan and F. Storz, Strain and As species dependent Group V incorporation in GaAsP during gas source molecular beam epitaxy 136 (1994) 282

Dabkowska, H.A., see Dabkowski 132 (1993) 205
Dabkowski, A., H.A. Dabkowska and J.E. Greedan, $SrLaGaO_4$ – Czochralski crystal growth and basic properties 132 (1993) 205
Dahl, M., see Buda 138 (1994) 652
Daiminger, F., see Bacher 138 (1994) 856
Dairaku, S., see Suzuki 138 (1994) 199
Damianova, S.B., see Bikov 140 (1994) 100
Dang, L.S., see Legras 138 (1994) 585
Dang, L.S., see Gourgon 138 (1994) 590
Danilewsky, A.N., see Weishart 131 (1993) 17
Davies, G.J., see Levoguer 136 (1994) 109
Davies, G.J., P.J. Skevington, J.C. Morris, A.C. Jones, S. Rushworth, J.S. Foord and C.L. Levoguer, Some comparisons of chemical beam epitaxy InGaAs/InP growth using triethylgallium, triisopropylgallium and triisobutylgallium sources 136 (1994) 133
Davies, J.J., see Dhese 138 (1994) 140
Davies, J.J., see Wolverson 138 (1994) 656
Davies, J.J., R.T. Cox and G. Feuillet, Optical studies of quantum wells induced by magnetic fields in $Cd_{1-x}Mn_xTe/Cd_{1-y}Zn_yTe$ epitaxial structures 138 (1994) 661
Davies, M., see Houghton 136 (1994) 56
Davies, M., see Sudersena Rao 136 (1994) 179
Davis, L., see Chen 136 (1994) 50
Davis, L., see Munns 136 (1994) 166
Davis, R.F., Deposition and characterization of diamond, silicon carbide and gallium nitride thin films 137 (1994) 161
Davis, R.W., E.F. Moore and M.R. Zachariah, Numerical modeling of particle dynamics in a rotating disk chemical vapor deposition reactor 132 (1993) 513
Davis, S.H., see Huntley 132 (1993) 141
Davis, T.J., T. McAllister, V. Maslen, S.W. Wilkins, M. Faith and P. Leech, Mathematical and numerical models of CdTe deposition in a pre-cracking metalorganic chemical vapour deposition reactor 133 (1993) 230
Day, D.E., see Pettit 139 (1994) 302
De Boer, J.L., see Balzuweit 131 (1993) 518
De Boer, R.C., P.H.M. van Loosdrecht and H.L.M. Meekes, Identification of gaseous oxygen and nitrogen in bubble inclusions in $Bi_4(GeO_4)_3$ (BGO) crystals by means of Raman spectroscopy 140 (1994) 361
De Fays, M., see Rudra 136 (1994) 173
De Groot, P.A.J., see Sawicki 138 (1994) 900
De Lima, C.J., see Prokofiev 137 (1994) 528
De Maeyer, E.A.P., R.M.H. Verbeeck and D.E. Naessens, Optimalization of the preparation of Na^+- and Co_3^{2-}-containing hydroxyapatite by the hydrolysis of monetite 135 (1994) 539
Deacon, G.B., see Leech 139 (1994) 247
Debnam, W., see Rosch 137 (1994) 54
Delalande, C., see Deleporte 138 (1994) 884
Deleporte, E., T. Lebihen, P. Roussignol, B. Ohnesorge, C. Delalande, S. Guha and

H. Munekata, Photoluminescence in a ZnSe/(Zn,Mn)Se heterostructure: magnetic-field induced transition from light to heavy excitons 138 (1994) 884
DeLucas, L.J., M.M. Long, K.M. Moore, W.M. Rosenblum, T.L. Bray, C. Smith, M. Carson, S.V.L. Narayana, M.D. Harrington, D. Carter, A.D. Clark, Jr., R.G. Nanni, J. Ding, A. Jacobo-Molina, G. Kramer, S.H. Hughes, E. Arnold, H.M. Einspahr, L.L. Clancy, G.S.J. Rao, P.F. Cook, B.G. Harris, S.H. Munson, B.C. Finzel, A. McPherson, P.C. Weber, F.A. Lewandowski, T.L. Nagabhushan, P.P. Trotta, P. Reichert, M.A. Navia, K.P. Wilson, J.A. Thomson, R.N. Richards, K.D. Bowersox, C.J. Meade, E.S. Baker, S.P. Bishop, B.J. Dunbar, E. Trinh, J. Prahl, A. Sacco, Jr. and C.E. Bugg, Recent results and new hardware developments for protein crystal growh in microgravity 135 (1994) 183
Demianets, L.N., see Bykov 139 (1994) 81
Demo, P., see Kožíšek 132 (1993) 491
Deppert, K., and J. Jönsson, On the effect of arsine for the decomposition of triethylgallium during epitaxial growth of GaAs 133 (1993) 296
DePuydt, J.M., M.A. Haase, S. Guha, J. Qiu, H. Cheng, B.J. Wu, G.E. Höfler, G. Meis-Haugen, M.S. Hagedorn and P.F. Baude, Room temperature II–VI lasers with 2.5 mA threshold 138 (1994) 667
Derby, J.J., see Brandon 132 (1993) 261
Derby, J.J., see Xiao 139 (1994) 147
Desatnik, N., B. Subramaniam and B.E. Thompson, A nonisothermal film model for mass-transfer-limited selective epitaxial growth of silicon on patterned surfaces 131 (1993) 589
Detchprohm, T., K. Hiramatsu, N. Sawaki and I. Akasaki, The homoepitaxy of GaN by metalorganic vapor phase epitaxy using GaN substrates 137 (1994) 170
Devine, P., see Dhese 138 (1994) 443
DeWitt, R., see Singh 135 (1994) 619
DeWitt, R., see Singh 139 (1994) 158
Dhanaraj, G., see Venkataramanan 140 (1994) 336
Dhanasekaran, R., see Gopalakrishnan 137 (1994) 235
Dhanasekaran, R., see Qhalid Fareed 140 (1994) 28
Dhas, R.C., J.B. Charles and F.D. Gnanam, Growth and microhardness studies on $NH_4Sb_3F_{10}$ single crystals 137 (1994) 295
Dhese, K.A., J.E. Nicholls, W.E. Hagston, P.J. Wright, B. Cockayne and J.J. Davies, The metalorganic chemical vapour deposition and photoluminescence of tellurium-doped ZnS/CdS : Te strained layer superlattices 138 (1994) 140
Dhese, K.A., D.E. Ashenford, J.E. Nicholls, P. Devine, B. Lunn, C.G. Scott and J. Jaroszyńsky, Nitrogen doping of molecular beam epitaxially grown CdTe with a radio-frequency plasma source 138 (1994) 443
Di Blasio, M., see Bouchara 138 (1994) 121
Di Marzio, D., see Casagrande 137 (1994) 195
Dickson, R.S., see Leech 139 (1994) 247
Didier, G., see El Mokri 138 (1994) 168
Dieker, C., see Bangert 132 (1993) 231
Diesner, K., see Schön 135 (1994) 601
Dietl, T., see Grabecki 138 (1994) 481
Diko, P., see Cloots 135 (1994) 496
Ding, J., see DeLucas 135 (1994) 183
Ding, J., M. Hagerott, P. Kelkar, A.V. Nurmikko, D.C. Grillo, L. He, J. Han and R.L. Gunshor, Gain and dynamics in ZnSe-based quantum wells 138 (1994) 719
Dion, M., see Houghton 136 (1994) 56
Diskett, D.J., see Fisher 138 (1994) 86
Dobrowolski, W., see Grodzicka 138 (1994) 1034
Docherty, R., see Clydesdale 135 (1994) 331
Doerschel, J., see Uecher 137 (1994) 278
Doi, Y., see Iijima 135 (1994) 229
Dold, P., see Cröll 137 (1994) 95
Doran, J.P., R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Polarization dependent dephasing measurements in $Cd_xZn_{1-x}Te/ZnTe$ multiple quantum well structures 138 (1994) 826
Dorman, D.R., see Wolk 138 (1994) 1071
Doyle, I.R., see Ryall 133 (1993) 87
Drake, G., see Jain 138 (1994) 709
Drenten, R., see Petruzzello 138 (1994) 686
Driad, R., see Kuhn 138 (1994) 448
Dudley, M., see Casagrande 137 (1994) 195
Duffar, T., see Harter 131 (1993) 157
Dunbar, B.J., see DeLucas 135 (1994) 183
Duncan, W.J., see Harlow 140 (1994) 19
Dunuwila, D.D., L.B. Carroll II and K.A. Berglund, An investigation of the applicability of attenuated total reflection infrared spectroscopy for measurement of solubility and supersaturation of aqueous citric acid solutions 137 (1994) 561
Durand, J., see Rodríguez-Clemente 133 (1993) 59
Durose, R., see Brown 138 (1994) 538
Dusserre, P., see Harter 131 (1993) 157
Duval, W.M.B., see Singh 135 (1994) 619
Duval, W.M.B., see Singh 139 (1994) 158
Duvigneaud, P.H., see Cloots 135 (1994) 496
Duxstad, K.J., see Wolk 138 (1994) 1071

Eason, D.B., see Ren 138 (1994) 455
Eason, D.B., Z. Yu, C. Boney, J. Ren, L.E. Churchill, J.W. Cook, Jr., J.F. Schetzina and N.A. El-Masry, Quaternary II–VI

alloys for blue and green light emitting diode applications 138 (1994) 703
Eastman, L.F., see Chen 134 (1993) 162
Eastman, L.F., see Teng 135 (1994) 36
Ebeling, W., see Nägele 138 (1994) 842
Ebisutani, T., see Zhu 138 (1994) 397
Ebling, D., see Fiederle 138 (1994) 529
Eckey, L., see Hoffmann 138 (1994) 1073
Eckstein, J., B. Erler, C. Eiche and K.W. Benz, Growth of bulk lead di-iodide crystals from the vapour phase 131 (1993) 453
Eddrief, M., see Le 135 (1994) 1
Edmonson, M., see Alexiev 135 (1994) 367
Egashira, K., see Matsumoto 138 (1994) 403
Egorov, A.V., see Salk 138 (1994) 161
Eguchi, M., see Watanabe 133 (1993) 23
Eguchi, M., see Kakimoto 139 (1994) 197
Eiche, C., see Zimmermann 131 (1993) 276
Eiche, C., see Eckstein 131 (1993) 453
Eiche, C., see Fiederle 138 (1994) 529
Eicher, S., see Moore 136 (1994) 230
Eidenzon, A.M., see Puzanov 137 (1994) 642
Einfeldt, S., see Schikora 138 (1994) 8
Einfeldt, S., H. Heinke, M. Behringer, C.R. Becker, E. Kurtz, D. Hommel and G. Landwehr, The growth of HgSe by molecular beam epitaxy for ohmic contacts to p-ZnSe 138 (1994) 471
Einset, E.O., K.F. Jensen and C.R. Kleijn, On the origin of return flows in horizontal chemical vapor deposition reactors 132 (1993) 483
Einspahr, H.M., see DeLucas 135 (1994) 183
Eisenbach, A., E. Kuphal, K. Miethe and H.L. Hartnagel, Sn-doped InGaAs layers grown by low-pressure metalorganic vapour phase epitaxy 135 (1994) 129
Elban, W.L., D.B. Sheen and J.N. Sherwood, Vickers hardness testing of sucrose single crystals 137 (1994) 304
Elliman, R.G., see Russo 131 (1993) 124
El-Masry, N.A., see Ren 138 (1994) 455
El-Masry, N.A., see Eason 138 (1994) 703
El-Mokri, A., R. Triboulet, A. Lusson, A. Tromson-Carli and G. Didier, Growth of large, high purity, low cost, uniform CdZnTe crystals by the "cold travelling heater method" 138 (1994) 168
Ema, K., see Saiki 138 (1994) 805
Emmerstorfer, B., see Knight 134 (1993) 19
Endoh, Y., see Imaizumi 136 (1994) 366
Enokida, M., see Asahi 136 (1994) 268
Erb, A., T. Biernath and G. Müller-Vogt, $YBa_2Cu_3O_{7-\delta}$–$BaCuO_2$–CuO: investigations on the phase diagram and growth of single crystals. I. The system $BaCuO_2$–CuO_x 132 (1993) 389
Erb, A., T. Traulsen and G. Müller-Vogt, $YBa_2Cu_3O_{7-\delta}$–$BaCuO_2$–CuO: investigations on the phase diagram and growth of single crystals. II 137 (1994) 487
Erbil, A., see Anderson 135 (1994) 383
Erdei, S., Growth of oxygen deficiency-free YVO_4 single crystal by top-seeded solution growth technique 134 (1993) 1
Erdei, S., Growth of oxygen deficiency-free YVO_4 single crystal by top-seeded solution growth technique (E) 135 (1994) 646
Erdei, S., L.E. Cross, F.W. Ainger and A. Bhalla, Ca–Sr–Ga–Nb mixed oxide system for high temperature superconductor substrate applications 139 (1994) 54
Eriksson, B., see Gourgon 138 (1994) 590
Erland, J., B.S. Razbirin, V.G. Lyssenko, K.-H. Pantke and J.M. Hvam, Nonlinear quantum beat spectroscopy of bound biexcitons in II–VI semiconductors 138 (1994) 800
Erler, B., see Eckstein 131 (1993) 453
Ernst, F., see Roos 137 (1994) 457
Eustathopoulos, N., see Harter 131 (1993) 157
Extrémet, G.P., see Fontaine 139 (1994) 67
Eyal, A., see Maayan 135 (1994) 23

Faith, M., see Davis 133 (1993) 230
Faith, M., see Leech 139 (1994) 247
Faivre, G., see Mergy 134 (1993) 353
Falini, G., M. Gazzano and A. Ripamonti, Crystallization of calcium carbonate in presence of magnesium and polyelectrolytes 137 (1994) 577
Fan, G.H., see Guan 138 (1994) 534
Fan, L., see Chen 136 (1994) 221
Fan, S.-J., see Xu 133 (1993) 95
Fan, X., see Li 138 (1994) 231
Fan, X.W., see Guan 138 (1994) 534
Fan, X.W., see Shen 138 (1994) 625
Fan, X.W., see Yang 138 (1994) 629
Fan, X.W., see Zhang 138 (1994) 838
Fan, Y., see Han 138 (1994) 464
Fan, Y., see Salokatve 138 (1994) 1077
Fang, S.F., see Hariu 136 (1994) 157
Farrow, R.F.C., G.R. Harp, R.F. Marks, T.A. Rabedeau, M.F. Toney, D. Weller and S.S.P. Parkin, Epitaxial growth of Pt on basal-plane sapphire: a seed film for artificially layered magnetic metal structures 133 (1993) 47
Faschinger, W., see Abramof 135 (1994) 447
Faschinger, W., see Fromherz 138 (1994) 580
Faschinger, W., see Neukirch 138 (1994) 849
Faschinger, W., see Giebultowicz 138 (1994) 877
Faschinger, W., see Ferreira 140 (1994) 282
Favier, J.J., see Sixou 137 (1994) 605
Favier, J.J., see Coriell 140 (1994) 139

Favier, J.J., J.P. Garandet, A. Rouzaud and D. Camel, Mass transport phenomena during solidification in microgravity; preliminary results of the first Mephisto flight experiment 140 (1994) 237
Fawcett, P.N., see Zhang 131 (1993) 300
Fawcett, P.N., see Zhang 132 (1993) 331
Fearheiley, M.L., see Schön 135 (1994) 601
Fedoroff, M., see Abousahl 137 (1994) 569
Feigelson, R.S., see Helbing 137 (1994) 150
Feigelson, R.S., see Helbing 138 (1994) 1075
Feldman, R.D., see Doran 138 (1994) 826
Feldmann, J., see Hellmann 138 (1994) 791
Feldstein, H., see Azoulay 137 (1994) 208
Feng, Y.P., see Feng 138 (1994) 239
Feng, Z.C., see Ji 138 (1994) 187
Feng, Z.C., P. Becla, L.S. Kim, S. Perkowitz, Y.P. Feng, H.C. Poon, K.P. Williams and G.D. Pitt, Raman, infrared, photoluminescence and theoretical studies of the II–VI–VI ternary CdSeTe 138 (1994) 239
Ferah, M.S., see Guergouri 139 (1994) 6
Ferguson, J.F., see Chiu 136 (1994) 148
Ferrari, C., see Bocchi 132 (1993) 427
Ferrari, C., see Bocchi 137 (1994) 680
Ferreira, S., see Brunthaler 138 (1994) 559
Ferreira, S.O., H. Sitter, W. Faschinger and G. Brunthaler, Growth of highly doped p-type ZnTe layers on GaAs using a nitrogen DC plasma cell 140 (1994) 282
Feuillet, G., see Legras 138 (1994) 585
Feuillet, G., see Davies 138 (1994) 661
Fiechter, S., see Schön 135 (1994) 601
Fiederle, M., see Salk 138 (1994) 161
Fiederle, M., D. Ebling, C. Eiche, D.M. Hofmann, M. Salk, W. Stadler, K.W. Benz and B.K. Meyer, Comparison of CdTe, $Cd_{0.9}Zn_{0.1}Te$ and $CdTe_{0.9}Se_{0.1}$ crystals: application for γ- and X-ray detectors 138 (1994) 529
Figueras, A., see Rodríguez-Clemente 133 (1993) 59
Filipović-Vinceković, N., see Škrtić 133 (1993) 189
Filo, A.J., see Wernberg 131 (1993) 176
Finsy, R., see Van Drunen 134 (1993) 196
Finzel, B.C., see DeLucas 135 (1994) 183
Fischer, F., see Waag 138 (1994) 155
Fischer, F., see Waag 138 (1994) 437
Fischer, K., N.M. Chebotaev and S. Naumov, Isothermal crystal growth of $YBa_2Cu_3O_{7-x}$ in $BaO–CuO–CuO_{0.5}$ flux melts at reduced oxygen partial pressures 132 (1993) 444
Fisher, J.M., L.E.A. Berlouis, L.J.M. Sawers, S.M. MacDonald, S. Affrossman, D.J. Diskett and M.G. Astles, Growth and characterization of electrodeposited films of cadmium telluride on silicon 138 (1994) 86
Fisher, P.A., see Lu 138 (1994) 1
Fitz Gerald, J.D., see Taylor 135 (1994) 157
Fleurial, J.-P., see Borschchevsky 137 (1994) 283
Floyd, P.D., see Yokogawa 138 (1994) 564
Foks, J. and M. Łuszczek, Effect of temperature and supersaturation on the crystallization of polyethylene adipate from dioxane solutions 134 (1993) 347
Follsteadt, D.M., see Biefeld 133 (1993) 38
Fontaine, J.P., G.P. Extrémet, V. Chevrier and J.C. Launay, Experimental and theoretical treatments of the Czochralski growth of $Bi_{12}GeO_{20}$ 139 (1994) 67
Foord, J.S., see Levoguer 136 (1994) 109
Foord, J.S., T.J. Whitaker, D. O'Hare and A.C. Jones, Investigations of the growth of GaAs using stable adducts of gallane 136 (1994) 127
Foord, J.S., see Davies 136 (1994) 133
Forchel, A., see Lang 138 (1994) 81
Forchel, A., see Tönnies 138 (1994) 362
Forchel, A., see Illing 138 (1994) 638
Forchel, A., see Bacher 138 (1994) 856
Foreman, B.A., see Boone 139 (1994) 27
Forstner, A., see Brunthaler 138 (1994) 559
Forsythe, E. and M.L. Pusey, The effects of temperature and NaCl concentration on tetragonal lysozyme face growth rates 139 (1994) 89
Foster, B., see Sudersena Rao 136 (1994) 179
Foster, D.F., see Hoare 137 (1994) 347
Fowler, B.O., see Marković 135 (1994) 533
Fox, K., see Knight 134 (1993) 19
Fradkov, V.E., see Glicksman 137 (1994) 1
Franc, J., see Belas 138 (1994) 940
Franc, J., see Höschl 138 (1994) 956
Franchi, S., see Bocchi 132 (1993) 427
Franchi, S., see Bocchi 137 (1994) 680
Franchini Angela, M., see Abbona 131 (1993) 331
Frandon, J., M.A. Renucci, N. Briot, O. Briot and R.L. Aulombard, Superlattice effects on phonons in strained ZnTe–ZnSe structures 138 (1994) 513
Franks, L.A., see Monchamp 140 (1994) 439
Franse, J.J.M., see Li 135 (1994) 481
Franzosi, P., see Bocchi 132 (1993) 427
Franzosi, P., see Leszczynski 134 (1993) 151
Franzosi, P., see Bocchi 137 (1994) 680
Freer, R.W., see Martin 136 (1994) 69
Freund, L.B., The stress distribution and curvature of a general compositionally graded semiconductor layer 132 (1993) 341
Freytag, B. and U. Rössler, Ab initio calculation of electronic structure and structural properties of $ZnSe_xTe_{1-x}$ 138 (1994) 499
Fricke, Ch., see Krause 138 (1994) 75
Fricke, Ch., see Hoffmann 138 (1994) 379
Fricke, Ch., see Taudt 138 (1994) 418

Fricke, Ch., R. Heitz, B. Lummer, V. Kutzer, A. Hoffmann, I. Broser, W. Taudt and M. Heuken, Time-resolved donor–acceptor pair recombination luminescence in highly n- and p-doped II–VI semiconductors 138 (1994) 815
Fricke, Ch., see Presser 138 (1994) 820
Fricke, Ch., see Hoffmann 138 (1994) 1073
Fripp, A., see Rosch 137 (1994) 54
Fripp, Jr., A.L., see Hubert 131 (1993) 75
Fromherz, T., E. Oh, A.K. Ramdas, E. Koppensteiner, G. Bauer, W. Faschinger and H. Sitter, Confined and propagating phonons in atomic layer epitaxy grown $(CdTe)_n(ZnTe)_n$ superlattices 138 (1994) 580
Frost, C.R., see Leech 139 (1994) 247
Frye, J.M., see Seki 132 (1993) 25
Fu, L.W., H. Wang, S.X. Shang, X.L. Wang and P.M. Xu, Preparation and characterization of $Bi_2Ti_2O_7$ thin films grown by metalorganic chemical vapor deposition 139 (1994) 319
Fu Peizhen, see Wang 132 (1993) 329
Fuchs, F., see Tomm 138 (1994) 175
Fujii, I., see Sakata 135 (1994) 555
Fujii, K., see Miyakoshi 136 (1994) 152
Fujii, M., see Iwanaga 134 (1993) 275
Fujii, N., see Kizuki 134 (1993) 35
Fujii, Y., see Suemune 138 (1994) 750
Fujimoto, M., see Suemune 138 (1994) 750
Fujimura, N., see Lee 134 (1993) 247
Fujimura, N., see Nagai 140 (1994) 65
Fujita, H., see Nishio 134 (1993) 97
Fujita, S., see Naritsuka 131 (1993) 186
Fujita, Sg., see Kawakami 136 (1994) 371
Fujita, Sg., see Ichino 138 (1994) 28
Fujita, Sg., see Fujita 138 (1994) 737
Fujita, Sz., see Kawakami 136 (1994) 371
Fujita, Sz., see Ichino 138 (1994) 28
Fujita, Sz., T. Asano, K. Maehara, T. Tojyo and Sg. Fujita, Photo-assisted metalorganic vapor-phase epitaxy for nitrogen doping and fabrication of blue-green light emitting devices of ZnSe-based semiconductors 138 (1994) 737
Fujiwara, S., see Takahashi 137 (1994) 240
Fujiwara, Y., see Takahashi 135 (1994) 61
Fujiyasu, H., see Minami 138 (1994) 796
Fujiyasu, H., see Kuwabara 138 (1994) 964
Fukatsu, S., N. Usami, Y. Kato, H. Sunamura, Y. Shiraki, H. Oku, T. Ohnishi, Y. Ohmori and K. Okumura, Gas-source molecular beam epitaxy and luminescence characterization of strained $Si_{1-x}Ge_x/Si$ quantum wells 136 (1994) 315
Fukatsu, S., see Kato 136 (1994) 355
Fukuda, T., see Hirata 131 (1993) 145
Fukuda, T., see Okano 131 (1993) 616
Fukuda, T., see Chani 132 (1993) 173
Fukuda, T., see Chani 132 (1993) 335
Fukuda, T., see Matsumoto 132 (1993) 348
Fukuda, T., see Chani 133 (1993) 181
Fukuda, T., see Kang 135 (1994) 623
Fukuda, T., see Machida 137 (1994) 82
Fukuda, T., see Machida 137 (1994) 516
Fukuda, T., see Kang 140 (1994) 435
Fukuma, Y., see Sasaki 136 (1994) 162
Funaki, M. and A.W. Brinkman, Experimental and computer simulation studies of the surface morphology of $Hg_{1-x}Mn_xTe$ epitaxial layers grown by metalorganic vapour phase epitaxy 139 (1994) 211
Furdyna, J.K., see Yokogawa 138 (1994) 564
Furdyna, J.K., see Giebultowicz 138 (1994) 877
Füredi-Milhofer, H., see Komunjer 132 (1993) 122
Furukawa, Y., see Markgraf 140 (1994) 343
Furukawa, Y., see Mikami 140 (1994) 429
Furuse, H., see Yano 131 (1993) 620
Fuyuki, T., see Hatayama 136 (1994) 333

Gadgil, P.N., Optimization of a stagnation point flow reactor design for metalorganic chemical vapor deposition by flow visualization 134 (1993) 302
Gailhanou, M., J.F. Carlin and U. Oesterle, X-ray diffraction analysis of low mismatch epitaxial layers grown on misoriented substrates 140 (1994) 205
Gaines, D.F., see Redwing 135 (1994) 423
Gaines, J.M. In-situ characterization of II/VI molecular beam epitaxy growth using reflection high-energy electron diffraction oscillations 137 (1994) 187
Gaines, J.M., see Petruzzello 138 (1994) 686
Gaines, J.M., see Chen 138 (1994) 1078
Galbraith, I., see Kawakami 138 (1994) 759
Gale, I.G., see Hastings 138 (1994) 917
Gallagher, D., W.E. Heady, J.M. Racz and R.N. Bhargava, Doped zinc sulfide nanocrystals precipitated within a poly(ethylene oxide) matrix – processing and optical characteristics 138 (1994) 970
Galperin, J., see Cheng 132 (1993) 289
Galperin, J., see Cheng 137 (1994) 107
Galtier, P., see Mathet 132 (1993) 241
Gandhi, D.P., see Muthe 139 (1994) 323
Ganière, J.D., see Rudra 136 (1994) 173
Garandet, J.P., Microsegregation in crystal growth from the melt: an analytical approach 131 (1993) 431
Garandet, J.P., see Favier 140 (1994) 237
Gauthier, F., see Lin 140 (1994) 72

Gavryushin, V., G. Račiukaitis, D. Juodžbalis, A. Kazlauskas and V. Kubertavičius, Characterization of intrinsic and impurity deep levels in ZnSe and ZnO crystals by nonlinear spectroscopy 138 (1994) 924
Gazzano, M., see Falini 137 (1994) 577
Ge, C.Z., see Zhang 132 (1993) 200
Ge, P., see Xu 137 (1994) 538
Gebhardt, W., see Wolf 135 (1994) 113
Gebhardt, W., see Grün 138 (1994) 150
Gebhardt, W., see Wolf 138 (1994) 412
Gebhardt, W., see Kuhn 138 (1994) 448
Gebhardt, W., see Naumov 138 (1994) 595
Gebhardt, W., see Klingshirn 138 (1994) 786
Gedridge, Jr., R.W., see Shin 132 (1993) 371
Geng Xingguo, see Huang 134 (1993) 105
Georgalis, Y., see Heinrichs 133 (1993) 196
George, M.A., M. Azoulay, H.N. Jayatirtha, Y. Biao, A. Burger, W.E. Collins and E. Silberman, Atomic force microscopy of lead iodide crystal surfaces 137 (1994) 299
George, M.A., see Biao 138 (1994) 219
George, M.A., see Azoulay 138 (1994) 517
Gerber, Ch., see Schlom 137 (1994) 259
Gerlach, P., see Zemke 139 (1994) 37
Geurts, J., see Gleitsmann 138 (1994) 324
Geurts, J., see Hermans 138 (1994) 612
Gevelber, M.A., Dynamics and control of the Czochralski process. III. Interface dynamics and control requirements 139 (1994) 271
Gevelber, M.A., Dynamics and control of the Czochralski process. IV. Control structure design for interface shape control and performance evaluation 139 (1994) 286
Geyzers, K.P., see Klingshirn 138 (1994) 786
Geyzers, K.P., see Nägele 138 (1994) 842
Giapis, K.P., see Skromme 138 (1994) 338
Gibbins, C.J., see Bangert 132 (1993) 231
Giebultowicz, T.M., W. Faschinger, V. Nunez, P. Klosowski, G. Bauer, H. Sitter and J.K. Furdyna, Antiferromagnetic spin ordering and interlayer magnetic correlations in MnTe/CdTe superlattices 138 (1994) 877
Giftge, C., see Schikora 138 (1994) 8
Giftge, C., see Lang 138 (1994) 81
Giftge, C., see Brunthaler 138 (1994) 559
Gil, B., see Cloitre 133 (1993) 101
Gil, B., see Bouchara 138 (1994) 121
Gil, B., T. Cloitre, N. Briot, O. Briot, P. Boring and R.L. Aulombard, Photo-induced screening of the excitonic interaction in ZnSe–ZnTe type II strained-layer superlattices 138 (1994) 868
Gil, E., see Piffault 135 (1994) 11
Gill, W.N., see Lee 132 (1993) 226
Gill, W.N., see Kim 140 (1994) 308
Gill, W.N., see Kim 140 (1994) 315
Gille, P., M. Hollatz, H. Kleessen and M. Schenk, Axially linear slopes of composition for "delta" crystals 139 (1994) 165
Gillen, G., see Kaiser 137 (1994) 136
Gillet, M.F. and V. Matolín, Reflection high-energy electron diffraction study of growth and modification of small particle model catalyst: Pd on mica 134 (1993) 75
Gillies, D.C., see Biao 138 (1994) 219
Giriat, W., see Martinez 138 (1994) 913
Glass, R.C., L.O. Kjellberg, V.F. Tsvetkov, J.E. Sundgren and E. Janzén, Structural macro-defects in 6H-SiC wafers 132 (1993) 504
Gleitsmann, G., N. Ammann, J. Hermans, A. Schneider, J. Geurts, P. Karduck and M. Heuken, Comparison between gallium-implanted layers of ZnSe and ZnS_xSe_{1-x} by optical, electrical and electron beam characterization methods 138 (1994) 324
Gleitsmann, G., see Hoffmann 138 (1994) 379
Glenton, P.A., see Khan 134 (1993) 211
Glicksman, M.E., M.B. Koss, V.E. Fradkov, M.E. Rettenmayr and S.S. Mani, Quantification of crystal morphology 137 (1994) 1
Glicksman, M.E., see Singh 137 (1994) 155
Glidewell, C., see Hoare 137 (1994) 347
Gnanam, F.D., see Dhas 137 (1994) 295
Gnezdilov, V.P., see Webb 137 (1994) 405
Göbbels, M., see Markgraf 135 (1994) 253
Göbel, E.O., see Bertram 132 (1993) 179
Göbel, E.O., see Hellmann 138 (1994) 791
Godelaine, P.A., see Cloots 135 (1994) 496
Goede, O., see Heimbrodt 138 (1994) 601
Goede, O., see Pier 138 (1994) 889
Goncharov, V.A. and E.V. Markov, Numerical study of thermoconvection and dopant transport mechanisms in the process of Si growth by floating-zone technique under microgravity 139 (1994) 266
Goncharova, E.V., see Jakobson 138 (1994) 225
Gonda, S., see Okuno 136 (1994) 83
Gonda, S., see Marx 136 (1994) 204
Gonda, S., see Liu 136 (1994) 250
Gonda, S., see Asahi 136 (1994) 268
Gonda, S., see Kim 136 (1994) 310
González, L., see Mazuelas 131 (1993) 465
Goodhew, P.J., see Sun 132 (1993) 592
Goossen, K.W., see Cunningham 136 (1994) 282
Gopalakrishnan, N., R. Dhanasekaran and P. Ramasamy, Investigations on the two-dimensional nucleation and growth kinetics of InP vapour phase epitaxy 137 (1994) 235
Gorochov, O., see Kuhn 138 (1994) 448
Gorochov, O., see Qu'Hen 138 (1994) 1079
Gortenmulder, T.J., see Mihalik 134 (1993) 342

Goswami, D.P. and M.L. Kalra, A new approach to molecular synthesis and crystal growth of one-dimensional organic charge transfer complex TTF–TCNQ 135 (1994) 196
Göthelid, M., see Vaitkus 138 (1994) 545
Goto, S., H. Ohno, Y. Nomura, Y. Morishita and Y. Katayama, Adsorption of carbon-related species onto GaAs(001), (011), and (111) surfaces exposed to trimethylgallium 136 (1994) 104
Goto, T., see Iijima 135 (1994) 229
Gotoda, M., Y. Nomura, T. Isu and S. Maruno, Optical properties of InGaAs/InP double-heterostructures selectively grown by chemical beam epitaxy 136 (1994) 246
Gotoda, M., H. Sugimoto, Y. Nomura, T. Isu, M. Nunoshita and S. Maruno, Selectively embedded growth by chemical beam epitaxy for the fabrication of InGaAs/InP double-heterostructure lasers 140 (1994) 277
Gotoh, J., see Migita 138 (1994) 391
Gottlieb, M., see Singh 137 (1994) 155
Gourgon, C., B. Eriksson, L.S. Dang, H. Mariette and C. Vieu, Photoluminescence of CdTe/ZnTe semiconductor wires and dots 138 (1994) 590
Grabecki, G., T. Dietl, W. Plesiewicz, A. Lenard, T. Skośkiewicz, E. Kamińska and A. Piotrowska, Mesoscopic phenomena in a dilute magnetic semiconductor $Hg_{1-x-y}Cd_yMn_xTe$ 138 (1994) 481
Gräber, J., see Mörsch 136 (1994) 256
Graham, S. and P.W. Brown, The low temperature formation of octacalcium phosphate 132 (1993) 215
Grandjean, N. and J. Massies, Epitaxial growth of highly strained $In_xGa_{1-x}As$ on GaAs(001): the role of surface diffusion length 134 (1993) 51
Granger, R. and C.M. Pelletier, A prediction of the electron mobility in medium gap HgCdTe and HgZnTe solid solutions 138 (1994) 486
Granger, R., see Quemerais 138 (1994) 934
Granier, W., see Allègre 138 (1994) 998
Grant, R.W., see Wang 138 (1994) 508
Grattepain, C., see Kuhn 138 (1994) 448
Gravey, P., see Rzepka 138 (1994) 244
Greedan, J.E., see Dabkowski 132 (1993) 205
Greggi, J., see Hobgood 137 (1994) 181
Griesche, J., see Reichow 131 (1993) 277
Griesche, J., see Weidemann 133 (1993) 75
Griesche, J., N. Hoffmann and K. Jacobs, Surface engineering during molecular beam epitaxial growth of wide-gap II–VI structures 138 (1994) 55
Griesche, J., N. Hoffmann and K. Jacobs, On the mechanism of reflection high-energy electron diffraction oscillations studied by phase-locked epitaxy of ZnSe 138 (1994) 59
Griesche, J., see Heimbrodt 138 (1994) 601
Grill, R., see Belas 138 (1994) 940
Grill, R., see Höschl 138 (1994) 956
Grillo, D.C., see Hua 138 (1994) 367
Grillo, D.C., see Han 138 (1994) 464
Grillo, D.C., see Ding 138 (1994) 719
Grillo, D.C., see Salokatve 138 (1994) 1077
Grodzicka, E., W. Dobrowolski, J. Kossut, T. Story and B. Witkowska, Peculiarities of transport properties in semiconductors with resonant impurities: HgSe:Fe versus PbTe:Cr 138 (1994) 1034
Groshens, T.J., see Bicknell-Tassius 138 (1994) 425
Grote, N., see Reier 135 (1994) 463
Gruehn, R., see Lenz 137 (1994) 499
Grün, M., M. Hetterich, C. Klingshirn, A. Rosenauer, J. Zweck and W. Gebhardt, Strain relief and growth modes in wurtzite type epitaxial layers of CdSe and CdS and in CdSe/CdS superlattices 138 (1994) 150
Grün, M., see Langbein 138 (1994) 191
Grün, M., see Klingshirn 138 (1994) 786
Gu, G.D., K. Takamuka, N. Koshizuka and S. Tanaka, Growth and superconductivity of $Bi_{2.1}Sr_{1.9}Ca_{1.0}(Cu_{1-y}Fe_y)_2O_x$ single crystal 137 (1994) 472
Gu, Y.S., see Chai 135 (1994) 639
Guan, Z.P., S.H. Song, G.H. Fan, X.W. Fan, Y.G. Peng and Y.K. Wu, The study of lattice strain and high-resolution transmission electron 138 (1994) 534
Guan, Z.P., see Yang 138 (1994) 629
Guan, Z.P., see Zhang 138 (1994) 838
Guergouri, K. and R. Triboulet, Determination of the PbTe–MnTe pseudo-binary phase diagram on the Pb-rich side 132 (1993) 20
Guergouri, K., M.S. Ferah, R. Triboulet and Y. Marfaing, Study of the crystalline quality of CdTe, CdZnTe and CdMnTe substrates used for liquid phase epitaxy of $Cd_{0.7}Hg_{0.3}Te$ 139 (1994) 6
Guha, S., see DePuydt 138 (1994) 667
Guha, S., see Deleporte 138 (1994) 884
Guille, J., see Benaissa 131 (1993) 5
Guilloux-Viry, M., C. Thivet, A. Perrin, M. Sergent, M.G. Karkut, Crystal growth of (110) and (103) $YBa_2Cu_3O_7$ thin films in-situ deposited by laser ablation on (110) $SrTiO_3$ single-crystal substrates 132 (1993) 396
Gumlich, H.-E., see Pier 138 (1994) 889
Gumlich, H.-E., see Jung 138 (1994) 905
Gumlich, H.-E., see Schumann 138 (1994) 910
Gumlich, H.-E., see Zeinert 138 (1994) 1023
Gumlich, H.-E., see Bressler 138 (1994) 1028
Gumlich, H.-E., see Jung 138 (1994) 1066

Gunshor, R.L., see Hua 138 (1994) 367
Gunshor, R.L., see Han 138 (1994) 464
Gunshor, R.L., see Ding 138 (1994) 719
Gunshor, R.L., see Salokatve 138 (1994) 1077
Guo, H., see Yan 136 (1994) 306
Gupta, K.P., see Anselmo 131 (1993) 247
Gupta, K.P., see Anselmo 134 (1993) 116
Gupta, M.K., see Muthe 139 (1994) 323
Gupta, S.R., see Sharma 131 (1993) 565
Gurin, V.S. and M.V. Artemyev, CdS quantum dots in colloids and polymer matrices: electronic structure and photochemical properties 138 (1994) 993
Gusev, G.M., see Lubyshev 132 (1993) 533
Guthmann, C., see Mergy 134 (1993) 353
Gutowski, J., see Schmolke 138 (1994) 213
Gutowski, J., see Bäume 138 (1994) 266
Gutowski, J., see Nägele 138 (1994) 842
Gutowski, J., see Neukirch 138 (1994) 861
Gysling, H.J., see Wernberg 131 (1993) 176
Gysling, H.J., see Wernberg 140 (1994) 57

Haacke, S., N.T. Pelekanos, H. Mariette, A.P. Heberle, W.W. Rühle and M. Zigone, Exciton transfer dynamics in CdTe/(Cd,Zn)Te asymmetric double quantum well structures 138 (1994) 831
Haase, M.A., see DePuydt 138 (1994) 667
Haddad, G.I., see Chen 136 (1994) 50
Haddad, G.I., see Munns 136 (1994) 166
Haga, T., M. Ohishi, K. Imai, K. Kumazaki, K. Ohmori, H. Saito and Y. Abe, Characterization by ion-channeling of ZnSe grown by photo-assisted molecular beam epitaxy 132 (1993) 575
Hage-Ali, M., see Rzepka 138 (1994) 244
Hagedorn, M.S., see DePuydt 138 (1994) 667
Hagerott, M., see Ding 138 (1994) 719
Haggerty, J.S., see Sigalovsky 134 (1993) 313
Hagston, W.E., see Dhese 138 (1994) 140
Hahn, B., see Wolf 138 (1994) 412
Hahn, I., see Brion 134 (1993) 281
Hahn, S.R. and J.D. Parsons, Direct growth of $Hg_{1-x}Cd_xTe$ alloys in a cold-wall, annular reactant inlet inverted-vertical organometallic vapor phase epitaxy reactor at 300°C 134 (1993) 90
Haile, S.M., B.J. Wuensch, T. Siegrist and R.A. Laudise, Hydrothermal synthesis of new alkali silicates. I. Potassium neodymium phases 131 (1993) 352
Haile, S.M., B.J. Wuensch and R.A. Laudise, Hydrothermal synthesis of new alkali silicates. II. Sodium neodymium and sodium yttrium phases 131 (1993) 373
Hails, J.E., see Cheng 135 (1994) 409
Haller, E.E., see Wolk 138 (1994) 1071
Halpern, J.B., see Seki 132 (1993) 25
Halsall, M.P., see Wolverson 138 (1994) 656
Hamacher, R.D., see Singh 135 (1994) 619
Hamacher, R.D., see Singh 139 (1994) 158
Hamada, T., see Hariu 136 (1994) 157
Hammar, M., see Vaitkus 138 (1994) 545
Han, J., see Hua 138 (1994) 367
Han, J., Y. Fan, M.D. Ringle, L. He, D.C. Grillo, R.L. Gunshor, G.C. Hua and N. Otsuka, Ohmic contacts and transport properties in ZnSe-based heterostructures 138 (1994) 464
Han, J., see Ding 138 (1994) 719
Han, J., see Salokatve 138 (1994) 1077
Han, Q. and J.D. Hunt, Particle pushing: the concentration of particles near a solid interface during downward flow 140 (1994) 398
Han, Q. and J.D. Hunt, Particle pushing: the attachment of particles on the solid–liquid interface during fluid flow 140 (1994) 406
Han, T.J.P., see Sharp 140 (1994) 79
Han, T.P.J., see Sharp 131 (1993) 457
Han, T.S., see Oka 137 (1994) 479
Han, Z.Y., see Yoon 134 (1993) 240
Handa, S., see Mochizuki 135 (1994) 259
Hannan, M., see Pandey 137 (1994) 268
Hanssen, L.M., see Snail 137 (1994) 676
Hansson, G.V., see Larsson 134 (1993) 203
Hao Zhaoyin, Chen Yufei and Chen Lizue, Relation between recrystallized graphite and diamond growth 135 (1994) 370
Hao Zhaoyin, He Yixing, Chen Yufei and Wang Derong, Nucleation and growth of diamond 140 (1994) 441
Happ, M., see Heimbrodt 138 (1994) 601
Hara, K., see Yanashima 138 (1994) 755
Harada, Y., see Chichibu 140 (1994) 388
Harbison, J.P., see Philips 140 (1994) 249
Harde, P., see Reier 135 (1994) 463
Hariu, T., S. Yamauchi, S.F. Fang, T. Ohshima and T. Hamada, Plasma-cracked supply of group V and group VI elements for low temperature epitaxy 136 (1994) 157
Harlow, M.J., W.J. Duncan, I.F. Lealman and P.C. Spurdens, Chromium-doped semi-insulating InP grown by metalorganic vapour phase epitaxy 140 (1994) 19
Harp, G.R., see Farrow 133 (1993) 47
Harrington, M.D., see DeLucas 135 (1994) 183
Harris, B.G., see DeLucas 135 (1994) 183
Harris, K.A., see Meyer 138 (1994) 981
Harris, M., J. Larkin, J.E. Cormier and A.F. Armington, Optical studies of Czochralski and hydrothermal bismuth silicate 137 (1994) 128
Harris, M., see Bliss 137 (1994) 145

Harris, S., Effects of impurity doping on terrace width stability 135 (1994) 354
Harsch, W.C., see Boone 139 (1994) 27
Harsdorff, M., see Heyn 133 (1993) 241
Hart, L., see Zhang 131 (1993) 300
Harter, I., P. Dusserre, T. Duffar, J.-Ph. Nabot and N. Eustathopoulos, Wetting of III–V melts on crucible materials 131 (1993) 157
Hartman, P., see Petit 137 (1994) 585
Hartmann, H., see Krause 138 (1994) 75
Hartmann, H. and D. Siche, ZnSe single crystal growth by the method of dissociative sublimation 138 (1994) 260
Hartnagel, H.L., see Eisenbach 135 (1994) 129
Harvanka, M., see Červeň 131 (1993) 546
Harvey, A.J., see Bangert 132 (1993) 231
Hashimoto, A., see Yamamoto 137 (1994) 415
Hashimoto, T., see Yoshimoto 136 (1994) 89
Hastings, M.P., C.D. Maxey, B.E. Matthews, N.E. Metcalfe, P. Capper, C.L. Jones and I.G. Gale, Electron beam induced current assessment of doped and diffused junctions in epitaxial $Cd_xHg_{1-x}Te$ 138 (1994) 917
Hata, S., see Uchiki 138 (1994) 873
Hatakeyama, I., see Sugiyama 134 (1993) 255
Hatakoshi, G., see Itaya 138 (1994) 768
Hatayama, T., Y. Tarui, T. Yoshinobu, T. Fuyuki and H. Matsunami, Controlled carbonization of Si(001) surface using hydrocarbon radicals in ultrahigh vacuum 136 (1994) 333
Hattori, T., see Taguchi 134 (1993) 147
Hauck, see Bickmann 131 (1993) 133
Hauksson, I., see Prior 138 (1994) 94
Hauksson, I., see Mullins 138 (1994) 357
Hauksson, I., see Wang 138 (1994) 647
Hauksson, I., see Kawakami 138 (1994) 759
Hausleitner, H., see Schikora 138 (1994) 8
Hayafuji, N., see Mihashi 133 (1993) 281
Hayafuji, N., see Kizuki 134 (1993) 35
Hayashi, M., see Inoue 138 (1994) 182
Hayashi, T., see Miyake 134 (1993) 174
Hayes, T.R., see Karlicek, Jr. 131 (1993) 204
He, Changzhen, see Mei 132 (1993) 609
He Chongfan, see Xu 133 (1993) 267
He Chongfan, see Xu 134 (1993) 337
He, L., see Hua 138 (1994) 367
He, L., see Han 138 (1994) 464
He, L., see Ding 138 (1994) 719
He, L., see Salokatve 138 (1994) 1077
He, X.Z., see Chen 140 (1994) 287
He Yixing, see Hao 140 (1994) 441
Heady, W.E., see Gallagher 138 (1994) 970
Heazle, K.D., see Leech 139 (1994) 247
Heberle, A.P., see Haacke 138 (1994) 831
Heberlein, J., see Snail 137 (1994) 676
Hegarty, J., see Doran 138 (1994) 826
Heimbrodt, W., O. Goede, V. Weinhold, M. Happ, R. Knoch, K. Hieke, N. Hoffmann, J. Griesche, K. Jacobs, F. Neugebauer, D. Suisky and J. Röseler, Magneto-optical study of ZnSe/(Zn,Mn)Se and ZnSe/(Zn,Cd,Mn)Se quantum well structures and superlattices 138 (1994) 601
Heimbrodt, W., see Pier 138 (1994) 889
Heime, K., see Behet 135 (1994) 434
Heinecke, H., Selective area growth of III/V materials in metalorganic molecular beam epitaxy (chemical beam epitaxy) 136 (1994) 18
Heinke, H., see Waag 131 (1993) 607
Heinke, H., M.O. Möller, D. Hommel and G. Landwehr, Relaxation and mosaicity profiles in epitaxial layers studied by high resolution X-ray diffraction 135 (1994) 41
Heinke, H., A. Waag, M.O. Müller, M.M. Regnet and G. Landwehr, Unusual strain in homoepitaxial CdTe(001) layers grown by molecular beam epitaxy 135 (1994) 53
Heinke, H., see Ruppert 138 (1994) 48
Heinke, H., see Waag 138 (1994) 155
Heinke, H., see Waag 138 (1994) 437
Heinke, H., see Einfeldt 138 (1994) 471
Heinrichs, W., Y. Georgalis, H. Schönert and W. Sänger, Influence of cyclic temperature changes on protein precrystalline aggregates 133 (1993) 196
Heitz, R., see Krause 138 (1994) 75
Heitz, R., see Hoffmann 138 (1994) 379
Heitz, R., see Broser 138 (1994) 809
Heitz, R., see Fricke 138 (1994) 815
Heitz, R., see Presser 138 (1994) 820
Heitz, R., see Hoffmann 138 (1994) 1073
Helbing, R. and R.S. Feigelson, Growth of SrS single crystals by physical vapor transport 137 (1994) 150
Helbing, R. and R.S. Feigelson, SrS single crystals grown by physical vapor transport 138 (1994) 1075
Hellmann, R., M. Koch, J. Feldmann, S.T. Cundiff, E.O. Göbel, D.R. Yakovlev, A. Waag and G. Landwehr, Dephasing excitons in a $CdTe/Cd_{0.86}Mn_{0.14}Te$ multiple quantum well 138 (1994) 791
Henderson, B., see Sharp 131 (1993) 457
Henderson, B., see Sharp 140 (1994) 79
Henderson, T.S., see Beam 136 (1994) 1
Hendrikx, R.W.A., see Mihalik 134 (1993) 342
Henneberger, F., see Reichow 131 (1993) 277
Henneberger, F., see Schülzgen 138 (1994) 575
Henneberger, F., see Puls 138 (1994) 1004
Hennessy, J., see Knight 134 (1993) 19
Hennig, M., M. Visanji, W. Weber, H. Janczikowski, A. Plaas-Link and C. Betzel, COSIMA – protein crystal growth facility for automatic processing on unmanned satellites 135 (1994) 513
Henninger, B., see Pier 138 (1994) 889

Henry, D., see Kaddeche 135 (1994) 341
Herberholz, R., see Taylor 132 (1993) 61
Hermans, J., see Gleitsmann 138 (1994) 324
Hermans, J., J. Woitok, W. Schiffers, J. Geurts, A. Schneider, M. Scholl, J. Söllner and M. Heuken, Optical and X-ray analysis of ZnS_xSe_{1-x}/ZnSe superlattices grown on GaAs by metalorganic vapour phase epitaxy 138 (1994) 612
Hernandes, A.C., see Prokofiev 137 (1994) 528
Herrmann, K.H., see Tomm 138 (1994) 175
Herrnberger, H., see Keller 140 (1994) 33
Herve, D., see Legras 138 (1994) 585
Hetterich, M., see Grün 138 (1994) 150
Hetterich, M., see Langbein 138 (1994) 191
Hetterich, M., see Klingshirn 138 (1994) 786
Heuken, M., see Söllner 138 (1994) 35
Heuken, M., see Gleitsmann 138 (1994) 324
Heuken, M., see Tönnies 138 (1994) 362
Heuken, M., see Hoffmann 138 (1994) 379
Heuken, M., see Taudt 138 (1994) 418
Heuken, M., see Hermans 138 (1994) 612
Heuken, M., see Klingshirn 138 (1994) 786
Heuken, M., see Fricke 138 (1994) 815
Heuken, M., see Nägele 138 (1994) 842
Heyn, Ch. and M. Harsdorff, Flux control and calibration of an As effusion cell in a molecular beam epitaxy system for GaAs and AlGaAs with a qudrupole mass spectrometer 133 (1993) 241
Heywood, B.R., see Walsh 133 (1993) 1
Hibiya, T., see Watanabe 133 (1993) 23
Hibiya, T., see Kakimoto 139 (1994) 197
Hidaka, T., see Miyakoshi 136 (1994) 152
Hieke, K., see Heimbrodt 138 (1994) 601
Hieke, K., see Pier 138 (1994) 889
Hien, N.T., see Li 135 (1994) 481
Higa, K.T., see Bicknell-Tassius 138 (1994) 425
Higgins, W.M., see Bliss 137 (1994) 145
Higuchi, H., see Chichibu 131 (1993) 551
Hildmann, B.O., see Möller 131 (1993) 165
Hirai, T., see Zhang 132 (1993) 337
Hiramatsu, K., see Detchprohm 137 (1994) 170
Hirano, M., see Ishibara 137 (1994) 375
Hirano, M., see Zeng 140 (1994) 148
Hirano, R., T. Kanazawa and S. Katsura, Microdefects in InP crystals grown by the liquid-encapsulated Czochralski method 134 (1993) 81
Hiraoka, Y.S. and M. Mashita, Ab initio study on the reaction of trimethylgallium with hydrogen molecule 136 (1994) 94
Hirata, A., M. Tachibana, T. Sugimoto, Y. Okano and T. Fukuda, Control of crystal–melt interface shape during growth of lithium niobate single crystal 131 (1993) 145
Hirata, S., see Tomomura 138 (1994) 764
Hiyamizu, S., see Marx 136 (1994) 204
Hlídek, P., see Höschl 138 (1994) 956
Ho, E., see Lu 138 (1994) 1
Hoare, R.D., M.E. Pemble, I.M. Povey, J.O. Williams, D.F. Foster, C. Glidewell and D.J. Cole-Hamilton, The use of hex-5-enylarsine as a chemically designed precursor to probe the mechanisms of the metalorganic vapour phase epitaxy growth of gallium arsenide; consequences for reactor design 137 (1994) 347
Hobgood, H.M., D.L. Barrett, J.P. McHugh, R.C. Clarke, S. Sriram, A.A. Burk, J. Greggi, C.D. Brandt, R.H. Hopkins and W.J. Choyke, Large diameter 6H-SiC for microwave device applications 137 (1994) 181
Hoerstel, W., see Tomm 138 (1994) 175
Hoffman, M.J., see Krämer 140 (1994) 157
Hoffmann, A., see Krause 138 (1994) 75
Hoffmann, A., R. Heitz, B. Lummer, Ch. Fricke, V. Kutzer, I. Broser, W. Taudt, G. Gleitsmann and M. Heuken, Incorporation of nitrogen in ZnSe grown by metalorganic vapour phase epitaxy 138 (1994) 379
Hoffmann, A., see Pohl 138 (1994) 385
Hoffmann, A., see Taudt 138 (1994) 418
Hoffmann, A., see Broser 138 (1994) 809
Hoffmann, A., see Fricke 138 (1994) 815
Hoffmann, A., see Presser 138 (1994) 820
Hoffmann, A., B. Lummer, L. Eckey, V. Kutzer, Ch. Fricke, R. Heitz, I. Broser, E. Kurtz, B. Jobst and D. Hommel, The influence of nitrogen on the p-conductivity in ZnSe epilayers grown by molecular beam epitaxy 138 (1994) 1073
Hoffmann, D.M., see Zimmermann 131 (1993) 276
Hoffmann, N., see Reichow 131 (1993) 277
Hoffmann, N., see Griesche 138 (1994) 55
Hoffmann, N., see Griesche 138 (1994) 59
Hoffmann, N., see Heimbrodt 138 (1994) 601
Höfler, G.E., see DePuydt 138 (1994) 667
Hofmann, D.M., see Fiederle 138 (1994) 529
Hofmeister, A. Yariv and A. Agranat, Growth and characterization of the perovskite $K_{1-y}Li_yTa_{1-x}Nb_xO_3$:Cu 131 (1993) 486
Hohl, H., see Oglesby 137 (1994) 289
Hollatz, M., see Gille 139 (1994) 165
Hollfelder, M., see Mörsch 136 (1994) 256
Holmes, K., see Rajendran 137 (1994) 77
Holy, V., see Lang 138 (1994) 81
Hommel, D., see Heinke 135 (1994) 41
Hommel, D., see Ruppert 138 (1994) 48
Hommel, D., B. Jobst, T. Behr, G. Bilger, V. Beyersdorfer, E. Kurtz and G. Landwehr, Correlation between electrical and structural properties of chlorine doped ZnSe epilayers grown by molecular beam epitaxy 138 (1994) 331

Hommel, D., see Tönnies 138 (1994) 362
Hommel, D., see Waag 138 (1994) 437
Hommel, D., see Einfeldt 138 (1994) 471
Hommel, D., see Neukirch 138 (1994) 861
Hommel, D., see Hoffmann 138 (1994) 1073
Hommel, D., E. Kurtz, T. Behr, A. Jakobs, B. Jobst, S. Scholl, K. Schüll, V. Beyersdorfer, G. Landwehr and H. Cerva, Studies of blue-green laser structures with asymmetric and pseudomorphic ZnSe wave guides 138 (1994) 1076
Honjo, H. and S. Ohta, Regular tip-splitting growth of an NH_4Cl dendrite 131 (1993) 111
Höök, M., see Christoffersen 137 (1994) 545
Hopkins, R.H., see Hobgood 137 (1994) 181
Horie, T., Y. Takakuwa, T. Yamaguchi and N. Miyamoto, Hydrogen desorption rate and surface hydrogen coverage during isothermal annealing for Si_2H_6-adsorbed Si(100) surfaces 136 (1994) 344
Horrigan, J., see Bliss 137 (1994) 145
Horsburgh, G., see Prior 138 (1994) 94
Horsburgh, G., see Mullins 138 (1994) 357
Horsburgh, G., see Wang 138 (1994) 647
Höschl, P., see Belas 138 (1994) 940
Höschl, P., R. Grill, J. Svoboda, P. Hlídek, P. Moravec, J. Franc and E. Belas, Bridgman growth of $Hg_{1-x}Cd_xTe$ from melt of constant composition 138 (1994) 956
Hoshikawa, K., see Okano 131 (1993) 616
Hoshikawa, K., see Matsumoto 132 (1993) 348
Hoshikawa, K., see Kang 135 (1994) 623
Hoshikawa, K., see Machida 137 (1994) 82
Hoshikawa, K., see Machida 137 (1994) 516
Hoshikawa, K., see Kang 140 (1994) 435
Hosoi, N., see Ohshita 131 (1993) 495
Hosomi, K., see Mozume 136 (1994) 287
Hou Wenbo, Yuan Duorong, Xu Dong, Zhang Nan, Yu Wentao, Liu Mingguo, Tao Xutang, Sun Suoying and Jiang Minhua, A new organometallic nonlinear optical material – triallylthiourea mercury bromide (ATMB) crystal: growth and structure 133 (1993) 71
Houdré, R., see Rudra 136 (1994) 278
Houghton, D.C., M. Davies, T. Sudersena Rao and M. Dion, Comparison of chemical beam epitaxy and metalorganic chemical vapour deposition for highly strained multiple quantum well InGaAsP/InP 1.5 μm lasers 136 (1994) 56
Houng, Y.M., M.R.T. Tan, B.W. Liang, S.Y. Wang, L. Yang and D.E. Mars, InGaAs (0.98 μm)/GaAs vertical cavity surface emitting laser grown by gas-source molecular beam epitaxy 136 (1994) 216
House, J.L., see Lu 138 (1994) 1
Hovestad, A., see Balzuweit 131 (1993) 518
Hovinen, M., see Salokatve 138 (1994) 1077
Hsieh, J.Y., see Hwang 132 (1993) 523
Hsu, C.C., T.K.S. Wong and I.H. Wilson, Surface morphology of metalorganic vapour phase epitaxy grown InP observed by atomic force microscopy 133 (1993) 185
Hu, J., see Moore 136 (1994) 230
Hu, W.R., see Xiong 133 (1993) 155
Hu, Z.W., see Zhang 132 (1993) 200
Hua, G.C., N. Otsuka, D.C. Grillo, J. Han, L. He and R.L. Gunshor, Phase separation in $ZnSe_{1-x}S_x$ and $Zn_{1-y}Mg_ySe_{1-x}S_x$ layers grown by molecular beam epitaxy 138 (1994) 367
Hua, G.C., see Han 138 (1994) 464
Huang, J.C.A., Y. Liou, H.L. Liu and Y.J. Wu, Epitaxial growth and structure characterization of single-crystal Co(11$\bar{2}$0) films on Cr(100) surfaces 139 (1994) 363
Huang, J.K., Y.S. Huang and T.R. Yang, The preparation and characterization of $RuTe_2$ single crystals 135 (1994) 224
Huang, K.T., C.T. Chiu, R.M. Cohen and G.B. Stringfellow, InAsBi alloys grown by organometallic vapor phase epitaxy 134 (1993) 29
Huang, W., see Jain 138 (1994) 709
Huang Weidong, Geng Xingguo and Zhou Yaohe, Primary spacing selection of constrained dendritic growth 134 (1993) 105
Huang, Y., see Yan 136 (1994) 306
Huang, Yidong, see Tu 135 (1994) 636
Huang, Y.S., see Huang 135 (1994) 224
Hubert, J.A., A.L. Fripp, Jr. and C.S. Welch, Resolution of the discrepancy between temperature indicated interface and radiographically determined interface in a vertical Bridgman furnace 131 (1993) 75
Hubík, P., see Šestáková 132 (1993) 345
Hughes, S.H., see DeLucas 135 (1994) 183
Hughes, Wm.C., J.C. Austin and M.L. Swanson, The thermodynamics of indium–vacancy pairs in $Hg_{0.79}Cd_{0.21}Te$ 138 (1994) 1040
Hultman, L., M. Shinn, P.B. Mirkarimi and S.A. Barnett, Characterization of misfit dislocations in epitaxial (001)-oriented TiN, NbN, VN, and (Ti,Nb)N film heterostructures by transmission electron microscopy 135 (1994) 309
Humenberger, J., see Lang 138 (1994) 81
Humphrey, D.A., see Chen 136 (1994) 221
Humphreys, C.J., see Brown 138 (1994) 538
Hunt, J.D., see Han 140 (1994) 398
Hunt, J.D., see Han 140 (1994) 406
Hunter, A.T., see Swenberg 138 (1994) 692
Huntley, D.A. and S.H. Davis, Thermal effects in rapid directional solidification:

weakly-nonlinear analysis of oscillatory instabilities 132 (1993) 141
Huo, C., see Xu 137 (1994) 538
Huppert, H.E., see Chiareli 139 (1994) 134
Hurle, D.T.J., see Joyce 132 (1993) 1
Hutchinson, J.W., see Bhihe 137 (1994) 86
Hutchison, J.L., see Benaissa 131 (1993) 5
Hüttl, B., see Troppenz 138 (1994) 1017
Hvam, J.M., see Erland 138 (1994) 800
Hwang, C.C., C.S. Wu and J.Y. Hsieh, The effect of curved interface shape on thermal stress during Czochralski crystal growth 132 (1993) 523
Hwang, C.-S., see Kaiser 137 (1994) 136
Hwang, J.-S., B.J. Koo, I.H. Chung, H.L. Park and C.H. Chung, Growth of CdTe/CdZnTe strained-layer single quantum wells by modified hot-wall epitaxy method and their properties 138 (1994) 131
Hwang, N.M., Thermodynamic analysis of the chemical vapor deposition of diamond in the C–H, C–O and C–H–O systems 135 (1994) 165

Ichida, A., see Kuwabara 138 (1994) 964
Ichikawa, S., N. Matsumura, K. Yamawaki, K. Senga and J. Saraie, Migration enhancement on ZnSe surface in photoassisted molecular beam epitaxy and long duration time of the effects 138 (1994) 14
Ichino, K., T. Onishi, Y. Kawakami, Sz. Fujita and Sg. Fujita, Growth of ZnS and ZnCdSSe alloys on GaP using an elemental sulfur source by molecular beam epitaxy 138 (1994) 28
Ida, M., see Kobayashi 140 (1994) 432
Iga, K., see Miyamoto 136 (1994) 210
Iga, K., see Inaba 136 (1994) 297
Iga, K., see Yokouchi 136 (1994) 302
Iga, R., see Sugiura 136 (1994) 64
Iga, R., see Mitsuhara 136 (1994) 195
Iga, R., T. Yamada and H. Sugiura, A new technique for fabricating InGaAsP superlattice by laser-assisted metalorganic molecular beam epitaxy 136 (1994) 273
Iguchi, Y., see Waseda 139 (1994) 357
Iida, F., see Takojima 138 (1994) 633
Iida, S., see Uchiki 138 (1994) 873
Iijima, H., H. Kamemizu, N. Wakamatsu, T. Goto, Y. Doi and Y. Moriwaki, Effects of CO_3^{2-} ion on the formation of octacalcium phosphate at pH 7.4 and 37°C 135 (1994) 229
Iijima, K., see Iijima 140 (1994) 91
Iijima, M., Y. Moriwaki and Y. Kuboki, In vitro crystal growth of oxtacalcium phosphate on type I collagen fiber 137 (1994) 553
Iijima, M., K. Iijima, Y. Moriwaki and Y. Kuboki, Oriented growth of octacalcium phosphate crystals on type I collagen fibrils under physiological conditions 140 (1994) 91
Iishi, K., see Sakata 135 (1994) 555
Ikarashi, T., see Aoyama 136 (1994) 349
Ikeya, T., see Okano 131 (1993) 616
Ikuta, K., J. Osaka and H. Yokoyama, Morphology on GaAs surfaces grown by metalorganic chemical vapor deposition and molecular beam epitaxy 136 (1994) 114
Ilegems, M., see Carlin 131 (1993) 387
Ilegems, M., see Rudra 136 (1994) 173
Ilegems, M., see Rudra 136 (1994) 278
Illing, M., G. Bacher, A. Forchel, A. Waag, T. Litz and G. Landwehr, Fabrication and optical characterization of wet chemically etched CdTe/CdMgTe wires 138 (1994) 638
Illingworth, R., see Sharp 131 (1993) 457
Illingworth, R., see Sharp 140 (1994) 79
Imai, K., see Haga 132 (1993) 575
Imai, K., see Takojima 138 (1994) 633
Imaizumi, M., Y. Endoh, K. Ohtsuka and T. Isu, Growth of n- and p-ZnSe by gas source molecular beam epitaxy using metal Zn and H_2Se 136 (1994) 366
Imoto, S., S. Kimura, Y. Anzai and Y. Kuwano, Physical properties of the BaB_2O_4 melt 135 (1994) 279
Inaba, T., see Matsumoto 138 (1994) 403
Inaba, Y., T. Uchida, N. Yokouchi, T. Miyamoto, K. Mori and F. Koyama and K. Iga, Growth of GaInAs(P)/InP multi-quantum barrier by chemical beam epitaxy 136 (1994) 297
Inaba, Y., see Yokouchi 136 (1994) 302
Inagaki, K., see Suzuki 138 (1994) 199
Ingle, N.K., see Mountziaris 131 (1993) 283
Inoue, K., see Chani 132 (1993) 173
Inoue, K., see Chani 132 (1993) 335
Inoue, K., see Chani 133 (1993) 181
Inoue, K., see Marx 136 (1994) 204
Inoue, K., see Liu 136 (1994) 250
Inoue, K., T. Kuroda, F. Minami, K. Yoshida, M. Hayashi, Study of electronic structure in strained ZnSe/GaAs thin films by nonlinear optical and Brewster-angle reflection spectroscopies 138 (1994) 182
Inoue, K., see Minami 138 (1994) 796
Inoue, M., see Yano 131 (1993) 620
Inoue, M., see Kim 136 (1994) 310
Inoue, T., T. Ohsuna, Y. Obara, Y. Yamamoto, M. Satoh and Y. Sakurai, Stripe-shaped facetted morphology and domain structure of epitaxial CeO_2(110) layers on Si(100) substrates 131 (1993) 347
Iradi, T., see Laudise 140 (1994) 51
Ishibashi, A. and Y. Mori, Advances in blue laser diodes 138 (1994) 677
Ishida, K., see Taki 131 (1993) 13

Ishihara, T., K. Murata, M. Sato, N. Kito and M. Hirano, New horizontal boat growth method of undoped semi-insulating GaAs with low dislocation density 137 (1994) 375
Ishii, K., see Kagawa 139 (1994) 309
Ishii, M., see Sakaki 133 (1993) 329
Ishikawa, H., see Mashita 131 (1993) 61
Ishizaka, K., see Kanie 138 (1994) 145
Ishizawa, Y., see Otani 140 (1994) 451
Isomura, S., see Chichibu 131 (1993) 551
Isomura, S., see Chichibu 140 (1994) 388
Isu, T., see Gotoda 136 (1994) 246
Isu, T., see Imaizumi 136 (1994) 366
Isu, T., see Gotoda 140 (1994) 277
Itaya, K., see Suzuki 133 (1993) 303
Itaya, K., H. Sugawara and G. Hatakoshi, InGaAlP visible light laser diodes and light-emitting diodes 138 (1994) 768
Ito, T., see Lee 134 (1993) 247
Ito, T., see Oka 137 (1994) 479
Ito, T., see Nagai 140 (1994) 65
Itoh, N., see Lee 134 (1993) 247
Itoyama, W., see Sakata 135 (1994) 555
Iwai, A., see Chichibu 131 (1993) 551
Iwai, Y., see Yano 131 (1993) 620
Iwanaga, H., M. Fujii and S. Takeuchi, Growth model of tetrapod zinc oxide particles 124 (1993) 275
Iwanaga, H., see Mochizuki 131 (1993) 41
Iwasa, I., see Ota 133 (1993) 207
Iwasa, I., see Ota 135 (1994) 646
Iwashita, T., see Matsumoto 138 (1994) 63
Iwata, H., see Suzuki 134 (1993) 67
Izumi, S., N. Yoshida, H. Takano, K. Nishitani and M. Otsubo, Study on the accumulated impurities at the epilayer/substrate interface and their influence on the leakage current of metal–semiconductor–field effect transistors 133 (1993) 123

Jääskeläinen, T., see Prokofiev 137 (1994) 528
Jacob, K.T., see Waseda 139 (1994) 357
Jacobo-Molina, A., see DeLucas 135 (1994) 183
Jacobs, K., see Reichow 131 (1993) 277
Jacobs, K., see Weidemann 133 (1993) 75
Jacobs, K., see Griesche 138 (1994) 55
Jacobs, K., see Griesche 138 (1994) 59
Jacobs, K., see Rudolph 138 (1994) 249
Jacobs, K., see Heimbrodt 138 (1994) 601
Jacobs, K., see Zemke 139 (1994) 37
Jahn, E., see Reier 135 (1994) 463
Jain, F., W. Huang, R. LaComb, C. Chung and G. Drake, Optical modulators using quantum confined Stark effect in ZnSe based multiple quantum well structures 138 (1994) 709
Jakobs, A., see Hommel 138 (1994) 1076
Jakobson, M.A., V.D. Kagan, R.P. Seisyan and E.V. Goncharova, Optical properties of "pure" CdS and metal–insulator–semiconductor structures on CdS at electrical operation 138 (1994) 225
Jamgotchian, H., R. Trivedi and B. Billia, Interface dynamics and coupled growth in directional solidification in presence of bubbles 134 (1993) 181
Jan, W., see Cunningham 136 (1994) 282
Janczikowski, H., see Hennig 135 (1994) 513
Jang, D.-H., see Yoo 132 (1993) 43
Janimak, J.J., see Point 131 (1993) 501
Janzén, E., see Glass 132 (1993) 504
Jaroszyński, J., see Dhese 138 (1994) 443
Jayaraman, D., see Kumar 137 (1994) 535
Jayatirtha, H.N., see George 137 (1994) 299
Jayavel, R., C. Sekar, P. Murugakoothan, C.R. Venkateswara Rao, C. Subramanian and P. Ramasamy, Growth of large size single crystals and whiskers of $Bi_2Sr_2CaCu_2O_8$ by step-cooling method 131 (1993) 105
Jayavel, R., A. Thamizhavel, P. Murugakoothan, C.R. Venkateswara Rao, C. Subramanian and P. Ramasamy, Growth of large size twin free $YBa_2Cu_3O_{7-\delta}$ single crystals by a temperature gradient technique 137 (1994) 273
Jensen, J.E., see Rajavel 138 (1994) 19
Jensen, K.F., see Einset 132 (1993) 483
Jensen, K.F., see Bohling 136 (1994) 118
Jensen, K.F., see Skromme 138 (1994) 338
Jeon, M.H., see Calhoun 138 (1994) 352
Jeon, M.H., see Salokatve 138 (1994) 1077
Jerman, Z., see Rieger 137 (1994) 595
Ji, W., A.K. Kukaswadia, Z.C. Feng, S.H. Tang and P. Becla, Nonlinear refraction and optical limiting in bulk ZnTe crystal 138 (1994) 187
Ji, Y., J. Liang and S. Xie, Phase relations in the system $BaO–Nd_2O_3–B_2O_3$ ($B_2O_3 \geq 50$ mol%) and crystal growth of $NdBaB_9O_{16}$ 137 (1994) 521
Jiang, M.H., see Wang 139 (1994) 86
Jiang Minhua, see Hou 133 (1993) 71
Jiang, S.S., see Zhang 132 (1993) 200
Jiang Xiaobo, see Li 139 (1994) 327
Jiang Yandao, see Li 139 (1994) 327
Jiang, Z.K., see Soga 132 (1993) 414
Jie, W., see Liang 135 (1994) 561
Jimbo, T., see Soga 132 (1993) 134
Jimbo, T., see Soga 132 (1993) 414
Jobst, B., see Hommel 138 (1994) 331
Jobst, B., see Hoffmann 138 (1994) 1073
Jobst, B., see Hommel 138 (1994) 1076
Johnson, M., see Watring 140 (1994) 41
Johnston, P.N., see Russo 131 (1993) 124
Jones, A.C., see Smith 134 (1993) 140
Jones, A.C., see Joyce 135 (1994) 31
Jones, A.C., J. Auld, S.A. Rushworth and G.W. Critchlow, Growth of aluminium

films by low pressure chemical vapour deposition using tritertiarybutylaluminium 135 (1994) 285
Jones, A.C., see Abernathy 136 (1994) 11
Jones, A.C., see Foord 136 (1994) 127
Jones, A.C., see Davies 136 (1994) 133
Jones, C.L., see Hastings 138 (1994) 917
Jones, E.D., J.C. Clark, J.B. Mullin and A.W. Brinkman, Studies on the diffusion of zinc in cadmium telluride at 800°C 138 (1994) 274
Jones, E.D., J. Malzbender, J.B. Mullin and N. Shaw, Incorporation of iodine into CdTe by diffusion 138 (1994) 279
Jones, H., see Liang 135 (1994) 561
Jones, I.P., see Cheng 135 (1994) 409
Jones, T.S., see Kaneko 136 (1994) 99
Jönsson, J., see Deppert 133 (1993) 296
Jordan, A.S. and A. Robertson, Copyrolysis of AsH_3 and PH_3 in the epitaxial growth of ternary and quaternary III–V alloys 137 (1994) 224
Joshin, K., see Bove 136 (1994) 261
Joshkin, V.A., S.R. Oktyabrsky, I.A. Bogonin and A.A. Orlikovsky, Low temperature preannealing for carbon removal from Si surface in GaAs-on-Si molecular beam epitaxial growth 132 (1993) 209
Jou, M.-J., see Lin 137 (1994) 400
Jowett, J.M., see Bangert 132 (1993) 231
Joyce, B.A., see Zhang 131 (1993) 300
Joyce, B.A., see Zhang 132 (1993) 331
Joyce, B.A., see Kaneko 136 (1994) 99
Joyce, G.C., D.T.J. Hurle and Q.A.E. Vaughan, Novel development of the weighing method for automatic Czochralski crystal growth of semiconductors 132 (1993) 1
Joyce, T.B., T. Pfeffer, T.J. Bullough and A.C. Jones, Metalorganic sulphur sources for the doping of GaAs grown by chemical beam epitaxy 135 (1994) 31
Joyce, T.B.F., see Sun 132 (1993) 592
Juhel, M., see Alexandre 136 (1994) 235
Jung, Ch., H.-Ch. Mertins, S. Katholy and H.-E. Gumlich, The influence of exchange interaction on the composition dependence of interband transitions in $Zn_{1-x}Mn_xSe$ 138 (1994) 905
Jung, Ch., H.-Ch. Mertins and H.-E. Gumlich, The influence of crystal structure on the Zn 3d states in $Zn_{1-x}Mn_xS$ 138 (1994) 1066
Jungnickel, V., see Puls 138 (1994) 1004
Junno, B., G. Paulsson, M. Miller and L. Samuelson, Reflection high energy electron diffraction and reflectance difference studies of surface anisotropy in InGaAs chemical beam epitaxy on flat and vicinal (001)GaAs 136 (1994) 78
Juodžbalis, D., see Gavryushin 138 (1994) 924
Juza, P., see Neukirch 138 (1994) 849

Kaddeche, S., H. Ben Hadid and D. Henry, Macrosegregation and convection in the horizontal Bridgman configuration. I. Dilute alloys 135 (1994) 341
Kagan, V.D., see Jakobson 138 (1994) 225
Kagawa, H., M. Sagawa, A. Kakuta, M. Kaji, H. Nakayama and K. Ishii, Single crystal growth and characterization of a new organic nonlinear optical material: 8-(4′-acetylphenyl)-1,4-dioxa-8-azaspiro[4.5]decane (APDA) 139 (1994) 309
Kageyama, S., see Mihashi 133 (1993) 281
Kahn, A., see Chen 138 (1994) 1078
Kaigawa, R., see Kaito 134 (1993) 157
Kaiser, D.L., M.D. Vaudin, G. Gillen, C.-S. Hwang, L.H. Robins and L.D. Rotter, Growth and characterization of barium titanate thin films prepared by metalorganic chemical vapor deposition 137 (1994) 136
Kaito, C., S. Kimura, T. Sakamoto, Y. Yoshimura, R. Kaigawa, T. Sakaguchi, Y. Nakayama and Y. Saito, Fullerence crystal prepared by evaporating amorphous carbon rod in inert gas 134 (1993) 157
Kaito, C., Y. Saito, T. Watanabe, K. Ohtsuka, F. Chen and M. Nakamura, Growth mechanism of ultrafine tellurium particles produced by the gas evaporation method 140 (1994) 123
Kaji, M., see Kagawa 139 (1994) 309
Kakibayashi, K., see Okuno 137 (1994) 313
Kakimoto, K., see Watanabe 133 (1993) 23
Kakimoto, K., M. Watanabe, M. Eguchi and T. Hibiya, Flow instability of the melt during Czochralski Si crystal growth: dependence on growth conditions; a numerical simulation study 139 (1994) 197
Kakuta, A., see Kagawa 139 (1994) 309
Kalejs, J.P., see Bhihe 137 (1994) 86
Kalra, M.L., see Goswami 135 (1994) 196
Kalt, H., see Langbein 138 (1994) 191
Kalt, H., see Klingshirn 138 (1994) 786
Kalyanasundaram, S., see Mountziaris 131 (1993) 283
Kamai, T., see Kato 138 (1994) 373
Kamemizu, H., see Iijima 135 (1994) 229
Kameyama, T., see Onuma 137 (1994) 610
Kamińska, E., see Grabecki 138 (1994) 481
Kamp, M., see Mörsch 136 (1994) 256
Kamshilin, A.A., see Prokofiev 137 (1994) 528
Kanakavel, M., see Narayana Kalkura 132 (1993) 617
Kanaya, M., see Takahashi 135 (1994) 61
Kanazawa, T., see Hirano 134 (1993) 81

Kaneko, T., O. Naji, T.S. Jones and B.A. Joyce, The role of excess arsenic during the metalorganic molecular beam epitaxial growth of GaAs from trimethylgallium and As_2 136 (1994) 99
Kanemitsu, Y., see Yamamoto 138 (1994) 643
Kaneno, N., see Mihashi 133 (1993) 281
Kaneno, N., see Kizuki 134 (1993) 35
Kaneyama, T., see Liliental-Weber 132 (1993) 103
Kang, J., K. Hoshikawa, M. Tajima and T. Fukuda, Effect of application of a magnetic field during crystal growth on the photoluminescence characteristics of Ge-doped liquid encapsulated Czochralski grown GaAs 135 (1994) 623
Kang, J., Y. Okano, K. Hoshikawa and T. Fukuda, Influence of a high vertical magnetic field on Te dopant segregation in InSb grown by the vertical gradient freeze method 140 (1994) 435
Kang, W.N., see Yoon 140 (1994) 355
Kanie, H., H. Araki, K. Ishizaka, H. Ohta and S. Murakami, Epitaxial growth of ZnS on GaP by molecular beam deposition 138 (1994) 145
Kaplun, L., see Angert 137 (1994) 116
Kapre, R., see Tsang 136 (1994) 42
Kapre, R., see Chen 136 (1994) 221
Kapre, R.M., see Tsang 135 (1994) 377
Karakida, S., see Mihashi 133 (1993) 281
Karczewski, G., see Leszczynski 135 (1994) 565
Karduck, P., see Gleitsmann 138 (1994) 324
Karkut, M.G., see Guilloux-Viry 132 (1993) 396
Karlicek, Jr., R.F., D.L. Coblentz, R.A. Logan, T.R. Hayes, R. Pawelek and E.K. Byrne, A modified metalorganic chemical vapor deposition chemistry for improved selective area regrowth 131 (1993) 204
Karlsson, U., see Vaitkus 138 (1994) 545
Kasai, K., see Bove 136 (1994) 261
Kash, K., see Caneau 132 (1993) 364
Kashima, H., see Mozume 136 (1994) 287
Kastner, M., see Wolf 135 (1994) 113
Katayama, Y., see Goto 136 (1994) 104
Katholy, S., see Jung 138 (1994) 905
Kato, J., see Sazaki 135 (1994) 199
Kato, J., see Sazaki 139 (1994) 95
Kato, K., F. Akinaga, T. Kamai and M. Wada, In-situ monitoring by spectroscopic ellipsometry in ZnSe crystal growth by molecular beam epitaxy 138 (1994) 373
Kato, T., see Matsumoto 138 (1994) 63
Kato, T., see Matsumoto 138 (1994) 403
Kato, Y., see Fukatsu 136 (1994) 315
Kato, Y., S. Fukatsu, N. Usami and Y. Shiraki, A $Si_{1-x}Ge_x$/Si single quantum well p–i–n structure grown by solid-source and gas-source "hybrid" Si molecular beam epitaxy 136 (1994) 355
Katsura, S., see Hirano 134 (1993) 81
Katsura, T., see Niimura 137 (1994) 671
Kawaguchi, Y., see Matsuoka 138 (1994) 727
Kawakami, Y., T. Toyoda, Sz. Fujita and Sg. Fujita, Effect of photo-irradiation on the growth of ZnSe in metalorganic molecular beam epitaxy 136 (1994) 371
Kawakami, Y., see Ichino 138 (1994) 28
Kawakami, Y., I. Hauksson, J. Simpson, H. Stewart, I. Galbraith, K.A. Prior and B.C. Cavenett, Photoluminescence excitation spectroscopy of the lasing transition in ZnSe–(Zn,Cd)Se quantum wells 138 (1994) 759
Kawakyu, Y., see Mashita 131 (1993) 61
Kawanishi, H., see Yoshida 136 (1994) 37
Kawano, T., see Okuno 137 (1994) 313
Kawarai, K., see Sugino 139 (1994) 15
Kaya, M., see Li 133 (1993) 175
Kayzel, F.E., see Mihalik 134 (1993) 342
Kazlauskas, A., see Ullrich 138 (1994) 234
Kazlauskas, A., see Gavryushin 138 (1994) 924
Kazlauskiene, V., see Vaitkus 138 (1994) 545
Kedar, E., see Weiss 132 (1993) 191
Kelkar, P., see Ding 138 (1994) 719
Kelkar, P., see Salokatve 138 (1994) 1077
Keller, B.P., S. Keller, H. Herrnberger, J. Lenzner, S. Nilsson and W. Seifert, Compositional gradients in $Ga_xIn_{1-x}As$ on patterned InP substrates grown by atmospheric-pressure metalorganic vapour phase epitaxy 140 (1994) 33
Keller, S., see Keller 140 (1994) 33
Keramidas, V.G., see Philips 140 (1994) 249
Kes, P.H., see Li 135 (1994) 481
Khan, S.R., P.O. Whalen and P.A. Glenton, Heterogeneous nucleation of calcium oxalate crystals in the presence of membrane vesicles 134 (1993) 211
Khattak, C.P., see Rao 139 (1994) 190
Khelladi, K.H., see Quemerais 138 (1994) 934
Kheng, K., see Bassani 138 (1994) 607
Kida, M., see Ono 132 (1993) 297
Kida, M., see Ono 135 (1994) 359
Kida, M., see Ono 137 (1994) 427
Kim, B.K., see Lee 138 (1994) 136
Kim, E.J. and W.N. Gill, A new model for low pressure chemical vapor deposition of SiO_2 films by ozone augmented tetraethoxysilane 140 (1994) 308
Kim, E.J. and W.N. Gill, Analytical model for chemical vapor deposition of SiO_2 films using tetraethoxysilane and ozone 140 (1994) 315
Kim, H.-M., see Yoo 132 (1993) 43
Kim, J.H., see Asahi 136 (1994) 268
Kim, J.-S., see Yoo 132 (1993) 43

Kim, J.W., see Lee 138 (1994) 136
Kim, L.S., see Feng 138 (1994) 239
Kim, M.-S., Y. Kim, M.-S. Lee, Y.J. Park, S.-I. Kim and S.K. Min, The facet evolution during metalorganic vapor phase epitaxial growth on V-grooved high Miller index GaAs substrates 139 (1994) 231
Kim, S.G., H. Asahi, M. Seta, K. Asami, S. Gonda, M. Yano and M. Inoue, Optical properties of InAs/AlSb superlattices grown by gas source molecular beam epitaxy 136 (1994) 310
Kim, S.-I., see Kim 139 (1994) 231
Kim, Y., see Kim 139 (1994) 231
Kim-Ngan, N.H., see Mihalik 134 (1993) 342
Kimoto, K., see Mochizuki 135 (1994) 318
Kimoto, T., see Chien 137 (1994) 175
Kimura, M., see Tanaka 135 (1994) 269
Kimura, S., see Kaito 134 (1993) 157
Kimura, S., see Anzai 134 (1993) 227
Kimura, S., see Anzai 134 (1993) 235
Kimura, S., see Markgraf 135 (1994) 253
Kimura, S., see Imoto 135 (1994) 279
Kimura, S., see Shigematsu 137 (1994) 509
Kimura, S., see Sasaki 139 (1994) 225
Kingetsu, T. and K. Sakai, Seeded epitaxial growth of close-packed metal films and their superlattices on silicon substrates 137 (1994) 633
Kingston, J.L., see Walsh 133 (1993) 1
Kinney, T.A. and R.A. Brown, Application of turbulence modeling to the integrated hydrodynamic thermal-capillary model of Czochralski crystal growth of silicon 132 (1993) 551
Kinto, H., see Uchiki 138 (1994) 873
Kirkaldy, J.S., see Liu 140 (1994) 115
Kirov, G.K., see Christov 131 (1993) 560
Kishimoto, S., see Mori 133 (1993) 80
Kissel, H., see Tomm 138 (1994) 175
Kitagawa, M., see Sasaki 136 (1994) 162
Kitagawa, M., see Tomomura 138 (1994) 764
Kitagawa, S., see Suzuki 134 (1993) 67
Kitamura, M., see Sasaki 132 (1993) 435
Kito, N., see Ishibara 137 (1994) 375
Kizuka, T., T. Sakamoto and N. Tanaka, Growth of fine crystals with A-15 type structure in vacuum-deposited tungsten films studied by high-resolution electron microscopy 131 (1993) 439
Kizuki, H., see Mihashi 133 (1993) 281
Kizuki, H., N. Hayafuji, N. Fujii, N. Kaneno, Y. Mihashi and T. Murotani, Selective metalorganic chemical vapor deposition growth of GaAs on AlGaAs combined with in situ HCl gas etching 134 (1993) 35
Kjellberg, L.O., see Glass 132 (1993) 504
Klaus, M., see Novák 139 (1994) 206
Kleessen, H., see Gille 139 (1994) 165
Kleijn, C.R., see Einset 132 (1993) 483
Klimakow, A., see Pohl 138 (1994) 385
Klimovitsky, I.K., Calculation of the growth velocity for liquid encapsulated Czochralski grown GaAs crystals 132 (1993) 614
Klingshirn, C., see Grün 138 (1994) 150
Klingshirn, C., see Langbein 138 (1994) 191
Klingshirn, C., H. Kalt, M. Umlauff, W. Petri, F.A. Majumder, S.V. Bogdanov, W. Langbein, M. Grün, M. Hetterich, K.P. Geyzers, M. Heuken, A. Naumov, H. Stanzl and W. Gebhardt, Stimulated emission of II–VI epitaxial layers 138 (1994) 786
Klingshirn, C., see Woggon 138 (1994) 988
Kloc, C., see Oglesby 137 (1994) 289
Kloc, Ch., G. Willeke and E. Bucher, Flux growth and electrical transport measurements of pyrite (FeS_2) 131 (1993) 448
Klosowski, P., see Giebultowicz 138 (1994) 877
Knight, D.G., C.J. Miner, B. Watt, C.M. Wu, K. Fox, B. Emmerstorfer, C. Maritan and J. Hennessy, Optimization of selective area epitaxy for fabrication of circular grating distributed-Bragg-reflector surface-emitting lasers 134 (1993) 19
Knightly, D., see Munns 136 (1994) 166
Knoch, R., see Heimbrodt 138 (1994) 601
Knutson, K.L., R.W. Carr, W.H. Liu and S.A. Campbell, A kinetics and transport model of dichlorosilane chemical vapor deposition 140 (1994) 191
Koai, K., A. Seidl, H.-J. Leister, G. Müller and A. Köhler, Modelling of thermal fluid flow in the liquid encapsulated Czochralski process and comparison with experiments 137 (1994) 41
Koai, K., K. Sonnenberg and H. Wenzl, Influence of crucible support and radial heating on the interface shape during vertical Bridgman GaAs growth 137 (1994) 59
Koak, B.-H., see Yoo 132 (1993) 43
Kobayashi, H., SrS–ZnS electroluminescence materials 138 (1994) 1010
Kobayashi, H., see Ohmi 138 (1994) 1061
Kobayashi, J., Y. Tazoh and S. Miyazawa, Epitaxial growth of $NdGaO_3$ thin films on (100) $SrTiO_3$ substrates 131 (1993) 138
Kobayashi, M., see Tokita 136 (1994) 376
Kobayashi, M., H. Tosaka, T. Nagatake, T. Yoshida and A. Yoshikawa, Helium gas mixing in nitrogen plasma for the control of the acceptor concentration in p-ZnSe 138 (1994) 745
Kobayashi, S., see Miura 138 (1994) 1046
Kobayashi, T., see Oshima 137 (1994) 48
Kobayashi, T., see Ullrich 138 (1994) 234

Kobayashi, T., M. Ida and K. Kurishima, Effects of susceptor rotation speed and total flow rate on selectivity in metalorganic chemical vapor deposition growth techniques 140 (1994) 432
Koch, M., see Hellmann 138 (1994) 791
Koebel, J.M., see Rzepka 138 (1994) 244
Koguchi, M., see Okuno 137 (1994) 313
Kohda, H. and K. Wada, A new model for carbon doping in GaAs – effect of the methyl radical 135 (1994) 629
Köhler, A., see Koai 137 (1994) 41
Kohno, K., see Takahashi 137 (1994) 240
Kolodziejski, L.A., see Lu 138 (1994) 1
Komatitsch, D., see Alexandre 136 (1994) 235
Komeno, J., see Bove 136 (1994) 261
Komunjer, Lj., M. Marković and H. Füredi-Milhofer, Influence of amino acids on the precipitation kinetics of calcium oxalate monohydrate 132 (1993) 122
Konagai, M., see Shirakashi 136 (1994) 186
Konagai, M., see Okamoto 138 (1994) 204
Konagai, M., see Tojima 138 (1994) 408
Kondo, S., S. Matsumoto and H. Nagai, Metalorganic chloride vapor phase epitaxial growth of III-V compounds in a single reactor 132 (1993) 305
Kong, M., see Yan 136 (1994) 306
Kong, Y., J. Wen and H. Wang, Dislocations and subgrain boundaries in highly magnesium-doped lithium niobate crystals 140 (1994) 45
Konuma, M., see Weishart 137 (1994) 335
Koo, B.J., see Hwang 138 (1994) 131
Kopp, O.C., see Bamberger 131 (1993) 473
Koppensteiner, E., see Fromherz 138 (1994) 580
Korol, A.S., see Oseledchik 135 (1994) 373
Korpela, S.A., A. Chait and D.H. Matthiesen, Lateral or radial segregation in solidification of binary alloy with a curved liquid–solid interface 137 (1994) 623
Koshizuka, N., see Gu 137 (1994) 472
Koss, M.B., see Glicksman 137 (1994) 1
Kossut, J., see Grodzicka 138 (1994) 1034
Koster, J.N., see Campbell 140 (1994) 414
Kothiyal, G.P., see Muthe 139 (1994) 323
Kou, S., see Lin 132 (1993) 461
Kou, S., see Lin 132 (1993) 467
Kou, S., see Lan 132 (1993) 471
Kou, S., see Lan 132 (1993) 578
Kou, S., see Lan 133 (1993) 309
Kou, S., see Lin 134 (1993) 287
Kou, S., see Lin 135 (1994) 643
Kou, S., see Tao 137 (1994) 72
Kou, S., and C.P. Chen, Modified floating-zone growth of organic single crystals 137 (1994) 663
Koutsoukos, P.G., see Sabbides 133 (1993) 13
Koyama, F., see Inaba 136 (1994) 297
Koyama, F., see Yokouchi 136 (1994) 302
Koza, M.A., see Caneau 132 (1993) 364
Koziol, J., see Anselmo 131 (1993) 247
Koziol, J., see Anselmo 134 (1993) 116
Kožíšek, Z. and P. Demo, Transient kinetics of binary nucleation 132 (1993) 491
Kozuch, D.M., see Abernathy 136 (1994) 11
Kramer, G., see DeLucas 135 (1994) 183
Krämer, M., D. Wittmüss, H. Küppers, M.J. Hoffmann and G. Petzow, Relations between crystal structure and growth morphology of β-Si_3N_4 140 (1994) 157
Krause, E., H. Hartmann, J. Menninger, A. Hoffmann, Ch. Fricke, R. Heitz, B. Lummer, V. Kutzer and I. Broser, Influence of growth non-stoichiometry on optical properties of doped and non-doped ZnSe grown by chemical vapour deposition 138 (1994) 75
Krause-Rehberg, R., see Polity 131 (1993) 271
Kreinin, O., see Maayan 135 (1994) 23
Kreller, F., see Schülzgen 138 (1994) 575
Krier, A., see Mao 133 (1993) 108
Krier, A., see Parry 139 (1994) 238
Krikunov, S.A., see Oseledchik 135 (1994) 373
Krištofik, J., see Šestáková 132 (1993) 345
Krüger, D., G. Lippert, R. Kurps and H.J. Osten, Lateral inhomogeneous boron segregation during silicon thin film growth with molecular beam epitaxy 135 (1994) 246
Kub, J., see Štěpánek 135 (1994) 290
Kubacki, F., see Bäume 138 (1994) 266
Kubat-Martin, K.A., see Pettit 139 (1994) 302
Kubertavičius, V., see Gavryushin 138 (1994) 924
Kuboki, Y., see Iijima 137 (1994) 553
Kuboki, Y., see Iijima 140 (1994) 91
Kubota, N., see Mori 133 (1993) 80
Kuciauskas, D., see Vaitkus 138 (1994) 545
Kúdela, R., Growth of $In_{1-x}Ga_xAs$ by vapour epitaxy and analysis of growth conditions 133 (1993) 289
Kudlek, G.H., see Pohl 138 (1994) 385
Kudlek, G.H., see Presser 138 (1994) 820
Kuech, T.F., see Redwing 135 (1994) 423
Kuhn, W., see Wolf 135 (1994) 113
Kuhn, W., see Wolf 138 (1994) 412
Kuhn, W.S., R. Driad, H. Stanzl, A. Lusson, K. Wolf, B. Qu'Hen, H. Sahin, L. Svob, C. Grattepain, X. Quesada, W. Gebhardt and O. Gorochov, Investigation of hydrogen, carbon and further impurities in the metalorganic vapour phase epitaxy of ZnSe with ditertiarybutylselenide and methylallylselenide 138 (1994) 448
Kuhn, W.S., see Qu'Hen 138 (1994) 1079
Kühne, H. and H. Richter, Control of $Si_{1-x}Ge_x$ growth from the gas phase. I. The effect of the layer source gases (E) 132 (1993) 357

Kuhn-Heinrich, B., see Waag 138 (1994) 155
Kukaswadia, A.K., see Ji 138 (1994) 187
Kukimoto, H., see Yanashima 138 (1994) 755
Kumagai, H., see Zeng 140 (1994) 148
Kumar, F.J., D. Jayaraman, C. Subramanian and P. Ramasamy, Nucleation kinetic study of $KTiOPO_4$ crystallizing from high temperature solution 137 (1994) 535
Kumashiro, Y., Y. Okada and H. Okumura, Isotope effects on boron phosphide single-crystal wafers 132 (1993) 611
Kumazaki, K., see Haga 132 (1993) 575
Kumazaki, K., see Takojima 138 (1994) 633
Kumon, S., see Mori 133 (1993) 80
Kuphal, E., see Eisenbach 135 (1994) 129
Küppers, H., see Krämer 140 (1994) 157
Kuriakose, A.K., see Quon 134 (1993) 266
Kurishima, K., see Kobayashi 140 (1994) 432
Kurita, S., see Takahashi 137 (1994) 240
Kuroda, T., see Inoue 138 (1994) 182
Kurps, R., see Krüger 135 (1994) 246
Kürten, M. and J. Schilz, Czochralski growth of Si_xGe_{1-x} single crystals 139 (1994) 1
Kurtz, E., see Hommel 138 (1994) 331
Kurtz, E., see Einfeldt 138 (1994) 471
Kurtz, E., see Hoffmann 138 (1994) 1073
Kurtz, E., see Hommel 138 (1994) 1076
Kurtz, S.R., see Biefeld 133 (1993) 38
Kurtz, S.R., see Biefeld 137 (1994) 231
Kutzer, V., see Krause 138 (1994) 75
Kutzer, V., see Hoffmann 138 (1994) 379
Kutzer, V., see Fricke 138 (1994) 815
Kutzer, V., see Hoffmann 138 (1994) 1073
Kuwabara, H., H. Tatsuoka, Y. Nakanishi, A. Ichida, H. Fujiyasu, M. Nakayama and T. Yamanari, HgTe and $Hg_{1-x}Cd_xTe$ vapor phase epitaxial growth under controlled Hg pressure 138 (1994) 964
Kuwano, Y., see Imoto 135 (1994) 279
Kuwata-Gonokami, M., see Saiki 138 (1994) 805
Kwak, N.J., I.H. Choi, S.W. Lim and S.H. Suh, $Hg_{0.8}Cd_{0.2}Te$ grown by liquid phase epitaxy using $Cd_{0.94}Zn_{0.06}Te$ buffer layer 138 (1994) 950

Lacelle, C., see Sudersena Rao 136 (1994) 179
Lacko, T., see Červeň 131 (1993) 546
Lacmann, R., see Meyer 135 (1994) 571
LaComb, R., see Jain 138 (1994) 709
Lagasse, R.R., Exceptionally large banded spherulites 140 (1994) 370
Lal, R.B., see Zhang 137 (1994) 141
Lan, C.W. and S. Kou, Formulation for correcting optical distortions due to a transparent floating zone 132 (1993) 471
Lan, C.W. and S. Kou, Radial dopant segregation in zero-gravity floating crystal growth 132 (1993) 578
Lan, C.W. and S. Kou, Effect of rotation on radial dopant segregation in microgravity floating-zone crystal growth 133 (1993) 309
Lan, C.W., Thermal-capillary analysis of floating-zone growth of tube crystals: steady-state and conduction dominated calculations 135 (1994) 606
Landwehr, G., see Waag 131 (1993) 607
Landwehr, G., see Heinke 135 (1994) 41
Landwehr, G., see Heinke 135 (1994) 53
Landwehr, G., see Schikora 138 (1994) 8
Landwehr, G., see Ruppert 138 (1994) 48
Landwehr, G., see Waag 138 (1994) 155
Landwehr, G., see Hommel 138 (1994) 331
Landwehr, G., see Tönnies 138 (1994) 362
Landwehr, G., see Waag 138 (1994) 437
Landwehr, G., see Einfeldt 138 (1994) 471
Landwehr, G., see Illing 138 (1994) 638
Landwehr, G., see Hellmann 138 (1994) 791
Landwehr, G., see Neukirch 138 (1994) 861
Landwehr, G., see Bacher 138 (1994) 856
Landwehr, G., see Hommel 138 (1994) 1076
Lane, P.A., see Martin 136 (1994) 69
Lang, M., D. Schikora, T. Widmer, C. Giftge, A. Forstner, V. Holy, J. Humenberger, K. Lischka, G. Brunthaler, H. Sitter and M. von Ortenberg, Structural properties of perfect ZnTe epilayers on (001) GaAs substrates 138 (1994) 81
Lang, M., see Brunthaler 138 (1994) 559
Langbein, W., H. Kalt, M. Hetterich, M. Grün and C. Klingshirn, Influence of the screening of piezo-fields on the carrier dynamics in CdS/CdSe superlattices 138 (1994) 191
Langbein, W., see Klingshirn 138 (1994) 786
Lanig, P., see Stein 131 (1993) 71
Lankes, S., see Naumov 138 (1994) 595
Larkin, J., see Harris 137 (1994) 128
Larson, Jr., D.J., see Casagrande 137 (1994) 195
Larsson, M.I. and G.V. Hansson, Method using reflection high-energy electron diffraction intensity to determine the solid solubility limit for boron in silicon and $Si_{1-x}Ge_x$ layers 134 (1993) 203
Lau, K.M., see Agahi 139 (1994) 344
Laudise, R.A., see Haile 131 (1993) 352
Laudise, R.A., see Haile 131 (1993) 373
Laudise, R.A., P.M. Bridenbaugh and T. Iradi, Pressure balance under hydrothermal conditions 140 (1994) 51
Laugier, J., see Rössner 137 (1994) 393
Launay, J.C., see Fontaine 139 (1994) 67
Launay, P., see Alexandre 136 (1994) 235
Laurila, J., see Tappura 131 (1993) 309
Law, K.S., see Rao 139 (1994) 190
Lawrence, D.J., see Wernberg 131 (1993) 176
Lawson, C.M. and R.R. Michael, Fiber optic

low-coherence interferometry for non-invasive silicon wafer characterization 137 (1994) 37
Lazzarini, L., see Rigo 136 (1994) 293
Le Thanh Vinh, M. Eddrief, C. Sébenne, A. Sacuto and M. Balkanski, Heteroepitaxy of GaSe layered semiconductor compound on Si(117)7 × 7 substrate: a Van der Waals epitaxy? 135 (1994) 1
Lealman, I.F., see Harlow 140 (1994) 19
Lebihen, T., see Deleporte 138 (1994) 884
Ledoux, M.J., see Benaissa 131 (1993) 5
Lee, A.K.K., see Yeboah 135 (1994) 323
Lee, B.-J., see Lin 137 (1994) 400
Lee, B.T. and R.A. Logan, Growth of InP on etched grooves using atmospheric pressure metalorganic vapor phase epitaxy 140 (1994) 1
Lee, C.D., B.K. Kim, J.W. Kim, H.L. Park, C.H. Chung, S.K. Chang, J.I. Lee and S.K. Noh, Thickness dependent properties of ZnSe on (100) GaAs grown by atomic layer epitaxy 138 (1994) 136
Lee, E.H., see Park 136 (1994) 138
Lee, E.H., see Park 136 (1994) 143
Lee, H.H., see Baek 131 (1993) 481
Lee, H.W., see Yi 132 (1993) 451
Lee, J.I., see Lee 138 (1994) 136
Lee, M.-S., see Kim 139 (1994) 231
Lee, S.T., see Ohmi 138 (1994) 1061
Lee, Y.K., N. Fujimura, T. Ito and N. Itoh, Epitaxial growth and structural characterization of erbium silicide formed on (100)Si through a solid phase reaction 134 (1993) 247
Lee, Y.-T., see Yoo 132 (1993) 43
Lee, Y.W., R. Ananth and W.N. Gill, Selection of a length scale in unconstrained dendritic growth with convection in the melt 132 (1993) 226
Leech, P., see Davis 133 (1993) 230
Leech, P.W., K.D. Heazle, G.B. Deacon, R.S. Dickson, B.O. West, M. Faith and C.R. Frost, p-Type doping of $Hg_{0.4}Cd_{0.6}Te$ using Et_4Sb_2 139 (1994) 247
Lefaucheux, F., see Boué 133 (1993) 246
Lefebvre, P., see Allègre 138 (1994) 998
Legras, R., L.S. Dang, C. Bodin, J. Cibert, F. Marcenat, G. Feuillet, J.L. Pautrat, D. Herve and E. Molva, Temperature dependence of optical gain in CdTe/CdMnTe heterostructures 138 (1994) 585
Lehoczky, S.L., see Price 137 (1994) 201
Lehoczky, S.L., see Singh 139 (1994) 158
Leister, H.-J., see Koai 137 (1994) 41
Leister, H.-J., see Seidl 137 (1994) 326
Lemaître, J., see Rubattel 135 (1994) 135
Lemoine, D., see Quemerais 138 (1994) 934
Lenard, A., see Grabecki 138 (1994) 481
Lenz, M. and R. Gruehn, Chemical vapour transport of tungsten dioxide using $HgBr_2$ as transport agent; experiments and thermochemical calculations 137 (1994) 499
Lenzner, J., see Keller 140 (1994) 33
Lester, T.P., see Moore 136 (1994) 230
Leszczynski, M. and P. Franzosi, X-ray diffractometric examinations of GaAs epitaxial layers grown by molecular beam epitaxy at low temperature 134 (1993) 151
Leszczynski, M., A. Szczerbakow and G. Karczewski, The properties of (Pb,Ge)Te single crsytals grown from the vapour phase 135 (1994) 565
Levoguer, C.L., J.S. Foord, G.J. Davies and P.J. Skevington, Modulated molecular beam mass spectrometry studies of the growth of GaAs and $In_xGa_{1-x}As$ using tri-isobutylgallium 136 (1994) 109
Levoguer, C.L., see Davies 136 (1994) 133
Lewandowski, F.A., see DeLucas 135 (1994) 183
Leymarie, J., see Piffault 135 (1994) 11
Li, H., X.-D. Peng and N.-B. Ming, Re-entrant corner mechanism of fcc crystal growth of A-type twin lamella: the Monte-Carlo simulation approach 139 (1994) 129
Li, H.M., see Yoon 131 (1993) 1
Li, H.M., see Yoon 134 (1993) 240
Li, J., J. Sun and Z. Saghir, Booyant and thermocapillary flow in liquid encapsulated floating zone 131 (1993) 83
Li, J.W., J.D. Chiang, Y.K. Su and M. Yokoyama, The preparation of ZnS thin films on an indium tin oxide/glass substrate by low-pressure metalorganic chemical vapor deposition 137 (1994) 421
Li, J.-Z., M. Kaya and R.W. Smith, Growth characteristics of γ-$(Fe,Cr)_3C$ eutectic during unidirectional solidification 133 (1993) 175
Li, M., see Chai 135 (1994) 639
Li, M.M., see Strachan 138 (1994) 318
Li, Q.Z., see Chai 135 (1994) 639
Li, S.H., see Zhang 132 (1993) 200
Li Shenjun, Liu Lin, Wang Zulun, Jiang Yandao, Jiang Xiaobo and Wu Xing, Growth and characteristics of Mg_2SiO_4:Ti crystal 139 (1994) 327
Li, T.W., P.H. Kes, N.T. Hien, J.J.M. Franse and A.A. Menovsky, Growth of $Bi_2Sr_2CaCu_2O_{8+x}$ single crystals at different oxygen ambient pressures 135 (1994) 481
Li, W., T. Anan and L.J. Schowalter, Optimization of GaAs epitaxy on CaF_2/Si(111) substrates 135 (1994) 78
Li, X., see Yan 136 (1994) 306
Li, Z., G. Xiong, Z. Zhao and X. Fan, Mea-

surement of optical nonlinear susceptibility of CdS single crystal using a single beam 138 (1994) 231
Liang, B.W., see Tu 136 (1994) 191
Liang, B.W., see Houng 136 (1994) 216
Liang, D., W. Jie and H. Jones, The effect of growth velocity on primary spacing of Al_3Fe dendrites in hypereutectic Al–Fe alloys 135 (1994) 561
Liang, J., see Ji 137 (1994) 521
Liang, W.Y., see Lin 140 (1994) 72
Liao Jingying, see Xu 133 (1993) 267
Liao Jingying, see Xu 134 (1993) 337
Liliental-Weber, Z., T. Kaneyama, M. Terauchi and M. Tanaka, Application of convergent-beam illumination methods to the study of lattice distortion across the interface 132 (1993) 103
Lim, L.C., see Zeng 140 (1994) 148
Lim, S.W., see Kwak 138 (1994) 950
Lin, C. and A.F. Witt, Decoration of dislocations in $Bi_{12}SiO_{20}$ crystals by annealing in a reducing atmosphere 140 (1994) 444
Lin, C.H., see Wang 139 (1994) 47
Lin, C.T., W. Zhou, A.P. Mackenzie, F. Gauthier and W.Y. Liang, Flux growth of $Sr_{1-x}Ca_xCuO_2$ single crystals 140 (1994) 72
Lin, J.-F., M.-C. Wu, M.-J. Jou, C.-M. Chang and B.-J. Lee, AlGaInP/GaInP double-heterostructure orange light-emitting diodes on GaAsP substrates prepared by metalorganic vapor-phase epitaxy 137 (1994) 400
Lin, L., see Chen 140 (1994) 287
Lin, M.E., see Zhou 134 (1993) 167
Lin, M.H. and S. Kou, Dopant segregation control in Czochralski crystal growth with a wetted float 132 (1993) 461
Lin, M.H. and S. Kou, Crystal pulling with floating wetted shapers 132 (1993) 467
Lin, M.H. and S. Kou, Simultaneous segregation and shape control in crystal pulling with a nonwetted float 134 (1993) 287
Lin, M.H. and S. Kou, Further report on dopant segregation control in Czochralski crystal growth with a wetted float 135 (1994) 643
Lin, X.Y., G. Arkenbout, P. Bennema and P. van Hoof, The relation between rough and flat growth of crystal faces: an effective approach to volume transport resistances 133 (1993) 322
Lindberg, E., see Vaitkus 138 (1994) 545
Lindstaedt, M., see Tomm 138 (1994) 175
Ling, D.L., see Zhang 132 (1993) 200
Ling, J., see Rudra 136 (1994) 173
Liou, Y., see Huang 139 (1994) 363
Lippert, G., see Krüger 135 (1994) 246
Lischka, K., see Schikora 138 (1994) 8
Lischka, K, see Lang 138 (1994) 81
Lischka, K., see Brunthaler 138 (1994) 559
Lischka, K., see Belas 138 (1994) 940
Litz, T., see Waag 138 (1994) 155
Litz, T., see Tönnies 138 (1994) 362
Litz, T., see Waag 138 (1994) 437
Litz, T., see Illing 138 (1994) 638
Litz, T., see Bacher 138 (1994) 856
Liu, E.H., see Chiang 135 (1994) 469
Liu, H.L., see Huang 139 (1994) 363
Liu Lin, see Li 139 (1994) 327
Liu, L.X. and J.S. Kirkaldy, Systematics of thin film cellular dendrites and the cell-to-dendrite transition in succinonitrile–salol, succinonitrile–acetone and pivalic acid–ethanol 140 (1994) 115
Liu Mingguo, see Hou 133 (1993) 71
Liu, W., see Beam 136 (1994) 1
Liu, W., see Zhang 138 (1994) 310
Liu, W., see Skromme 138 (1994) 338
Liu, W.H., see Knutson 140 (1994) 191
Liu, X.F., see Marx 136 (1994) 204
Liu, X.F., H. Asahi, Y. Okuno, D. Marx, K. Inoue and S. Gonda, Selective area epitaxy of GaSb and AlGaSb by metalorganic molecular beam epitaxy 136 (1994) 250
Liu, X.Y. and P. Bennema, On the morphology of crystals of triclinic even normal alkanes: theory and observation 135 (1994) 209
Liu, X.Y. and P. Bennema, Observations on the roughening transition and the influence on morphology of crystals 139 (1994) 179
Liu, Z.T., see Zhang 133 (1993) 117
Lockwood, D.J., see Webb 137 (1994) 405
Logan, R.A., see Karlicek, Jr. 131 (1993) 204
Logan, R.A., see Lee 140 (1994) 1
Loginov, Y.Y., see Brown 138 (1994) 538
Loiacono, D.N., see Loiacono 131 (1993) 323
Loiacono, G.M., D.N. Loiacono and R.A. Stolzenberger, Crystal growth and characterization of ferroelectric $CsTiOAsO_4$ 131 (1993) 323
Long, M.M., see DeLucas 135 (1994) 183
Loos-Neskovic, C., see Abousahl 137 (1994) 569
Lopez-Rivera, S.A., see Martinez 138 (1994) 913
Louchev, O.A., Onset of supercooling in front of the solidification interface in zone melting materials processing 131 (1993) 209
Louchev, O.A., The influence of natural convection on the formation of a molten zone under optical heating 133 (1993) 261
Louchev, O.A., Diffusion, heat transfer, equilibrium molecular density and kinetic mechanism of morphological instability in physical vapor deposition 140 (1994) 219
Lowisch, M., see Schülzgen 138 (1994) 575

Lu, J.W. and F. Chen, Instability-mode competition due to change of partition coefficient of binary alloy unidirectionally solidified from below 140 (1994) 182
Lu, K., J.L. House, P.A. Fisher, C.A. Coronado, E. Ho, G.S. Petrich and L.A. Kolodziejski, (In,Ga)P buffer layers for ZnSe-based visible emitters 138 (1994) 1
Lu Taijing, see Ng 131 (1993) 265
Lu, Y.M., see Yang 138 (1994) 629
Lu, Y.M., see Zhang 138 (1994) 838
Lu, Z.P., see Snail 137 (1994) 676
Lübke, K., see Schikora 138 (1994) 8
Lubyshev, D.I., J.C. Rossi, G.M. Gusev and P. Basmaji, Nano-scale wires of GaAs on porous Si grown by molecular beam epitaxy 132 (1993) 533
Lummer, B., see Krause 138 (1994) 75
Lummer, B., see Hoffmann 138 (1994) 379
Lummer, B., see Broser 138 (1994) 809
Lummer, B., see Fricke 138 (1994) 815
Lummer, B., see Hoffmann 138 (1994) 1073
Lundager Madsen, H.E., see Abbona 131 (1993) 331
Lundblad, W., see Beske 137 (1994) 102
Lunn, B., see Dhese 138 (1994) 443
Lunn, B., see Wolverson 138 (1994) 656
Lunn, B., see Pier 138 (1994) 889
Lunn, B., see Sawicki 138 (1994) 900
Luo, C.P., see Chen 140 (1994) 287
Luo, H., see Yokogawa 138 (1994) 564
Luo, Zundu, see Tu 135 (1994) 636
Lusson, A., see El Mokri 138 (1994) 168
Lusson, A., see Rzepka 138 (1994) 244
Lusson, A., see Kuhn 138 (1994) 448
Lusson, A., see Qu'Hen 138 (1994) 1079
Łuszczek, M., see Foks 134 (1993) 347
Lüth, H., see Mörsch 136 (1994) 256
Lutz, Jr., C.R., see Agahi 139 (1994) 344
Lyssenko, V.G., see Erland 138 (1994) 800

Ma, Z., see Zhou 134 (1993) 167
Maayan, E., O. Kreinin, G. Bahir, J. Salzman, A. Eyal and R. Beserman, Selective growth of GaAs/InGaP heterostructures by photo-enhanced organometallic chemical vapor deposition 135 (1994) 23
MacDonald, S.M., see Fisher 138 (1994) 86
Maček, J., S. Zakrajšek, J. Radkovič and V. Bole, Crystallization of gypsum from batch chemical neutralizations 132 (1993) 99
Machida, H., K. Hoshikawa and T. Fukuda, Spiral growth of rutile single crystal boules in the edge-defined film-fed growth process 137 (1994) 82
Machida, H., K. Hoshikawa and T. Fukuda, Growth of TiO_2 single crystals using the edge-defined, film-fed growth technique 137 (1994) 516
Mackenzie, A.P., see Lin 140 (1994) 72
Maeda, M., see Sugino 139 (1994) 15
Maehara, K., see Fujita 138 (1994) 737
Magnea, N., see Rössner 137 (1994) 393
Magnea, N., ZnTe fractional monolayers and dots in a CdTe matrix 138 (1994) 550
Magnea, N., see Bassani 138 (1994) 607
Mahajan, S., see Philips 140 (1994) 249
Mahnke, H.-E., see Schumann 138 (1994) 910
Mai, Z.H., see Chai 135 (1994) 639
Mainzer, N., see Weiss 132 (1993) 191
Majewski, J.A. and D.H. Matthiesen, Quantitative infrared imaging for the measurement of dopant distribution in gallium arsenide 137 (1994) 249
Majumder, F.A., see Klingshirn 138 (1994) 786
Mäkinen, S., see Polity 131 (1993) 271
Malkin, A.J. and A. McPherson, Crystallization of pumpkin seed globulin: growth and dissolution kinetics 133 (1993) 29
Málková, Z., see Nitsch 131 (1993) 612
Malzbender, J., see Jones 138 (1994) 279
Mamor, M., see Bassani 138 (1994) 607
Mandeville, P., see Teng 135 (1994) 36
Mangat, P.S., see Chen 138 (1994) 1078
Mani, S.S., see Glicksman 137 (1994) 1
Mann, S., see Titiloye 131 (1993) 533
Mann, S., see Walsh 133 (1993) 1
Mannhart, J., see Schlom 137 (1994) 259
Mao, Y., and A. Krier, Liquid phase epitaxial growth and photoluminescence of InAsb grown on GaSb substrates from antimony solution 133 (1993) 108
Marcenat, F., see Legras 138 (1994) 585
Marek, T., H.P. Strunk, H. Weishart and E. Bauser, Microtopology of terrace risers and treads on solution-grown GaAs(001) vicinal surfaces 134 (1993) 14
Mareš, J.J., see Šestáková 140 (1994) 426
Marfaing, J., see Bettahi 135 (1994) 487
Marfaing, Y., see Rzepka 138 (1994) 244
Marfaing, Y., Limits of acceptor impurity doping in wide band gap II–VI semiconductors 138 (1994) 305
Marfaing, Y., see Guergouri 139 (1994) 6
Mariette, H., see Gourgon 138 (1994) 590
Mariette, H., see Haacke 138 (1994) 831
Maritan, C., see Knight 134 (1993) 19
Markgraf, S.A., S. Kimura, T. Sawada and M. Göbbels, Metastable crystallization of $Nd_3Ga_5O_{12}$ melts: effects of time and temperature 135 (1994) 253
Markgraf, S.A., Y. Furukawa and M. Sato, Top-seeded solution growth of LiB_3O_5 140 (1994) 343
Markov, E.V., see Goncharov 139 (1994) 266
Marković, M., see Komunjer 132 (1993) 122
Marković, M., B.O. Fowler and W.E. Brown, Octacalcium phosphate carboxylates. IV.

Kinetics of formation and solubility of octacalcium phosphate succinate 135 (1994) 533
Marks, R.F., see Farrow 133 (1993) 47
Maroudas, D., see Brown 137 (1994) 12
Marrakchi, G., see Rzepka 138 (1994) 244
Mars, D.E., see Houng 136 (1994) 216
Marshall, V.R., see Ryall 133 (1993) 87
Martin, T., R.W. Freer, C.R. Whitehouse and P.A. Lane, Advances in the understanding of chemical beam epitaxy growth meachnisms 136 (1994) 69
Martinez, L., S.A. Lopez-Rivera, W. Giriat and F. Medina, Nature of the absorption bands in $Zn_{1-x}Co_xS$ 138 (1994) 913
Maruno, S., see Gotoda 136 (1994) 246
Maruno, S., see Gotoda 140 (1994) 277
Maruyama, H., K. Pak, K. Sakakibara, H. Yonezu and Y. Takano, Study on initial growth process of Si on InP(100) substrate grown by molecular beam epitaxy 131 (1993) 316
Maruyama, H., K. Pak and H. Yonezu, Initial growth modes on InP layer grown by molecular beam epitaxy and migration enhanced epitaxy on Si films grown on InP(100) substrates 139 (1994) 19
Maruyama, K., R.G. Benz II, A. Conte-Matos, B.K. Wagner and C.J. Summers, Gas source doping of molecular beam epitaxially grown CdTe using arsine 137 (1994) 435
Marx, D., H. Asahi, X.F. Liu, Y. Okuno, K. Inoue, S. Gonda, S. Shimomura and S. Hiyamazu, Metalorganic molecular beam epitaxy growth of GaAs on patterned GaAs substrates 136 (1994) 204
Marx, D., see Liu 136 (1994) 250
Mashita, M., M. Sasaki, Y. Kawakyu and H. Ishikawa, Surface reaction mechanisms in GaAs atomic layer epitaxy 131 (1993) 61
Mashita, M., see Hiraoka 136 (1994) 94
Maslen, V., see Davis 133 (1993) 230
Mason, N.J., see Aindow 133 (1993) 168
Massies, J., see Grandjean 134 (1993) 51
Masumoto, K., see Mochizuki 131 (1993) 41
Masumoto, K., see Mochizuki 135 (1994) 318
Masumoto, Y., see Yamada 138 (1994) 570
Masumoto, Y., see Yamamoto 138 (1994) 643
Mataga, P.A., see Bhihe 137 (1994) 86
Mathet, V., P. Galtier, F. Nguyen-Van-Dau, G. Padeletti and J. Olivier, A microstructural study of crystalline defects in $PbSe/BaF_2/CaF_2$ on (111) Si grown by molecular beam epitaxy 132 (1993) 241
Mathieu, H., see Allègre 138 (1994) 998
Matioukhin, D.G., see Salk 138 (1994) 161
Matolín, V., see Gillet 134 (1993) 75
Matsumoto, F., Y. Okano, I. Yonenaga, K. Hoshikawa and T. Fukuda, Growth of twin-free ⟨100⟩ InP single crystals by the liquid encapsulated vertical Bridgman technique 132 (1993) 348
Matsumoto, H., see Miura 138 (1994) 1046
Matsumoto, K., E. Schönherr and M. Wojnowski, Growth of C_{60} crystals by the Pizzarello method 135 (1994) 154
Matsumoto, S., see Chichibu 131 (1993) 551
Matsumoto, S., see Kondo 132 (1993) 305
Matsumoto, S., see Chichibu 140 (1994) 388
Matsumoto, T., T. Iwashita, K. Sasamoto and T. Kato, Atomic layer epitaxy of CdSe/ZnSe short period superlattices 138 (1994) 63
Matsumoto, T., see Yao 138 (1994) 290
Matsumoto, T., T. Inaba, Y. Yoda, K. Egashira, T. Kato and T. Akitsu, p-Type doping of ZnSe with a novel nitrogen exciter 138 (1994) 403
Matsumura, N., see Ichikawa 138 (1994) 14
Matsunami, H., see Yoshimoto 136 (1994) 89
Matsunami, H., see Hatayama 136 (1994) 333
Matsunami, H., see Chien 137 (1994) 175
Matsuoka, T., A. Ohki, T. Ohno and Y. Kawaguchi, Comparison of GaN- and ZnSe-based materials for light emitters 138 (1994) 727
Matsushige, K., see Taki 131 (1993) 13
Matsuura, K., see Seto 138 (1994) 346
Matthews, B.E., see Hastings 138 (1994) 917
Matthiesen, D.H., see Majewski 137 (1994) 249
Matthiesen, D.H., The total pressure of arsenic over molten gallium arsenide at 1260°C 137 (1994) 255
Matthiesen, D.H., see Korpela 137 (1994) 623
Matugatani, K., see Taguchi 134 (1993) 147
Mauch, R.H., see Troppenz 138 (1994) 1017
Maxey, C.D., see Hastings 138 (1994) 917
Mayer, H., U. Rössler, S. Permogorov, H. Stolz, H. Vogelsang and W. von der Osten, Resonant Brillouin scattering in biaxially strained ZnSe 138 (1994) 195
Mazelsky, R., see Singh 135 (1994) 619
Mazelsky, R., see Singh 137 (1994) 155
Mazelsky, R., see Singh 139 (1994) 158
Mazuelas, A., L. González, F.A. Ponce, L. Tapfer and F. Briones, Critical thickness determination of InAs, InP and GaP on GaAs by X-ray interference effect and transmission electron microscopy 131 (1993) 465
Mazuelas, A. and A. Ruiz, Growth and characterization by X-ray diffraction of GaP/InP short-period superlattices 135 (1994) 123
McAllister, T., see Davis 133 (1993) 230
McCaffery, J., see Sudersena Rao 136 (1994) 179
McCaldin, J.O., see Wang 138 (1994) 508
McCaldin, J.O., see Swenberg 138 (1994) 692
McCarron III, E.M., see Cheng 132 (1993) 280
McCay, M.H. and T.D. McCay, The influ-

ence of microgravity on the dendritic growth rates of NH_4Cl–H_2O: an international microgravity laboratory experiment 135 (1994) 594
McCay, T.D., see McCay 135 (1994) 594
McCord, G., see Seidl 137 (1994) 326
McFadden, G.B., see Brush 137 (1994) 355
McFadden, G.B., see Coriell 140 (1994) 139
McGill, T.C., see Wang 138 (1994) 508
McGill, T.C., see Miles 138 (1994) 523
McGill, T.C., see Swenberg 138 (1994) 692
McHugh, J.P., see Hobgood 137 (1994) 181
McPherson, A., see Malkin 133 (1993) 29
McPherson, A., DeLucas 135 (1994) 183
Meade, C.J., see DeLucas 135 (1994) 183
Medina, F., see Martinez 138 (1994) 913
Meekes, H., see Balzuweit 131 (1993) 518
Meekes, H.L.M., see De Boer 140 (1994) 361
Meese, J.M., see Chao 140 (1994) 454
Mei, Linfeng, Changzhen He and Chuangtian Chen, Flux growth of $KBe_2BO_3F_2$ 132 (1993) 609
Meier, J., see Rüb 138 (1994) 285
Meis-Haugen, G., see DePuydt 138 (1994) 667
Mellet, R., see Mergy 134 (1993) 353
Mendicino, M.A. and E.G. Seebauer, Detailed in-situ monitoring of film growth: application to $TiSi_2$ chemical vapor deposition 134 (1993) 377
Menken, M.J.V., see Oka 137 (1994) 479
Menna, A., see Rajendran 137 (1994) 77
Menninger, J., see Krause 138 (1994) 75
Menovsky, A.A., see Mihalik 134 (1993) 342
Menovsky, A.A., see Li 135 (1994) 481
Menovsky, A.A., see Oka 137 (1994) 479
Mensz, P.M., Electrical and optical modeling of II–VI semiconductor diode lasers 138 (1994) 697
Mergy, J., G. Faivre, C. Guthmann and R. Mellet, Quantitative determination of the physical parameters relevant to the thin-film directional solidification of the CBr_2–C_2Cl_6 eutectic alloy 134 (1993) 353
Merkus, H.G., see Van Drunen 134 (1993) 196
Mertins, H.-Ch., see Jung 138 (1994) 905
Mertins, H.-Ch., see Jung 138 (1994) 1066
Merz, J.L., see Yokogawa 138 (1994) 564
Metcalfe, N.E., see Hastings 138 (1994) 917
Mewes, C., see Brion 134 (1993) 281
Meyer, B.K., see Zimmermann 131 (1993) 276
Meyer, B.K., see Fiederle 138 (1994) 529
Meyer, H.-J., R. Lacmann and H. Zimmermann, Random space filling by nucleation and growth 135 (1994) 571
Meyer, J.R., A.R. Reisinger, K.A. Harris, R.W. Yanka, L.M. Mohnkern and L.R. Ram-Mohan, Photoluminescence study of $HgTe$–$Hg_{0.9}Cd_{0.1}Te$ superlattices 138 (1994) 981
Michael, R.R., see Lawson 137 (1994) 37
Michel, B., see Barrette 131 (1993) 153
Miethe, K., see Eisenbach 135 (1994) 129
Migita, M., A. Taike, M. Momose and J. Gotoh, Blue-green light-emitting diodes with p-ZnSSe highly doped with nitrogen grown by metalorganic molecular beam epitaxy and molecular beam epitaxy 138 (1994) 391
Mihalik, G.B., see Monchamp 140 (1994) 439
Mihalik, M., N.H. Kim-Ngan, F.E. Kayzel, A.A. Menovsky, R.W.A. Hendrikx and T.J. Gortenmulder, Crystal growth and characterization of $U_xCe_{1-x}Ru_2Si_2$ pseudo-ternary system 134 (1993) 342
Mihashi, Y., M. Miyashita, N. Hayafuji, N. Kaneno, S. Kageyama, S. Karakida, H. Kizuki, A. Shima and T. Murotani, Large-scale metalorganic chemical vapor deposition growth of highly reliable 780 mm AlGaAs multiple quantum well high-power lasers 133 (1993) 281
Mihashi, Y., see Kizuki 134 (1993) 35
Mikami, M., K.-S. Park, Y. Noda and Y. Furukawa, Radical-assisted metalorganic chemical vapor deposition of ZnSe 140 (1994) 429
Miles, R.J., see Wang 138 (1994) 508
Miles, R.J., J.F. Swenberg, M.W. Wang, M.C. Phillips and T.C. McGill, Investigation of crystal quality and surface morphology of ZnTe:N epilayers grown on ZnTe and GaSb substrates 138 (1994) 523
Miles, R.J., see Swenberg 138 (1994) 692
Miller, M., see Junno 136 (1994) 78
Mil'vidskii, M.G., see Vdovin 132 (1993) 477
Min, S.K., see Kim 139 (1994) 231
Minami, F., see Inoue 138 (1994) 182
Minami, F., K. Yoshida, K. Inoue and H. Fujiyasu, Two-photon spectroscopy in ZnSe/ZnS quantum wells 138 (1994) 796
Minari, F. and B. Billia, Mixed cells in directional solidification of In-doped GaAs; cellular profile and shape-induced stresses 140 (1994) 264
Miner, C.J., see Knight 134 (1993) 19
Miner, C.J., see Moore 136 (1994) 230
Minezaki, Y., see Niimura 137 (1994) 671
Ming, N.B., see Zhang 132 (1993) 200
Ming, N.B., see Li 139 (1994) 129
Mir, J., see Baetzold 135 (1994) 145
Mirkarimi, P.B., see Hultman 135 (1994) 309
Misawa, S., see Okumura 136 (1994) 361
Miskinis, J., see Vaitkus 138 (1994) 545
Mito, I., see Sasaki 132 (1993) 435
Mitrović, M.M., Influence of initial crystal size on growth rate of crystals from solutions 139 (1994) 332
Mitsuhara, M., M. Okamoto, R. Iga, T. Yamada and H. Sugiura, InP and related compounds grown on (110) InP sub-

strates by metalorganic molecular beam epitaxy (chemical beam epitaxy) 136 (1994) 195
Mitsuyu, T., see Saiki 138 (1994) 805
Miura, N., K. Ogawa, S. Kobayashi, H. Matsumoto and R. Nakano, Electroluminescence spectra of rare-earth-doped $ZnS_{1-x}Se_x$ thin films 138 (1994) 1046
Miyake, H., T. Hayashi and K. Sugiyama, Preparation of $CuGa_xIn_{1-x}S_2$ alloys from In solutions 134 (1993) 174
Miyakoshi, K., K. Fujii, T. Hidaka, I. Suemune, M. Nakagawa and T. Ogawa, Comparison of triethylgallium and its amine-adduct on gas-phase reaction with trimethylamine-alane 136 (1994) 152
Miyamoto, N., see Takakuwa 136 (1994) 328
Miyamoto, N., see Horie 136 (1994) 344
Miyamoto, T., T. Uchida, N. Yokouchi and K. Iga, Surface emitting lasers grown by chemical beam epitaxy 136 (1994) 210
Miyamoto, T., see Inaba 136 (1994) 297
Miyamoto, T., see Yokouchi 136 (1994) 302
Miyanaga, K., see Aoyama 136 (1994) 349
Miyano, A., see Shirakashi 136 (1994) 186
Miyashita, M., see Mihashi 133 (1993) 281
Miyazawa, S., see Kobayashi 131 (1993) 138
Miyazawa, S., see Sasaura 131 (1993) 413
Mizrachi, M., see Azoulay 137 (1994) 208
Mochizuki, K., E. Niwa, H. Iwanaga and K. Masumoto, Some characteristics of $AgGaS_2$ single crystals grown from the melt 131 (1993) 41
Mochizuki, K., K. Masumoto, T. Yasuda, Y. Segawa and K. Kimoto, Sublimation growth of high-purity ZnSe single crystals and photoluminescence 135 (1994) 318
Mochizuki, Y., T. Takada, T. Sakuma, S. Handa, C. Sasaoka and A. Usui, Theoretical study of the Cl desorption reaction induced by H_2 in the chloride atomic layer epitaxy 135 (1994) 259
Möck, P., see Bickmann 131 (1993) 133
Moe, A.M., see Oka 137 (1994) 479
Mohnkern, L.M., see Meyer 138 (1994) 981
Moine, O., see Rzepka 138 (1994) 244
Moisan, J.Y., see Rzepka 138 (1994) 244
Moiseev, I.I., see Volkov 132 (1993) 359
Möller, J., see Slezov 132 (1993) 419
Möller, M.O., see Heinke 135 (1994) 41
Möller, U., B.O. Hildmann and G. Bähr, Shape of the solid–liquid interface and dopant distribution of Bridgman grown Ge:Ga 131 (1993) 165
Molva, E., see Legras 138 (1994) 585
Momose, M., see Migita 138 (1994) 391
Monchamp, R.R., G.B. Mihalik and L.A. Franks, Octagonal crystals of strontium barium niobate (SBN:61) 140 (1994) 439
Monier, C., see Piffault 135 (1994) 11
Moon, S.W., S.H. Suh and C.S. Choi, Indium doped $Hg_{0.7}Cd_{0.3}Te$/undoped $Hg_{0.8}Cd_{0.2}Te$/CdTe heterojunction grown by Te-rich liquid phase epitaxy 138 (1994) 944
Moore, E.F., see Davis 132 (1993) 513
Moore, K.M., see DeLucas 135 (1994) 183
Moore, W.T., A.J. SpringThorpe, T.P. Lester, S. Eicher, R.K. Surridge, J. Hu and C.J. Miner, The effect of emitter layer variations on the current gain of AlGaAs–GaAs heterojunction bipolar transistors grown by chemical beam epitaxy 136 (1994) 230
Moravec, P., see Belas 138 (1994) 940
Moravec, P., see Höschl 138 (1994) 956
Mori, H., InP heteroepitaxy on Si substrates in In–PH_3–HCl–H_2 systems 140 (1994) 291
Mori, K., see Inaba 136 (1994) 297
Mori, K., see Yokouchi 136 (1994) 302
Mori, M., see Soga 132 (1993) 134
Mori, M., see Soga 132 (1993) 414
Mori, T., N. Kubota, S. Abe, S. Kishimoto, S. Kumon and M. Naruse, Spherulitic crystallization of aspartame from aqueous solution in a two-dimensional cell 133 (1993) 80
Mori, Y., see Ishibashi 138 (1994) 677
Morishita, T., see Chin 132 (1993) 82
Morishita, Y., see Goto 136 (1994) 104
Moriwaki, Y., see Iijima 135 (1994) 229
Moriwaki, Y., see Iijima 137 (1994) 553
Moriwaki, Y., see Iijima 140 (1994) 91
Moriyama, T., see Uchiki 138 (1994) 873
Morkoç, H., see Zhou 134 (1993) 167
Morris Hotsenpiller, P.A., see Cheng 137 (1994) 107
Morris, J.C., see Davies 136 (1994) 133
Mörsch, G., J. Gräber, M. Kamp, M. Hollfelder and H. Lüth, The selectively grown permeable junction base transistor with a gate of highly carbon doped GaAs 136 (1994) 256
Mountziaris, T.J., S. Kalyanasundaram and N.K. Ingle, A reaction-transport model of GaAs growth by metalorganic chemical vapor deposition using trimethyl-gallium and tertiary-butyl-arsine 131 (1993) 283
Moy, K., see Anderson 135 (1994) 383
Mozume, T., H. Kashima, K. Hosomi, K. Ogata, K. Suenaga and A. Nakano, Gas source molecular beam epitaxy and X-ray absorption fine structure characterization of InGaAs/InP short period superlattices 136 (1994) 287
Muggelberg, C., see Reichow 131 (1993) 277
Muhr, G.T., see Abernathy 136 (1994) 11
Mukai, K., M. Sugawara and S. Yamazaki, Enhancement of thermal stability in $In_{0.53}Ga_{0.47}As$/InP quantum wells 137 (1994) 388

Müller, G., see Koai 137 (1994) 41
Müller, G., see Ostrogorsky 137 (1994) 64
Müller, G., see Seidl 137 (1994) 326
Müller, M.O., see Heinke 135 (1994) 53
Müller, R., see Rothfritz 136 (1994) 225
Müller-Vogt, G., see Erb 132 (1993) 389
Müller-Vogt, G., see Erb 137 (1994) 487
Mullin, J.B., see Jones 138 (1994) 274
Mullin, J.B., see Jones 138 (1994) 279
Mullins, J.T., see Prior 138 (1994) 94
Mullins, J.T., G. Horsburgh, J. Simpson, P. Thompson, M.R. Taghizadeh, I. Hauksson, S.Y. Wang, K.A. Prior, B.C. Cavenett, G.M. Williams and A.G. Cullis, Laser induced doping profiles in molecular beam epitaxy grown ZnSe doped with iodine 138 (1994) 357
Mullins, J.T., see Brown 138 (1994) 538
Mullins, J.T., see Wang 138 (1994) 647
Munekata, H., see Deleporte 138 (1994) 884
Munns, G.O., see Chen 136 (1994) 50
Munns, G.O., W.L. Chen, M.E. Sherwin, D. Knightly, G.I. Haddad, L. Davis and P.K. Bhattacharya, Influence of hydride purity on InP and InAlAs grown by chemical beam epitaxy 136 (1994) 166
Munson, S.H., see DeLucas 135 (1994) 183
Murakami, S., see Kanie 138 (1994) 145
Muranoi, T., S. Onizawa and M. Sasaki, Iodine doping in ZnSe films grown by vapor phase epitaxy 138 (1994) 255
Murata, K., see Ishibara 137 (1994) 375
Murdin, B., see Prior 138 (1994) 94
Mullins, J.T., see Prior 138 (1994) 94
Murotani, T., see Mihashi 133 (1993) 281
Murotani, T., see Kizuki 134 (1993) 35
Murray, B.T., see Chernov 132 (1993) 405
Murugakoothan, P., see Jayavel 131 (1993) 105
Murugakoothan, P., see Jayavel 137 (1994) 273
Muthe, K.P., M.K. Gupta, D.P. Gandhi, J.C. Vyas, G.P. Kothiyal, K.D. Singh and S.C. Sabharwal, The effect of growth temperature on thin film deposition of yttrium under molecular beam epitaxial conditions 139 (1994) 323
Myerson, A.S., see Na 139 (1994) 104
Mzerd, A., D. Sayah, J.C. Tedenac and A. Boyer, Optimal crystal growth conditions of thin films of Bi_2Te_3 semiconductors 140 (1994) 365

Na, H.-S., S. Arnold and A.S. Myerson, Cluster formation in highly supersaturated solution droplets 139 (1994) 104
Nabot, J.-Ph., see Harter 131 (1993) 157
Nacer, A. and M. Bourkiza, Diffusion coefficients in solid systems 137 (1994) 91
Naessens, D.E., see De Maeyer 135 (1994) 539
Nagabhushan, T.L., see DeLucas 135 (1994) 183
Nagai, H., see Kondo 132 (1993) 305
Nagai, S., N. Fujimura, H. Tanaka and T. Ito, (115)$Bi_2Sr_2CuO_x$ epitaxial films on (110)$SrTiO_3$ by solid phase epitaxy 140 (1994) 65
Nagao, Y., see Nishimura 134 (1993) 293
Nagao, Y., see Nishimura 138 (1994) 114
Nagatake, T., see Kobayashi 138 (1994) 745
Nägele, M., see Schmolke 138 (1994) 213
Nägele, M., W. Ebeling, J. Gutowski, K.P. Geyzers and M. Heuken, Nonlinear transmission dynamics of ZnS_xSe_{1-x}/ZnSe and $ZnS_xSe_{1-x}/ZnS_ySe_{1-y}$ ($x > y$) waveguide structures 138 (1994) 842
Naji, O., see Kaneko 136 (1994) 99
Nakagawa, M., see Miyakoshi 136 (1994) 152
Nakajima, K., Stress calculation based on three-dimensional deformation of InGaAs/GaAs heterostructure with a graded layer 137 (1994) 667
Nakamura, K., see Okuno 137 (1994) 313
Nakamura, M., see Kaito 140 (1994) 123
Nakamuta, Y., see Sakaki 133 (1993) 329
Nakanishi, Y., see Kuwabara 138 (1994) 964
Nakano, A., see Mozume 136 (1994) 287
Nakano, R., see Miura 138 (1994) 1046
Nakao, T., see Uenoyama 138 (1994) 301
Nakayama, H., see Kagawa 139 (1994) 309
Nakayama, M., see Kuwabara 138 (1994) 964
Nakayama, Y., see Kaito 134 (1993) 157
Nanev, Chr.N., Critical size of crystals growing under diffusion conditions for loss of polyhedral stability 140 (1994) 381
Nanni, R.G., see DeLucas 135 (1994) 183
Narayana Kalkura, S., V.K. Vaidyan, M. Kanakavel and P. Ramasamy, Crystallization of uric acid 132 (1993) 617
Narayana, S.V.L., see DeLucas 135 (1994) 183
Naritsuka, S., T. Noda, A. Wagai, S. Fujita and Y. Ashizawa, Electrical properties and deep levels of InAlAs layers grown by metalorganic chemical vapor deposition 131 (1993) 186
Naruse, M., see Mori 133 (1993) 80
Narushima, T., see Waseda 139 (1994) 357
Naumov, A., see Wolf 135 (1994) 113
Naumov, A., see Wolf 138 (1994) 412
Naumov, A., H. Stanzl, K. Wolf, A. Rosenauer, S. Lankes and W. Gebhardt, Exciton recombination in $ZnSe_xTe_{1-x}$/ZnTe QWs and $ZnSe_xTe_{1-x}$ epilayers grown by metalorganic vapour phase epitaxy 138 (1994) 595
Naumov, A., see Klingshirn 138 (1994) 786
Naumov, S., see Fischer 132 (1993) 444
Navia, M.A., see DeLucas 135 (1994) 183

Nayyar, N.K., see Sharma 131 (1993) 565
Neave, J.H., see Zhang 131 (1993) 300
Neave, J.H., see Zhang 132 (1993) 331
Nelson, C.R., see Anderson 135 (1994) 383
Nelson, J., Heat conduction problems in crystal growth from the vapor 132 (1993) 538
Neugebauer, F., see Heimbrodt 138 (1994) 601
Neukirch, U., D. Weckendrup, W. Faschinger, P. Juza and H. Sitter, Exciton relaxation dynamics in ultrathin CdSe/ZnSe single quantum wells 138 (1994) 849
Neukirch, U., D. Weckendrup, J. Gutowski, D. Hommel and G. Landwehr, Dynamical properties of excitons in $Zn_{1-x}Cd_xSe/ZnSe$ quantum wells and $Zn_{1-x}Cd_xSe$ epilayers grown by molecular beam epitaxy 138 (1994) 861
Neumark, G.F., see Radomsky 138 (1994) 99
Neumark, G.F., see Yi 138 (1994) 208
Ng, S.C. and Lu Taijing, Detection of oxidation stacking faults in silicon wafers by a multipass Fabry–Perot Rayleigh–Brillouin scattering spectrometer 131 (1993) 265
Nguyen-Van-Dau, F., see Mathet 132 (1993) 241
Nicholls, J.E., see Dhese 138 (1994) 140
Nicholls, J.E., see Dhese 138 (1994) 443
Nicholls, J.E., see Pier 138 (1994) 889
Niimura, N., Y. Minezaki, M. Ataka and T. Katsura, Small angle neutron scattering from lysozyme in unsaturated solutions, to characterize the pre-crystallization process 137 (1994) 671
Nikolov, V., see Varadinov 131 (1993) 97
Nilsson, S., see Keller 140 (1994) 33
Nishida, I., see Arita 132 (1993) 71
Nishida, T., H. Suriura, M. Notomi and T. Tamamura, InGaAs/InP quantum wires selectively grown by chemical beam epitaxy 132 (1993) 91
Nishihata, A., see Suzuki 138 (1994) 199
Nishikawa, Y., see Suzuki 133 (1993) 303
Nishimura, K., Y. Nagao and K. Sakai, Low temperature metalorganic vapor phase epitaxy of ZnSe and ZnSSe onto GaAs using tertiarybutylselenol 134 (1993) 293
Nishimura, K., Y. Nagao and K. Sakai, Low pressure growth and nitrogen doping in metalorganic vapor phase epitaxy of ZnSe 138 (1994) 114
Nishinaga, T., see Shen 135 (1994) 85
Nishio, J. and H. Fujita, Ambient gas constituents and segregation of carbon and boron in LEC GaAs single crystals: the role of water in boric oxide encapsulants 134 (1993) 97
Nishitani, K., see Izumi 133 (1993) 123
Nishiyama, F., see Yao 138 (1994) 290
Nitsch, K., A. Cihlář, Z. Málková, M. Rodová and M. Vaněček, The purification and preparation of high-purity $PbCl_2$ and ternary alkali lead chloride single crystals 131 (1993) 612
Nitsch, K. and M. Rodová, Differential thermal analysis study of lead bromide 134 (1993) 386
Niwa, E., see Mochizuki 131 (1993) 41
Nobe, Y., see Sugimoto 140 (1994) 349
Noda, T., see Naritsuka 131 (1993) 186
Noda, Y., see Mikami 140 (1994) 429
Noh, S.K., see Lee 138 (1994) 136
Nomura, Y., see Goto 136 (1994) 104
Nomura, Y., see Gotoda 136 (1994) 246
Nomura, Y., see Gotoda 140 (1994) 277
Norman, A.G., see Philips 140 (1994) 249
Notomi, M., see Nishida 132 (1993) 91
Novák, J., M. Klaus and K.W. Benz, Sulphur incorporation in GaSb layers grown by liquid phase electroepitaxy 139 (1994) 206
Novin, F., see Brown 135 (1994) 523
Novotný, I., see Červeň 131 (1993) 546
Nunez, V., see Giebultowicz 138 (1994) 877
Nunoshita, M., see Gotoda 140 (1994) 277
Nurmikko, A.V., see Ding 138 (1994) 719
Nurmikko, A.V., see Salokatve 138 (1994) 1077
Nutt, S.R., see Chien 137 (1994) 175

Obara, Y., see Inoue 131 (1993) 347
Oesterle, U., see Gailhanou 140 (1994) 205
Ogata, K., see Mozume 136 (1994) 287
Ogawa, A., see Chichibu 140 (1994) 388
Ogawa, H., H. Ohta and Y. Waseda, Thermal diffusivity measurement of $LiNbO_3$ melts doped with MgO by the laser flash method 133 (1993) 255
Ogawa, K., see Miura 138 (1994) 1046
Ogawa, T., see Miyakoshi 136 (1994) 152
Oglebsy, C.S., E. Bucher, C. Kloc and H. Hohl, Growth of faceted niobium diselenide 137 (1994) 289
Oh, D.-K., see Yoo 132 (1993) 43
Oh, E., see Fromherz 138 (1994) 580
O'Hare, D., see Foord 136 (1994) 127
Ohashi, Y., see Oka 137 (1994) 479
Ohishi, M., see Haga 132 (1993) 575
Ohishi, M., see Yoneta 138 (1994) 110
Ohkawa, K., see Saiki 138 (1994) 805
Ohki, A., see Matsuoka 138 (1994) 727
Ohkubo, M., see Yamamoto 137 (1994) 415
Ohmi, K., Y. Yamano, S.T. Lee, T. Ueda, S. Tanaka and H. Kobayashi, Growth and characterization of SrS/ZnS multilayered electroluminescent thin films grown by hot wall technique 138 (1994) 1061
Ohmori, K., see Haga 132 (1993) 575
Ohmori, Y., see Fukatsu 136 (1994) 315
Ohnesorge, B., see Deleporte 138 (1994) 884
Ohnishi, T., see Fukatsu 136 (1994) 315

Ohno, H., see Goto 136 (1994) 104
Ohno, T., see Matsuoka 138 (1994) 727
Ohshima, N., see Pak 140 (1994) 244
Ohshima, T., see Hariu 136 (1994) 157
Ohshita, Y. and N. Hosoi, In-situ monitoring of surface reactions in Si vapor phase epitaxial growth by surface photo-absorption method 131 (1993) 495
Ohsuna, T., see Inoue 131 (1993) 347
Ohta, H., see Ogawa 133 (1993) 255
Ohta, H., see Kanie 138 (1994) 145
Ohta, S., see Honjo 131 (1993) 111
Ohtsuka, K., see Imaizumi 136 (1994) 366
Ohtsuka, K., see Kaito 140 (1994) 123
Oka, K., M.J.V. Menken, Z. Tarnawski, A.A. Menovsky, A.M. Moe, T.S. Han, H. Unoki, T. Ito and Y. Ohashi, Crystal growth of $La_{2-x}Sr_xCuO_{4-\delta}$ by the travelling-solvent floating-zone method 137 (1994) 479
Okabe, H., see Taki 131 (1993) 13
Okabe, H., see Seki 132 (1993) 25
Okada, Y., see Kumashiro 132 (1993) 611
Okahisa, T., see Okumura 136 (1994) 361
Okajima, M., see Suzuki 133 (1993) 303
Okamoto, M., see Mitsuhara 136 (1994) 195
Okamoto, T., A. Yamada, M. Konagai and K. Takahashi, Polarized photoluminescence in vacancy-ordered Ga_2Se_3 138 (1994) 204
Okamoto, T., see Tojima 138 (1994) 408
Okano, Y., see Hirata 131 (1993) 145
Okano, Y., T. Ikeya, K. Hoshikawa and T. Fukuda, Behavior of $RAlO_3$ (R = Ho, Er and Dy) during crystal growth by the Czochralski method 131 (1993) 616
Okano, Y., see Matsumoto 132 (1993) 348
Okano, Y., see Kang 140 (1994) 435
Okazaki, M., see Wada 132 (1993) 115
Oktyabrsky, S.R., see Joshkin 132 (1993) 209
O'Keefe, S.S., see Chen 134 (1993) 162
Oku, H., see Fukatsu 136 (1994) 315
Okumura, H., S. Misawa, T. Okahisa and S. Yoshida, Epitaxial growth of cubic and hexagonal GaN by gas source molecular beam epitaxy using a microwave plasma nitrogen source 136 (1994) 361
Okumura, K., see Fukatsu 136 (1994) 315
Okumura, M., see Kumashiro 132 (1993) 611
Okumura, T., see Tomomura 138 (1994) 764
Okuno, Y., H. Asahi and S. Gondo, Theoretical consideration on the metalorganic molecular beam epitaxy growth mechanism of III–V semiconductors by molecular orbital calculation 136 (1994) 83
Okuno, Y., see Marx 136 (1994) 204
Okuno, Y., see Liu 136 (1994) 250
Okuno, Y., T. Kawano, M. Koguchi, K. Nakamura and K. Kakibayashi, Dislocation reduction in InP layers grown on sawtooth-patterned GaAs substrates 137 (1994) 313
Olego, D.J., see Wolk 138 (1994) 1071
Olego, D.J., see Chen 138 (1994) 1078
Olivier, J., see Mathet 132 (1993) 241
Omote, K., see Shigematsu 137 (1994) 509
O'Neill, M., see Pier 138 (1994) 889
Onishi, T., see Ichino 138 (1994) 28
Onizawa, S., see Muranoi 138 (1994) 255
Ono, K., see Bove 136 (1994) 261
Ono, N., M. Kida, Y. Arai and K. Sahira, A numerical study of the influence of feeding polycrystalline silicon granules on melt temperature in the continuous Czochralski process 132 (1993) 297
Ono, N., M. Kida, Y. Arai, K. Abe and K. Sahira, A new technique for controlling the dopant concentration in the double-crucible method 135 (1994) 359
Ono, N., M. Kida, Y. Arai and K. Sahira, A numerical study on oxygen transport in silicon melt in a double-crucible method 137 (1994) 427
Onuma, K., T. Kameyama and K. Tsukamoto, In situ study of surface phenomena by real time phase shift interferometry 137 (1994) 610
Ooshima, H., see Sazaki 135 (1994) 199
Ooshima, H., see Sazaki 139 (1994) 95
Orlikovsky, A.A., see Joshkin 132 (1993) 209
Ortenberg, M. von, see Schikora 138 (1994) 8
Ortenberg, M. von, see Lang 138 (1994) 81
Ortiz, C., see Blatter 139 (1994) 120
Osadchuk, V.V., see Oseledchik 131 (1993) 199
Osadchuk, V.V., see Oseledchik 135 (1994) 373
Osaka, J., see Ikuta 136 (1994) 114
Oseledchik, Yu.S., V.V. Osadchuk, A.L. Prosvirnin and A.F. Selevich, Growth of high-quality barium metaborate crystals from Na_2O–NaF solution 131 (1993) 199
Oseledchik, Yu.S., A.L. Prosvirnin, V.V. Starshenko, V.V. Osadchuk, A.I. Pisarevsky, S.P. Belokrys, A.S. Korol, N.V. Svitanko, A.F. Selevich and S.A. Krikunov, Crystal growth and properties of strontium tetraborate 135 (1994) 373
Oshima, M., N. Taniguchi and T. Kobayashi, Numerical investigation of three-dimensional melt convection with the magnetic Czochralski method 137 (1994) 48
Ossau, W., see Waag 138 (1994) 155
Osten, H.J., see Krüger 135 (1994) 246
Osten, W. von der, see Mayer 138 (1994) 195
Ostrogorsky, A.G. and G. Müller, Normal and zone solidification using the submerged heater method 137 (1994) 64
Ota, T., S. Otake and I. Iwasa, Metalorganic chemical vapor deposition growth of Ga-rich ($x < 0.5$) $Ga_xIn_{1-x}P$ on GaAs 133 (1993) 207

Ota, T., S. Otake and I. Iwasa, Metalorganic chemical vapor deposition growth of Ga-rich ($x > 0.5$) $Ga_xIn_{1-x}P$ on GaAs (E) 135 (1994) 646
Otake, S., see Ota 133 (1993) 207
Otake, S., see Ota 135 (1994) 646
Otani, S. and Y. Ishizawa, Preparation of TiB_2 single crystals by the floating zone method 140 (1994) 451
Otsubo, M., see Izumi 133 (1993) 123
Otsuka, N., see Hua 138 (1994) 367
Otsuka, N., see Han 138 (1994) 464

Padeletti, G., see Mathet 132 (1993) 241
Pain, G.N., see Russo 131 (1993) 124
Pak, K., see Maruyama 131 (1993) 316
Pak, K., see Maruyama 139 (1994) 19
Pak, K., I. Saitoh, N. Ohshima and H. Yonezu, In-situ maskless selective area epitaxy of GaAs using a low-energy Ga focused ion beam 140 (1994) 244
Palosz, W. and H. Wiedemeier, Residual gas pressures in sealed fused silica glass ampoules 131 (1993) 193
Pandey, R.K., M. Hannan and K.K. Raina, Single crystal growth of $Bi_2CaSr_2Cu_2O_{8+x}$ superconductor by traveling zone method 137 (1994) 268
Pang, L., see Taylor 135 (1994) 157
Pang, S.J., see Chai 135 (1994) 639
Pantke, K.-H., see Erland 138 (1994) 800
Park, H.L., see Hwang 138 (1994) 131
Park, H.L., see Lee 138 (1994) 136
Park, H.M., K.I. Seo and S.J. Chung, Morphology of $Y_3Fe_5O_{12}$ single crystals grown from high temperature solution 134 (1993) 43
Park, K.-S., see Mikami 140 (1994) 429
Park, R.M., see Calhoun 138 (1994) 352
Park, S.J., J.R. Ro, J.K. Sim and E.H. Lee, Monoethylarsine as a novel replacement for unprecracked arsine source in the chemical beam epitaxial growth of GaAs using trimethylgallium and triethylgallium 136 (1994) 138
Park, S.J., J.R. Ro, J.K. Sim and E.H. Lee, Low carbon incorporation in GaAs grown by chemical beam epitaxy using unprecracked arsine, trimethylgallium and triethylgallium 136 (1994) 143
Park, Y., M. Skowronski and T.M. Rosseel, Incorporation of aluminum and oxygen in dimethylaluminum methoxide doped GaAs during organometallic vapor phase epitaxy 137 (1994) 442
Park, Y.J., see Kim 139 (1994) 231
Parker, S.C., see Titiloye 131 (1993) 533
Parkin, S.S.P., see Farrow 133 (1993) 47
Parry, M.K. and A. Krier, Liquid phase epitaxial growth and photoluminescence of Mn-doped InGaAs with InAs-enriched composition 139 (1994) 238
Parsons, J.D., see Hahn 134 (1993) 90
Partanen, J., see Prieur 132 (1993) 599
Pashley, D.W., see Zhang 131 (1993) 300
Pashley, D.W., see Zhang 132 (1993) 331
Patel, D.H., see Arora 131 (1993) 268
Paulsson, G., see Junno 136 (1994) 78
Pautrat, J.L., see Legras 138 (1994) 585
Pawelek, R., see Karlicek, Jr. 131 (1993) 204
Pearton, S.J., see Abernathy 136 (1994) 11
Pelekanos, N.T., see Haacke 138 (1994) 831
Pelletier, C.M., see Granger 138 (1994) 486
Pemble, M.E., see Hoare 137 (1994) 347
Pendergrass, T.K., see Rosch 137 (1994) 54
Peng, X.-D., see Li 139 (1994) 129
Peng, Y.G., see Guan 138 (1994) 534
Perkowitz, S., see Feng 138 (1994) 239
Perlov, D. and M. Roth, Isothermal growth of β-barium metaborate single crystals by continuous feeding in the top-seeded solution growth configuration 137 (1994) 123
Permogorov, S., see Mayer 138 (1994) 195
Perrin, A., see Guilloux-Viry 132 (1993) 396
Perrin, S.D., see Bangert 132 (1993) 231
Peschiera, E., see Benaissa 131 (1993) 5
Pesek, A., see Abramof 135 (1994) 447
Peshev, P., see Varadinov 131 (1993) 97
Péter, Á., see Polgár 134 (1993) 219
Peterson, D.E., see Pettit 139 (1994) 302
Petit, S., G. Coquerel and P. Hartman, Nucleation and crystal growth of molecular solvates with several conformations both in solution and in solid state; application to some hydrated copper(II) sulfoxinates 137 (1994) 585
Pet'kov, I.S. and B.S. Red'kin, Calculation of the stationary cross-section form of non-axisymmetrical crystals growing from the melt 131 (1993) 598
Petri, W., see Klingshirn 138 (1994) 786
Petrich, G.S., see Lu 138 (1994) 1
Petrosyan, A.G., Crystal growth of laser oxides in the vertical Bridgman configuration 139 (1994) 372
Petrovic, J.J., see Pettit 139 (1994) 302
Petruzzello, J., R. Drenten and J.M. Gaines, Improvement in lasing characteristics of II–VI blue-green lasers using quaternary and ternary alloys to produce pseudomorphic heterostructures 138 (1994) 686
Pettit, D.R., D.E. Peterson, K.A. Kubat-Martin, J.J. Petrovic, H. Sheinberg, Y. Coulter and D.E. Day, Processing yttrium barium copper oxide superconductor in near-zero gravity 139 (1994) 302

Petzow, G., see Krämer 140 (1994) 157
Pfeffer, T., see Joyce 135 (1994) 31
Pfender, E., see Snail 137 (1994) 676
Philips, B.A., A.G. Norman, T.Y. Seong, S. Mahajan, G.R. Booker, M. Skowronski, J.P. Harbison and V.G. Keramidas, Mechanism for CuPt-type ordering in mixed III–V epitaxial layers 140 (1994) 249
Phillips, M.C., see Wang 138 (1994) 508
Phillips, M.C., see Miles 138 (1994) 523
Phillips, M.C., see Swenberg 138 (1994) 692
Pidgeon, C.R., see Prior 138 (1994) 94
Piekarczyk, W. and S. Prawer, Diamond–vapour interface and processes proceeding on it during growth of diamond crystals. II. Diamond (011) face 135 (1994) 172
Pier, Th., K. Hieke, B. Henninger, W. Heimbrodt, O. Goede, H.-E. Gumlich, J.E. Nicholls, M. O'Neill, S.J. Weston and B. Lunn, Magnetic field dependence of the exciton transfer in semimagnetic double quantum well structures 138 (1994) 889
Piffault, N., E. Gil, J. Leymarie, C. Monier, S.A. Clark, M. Anderson, R. Cadoret, A. Vasson and A.M. Vasson, Epitaxial growth and kinetic study of mismatched (Ga,In)As/InP layers grown by hydride vapour phase epitaxy 135 (1994) 11
Piotrowska, A., see Grabecki 138 (1994) 481
Pisarevsky, A.I., see Oseledchik 135 (1994) 373
Pitt, G.D., see Feng 138 (1994) 239
Plaas-Link, A., see Hennig 135 (1994) 513
Plesiewicz, W., see Grabecki 138 (1994) 481
Ploog, K.H., see Tournié 135 (1994) 97
Pohl, U.W., G.H. Kudlek, A. Klimakow and A. Hoffmann, Shallow impurity- and defect-related complexes in undoped ZnSe crystals 138 (1994) 385
Pohl, U.W., see Schumann 138 (1994) 910
Point, J.-J. and J.J. Janimak, An evaluation of the theories of regimes of nucleation controlled crystal growth as applied to polymers 131 (1993) 501
Polgár, K. and Á. Péter, Etching study on beta barium metaborate (β-BaB_2O_4) single crystals 134 (1993) 219
Polity, A., R. Krause-Rehberg, V. Zlomanov, V. Stanov, A. Chatchaturov and S. Mäkinen, Study of vacancy defects in PbSe and $Pb_{1-x}Sn_xSe$ by positron annihilation 131 (1993) 271
Ponce, F.A., see Mazuelas 131 (1993) 465
Ponzoni, C., see Chen 138 (1994) 1078
Poon, H.C., see Feng 138 (1994) 239
Popovici, G., see Chao 140 (1994) 454
Portuné, M., see Woggon 138 (1994) 988
Potapenko, S.Yu., Two-dimensional mass transfer models for high-rate crystal growth from solution 133 (1993) 132
Potapenko, S.Yu., Threshold for step percolation through impurity fence 133 (1993) 141
Potapenko, S.Yu., Moving of step through impurity fence 133 (1993) 147
Povey, I.M., see Hoare 137 (1994) 347
Prahl, J., see DeLucas 135 (1994) 183
Prasad, V., see Anselmo 131 (1993) 247
Prasad, V., see Anselmo 134 (1993) 116
Prawer, S., see Piekarczyk 135 (1994) 172
Prelas, M.A., see Chao 140 (1994) 454
Presser, N., Ch. Fricke, G. Kudlek, R. Heitz, A. Hoffmann and I. Broser, Energy transfer processes via the interface of ZnSe/GaAs epilayers 138 (1994) 820
Price, M.W., R.N. Andrews, C.H. Su, S.L. Lehoczky and F.R. Szofran, The effect of a transverse magnetic field on the microstructure of directionally solidified CdTe 137 (1994) 201
Prieur, E., T. Tuomi, J. Partanen, E. Yli-Juuti and M. Tilli, Synchrotron topographic study of defects in liquid-encapsulated Czochralski-grown semi-insulating gallium arsenide wafers 132 (1993) 599
Prior, K.A., B. Murdin, C.R. Pidgeon, S.Y. Wang, I. Hauksson, J.T. Mullins, G. Horsburgh and B.C. Cavenett, Compensation processes in molecular beam epitaxially grown zinc selenide doped with nitrogen 138 (1994) 94
Prior, K.A., see Mullins 138 (1994) 357
Prior, K.A., see Wang 138 (1994) 647
Prior, K.A., see Kawakami 138 (1994) 759
Prokofiev, V.V., J.P. Andreeta, C.J. de Lima, M.R.B. Andreeta, A.C. Hernandes, J.F. Carvalho, A.A. Kamshilin and T. Jääskeläinen, Growth of single-crystal photorefractive fibers of $Bi_{12}SiO_{20}$ and $Bi_{12}TiO_{20}$ by the laser-heated pedestal growth method 137 (1994) 528
Prosvirnin, A.L., see Oseledchik 131 (1993) 199
Prosvirnin, A.L., see Oseledchik 135 (1994) 373
Puls, J., see Schülzgen 138 (1994) 575
Puls, J., V. Jungnickel, F. Henneberger and A. Schülzgen, Carrier dynamics in CdS quantum dots embedded in glass 138 (1994) 1004
Purich, D.L., see Brown 135 (1994) 523
Pusey, M.L., see Forsythe 139 (1994) 89
Puzanov, N.I. and A.M. Eidenzon, Formation of the bands of anomalous oxygen precipitation in Czochralski-grown Si crystals 137 (1994) 642

Qhalid Fareed, R.S., R. Dhanasekaran and P. Ramasamy, Investigation on the con-

centration profiles of As during the current-controlled liquid phase epitaxial growth of GaAs 140 (1994) 28
Qiu, J., see DePuydt 138 (1994) 667
Queisser, H.-J., see Weishart 137 (1994) 335
Quemerais, A., K.H. Khelladi, D. Lemoine, R. Granger and R. Triboulet, Angle resolved X-ray photoelectron spectroscopy of the surface of $Hg_{0.85}Zn_{0.15}Te$ and after passivation processes 138 (1994) 934
Quesada, X., see Kuhn 138 (1994) 448
Quesada, X., see Qu'Hen 138 (1994) 1079
Qu'Hen, B., see Kuhn 138 (1994) 448
Qu'Hen, B., X. Quesada, W.S. Kuhn, J.E. Bourée, L. Svob, A. Lusson and O. Gorochov, Growth of MgTe and $Zn_{1-x}Mg_xTe$ thin films by metalorganic vapour phase epitaxy 138 (1994) 1079
Quon, D.H.H., S. Chehab, J. Aota, A.K. Kuriakose, S.S.B. Wang, M.Z. Saghir and H.L. Chen, Float-zone crystal growth of bismuth germanate and numerical simulation 134 (1993) 266

Rabedeau, T.A., see Farrow 133 (1993) 47
Račiukaitis, G., see Gavryushin 138 (1994) 924
Racz, J.M., see Gallagher 138 (1994) 970
Radelaar, S., see Werner 136 (1994) 322
Radelaar, S., see Werner 136 (1994) 338
Radhakrishan, K. see Yoon 131 (1993) 1
Radhakrishnan, K., see Yoon 134 (1993) 240
Radhakrishnan, K., see Zhang 135 (1994) 441
Radkovič, J., see Maček 132 (1993) 99
Radomsky, L., G.-J. Yi and G.F. Neumark, Observation of preferential donor–acceptor pairing in ZnSe:Na 138 (1994) 99
Radomsky, L., see Yi 138 (1994) 208
Railson, S.V., see Wolverson 138 (1994) 656
Raina, K.K., see Pandey 137 (1994) 268
Rajavel, D., J.J. Zinck and J.E. Jensen, Metalorganic molecular beam epitaxial growth kinetics and doping studies of (001) ZnSe 138 (1994) 19
Rajavel, D., A. Conte and C.J. Summers, Pyrolysis characteristics of iodine precursors for gas source n-type doping of II–VI compounds 140 (1994) 327
Rajendran, S., K. Holmes and A. Menna, Three-dimensional magnetic induction model of an octagonal edge-defined film-fed growth system 137 (1994) 77
Rajendran, S., see Bhihe 137 (1994) 86
Ramasamy, P., see Jayavel 131 (1993) 105
Ramasamy, P., see Narayana Kalkura 132 (1993) 617
Ramasamy, P., see Ravi 133 (1993) 212
Ramasamy, P., see Gopalakrishnan 137 (1994) 235
Ramasamy, P., see Jayavel 137 (1994) 273
Ramasamy, P., see Balakrishnan 137 (1994) 309
Ramasamy, P., see Kumar 137 (1994) 535
Ramasamy, P., see Ravi 137 (1994) 598
Ramasamy, P., see Qhalid Fareed 140 (1994) 28
Ramda, A.K., see Fromherz 138 (1994) 580
Ramirez-Piscina, L., see Caroli 132 (1993) 377
Ram-Mohan, L.R., see Meyer 138 (1994) 981
Rao, G.S.J., see DeLucas 135 (1994) 183
Rao, S.M., K.M. Chen, K.S. Law, S.R. Sheen, Y.F. Chen, M.K. Wu and C.P. Khattak, Influence of Ta doping on the growth and superconducting properties of $YBa_2Cu_3O_{6+\delta}$ crystals 139 (1994) 190
Ravi, G., S. Ankubumar and P. Ramasamy, On the growth and characterization of mixed crystals of the triglycine sulphate family 133 (1993) 212
Ravi, G., K. Srinivasan, S. Anbukumar and P. Ramasamy, Growth and characterization of sulphate mixed L-arginine phosphate and ammonium dihydrogen phosphate/potassium dihydrogen phosphate mixed crystals 137 (1994) 598
Ray, B., see Arterton 138 (1994) 1051
Ray, B., see Viney 138 (1994) 1055
Razbirin, B.S., see Erland 138 (1994) 800
Red'kin, B.S., see Pet'kov 131 (1993) 598
Redwing, J.M., T.F. Kuech, D. Saulys and D.F. Gaines, Study of the gas phase chemistry in the silicon doping of GaAs grown by metalorganic vapor phase epitaxy using tertiarybutylarsine as the Group V source 135 (1994) 423
Reed, J.D., see Chen 134 (1993) 162
Regel, L.L, see Shen 132 (1993) 250
Regel, L.L, see Shen 132 (1993) 351
Regnet, M.M., see Heinke 135 (1994) 53
Reiche, P., see Uecker 137 (1994) 278
Reichert, P., see DeLucas 135 (1994) 183
Reichow, J., J. Griesche, N. Hoffmann, C. Muggelberg, H. Rossmann, L. Wilde, F. Henneberger and K. Jacobs, Molecular beam epitaxial growth and characterization of ZnSe of GaAs 131 (1993) 277
Reier, F.W., E. Jahn, N. Agrawal, P. Harde and N. Grote, Doping characteristics of undoped and Zn-doped In(Ga)AlAs layers grown by low-pressure metalorganic vapour phase epitaxy 135 (1994) 463
Reisinger, A.R., see Meyer 138 (1994) 981
Reisinger, T., see Wolf 135 (1994) 113
Reislöhner, U., see Rüb 138 (1994) 285
Reithmaier, J.P., see Baxter 131 (1993) 419
Ren, F., see Abernathy 136 (1994) 11
Ren, J., D.B. Eason, L.E. Churchill, Z. Yu, C. Boney, J.W. Cook, Jr., J.F. Schetzina and N.A. El-Masry, Integrated het-

erostructure devices composed of II–VI materials with Hg-based contact layers 138 (1994) 455
Ren, J., see Eason 138 (1994) 703
Renucci, M.A., see Frandon 138 (1994) 513
Rettenmayr, M.E., see Glicksman 137 (1994) 1
Richards, R.N., see DeLucas 135 (1994) 183
Richter, H., see Kühne 132 (1993) 357
Riedel, R., see Seher 137 (1994) 452
Rieger, A., Z. Jerman and O. Söhnel, A new crystal modification of $MgSO_3 \cdot 3H_2O$ 137 (1994) 595
Riesz, F., Rotated tilting in lattice-mismatched heteroepitaxial systems 140 (1994) 213
Rigo, C., A. Antolini, C. Cacciatore, C. Coriasso, L. Lazzarini and G. Salviati, Growth parameter optimization of short period (< 50 Å) InGaAs/InP short period superlattices by chemical beam epitaxy for photonic devices 136 (1994) 293
Rinas, U., see Rudolph 138 (1994) 249
Ring, T.A., see Rubattel 135 (1994) 135
Ringle, M.D., see Han 138 (1994) 464
Ripamonti, A., see Falini 137 (1994) 577
Ristić, R., B.Yu. Shekunov and J.N. Sherwood, Growth of the tetrahedral faces of sodium chlorate crystals in the presence of dithionate impurity 139 (1994) 336
Ro, J.R., see Park 136 (1994) 138
Ro, J.R., see Park 136 (1994) 143
Robert, M.C., see Boué 133 (1993) 246
Roberts, D.H., see Brandon 132 (1993) 261
Roberts, J.S., see Smith 134 (1993) 140
Roberts, J.S., C.C. Button and A. Chew, The incorporation of oxygen into InAlAs, the role of trimethylindium (TMI) 135 (1994) 365
Roberts, K.J., see Clydesdale 135 (1994) 331
Robertson, A., see Jordan 137 (1994) 224
Robins, L.H., see Kaiser 137 (1994) 136
Rodová, M., see Nitsch 131 (1993) 612
Rodová, M., see Nitsch 134 (1993) 386
Rodríguez-Clemente, R., B. Aspar, N. Azema, B. Armas, C. Combescure, J. Durand and A. Figueras, Morphological properties of chemical vapour deposited AlN films 133 (1993) 59
Rodríguez-Clemente, R., see Sangwal 140 (1994) 447
Rodriguez, R., see Torrent 131 (1993) 115
Rolfe, S.J., see Sudersena Rao 136 (1994) 179
Roos, B. and F. Ernst, Thermal-stress-induced dislocations in GeSi/Si heterostructures 137 (1994) 457
Rosch, W., A. Fripp, W. Debnam and T.K. Pendergrass, Heat transfer measurements in the Bridgman configuration 137 (1994) 54
Röseler, J., see Heimbrodt 138 (1994) 601
Rosenauer, A., see Grün 138 (1994) 150
Rosenauer, A., see Naumov 138 (1994) 595
Rosenblum, W.M., see DeLucas 135 (1994) 183
Rosenman, I., see Boué 133 (1993) 246
Rosseel, T.M., see Park 137 (1994) 442
Rossel, C., see Guilloux-Viry 132 (1993) 396
Rossi, J.C., see Lubyshev 132 (1993) 533
Rössler, U., see Mayer 138 (1994) 195
Rössler, U., see Freytag 138 (1994) 499
Rossmann, H., see Reichow 131 (1993) 277
Rössner, U., J. Laugier and N. Magnea, Structural characterization of $Cd_{1-x}Zn_xTe(001)$ layers grown by molecular beam epitaxy on $Cd_{0.96}Zn_{0.04}Te$ substrates 137 (1994) 393
Roth, A.P., see Sudersena Rao 136 (1994) 179
Roth, M., see Angert 137 (1994) 116
Roth, M., see Perlov 137 (1994) 123
Rothfritz, H., R. Müller, C. Buchegger, G. Tränkle and G. Weimann, Chemical beam epitaxial growth of GaInAs(P)/InP heterostructures for laser applications 136 (1994) 225
Rotter, L.D., see Kaiser 137 (1994) 136
Rouleau, C.M., see Calhoun 138 (1994) 352
Roure, S., see Veesler 135 (1994) 505
Roussignol, P., see Deleporte 138 (1994) 884
Rouzaud, A., see Sixou 137 (1994) 605
Rouzaud, A., see Favier 140 (1994) 237
Rüb, M., N. Achtziger J. Meier, U. Reislöhner, P. Rudolph, M. Wienecke and W. Witthuhn, Complex formation in In- and Ag/Cu-doped CdTe 138 (1994) 285
Rubattel, S., J. Lemaître, P. Bowen and T.A. Ring, Aqueous solubility of Y, Ba and Cu oxalates in the system $[Y(OH)_3$, $Ba(OH)_2$, $Cu(OH)_2]$–$H_2C_2O_4$–$[HNO_3/NaOH]$–H_2O 135 (1994) 135
Ruddock, I.S., see Sharp 131 (1993) 457
Rudolph, P., see Zimmermann 131 (1993) 276
Rudolph, P., U. Rinas and K. Jacobs, Systematic steps towards exactly stoichiometric and uncompensated CdTe Bridgman crystals 138 (1994) 249
Rudolph, P., see Rüb 138 (1994) 285
Rudolph, T., see Anzai 134 (1993) 227
Rudra, A., see Carlin 131 (1993) 387
Rudra, A., H. Sugiura, J. Ling, J.M. Bonard, J.D. Ganière, M. de Fays, D. Araujo and M. Ilegems, One-step growth of buried heterostructures by chemical beam epitaxy over patterned InP substrates 136 (1994) 173
Rudra, A., R. Houdré, J.F. Carlin and M. Ilegems, Dynamics of island formation in the growth of InAs/InP quantum wells 136 (1994) 278
Rueter, M.A. and J.M. Vohs, The chemistry of the initial stages of the growth of ZnSe on GaAs(100) using diethylzinc and diethylselenium precursors 131 (1993) 49
Rühle, W.W., see Haacke 138 (1994) 831
Ruiz, A., see Mazuelas 135 (1994) 123

Rulmont, A., see Cloots 135 (1994) 496

Ruppert, P., D. Hommel, T. Behr, H. Heinke, A. Waag and G. Landwehr, Molecular beam epitaxial growth mechanism of ZnSe epilayers on (100) GaAs as determined by reflection high-energy electron diffraction, transmission electron microscopy and X-ray diffraction 138 (1994) 48

Rushworth, S.A., see Smith 134 (1993) 140

Rushworth, S.A., see Jones 135 (1994) 285

Rushworth, S.A., see Davies 136 (1994) 133

Russo, S.P., G.N. Pain, P.N. Johnston and R.G. Elliman, Determination of composition, thickness and growth rate profiles of MOCVD grown $Hg_{1-x}Cd_xTe$ 131 (1993) 124

Ryall, R.G., see Ryall 133 (1993) 87

Ryall, R.L., R.G. Ryall, I.R. Doyle and V.R. Marshall, The dependence of the measurement of crystal growth on the state of crystal aggregation: implication for urolithiasis research 133 (1993) 87

Rzepka, E., A. Aoudia, M. Cuniot, A. Lusson, Y. Marfaing, R. Triboulet, G. Brémond, G. Marrakchi, K. Cherkaoui, M.C. Busch, J.M. Koebel, M. Hage-Ali, P. Siffert, J.Y. Moisan, P. Gravey, N. Wolffer and O. Moine, Optical and thermal spectroscopy of vanadium-doped CdTe and related photorefractive effect 138 (1994) 244

Sabbides, T.G. and P.G. Koutsoukos, The crystallization of calcium carbonate in artificial seawater; role of the substrate 133 (1993) 13

Sabharwal, S.C., see Muthe 139 (1994) 323

Sacco, Jr., A., see DeLucas 135 (1994) 183

Sacuto, A., see Le 135 (1994) 1

Saeed, M.R., see Yeboah 135 (1994) 323

Sagawa, M., see Kagawa 139 (1994) 309

Saghir, M.Z., see Quon 134 (1993) 266

Saghir, Z., see Li 131 (1993) 83

Sahin, H., see Kuhn 138 (1994) 448

Sahira, K., see Ono 132 (1993) 297

Sahira, K., see Ono 135 (1994) 359

Sahira, K., see Ono 137 (1994) 427

Saiki, T., K. Takeuchi, K. Ema, M. Kuwata-Gonokami, K. Ohkawa and T. Mitsuyu, Free induction decay and quantum beat of excitons in ZnSe 138 (1994) 805

Saito, H., see Haga 132 (1993) 575

Saito, H., see Yoneta 138 (1994) 110

Saito, Y. and T. Yoshikawa, Bamboo-shaped carbon tube filled partially with nickel 134 (1993) 154

Saito, Y., see Kaito 134 (1993) 157

Saito, Y., see Kaito 140 (1994) 123

Saitoh, I., see Pak 140 (1994) 244

Saitoh, M., see Yamada 132 (1993) 48

Sakaguchi, T., see Kaito 134 (1993) 157

Sakai, K., see Mishimura 134 (1993) 293

Sakai, K., see Kingetsu 137 (1994) 633

Sakai, K., see Nishimura 138 (1994) 114

Sakaki, M., Y. Aoki, Y. Nakamuta and M. Ishii, Dendritic diamonds synthesized by simple hot-filament-assisted chemical vapor deposition 133 (1993) 329

Sakakibara, K., see Maruyama 131 (1993) 316

Sakamoto, T., see Kizuka 131 (1993) 439

Sakamoto, T., see Kaito 134 (1993) 157

Sakata, S., W. Itoyama, I. Fujii and K. Iishi, Preparation of low-temperature Li_3VO_4 single crystal by floating zone technique 135 (1994) 555

Sakuma, T., see Mochizuki 135 (1994) 259

Sakurai, Y., see Inoue 131 (1993) 347

Saleh, M., see Woggon 138 (1994) 988

Salk, M., M. Fiederle, K.W. Benz, A.S. Senchenkov, A.V. Egorov and D.G. Matioukhin, CdTe and $CdTe_{0.9}Se_{0.1}$ crystals grown by the travelling heater method using a rotating magnetic field 138 (1994) 161

Salk, M., see Fiederle 138 (1994) 529

Salokatve, A., H. Jeon, M. Hovinen, P. Kelkar, A.V. Nurmikko, D.C. Grillo, L. He, J. Han, Y. Fan and R.L. Gunshor, Ridge waveguide, separate confinement green-blue heterostructure lasers 138 (1994) 1077

Salviati, G., see Rigo 136 (1994) 293

Salzman, J., see Maayan 135 (1994) 23

Saminadayar, K., see Bassani 138 (1994) 607

Samuelson, L., see Junno 136 (1994) 78

Sänger, W., see Heinrichs 133 (1993) 196

Sangwal, K., S. Veintemillas-Verdaguer, J. Torrent-Burgués and R. Rodríguez-Clemente, Decoration of growth and dissolution steps on the surfaces of L-arginine phosphate monohydrate crystals 140 (1994) 447

Santoro, G.J., see Singh 135 (1994) 619

Santoro, G.J., see Singh 139 (1994) 158

Santos, M.B., see Cunningham 136 (1994) 282

Saraie, J., see Ichikawa 138 (1994) 14

Sasaki, H., E. Tokizaki, K. Terashima and S. Kimura, Density measurement of molten silicon by an improved Archimedian method 139 (1994) 225

Sasaki, M., see Mashita 131 (1993) 61

Sasaki, M., see Zhang 132 (1993) 337

Sasaki, M., see Yoshida 133 (1993) 201

Sasaki, M., see Yoshida 135 (1994) 633

Sasaki, M., see Yoshida 136 (1994) 37

Sasaki, M. and S. Yoshida, Surface reactivity and stability of Ga-deposited GaAs oxide mask for selective area growth of GaAs 136 (1994) 241

Sasaki, M., see Muranoi 138 (1994) 255

Sasaki, S., see Yao 138 (1994) 290

Sasaki, T., M. Kitamura and I. Mito, Selec-

tive metalorganic vapor phase epitaxial growth of InGaAsP/InP layers with bandgap energy control in InGaAs/InGaAsP multiple-quantum well structures 132 (1993) 435
Sasaki, Y., see Suzuki 134 (1993) 67
Sasaki, Y., Y. Fukuma, T. Abe, Z. Zhu, T. Yao, J. Takehara and M. Kitagawa, Metalorganic molecular beam epitaxy of III–V compounds using tertiarybutyl-V as group-V sources 136 (1994) 162
Sasamoto, K., see Matsumoto 138 (1994) 63
Sasaoka, C., see Mochizuki 135 (1994) 259
Sasaura, M. and S. Miyazawa, Twin-free single crystal growth of $NdGaO_3$ 131 (1993) 413
Sato, M., see Ishibara 137 (1994) 375
Sato, M., see Markgraf 140 (1994) 343
Satoh, M., see Inoue 131 (1993) 347
Saulys, D., see Redwing 135 (1994) 423
Savino, R., see Viviani 133 (1993) 217
Sawada, T., see Anzai 134 (1993) 227
Sawada, T., see Markgraf 135 (1994) 253
Sawaki, N., see Detchprohm 137 (1994) 170
Sawers, L.J.M., see Fisher 138 (1994) 86
Sawicki, M., M.A. Brummell, P.A.J. de Groot, G.J. Tomka, D.E. Ashenford and B. Lunn, Magnetic properties of $Cd_{1-x}Mn_xTe$ grown by molecular beam epitaxy 138 (1994) 900
Sayah, D., see Mzerd 140 (1994) 365
Sazaki, G., H. Ooshima and J. Kato, Effect of supersaturation ratio on the growth rate and number of protease thermolysin crystals 135 (1994) 199
Sazaki, G., S. Aoki, H. Ooshima and J. Kato, Effect of self-degradation products on crystallization of protease thermolysin 139 (1994) 95
Scarlett, B., see Van Drunen 134 (1993) 196
Schaff, W.J., see Chen 134 (1993) 162
Schalge, R., see Uecher 137 (1994) 278
Schall, C.A., J.M. Wiencek, M. Yarmush and E. Arnold, Lysozyme crystal growth reduced at high pressure 135 (1994) 548
Schanz, U., see Yu 132 (1993) 606
Schäufele, U., see Brion 134 (1993) 281
Schenk, M., see Gille 139 (1994) 165
Schetzina, J.F., see Vaudo 138 (1994) 430
Schetzina, J.F., see Ren 138 (1994) 455
Schetzina, J.F., see Eason 138 (1994) 703
Schiffers, W., see Hermans 138 (1994) 612
Schikora, D., H. Hausleitner, S. Einfeldt, C.R. Becker, Th. Widmer, C. Giftge, K. Lübke, K. Lischka, M. von Ortenberg and G. Landwehr, Epitaxial overgrowth of II–VI compounds on patterned substrates 138 (1994) 8
Schikora, D., see Lang 138 (1994) 81
Schikora, D., see Brunthaler 138 (1994) 559
Schilz, J., see Kürten 139 (1994) 1
Schlom, D.G., D. Anselmetti, J.G. Bednorz, Ch. Gerber and J. Mannhart, Epitaxial growth of cuprate superconductors from the gas phase 137 (1994) 259
Schmelzer, J., see Slezov 132 (1993) 419
Schmidbauer, E., see Yu 132 (1993) 606
Schmolke, R., E. Schöll, M. Nägele and J. Gutowski, Nonlinear optical switching fronts in CdS 138 (1994) 213
Schneider, A., see Söllner 138 (1994) 35
Schneider, A., see Gleitsmann 138 (1994) 324
Schneider, A., see Taudt 138 (1994) 418
Schneider, A., see Hermans 138 (1994) 612
Schöll, E., see Schmolke 138 (1994) 213
Scholl, M., see Söllner 138 (1994) 35
Scholl, M., see Tönnies 138 (1994) 362
Scholl, M., see Waag 138 (1994) 437
Scholl, M., see Hermans 138 (1994) 612
Scholl, S., see Waag 131 (1993) 607
Scholl, S., see Hommel 138 (1994) 1076
Schön, S., M.L. Fearheiley, K. Diesner and S. Fiechter, The phase relations in the system $ZnAs_2$–Ge 135 (1994) 601
Schönert, H., see Heinrichs 133 (1993) 196
Schönherr, E., see Matsumoto 135 (1994) 154
Schowalter, L.J., see Li 135 (1994) 78
Schüll, K., see Hommel 138 (1994) 1076
Schülzgen, A., F. Kreller, F. Henneberger, M. Lowisch and J. Puls, Exciton dynamics and high density effects in ZnSe/ZnMnSe quantum structures grown by molecular beam epitaxy 138 (1994) 575
Schülzgen, A., see Puls 138 (1994) 1004
Schumann, D., H.-E. Mahnke, B. Spellmeyer, G. Sulzer, H. Waldmann, W.-D. Zeitz, U.W. Pohl and H.-E. Gumlich, Magnetic or nonmagnetic behavior of isolated scandium ions in II–VI compounds 138 (1994) 910
Schwerdtfeger, K., see Brückner 139 (1994) 351
Sciortino, Jr., P.F., see Tsang 136 (1994) 42
Scott, C.G., see Dhese 138 (1994) 443
Seabaugh, A.C., see Beam 136 (1994) 1
Sébenne, C., see Le 135 (1994) 1
Seebauer, E.G., see Mendicino 134 (1993) 377
Segawa, Y., see Mochizuki 135 (1994) 318
Seher, M., J. Bill, F. Aldinger and R. Riedel, Crystallization kinetics of polysilazane-derived amorphous silicon nitride 137 (1994) 452
Seidl, A., see Koai 137 (1994) 41
Seidl, A., G. McCord, G. Müller and H.-J. Leister, Experimental observation and numerical simulation of wave patterns in a Czochralski silicon melt 137 (1994) 326
Seifert, W., see Keller 140 (1994) 33
Seisyan, R.P., see Jakobson 138 (1994) 225

Sekar, C., see Jayavel 131 (1993) 105
Seki, K., J.M. Frye, H. Okabe and J.B. Halpern, Laser-induced chemical vapor deposition of aluminum from trimethylaluminum: wavelength and temperature dependence 132 (1993) 25
Selevich, A.F., see Oseledchik 131 (1993) 199
Selevich, A.F., see Oseledchik 135 (1994) 373
Senchenkov, A.S., see Salk 138 (1994) 161
Senga, K., see Ichikawa 138 (1994) 14
Seo, K.I., see Park 134 (1993) 43
Seong, T.-Y., see Aindow 133 (1993) 168
Seong, T.Y., see Philips 140 (1994) 249
Sergent, M., see Guilloux-Viry 132 (1993) 396
Sermage, B., see Alexandre 136 (1994) 235
Šesták, J., see Štěpánek 135 (1994) 290
Šesták, J., see Šestáková 140 (1994) 426
Šestáková, V., P. Hubík, B. Štěpánek and J. Krištofik, GaSb single crystals doped with manganese 132 (1993) 345
Šestáková, V., see Štěpánek 135 (1994) 290
Šestáková, V., B. Štěpánek, J.J. Mareš and J. Šesták, Hydrogen passivation of residual acceptors in GaSb single crystals 140 (1994) 426
Seta, M., see Kim 136 (1994) 310
Seth, G.L., see Bagai 139 (1994) 259
Seto, S., A. Tanaka, F. Takeda and K. Matsuura, Defect-induced emission band in CdTe 138 (1994) 346
Sha, Y.-G., C.-H. Su and F.R. Szofran, Thermodynamic analysis and mass flux of the HgZnTe–HgI_2 chemical vapor transport system 131 (1993) 574
Shang, S.X., see Wang 139 (1994) 86
Shang, S.X., see Fu 139 (1994) 319
Shao Peifa, see Xu 133 (1993) 267
Sharma, B.B., see Sharma 131 (1993) 565
Sharma, R.K., V.K. Singh, N.K. Nayyar, S.R. Gupta and B.B. Sharma, Horizontal casting for the growth of $Hg_{1-x}Cd_xTe$ by solid state recrystallization 131 (1993) 565
Sharp, J.H., T.P.J. Han, B. Henderson, R. Illingworth and I.S. Ruddock, Dopant incorporation in single-crystal fibre growth by the laser-heated miniature pedestal growth technique 131 (1993) 457
Sharp, J.H., T.J.P. Han, B. Henderson and R. Illingworth, Instability in the growth of Ti:Al_2O_3 single-crystal fibres 140 (1994) 79
Shaw, N., see Jones 138 (1994) 279
Sheeham, J.E., see Sigalovsky 134 (1993) 313
Sheen, D.B., see Elban 137 (1994) 304
Sheen, S.R., see Rao 139 (1994) 190
Sheinberg, H., see Pettit 139 (1994) 302
Shekunov, B.Yu., see Ristić 139 (1994) 336
Shen Bingfu, see Xu 133 (1993) 267
Shen Bingfu, see Xu 134 (1993) 337
Shen, D.Z., X.W. Fan and B.J. Yang, Light interference effect in optical bistability of multiple quantum well etalons 138 (1994) 625
Shen, D.Z., see Zhang 138 (1994) 838
Shen, J., D.K. Aidun, L.L. Regel and W.R. Wilcox, Characterization of precipitates in CdTe and $Cd_{1-x}Zn_xTe$ grown by vertical Bridgman–Stockbarger technique 132 (1993) 250
Shen, J., D.K. Aidun, L.L. Regel and W.R. Wilcox, Etch pits originating from precipitates in CdTe and $Cd_{1-x}Zn_xTe$ grown by the vertical Bridgman–Stockbarger method 132 (1993) 351
Shen, T.C., see Zhou 134 (1993) 167
Shen, X.Q., M. Tanaka, K. Wada and T. Nishinaga, Molecular beam epitaxial growth of GaAs, AlAs and $Al_{0.45}Ga_{0.55}As$ on (111)A-(001) V-grooved substrates 135 (1994) 85
Sherwin, M.E., see Munns 136 (1994) 166
Sherwood, J.N., see Elban 137 (1994) 304
Sherwood, J.N., see Ristić 139 (1994) 336
Shi, Z., Solution growth of silicon on patterned amorphous SiO_2 substrates 135 (1994) 273
Shibano, E., see Takahashi 137 (1994) 240
Shibli, S.M., see Zhang 138 (1994) 310
Shigematsu, K., see Anzai 134 (1993) 227
Shigematsu, K., Y. Anzai, K. Omote and S. Kimura, Thermal properties of molten bismuth germanates 137 (1994) 509
Shih, W.-C. and M.-S. Wu, Growth of ZnO films on GaAs substrates with a SiO_2 buffer layer by RF planar magnetron sputtering for surface acoustic wave applications 137 (1994) 319
Shih, Z.W., see Wang 139 (1994) 47
Shima, A., see Mihashi 133 (1993) 281
Shimamura, K., see Chani 132 (1993) 173
Shimamura, K., see Chani 132 (1993) 335
Shimamura, K., see Chani 133 (1993) 181
Shimomura, S., see Marx 136 (1994) 204
Shin, J., K. Chiu, G.B. Stringfellow and R.W. Gedridge, Jr., Diisopropylantimonyhydride (DIPSbH) for low temperature epitaxial growth of InSb 132 (1993) 371
Shinn, M., see Hultman 135 (1994) 309
Shirafuji, J. see Sugino 139 (1994) 15
Shirakashi, J., R.T. Yoshioka, A. Miyano, M. Konagai and K. Takahashi, Effect of the addition of an elemental Ga flux on the metalorganic molecular beam epitaxial growth of heavily carbon-doped InGaAs 136 (1994) 186
Shirakata, S., see Chichibu 131 (1993) 551
Shirakata, S., see Chichibu 140 (1994) 388
Shiraki, Y., see Fukatsu 136 (1994) 315
Shiraki, Y., see Kato 136 (1994) 355

Shishikura, M., see Chichibu 140 (1994) 388
Shupegin, M.L., see Bublik 140 (1994) 84
Siche, D., see Hartmann 138 (1994) 260
Sidawi, I.M.S. and S.N. Tewari, Macrosegregation during plane front directional solidification of CsI–1 wt% TlI alloy 131 (1993) 230
Siegrist, T., see Haile 131 (1993) 352
Siffert, P., see Rzepka 138 (1994) 244
Sigalovsky, J., J.S. Haggerty and J.E. Sheeham, Growth of spinel single crystal fibers by the laser-heated floating-zone technique and their characterization as high temperature reinforcements 134 (1993) 313
Silberman, E., see George 137 (1994) 299
Silberman, E., see Biao 138 (1994) 219
Silberman, E., see Azoulay 138 (1994) 517
Sim, J.K., see Park 136 (1994) 138
Sim, J.K., see Park 136 (1994) 143
Simpson, J., see Mullins 138 (1994) 357
Simpson, I., see Kawakami 138 (1994) 759
Sinerius, D., see Zimmermann 131 (1993) 276
Singh, K.D., see Muthe 139 (1994) 323
Singh, N.B., A.M. Stewart, R.D. Hamacher, J. Talvacchio, R. Mazelsky, G.J. Santoro, W.M.B. Duval and R. DeWitt, Effect of thermal convection on the quality of lead bromide crystals 135 (1994) 619
Singh, N.B., M. Gottlieb, G.B. Brandt, A.M. Stewart, R. Mazelsky and M.E. Glicksman, Growth and characterization of mercurous halide crystals: mercurous bromide system 137 (1994) 155
Singh, N.B., A.M. Stewart, R.D. Hamacher, R. Mazelsky, W.M.B. Duval, G.J. Santoro, R. DeWitt and S.L. Lehoczky, Convecto-diffusive growth of lead bromide crystals: a test of theories 139 (1994) 158
Singh, V.K., see Sharma 131 (1993) 565
Sinno, T., see Brown 137 (1994) 12
Sinvani, M., see Azoulay 137 (1994) 208
Sitter, H., see Abramof 135 (1994) 447
Sitter, H., see Lang 138 (1994) 81
Sitter, H., see Brunthaler 138 (1994) 559
Sitter, H., see Fromherz 138 (1994) 580
Sitter, H., see Neukirch 138 (1994) 849
Sitter, H., see Giebultowicz 138 (1994) 877
Sitter, H., see Belas 138 (1994) 940
Sitter, H., see Ferreira 140 (1994) 282
Sixou, B., A. Rouzaud and J.J. Favier, Growth kinetics in ultra-pure bismuth using a thermoelectric method for interface temperature measurements 137 (1994) 605
Skevington, P.J., see Levoguer 136 (1994) 109
Skevington, P.J., see Davies 136 (1994) 133
Skośkiewicz, T., see Grabecki 138 (1994) 481
Skowronski, M., see Park 137 (1994) 442
Skowronski, M., see Philips 140 (1994) 249
Škrić, D., N. Filipovic-Vinceković, V. Babić-Ivančić and Lj. Tušek-Božić, Influence of sodium cholate on the crystallization of calcium oxalate 133 (1993) 189
Skromme, B.J., see Zhang 138 (1994) 310
Skromme, B.J., W. Liu, K.F. Jensen and K.P. Giapis, Effects of C incorporation on the luminescence properties of ZnSe grown by metalorganic chemical vapor deposition 138 (1994) 338
Slezov, V.V., J. Schmelzer and J. Möller, Ostwald ripening in porous materials 132 (1993) 419
Slobozhanin, L.A., M.A. Svechkareva and V.A. Tatarchenko, Stability of the melt meniscus during growth of crystals by the technique of pulling from shaper (TPS) under zero-gravity conditions 133 (1993) 273
Sluyters, J.H., see Torrent 131 (1993) 115
Smith, A.D., see Bangert 132 (1993) 231
Smith, C., see DeLucas 135 (1994) 183
Smith, L.M., S.A. Rushworth, A.C. Jones, J.S. Roberts, A. Chew and D.E. Sykes, Oxygen incorporation in aluminium-based semiconductors grown by metalorganic vapour phase epitaxy 134 (1993) 140
Smith, R.W., see Li 133 (1993) 175
Snail, K.A., Z.P. Lu, R. Weimer, J. Heberlein, E. Pfender and L.M. Hanssen, Confirmation of {113} facets on diamond grown by chemical vapor deposition 137 (1994) 676
Södervall, U., see Wang 135 (1994) 455
Soga, T., T. Suzuki, M. Mori, T. Jimbo and M. Umeno, The effects of the growth parameters on the initial stage of epitaxial growth of GaP on Si by metalorganic chemical vapor deposition 132 (1993) 134
Soga, T., T. Suzuki, M. Mori, Z.K. Jiang, T. Jimbo and M. Umeno, Electrical properties of GaP on Si grown by metalorganic chemical vapor deposition 132 (1993) 414
Söhnel, O., see Reiger 137 (1994) 595
Söllner, J., M. Scholl, A. Schneider, M. Heuken and J. Woitok, Optimization of strained short-period ZnSSe/ZnSe superlattices grown by metalorganic vapour phase epitaxy 138 (1994) 35
Söllner, J., see Hermans 138 (1994) 612
Someno, Y., see Zhang 132 (1993) 337
Song, S.H., see Guan 138 (1994) 534
Soni, R.K., see Asahi 136 (1994) 268
Sonnenberg, K., see Koai 137 (1994) 59
Soukiassian, P., see Chen 138 (1994) 1078
Šourek, Z., see Štěpánek 135 (1994) 290
Spahn, W., see Waag 138 (1994) 155
Spellmeyer, B., see Schumann 138 (1994) 910
Sperling, V., see Woggon 138 (1994) 976
SpringThorpe, A.J., see Moore 136 (1994) 230

Spurdens, P.C., see Harlow 140 (1994) 19
Srinivasan, K., see Ravi 137 (1994) 598
Sriram, S., see Hobgood 137 (1994) 181
Stadler, W., see Fiederle 138 (1994) 529
Stander, E., see Barrette 131 (1993) 153
Stanley, R.P., see Doran 138 (1994) 826
Stanov, V., see Polity 131 (1993) 271
Stanzl, H., see Wolf 135 (1994) 113
Stanzl, H., see Wolf 138 (1994) 412
Stanzl, H., see Kuhn 138 (1994) 448
Stanzl, H., see Naumov 138 (1994) 595
Stanzl, H., see Klingshirn 138 (1994) 786
Starshenko, V.V., see Oseledchik 135 (1994) 373
Stassen, S., see Cloots 135 (1994) 496
Stavola, M., see Abernathy 136 (1994) 11
Stein, R.A. and P. Lanig, Control of polytype formation by surface energy effects during the growth of SiC monocrystals by the sublimation method 131 (1993) 71
Štěpánek, B., see Šestáková 132 (1993) 345
Štěpánek, B., Z. Šourek, V. Šestáková, J. Šesták and J. Kub, Study of low Te-doped GaSb single crystals 135 (1994) 290
Štěpánek, B., see Šestáková 140 (1994) 426
Stewart, A.M., see Singh 135 (1994) 619
Stewart, A.M., see Singh 137 (1994) 155
Stewart, A.M., see Singh 139 (1994) 158
Stewart, H., see Kawakami 138 (1994) 759
Stobbs, W.M., see Baxter 131 (1993) 419
Stoica, T. and L. Vescan, Misfit dislocations in finite lateral size $Si_{1-x}Ge_x$ films grown by selective epitaxy 131 (1993) 32
Stoichkov, S.D., see Bikov 140 (1994) 100
Stoll, B., see Behet 135 (1994) 434
Stolz, H., see Mayer 138 (1994) 195
Stolz, W., see Bertram 132 (1993) 179
Stolzenberger, R.A., see Loiacono 131 (1993) 323
Story, T., see Grodzicka 138 (1994) 1034
Storz, F.G., see Chiu 136 (1994) 148
Storz, F.G., see Cunningham 136 (1994) 282
Strachan, D.J., M.M. Li, M.C. Tamargo and B.A. Weinstein, Acceptor state instabilities in ZnSe under hydrostatic pressure 138 (1994) 318
Stringfellow, G.B., see Shin 132 (1993) 371
Stringfellow, G.B., see Huang 134 (1993) 29
Stringfellow, G.B., Fundamentals of thin film growth 137 (1994) 212
Strunk, H.P., see Marek 134 (1993) 14
Su, C.-H., see Sha 131 (1993) 574
Su, C.-H., see Price 137 (1994) 201
Su, C.-H., see Biao 138 (1994) 219
Su, Y.K., see Li 137 (1994) 421
Subramanian, B., see Desatnik 131 (1993) 589
Subramanian, C., see Jayavel 131 (1993) 105
Subramanian, C., see Jayavel 137 (1994) 273
Subramanian, C., see Kumar 137 (1994) 535
Sudersena Rao, T., see Houghton 136 (1994) 56
Sudersena Rao, T., C. Lacelle, M. Davies, R. Barber, P. Chow-Chong, J. McCaffery, S.J. Rolfe, A.P. Roth, B. Benyon and B. Foster, Chemical beam epitaxy of InP on planar and non-planar substrates 136 (1994) 179
Sudo, R., see Chichibu 140 (1994) 388
Suemune, I., see Miyakoshi 136 (1994) 152
Suemune, I., Quantitative study of mechanism responsible for high operating voltage in II–VI laser diodes 138 (1994) 714
Suemune, I., Y. Fujii and M. Fujimoto, Improvement of electrical and optical properties of ZnSSe p–n heterostructure diodes with optimization in metalorganic vapor phase epitaxy 138 (1994) 750
Suenaga, K., see Mozume 136 (1994) 287
Sugawara, H., see Suzuki 133 (1993) 303
Sugawara, H., see Itaya 138 (1994) 768
Sugawara, M., see Mukai 137 (1994) 388
Sugimoto, A., Y. Nobe and K. Yamagishi, Crystal growth and optical characterization of $Cr,Ca:Y_3Al_5O_{12}$ 140 (1994) 349
Sugimoto, H., see Gotoda 140 (1994) 277
Sugimoto, T., see Hirata 131 (1993) 145
Sugimoto, T., see Chin 132 (1993) 82
Sugino, T., K. Kawarai, M. Maeda and J. Shirafuji, Low temperature epitaxial growth of InP by remote plasma-assisted metalorganic chemical vapor deposition 139 (1994) 15
Sugiura, H., see Yamaguchi 136 (1994) 29
Sugiura, H., K. Wakita, R. Iga and T. Yamada, Electroabsorption and modulator characteristics of InGaAsP multiple quantum well laser structures grown by laser-assisted metalorganic molecular beam epitaxy 136 (1994) 64
Sugiura, H., see Rudra 136 (1994) 173
Sugiura, H., see Mitsuhara 136 (1994) 195
Sugiura, H., see Iga 136 (1994) 273
Sugiyama, K., see Chani 132 (1993) 173
Sugiyama, K., see Chani 132 (1993) 335
Sugiyama, K., see Miyake 134 (1993) 174
Sugiyama, Y., see Taguchi 134 (1993) 147
Sugiyama, Y., I. Hatakeyama and I. Yokohama, Growth of *a*-axis strontium barium niobate single crystal fibers 134 (1993) 255
Suh, S.H., see Moon 138 (1994) 944
Suh, S.H., see Kwak 138 (1994) 950
Suisky, D., see Heimbrodt 138 (1994) 601
Suito, H., see Takaoka 137 (1994) 493
Sukegawa, T., see Tanaka 135 (1994) 269
Sukegawa, T., see Watanabe 137 (1994) 245
Sulzer, G., see Schumann 138 (1994) 910
Summers, C.J., see Maruyama 137 (1994) 435
Summers, C.J., see Rajavel 140 (1994) 327

Sun, D. and E. Towe, Molecular beam epitaxial growth of (Al,Ga)As/GaAs heterostructures and Si doping characterization study on vicinal (110) GaAs substrates 132 (1993) 166

Sun, D., R. Beanland, T.B.F. Joyce, J.V. Armstrong, T.J. Bullough and P.J. Goodhew, Orientations and morphology of Al layers grown on GaAs by chemical beam epitaxy 132 (1993) 592

Sun, D., see Yan 136 (1994) 306

Sun, J., see Li 131 (1993) 83

Sun Suoying, see Hou 133 (1993) 71

Sunamura, H., see Fukatsu 136 (1994) 315

Sundersheshu, B.S., see Bagai 139 (1994) 259

Sundgren, J.E., see Glass 132 (1993) 504

Suriura, H., see Nishida 132 (1993) 91

Surridge, R.K., see Moore 136 (1994) 230

Suzuki, A., see Tomomura 138 (1994) 764

Suzuki, K., N. Akita, K. Inagaki, A. Nishihata, N. Takojima and S. Dairaku, Alloy broadening in photoluminescence spectra of $Cd_{1-x}Zn_xTe$ crystals grown from Te solution 138 (1994) 199

Suzuki, M., K. Itaya, Y. Nishikawa, H. Sugawara and M. Okajima, Reduction of residual oxygen incorporation and deep levels by substrate misorientation on InGaAlP alloys 133 (1993) 303

Suzuki, M., see Uenoyama 138 (1994) 301

Suzuki, N., see Arita 132 (1993) 71

Suzuki, S., S. Kitagawa, H. Iwata and Y. Sasaki, Structure and resistivity of heat-treated polycrystalline zinc sulfide prepared by chemical vapor deposition 134 (1993) 67

Suzuki, T., see Soga 132 (1993) 134

Suzuki, T., see Soga 132 (1993) 414

Svechkareva, M.A., see Slobozhanin 133 (1993) 273

Svitanko, N.V., see Oseledchik 135 (1994) 373

Svob, L., see Kuhn 138 (1994) 448

Svob, L., see Qu'Hen 138 (1994) 1079

Svoboda, J., see Höschl 138 (1994) 956

Swanson, M.L., see Hughes 138 (1994) 1040

Swenberg, J.F., see Wang 138 (1994) 508

Swenberg, J.F., see Miles 138 (1994) 523

Swenberg, J.F., M.W. Wang, R.J. Miles, M.C. Phillips, A.T. Hunter, J.O. McCaldin and T.C. McGill, Advances in the development of graded injector visible light emitters 138 (1994) 692

Sykes, D.E., see Smith 134 (1993) 140

Szczerbakow, A., and H. Berger, Investigation of the composition of vapour-grown $Pb_{1-x}Sn_xSe$ crystals ($x \leqslant 0.4$) by means of lattice parameter measurements 139 (1994) 172

Szczerbakow, A., see Leszczynski 135 (1994) 565

Szofran, F.R., see Sha 131 (1993) 574

Szofran, F.R., see Price 137 (1994) 201

Szofran, F.R., see Biao 138 (1994) 219

Tacano, M., see Taguchi 134 (1993) 147

Tachibana, M., see Hirata 131 (1993) 145

Tachikawa, S., see Wada 132 (1993) 115

Tadatomo, K., see Watanabe 137 (1994) 245

Taghizadeh, M.R., see Mullins 138 (1994) 357

Taguchi, F., see Watanabe 131 (1993) 181

Taguchi, T., Y. Takeuchi, K. Matugatani, Y. Ueno, T. Hattori, Y. Sugiyama and M. Tacano, Critical layer thickness of $In_{0.80}Ga_{0.20}As/In_{0.52}Al_{0.48}As$ heterostructures 134 (1993) 147

Taguchi, T., see Yamada 138 (1994) 570

Taike, A., see Migita 138 (1994) 391

Tajima, M., see Kang 135 (1994) 623

Takada, T., see Mochizuki 135 (1994) 259

Takahashi, J., M. Kanaya and Y. Fujiwara, Sublimation growth of SiC single crystalline ingots on faces perpendicular to the (0001) basal plane 135 (1994) 61

Takahashi, K., see Shirakashi 136 (1994) 186

Takahashi, K., see Okamoto 138 (1994) 204

Takahashi, K., see Tojima 138 (1994) 408

Takahashi, N.S., S. Fujiwara, K. Kohno, E. Shibano and S. Kurita, AlGaInP/AlGaAs double heterostructure light emitting diode grown by liquid phase epitaxy 137 (1994) 240

Takakuwa, Y., T. Yamaguchi and N. Miyamoto, Si dangling bonds on Si(100) surface during gas-source molecular beam epitaxy with Si_2H_6 136 (1994) 328

Takakuwa, Y., see Horie 136 (1994) 344

Takamura, K., see Gu 137 (1994) 472

Takano, H., see Izumi 133 (1993) 123

Takano, Y., see Maruyama 131 (1993) 316

Takaoka, H. and H. Suito, Substitution of Co^{2+} and/or Ti^{4+} ions in strontium hexaferrite grown from $SrO–Fe_2O_3–B_2O_3$ melts 137 (1994) 493

Takebayashi, K., see Zhu 138 (1994) 397

Takebayashi, K., see Zhu 138 (1994) 619

Takeda, F., see Seto 138 (1994) 346

Takehara, J., see Sasaki 136 (1994) 162

Takeuchi, K., see Saiki 138 (1994) 805

Takeuchi, S., see Iwanaga 134 (1993) 275

Takeuchi, Y., see Taguchi 134 (1993) 147

Taki, S., K. Ishida, H. Okabe and K. Matsushige, Direct observation of the growth process of organic crystals by scanning tunnelling microscopy 131 (1993) 13

Takiguchi, H., see Tomomura 138 (1994) 764

Takojima, N., see Suzuki 138 (1994) 199

Takojima, N., F. Iida, K. Imai and K. Kumazaki, Photoluminescence of ultrathin ZnSe–ZnTe superlattices 138 (1994) 633
Talvacchio, J., see Singh 135 (1994) 619
Tamada, H., see Yamada 132 (1993) 48
Tamamura, T., see Nishida 132 (1993) 91
Tamargo, M.C., see Zhang 138 (1994) 310
Tamargo, M.C., see Strachan 138 (1994) 318
Tan, M.R.T., see Houng 136 (1994) 216
Tanaka, A., A. Watanabe, M. Kimura and T. Sukegawa, The solute-feeding Czochralski method for homogeneous GaInSb bulk alloy pulling 135 (1994) 269
Tanaka, A., see Zhang 136 (1994) 200
Tanaka, A., see Watanabe 137 (1994) 245
Tanaka, A., see Seto 138 (1994) 346
Tanaka, H., see Bove 136 (1994) 261
Tanaka, H., see Nagai 140 (1994) 65
Tanaka, K., see Zhu 138 (1994) 397
Tanaka, M., see Liliental-Weber 132 (1993) 103
Tanaka, M., see Shen 135 (1994) 85
Tanaka, N., see Kizuka 131 (1993) 439
Tanaka, S., see Gu 137 (1994) 472
Tanaka, S., see Ohmi 138 (1994) 1061
Tang, S.H., see Ji 138 (1994) 187
Taniguchi, N., see Oshima 137 (1994) 48
Tansley, T.L., see Alexiev 135 (1994) 367
Tansley, T.L., see Butcher 140 (1994) 9
Tao Xutang, see Hou 133 (1993) 71
Tao, Y. and S. Kou, Flow visualization in floating zone crystal growth – a videotape movie 137 (1994) 72
Tapfer, L., see Mazuelas 131 (1993) 465
Tappura, K. and J. Laurila, Unstable regions in the growth of GaInAsP by gas-source molecular beam epitaxy 131 (1993) 309
Tarnawski, Z., see Oka 137 (1994) 479
Tarui, Y., see Hatayama 136 (1994) 333
Taskar, N.T., see Wolk 138 (1994) 1071
Tatarchenko, V.A., see Slobozhanin 133 (1993) 273
Tatarenko, S., see Bassani 138 (1994) 607
Tate, A., see Chen 136 (1994) 221
Tatsumi, T., see Aoyama 136 (1994) 349
Tatsuoka, H., see Kuwabara 138 (1994) 964
Taudt, W., see Hoffmann 138 (1994) 379
Taudt, W., A. Schneider, M. Heuken, Ch. Fricke and A. Hoffmann, Low temperature growth and plasma enhanced nitrogen doping of ZnSe by metalorganic vapour phase epitaxy 138 (1994) 418
Taudt, W., see Fricke 138 (1994) 815
Taylor, G.H., J.D. Fitz Gerald, L. Pang and M.A. Wilson, Cathode deposits in fullerene formation – microstructural evidence for independent pathways of pyrolytic carbon and nanobody formation 135 (1994) 157
Taylor, S.J., B. Beaumont and R. Herberholz, Carbon doping of $Ga_xIn_{1-x}As$ by atmospheric pressure organometallic vapour phase epitaxy 132 (1993) 61
Tazoh, Y., see Kobayashi 131 (1993) 138
Tedenac, J.C., see Mzerd 140 (1994) 365
Temkin, D.E., Interface structure with meniscus in free solidification of a thin sample 139 (1994) 113
Teng, D., P. Mandeville and L.F. Eastman, Growth limitations of strained multiple quantum wells 135 (1994) 36
Terashima, K., see Anzai 134 (1993) 235
Terashima, K., see Sasaki 139 (1994) 225
Terauchi, M., see Liliental-Weber 132 (1993) 103
Tewari, S.N., see Sidawi 131 (1993) 230
Thamizhavel, A., see Jayavel 137 (1994) 273
Theis, W.M., see Bicknell-Tassius 138 (1994) 425
Thivet, C., see Guilloux-Viry 132 (1993) 396
Thomas, J.E., see Boone 139 (1994) 27
Thompson, B.E., see Desatnik 131 (1993) 589
Thompson, P., see Mullins 138 (1994) 357
Thompson, P., see Wang 138 (1994) 647
Thomson, J.A., see DeLucas 135 (1994) 183
Thordson, J., see Wang 135 (1994) 455
Tilli, M., see Prieur 132 (1993) 599
Titiloye, J.O., S.C. Parker and S. Mann, Atomistic simulation of calcite surfaces and the influence of growth additives on their morphology 131 (1993) 533
Tkalich, A.K., see Bublik 140 (1994) 84
Tojima, H., T. Okamoto, A. Yamada, M. Konagai and K. Takahashi, Nitrogen doping into ZnSe by the catalysis of transition metal 138 (1994) 408
Tojyo, T., see Fujita 138 (1994) 737
Tokita, S., M. Kobayashi and A. Yoshikawa, In-situ probing the ZnSe metalorganic molecular beam growth process by surface photo-interference method 136 (1994) 376
Tokizaki, E., see Sasaki 139 (1994) 225
Tomka, G.J., see Sawicki 138 (1994) 900
Tomm, J.W., K.H. Herrmann, W. Hoerstel, M. Lindstaedt, H. Kissel and F. Fuchs, On the nature of the excitonic luminescence in narrow-gap $Hg_{1-x}Cd_xTe$ ($x \approx 0.3$) 138 (1994) 175
Tomomura, Y., S. Hirata, T. Okumura, M. Kitagawa, A. Suzuki and H. Takiguchi, Dependence of device characteristics on quantum well thickness in ZnSe/ZnCdSe multi-quantum well blue-green laser diodes 138 (1994) 764
Tompa, G.S., see Anderson 135 (1994) 383
Toney, M.F., see Farrow 133 (1993) 47
Tönnies, D., G. Bacher, A. Forchel, A. Waag, Th. Litz, D. Hommel, Ch. Becker, G. Landwehr, M. Heuken and M. Scholl, Optical study of interdiffusion in CdTe and ZnSe based quantum wells 138 (1994) 362

Torrent, J., R. Rodriguez and J.H. Sluyters, The induction time in the electrocrystallization of lead chloride and lead sulphate on an amalgamated lead electrode 131 (1993) 115
Torrent-Burgués, J., The Gibbs energy and the driving force at crystallization from solution 140 (1994) 107
Torrent-Burgués, J., see Sangwal 140 (1994) 447
Tosaka, H., see Kobayashi 138 (1994) 745
Toth, A., see Belas 138 (1994) 940
Tournié, E. and K.H. Ploog, Surface stoichiometry, epitaxial morphology and strain relaxation during molecular beam epitaxy of highly strained InAs/$Ga_{0.47}In_{0.53}As$ heterostructures 135 (1994) 97
Towe, E., see Sun 132 (1993) 166
Toyoda, T., see Kawakami 136 (1994) 371
Tränckle, G., see Rothfritz 136 (1994) 225
Traulsen, T., see Erb 137 (1994) 487
Triboulet, R., see Guergouri 132 (1993) 20
Triboulet, R., see El Mokri 138 (1994) 168
Triboulet, R., see Rzepka 138 (1994) 244
Triboulet, R., see Quemerais 138 (1994) 934
Triboulet, R., see Guergouri 139 (1994) 6
Trinh, E., see DeLucas 135 (1994) 183
Trivedi, R., see Jamgotchian 134 (1993) 181
Tromson-Carli, A., see El Mokri 138 (1994) 168
Troppenz, U., B. Hüttl, K.O. Velthaus and R.H. Mauch, Trailing edge phenomena in SrS:$CeCl_3$ thin film electroluminescent devices 138 (1994) 1017
Trotta, P.P., see DeLucas 135 (1994) 183
Truchsess, N. von, see Buda 138 (1994) 652
Tsang, W.T., T.H. Chiu and R.M. Kapre, Monolayer chemical beam etching 135 (1994) 377
Tsang, W.T., R. Kapre and P.F. Sciortino, Jr., In-situ dry etching of InP using phosphorus trichloride and regrowth inside a chemical beam epitaxial growth chamber 136 (1994) 42
Tsang, W.T., see Chen 136 (1994) 221
Tseitlin, M., see Angert 137 (1994) 116
Tsuboi, N., see Uchiki 138 (1994) 873
Tsujino, M., see Yamamoto 137 (1994) 415
Tsukamoto, K., see Onuma 137 (1994) 610
Tsvetkov, V.F., see Glass 132 (1993) 504
Tu, Chaoyang, Yidong Huang, Zundu Luo and Guang Chen, Crystal growth of $KY(WO_4)_2:Er^{3+}:Nd^{3+}$ 135 (1994) 636
Tu, C.W., B.W. Liang and T.P. Chin, Heavily carbon-doped p-type GaAs and $In_{0.53}Ga_{0.47}As$ grown by gas-source molecular beam epitaxy using carbon tetrabromide 136 (1994) 191
Tuomi, T., see Prieur 132 (1993) 599
Tušek-Božić, Lj., see Škrtić 133 (1993) 189
Tvarožek, V., see Červeň 131 (1993) 546
Uchida, M., see Chichibu 140 (1994) 388
Uchida, T., see Miyamoto 136 (1994) 210
Uchida, T., see Inaba 136 (1994) 297
Uchida, T., see Yokouchi 136 (1994) 302
Uchiki, H., H. Kinto, T. Moriyama, S. Hata, N. Tsuboi, J. Wang and S. Iida, Exciton and Raman processes of ZnS under tunable picosecond light pulse excitations 138 (1994) 873
Uda, S., Influence of unit cluster size on nucleation rate of $Li_2B_4O_7$ melt 140 (1994) 128
Uecker, R., P. Reiche, V. Alex, J. Doerschel and R. Schalge, The problem of twinning in $NdGaO_3$ Czochralski crystals 137 (1994) 278
Ueda, T., see Ohmi 138 (1994) 1061
Ueltzen, M., The Verneuil flame fusion process: substances 132 (1993) 315
Ueno, Y., see Taguchi 134 (1993) 147
Uenoyama, T., T. Nakao and M. Suzuki, Interaction between N_2 and stabilized ZnSe surface 138 (1994) 301
Uhrig, A., see Woggon 138 (1994) 988
Ullrich, B., A. Kazlauskas, S. Zerlauth and T. Kobayashi, First realization of bistable light emitting devices 138 (1994) 234
Umeno, M., see Soga 132 (1993) 134
Umeno, M., see Soga 132 (1993) 414
Umlauff, M., see Klingshirn 138 (1994) 786
Unoki, H., see Oka 137 (1994) 479
Usami, N., see Fukatsu 136 (1994) 315
Usami, N., see Kato 136 (1994) 355
Usui, A., see Mochizuki 135 (1994) 259

Vaccaro, P., see Yoshimoto 136 (1994) 89
Vaidyan, V.K., see Narayana Kalkura 132 (1993) 617
Vaitkus, J., R. Baubinas, V. Kazlauskiene, D. Kuciauskas, J. Miskinis, U. Karlsson, M. Hammar, M. Göthelid, M. Björqvist and E. Lindberg, Scanning tunneling microscopy of CdSe single crystal cleaved and "real" surface 138 (1994) 545
Van Drunen, M.A., R. Finsy, H.G. Merkus, B. Scarlett and G.M. van Rosmalen, Measurement of cluster formation in aqueous citric acid solutions by photon correlation spectroscopy 134 (1993) 196
Van Enckevort, W.J.P., see Balzuweit 135 (1994) 297
Van Hoof, P., see Lin 133 (1993) 322
Van Loosdrecht, P.H.M., see De Boer 140 (1994) 361
Van Rosmalen, G.M., see Van Drunen 134 (1993) 196
Van Tendeloo, G., see Volkov 132 (1993) 359
Vanecek, M., see Nitsch 131 (1993) 612
Varadinov, R., V. Nikolov and P. Peshev, Growth of single crystals of Ga-, Al- or (Mn + Ti)-substituted barium hexaferrite 131 (1993) 97
Vargaftik, M.N., see Volkov 132 (1993) 359
Vasson, A., see Piffault 135 (1994) 11

Vasson, A.M., see Piffault 135 (1994) 11
Vaudin, M.D., see Kaiser 137 (1994) 136
Vaudo, R.P., J.W. Cook, Jr. and J.F. Schetzina, Atomic nitrogen production in nitrogen-plasma sources used for the growth of ZnSe:N and related alloys by molecular-beam epitaxy 138 (1994) 430
Vaughan, Q.A.E., see Joyce 132 (1993) 1
Vdovin, V.I., M.G. Mil'vidskii and T.G. Yugova, Antiphase boundaries in GaAs layers on Si and Ge 132 (1993) 477
Veesler, S., S. Roure and R. Boistelle, General concepts of hydrargillite $Al(OH)_3$ agglomeration 135 (1994) 505
Veintemillas-Verdaguer, S., see Sangwal 140 (1994) 447
Velthaus, K.O., see Troppenz 138 (1994) 1017
Venkataramanan, V., G. Dhanaraj and H.L. Bhat, Growth mechanism, dislocation etching and mechanical properties of L-arginine phosphate and deuterated L-arginine phosphate 140 (1994) 336
Venkateswara Rao, C.R., see Jayavel 131 (1993) 105
Venkateswara Rao, C.R., see Jayavel 137 (1994) 273
Verbeeck, R.M.H., see De Maeyer 135 (1994) 539
Vescan, L., see Stoica 131 (1993) 32
Vieu, C., see Gourgon 138 (1994) 590
Vilenkin, A.J. and A. Brokman, Geometric model of crystal growth between rigid walls. III. Kinetic faceting in presence of preferred interface inclination 131 (1993) 239
Viney, I.V.F., see Arterton 138 (1994) 1051
Viney, I.V.F., B.W. Arterton, B. Ray and J.W. Brightwell, Electrical and optical stimulation of luminescence in $Ca_{1-x}Cd_xS$ 138 (1994) 1055
Vinh, Le Thanh, see Le 135 (1994) 1
Vinsanji, M., see Hennig 135 (1994) 513
Vital, R.L., see Brandon 132 (1993) 261
Vivès, C., Crystallization of semi-solid magnesium alloys and composites in the presence of magnetohydrodynamic shear flows 147 (1994) 653
Viviani, A. and R. Savino, Recent developments in vapour cyrstal growth fluid dynamics 133 (1993) 217
Vogelsang, H., see Mayer 138 (1994) 195
Vohs, J.M., see Rueter 131 (1993) 49
Volkov, V.V., G. Van Tendeloo, M.N. Vargaftik and I.I. Moiseev, High-resolution electron microscopy observations of large Pd clusters 132 (1993) 359
Volz, M.E., see Biao 138 (1994) 219
Von der Osten, W., see Mayer 138 (1994) 195
Von Ortenberg, M., see Schikora 138 (1994) 8
Von Ortenberg, M., see Lang 138 (1994) 81
Von Truchsess, N., see Buda 138 (1994) 652
Vyas, J.C., see Muthe 139 (1994) 323
Waag, A., H. Heinke, S. Scholl, C.R. Becker and G. Landwehr, Growth of MgTe and $Cd_{1-x}Mg_xTe$ thin films by molecular beam epitaxy 131 (1993) 607
Waag, A., see Heinke 135 (1994) 53
Waag, A., see Ruppert 138 (1994) 48
Waag, A., F. Fischer, Th. Litz, B. Kuhn-Heinrich, U. Zehnder, W. Ossau, W. Spahn, H. Heinke and G. Landwehr, Wide gap $Cd_{1-x}Mg_xTe$: molecular beam epitaxial growth and characterization 138 (1994) 155
Waag, A., see Tönnies 138 (1994) 362
Waag, A., Th. Litz, F. Fischer, H. Heinke, S. Scholl, D. Hommel, G. Landwehr and G. Bilger, Halogen doping of II–VI semiconductors during molecular beam epitaxy 138 (1994) 437
Waag, A., see Illing 138 (1994) 638
Waag, A., see Buda 138 (1994) 652
Waag, A., see Hellmann 138 (1994) 791
Waag, A., see Bacher 138 (1994) 856
Wada, K., see Shen 135 (1994) 85
Wada, K., see Kohda 135 (1994) 629
Wada, M., see Kato 138 (1994) 373
Wada, N., M. Okazaki and S. Tachikawa, Effects of calcium-binding polysaccharides from calcareous algae on calcium carbonate polymorphs under conditions of double diffusion 132 (1993) 115
Wade, A.P., see Cook 131 (1993) 395
Wagai, A., see Naritsuka 131 (1993) 186
Wagner, B.K., see Maruyama 137 (1994) 435
Wagner, H.P., see Wolf 138 (1994) 412
Wakamatsu, N., see Iijima 135 (1994) 229
Wakita, K., see Sugiura 136 (1994) 64
Wakiyama, T., see Chichibu 140 (1994) 388
Waldmann, H., see Schumann 138 (1994) 910
Walker, J.S., and M.G. Williams, Effects of the crystal's non-zero electrical conductivity on the rotationally driven melt motion during Czochralski silicon growth with a uniform, transverse magnetic field 132 (1993) 31
Walker, J.S. and M.G. Williams, Centrifugal pumping during Czochralski silicon growth with a strong transverse magnetic field 137 (1994) 32
Walker, P.J., see Aindow 133 (1993) 168
Walsh, D., J.L. Kingston, B.R. Heywood and S. Mann, Influence of monosaccharides and related molecules on the morphology of hydroyxapatite 133 (1993) 1
Walukiewicz, W., see Wolk 138 (1994) 1071
Wang Derong, see Hao 140 (1994) 441
Wang, H., see Wang 139 (1994) 86
Wang, H., see Fu 139 (1994) 319
Wang, H., see Kong 140 (1994) 45
Wang, J., see Uchiki 138 (1994) 873

Wang Junxin, Fu Peizhen and Wu Yicheng, Growth and characterization of $Pb_xSr_{1-x}B_4O_7$ solid solution crystals 132 (1993) 329

Wang, M.L., Z.W. Shih and C.H. Lin, Reaction of α-Fe_2O_3 with $Ba(OH)_2$ under hydrothermal conditions 139 (1994) 47

Wang, M.W., J.F. Swenberg, R.J. Miles, M.C. Phillips, E.T. Yu, J.O. McCaldin, R.W. Grant and T.C. McGill, Measurement of the MgSe/$Cd_{0.54}Zn_{0.46}$Se valence band offsett by X-ray photoelectron spectroscopy 138 (1994) 508

Wang, M.W., see Miles 138 (1994) 523

Wang, M.W., see Swenberg 138 (1994) 692

Wang, S.J., see Zhang 132 (1993) 200

Wang, S.M., T.G. Andersson, W.Q. Chen, U. Södervall and J. Thordson, Growth and characterization of digital and compositionally graded AlGaAs/GaAs nonrectangular quantum wells 135 (1994) 455

Wang, S.M., see Yang 138 (1994) 629

Wang, S.S.B., see Quon 134 (1993) 266

Wang, S.Y., see Houng 136 (1994) 216

Wang, S.Y., see Prior 138 (1994) 94

Wang, S.Y., see Mullins 138 (1994) 357

Wang, S.Y., P. Thompson, G. Horsburgh, J.T. Mullins, I. Hauksson, K.A. Prior and B.C. Cavenett, A ZnSe/ZnCdSe quantum well symmetric self-electro-optic effect device operating in the blue-green region 138 (1994) 647

Wang, W.-S. and I. Bhat, Use of germanium interfacial layer for the hetero-epitaxial growth of CdTe on Si substrates 138 (1994) 43

Wang, W.S., see Aggarwal 137 (1994) 132

Wang, X.L., Z.P. Ai, S.X. Shang, H. Wang, M.H. Jiang, X.Z. Wang and D. Bäuerle, Segregation growth of large Bi_2Sr_2Ca-Cu_2O_y 90° (100) bicrystal by the self-flux method 139 (1994) 86

Wang, X.L., see Fu 139 (1994) 319

Wang, X.Z., see Wang 139 (1994) 86

Wang Zulun, see Li 139 (1994) 327

Wang, Z.Y., see Aggarwal 137 (1994) 132

Warabisako, T., see Yamaguchi 136 (1994) 29

Waseda, Y., see Ogawa 133 (1993) 255

Waseda, Y., K.T. Jacob, Y. Iguchi and T. Narushima, Theoretical estimation of the effect of minor elements on the solubility of oxygen in silicon melt 139 (1994) 357

Watabe, S., see Yanashima 138 (1994) 755

Watanabe, A., see Tanaka 135 (1994) 269

Watanabe, K. and F. Taguchi, Growth of fine and mono-sized Cr:YAG single crystals from KF solvent 131 (1993) 181

Watanabe, M., M. Eguchi, K. Kakimoto and T. Hibiya, Double-beam X-ray radiography system for three-dimensional flow visualization of molten silicon convection 133 (1993) 23

Watanabe, M., see Kakimoto 139 (1994) 197

Watanabe, S., K. Tadatomo, T. Sukegawa and A. Tanaka, The effect of indium–bismuth solvent on the composition of InGaP grown by the "yo-yo" solute feeding method 137 (1994) 245

Watanabe, T., see Asahi 136 (1994) 268

Watanabe, T., see Kaito 140 (1994) 123

Watring, D.A. and M. Johnson, Ampoule failure sensor development for semiconductor crystal growth experiments 140 (1994) 41

Watt, B., see Knight 134 (1993) 19

Webb, J.B., D.J. Lockwood and V.P. Gnezdilov, Magnetron sputter epitaxy and characterization of InSb/$In_{1-x}Al_xSb$ strained layer superlattices 137 (1994) 405

Weber, P.C., see DeLucas 135 (1994) 183

Weber, W., see Hennig 135 (1994) 513

Weckendrup, D., see Neukirch 138 (1994) 849

Weckendrup, D., see Neukirch 138 (1994) 861

Weidemann, G., J. Griesche and K. Jacobs, Kinematical calculations on reflection high-energy electron diffraction involving absorption 133 (1993) 75

Weimann, G., see Rothfritz 136 (1994) 225

Weimer, R., see Snail 137 (1994) 676

Weinhold, V., see Heimbrodt 138 (1994) 601

Weinstein, B.A., see Strachan 138 (1994) 318

Weisbuch, Recent progress in III–V quantum optoelectronic devices 138 (1994) 776

Weishart, H., A.N. Danilewsky, K.W. Benz and E. Bauser, Morphological stability during GaAs solution growth: liquid phase epitaxy versus the travelling heater method 131 (1993) 17

Weishart, H., see Marek 134 (1993) 14

Weishart, H., E. Bauser, M. Konuma and H.-J. Queisser, Monomolecular steps of ultra-low density on (100) growth faces of liquid phase epitaxial GaAs 137 (1994) 335

Weiss, E., E. Kedar and N. Mainzer, The formation of twins in ⟨111⟩ HgCdTe grown by traveling heater method and their effect on device quality 132 (1993) 191

Weiss, R., see Buhl 131 (1993) 470

Welch, C.S., see Hubert 131 (1993) 75

Weller, D., see Farrow 133 (1993) 47

Wen, J., see Kong 140 (1994) 45

Wenzl, H., see Koai 137 (1994) 59

Werckmann, J. see Benaissa 131 (1993) 5

Wernberg, A.A., D.J. Lawrence, H.J. Gysling, A.J. Filo and T.N. Blanton, Epitaxial growth of gallium arsenide thin films by spray pyrolysis using a single-source organometallic precursor 131 (1993) 176

Wernberg, A.A., H.J. Gysling and G. Braunstein, Single crystalline growth of $LiNbO_3$ on $LiTaO_5$ by spray metalorganic chemical vapor deposition using the single source precursor $LiNb(OEt)_6$ 140 (1994) 57

Werner, K., S. Butzke, S. Radelaar and P. Balk, Determination of the sticking coefficient of disilane on Si(001) using the first reflection high energy electron diffraction oscillation period 136 (1994) 322

Werner, K., S. Butzke, S. Radelaar and P. Balk, Evidence for non-hydrogen desorption limited growth of Si from disilane at very low temperatures in gas source molecular beam epitaxy? 136 (1994) 338

West, B.O., see Leech 139 (1994) 247

Weston, S.J., see Pier 138 (1994) 889

Whalen, P.O., see Khan 134 (1993) 211

Whitaker, T.J., see Foord 136 (1994) 127

Whitehouse, C.R., see Martin 136 (1994) 69

Widmer, T., see Schikora 138 (1994) 8

Widmer, T., see Lang 138 (1994) 81

Wiedemeier, H., see Palosz 131 (1993) 193

Wiencek, J.M., see Schall 135 (1994) 548

Wienecke, M., see Rüb 138 (1994) 285

Wilcox, W.R., see Shen 132 (1993) 250

Wilcox, W.R., see Shen 132 (1993) 351

Wilde, L., see Reichow 131 (1993) 277

Wilkins, S.W., see Davis 133 (1993) 230

Wilkinson, V.A., see Bangert 132 (1993) 231

Willeke, G., see Kloc 131 (1993) 448

Williams, D.J., see Cheng 135 (1994) 409

Williams, G.M., see Mullins 138 (1994) 357

Williams, J.O., see Hoare 137 (1994) 347

Williams, K.P., see Feng 138 (1994) 239

Williams, M.D., see Chiu 136 (1994) 148

Williams, M.D., see Cunningham 136 (1994) 282

Williams, M.G., see Walker 132 (1993) 31

Williams, M.G., see Walker 137 (1994) 32

Wilson, I.H., see Hsu 133 (1993) 185

Wilson, K.P., see DeLucas 135 (1994) 183

Wilson, M.A., see Taylor 135 (1994) 157

Wind, O., see Woggon 138 (1994) 976

Wisk, P.W., see Abernathy 136 (1994) 11

Witkowska, B., see Grodzicka 138 (1994) 1034

Witt, A.F., see Lin 140 (1994) 444

Witthuhn, W., see Rüb 138 (1994) 285

Wittmüss, D., see Krämer 140 (1994) 157

Woensdregt, C.F., see Boutz 134 (1993) 325

Woggon, U., S.V. Bogdanov, O. Wind and V. Sperling, Electric field induced absorption modulation of CdS quantum dots in an organic matrix 138 (1994) 976

Woggon, U., M. Saleh, A. Uhrig, M. Portuné and C. Klingshirn, CdS quantum dots in the weak confinement 138 (1994) 988

Woitok, J., see Söllner 138 (1994) 35

Woitok, J., see Hermans 138 (1994) 612

Wojnowski, M., see Matsumoto 135 (1994) 154

Wolf, K., A. Naumov, T. Reisinger, M. Kastner, H. Stanzl, W. Kuhn and W. Gebhardt, Luminescence caused by extended lattice defects in epitaxially grown ZnTe layers 135 (1994) 113

Wolf, K., H. Stanzl, A. Naumov, H.P. Wagner, W. Kuhn, B. Hahn and W. Gebhardt, Growth and doping of ZnTe and ZnSe epilayers with metalorganic vapour phase epitaxy 138 (1994) 412

Wolf, K., see Kuhn 138 (1994) 448

Wolf, K., see Naumov 138 (1994) 595

Wolffer, N., see Rzepka 138 (1994) 244

Wolk, J.A., J.W. Ager III, K.J. Duxstad, W. Walukiewicz, E.E. Haller, N.R. Taskar, D.R. Dorman and D.J. Olego, The nitrogen–hydrogen complex in ZnSe 138 (1994) 1071

Wolverson, D., J.J. Davies, S.V. Railson, M.P. Halsall, D.E. Ashenford and B. Lunn, Spin-flip Raman scattering by electrons bound to donors in CdTe/$Cd_{1-x}Mn_xTe$ multiple quantum well structures as a function of barrier composition 138 (1994) 656

Wong, T.K.S., see Hsu 133 (1993) 185

Worster, M.G., see Chiareli 139 (1994) 134

Wright, P.J., see Dhese 138 (1994) 140

Wu, B.J., see DePuydt 138 (1994) 667

Wu, C.M., see Knight 134 (1993) 19

Wu, C.S., see Hwang 132 (1993) 523

Wu, J., see Casagrande 137 (1994) 195

Wu, M.-C., see Lin 137 (1994) 400

Wu, M.-C. and E.-H. Chen, Investigation of Er-doped 1.55 μm InGaAsP single-heterostructure light-emitting diodes 139 (1994) 251

Wu, M.K., see Rao 139 (1994) 190

Wu, M.-S., see Shih 137 (1994) 319

Wu Xing, see Li 139 (1994) 327

Wu Yicheng, see Wang 132 (1993) 329

Wu, Y.J., see Huang 139 (1994) 363

Wu, Y.K., see Guan 138 (1994) 534

Wuensch, B.J., see Haile 131 (1993) 352

Wuensch, B.J., see Haile 131 (1993) 373

Xiao, Q. and J.J. Derby, Heat transfer and interface inversion during the Czochralski growth of yttrium aluminum garnet and gadolinium gallium garnet 139 (1994) 147

Xie, S., see Ji 137 (1994) 521

Xiong, B., and W.R. Hu, Influence of low-gravity level on crystal growth in floating zone 133 (1993) 155

Xiong, G., see Li 138 (1994) 231

Xu Dong, see Hou 133 (1993) 71

Xu, J.Z., see Chen 140 (1994) 287
Xu, P.M., see Fu 139 (1994) 319
Xu Xuewu, Liao Jingying, Shen Bingfu, Shao Peifa, Chen Xianqiu and He Chongfan, $Bi_{12}SiO_{20}$ single crystal growth by the Bridgman method 133 (1993) 267
Xu Xuewu, Liao Jingying, Shen Bingfu, Chen Xianqiu and He Chongfan, Polar habits of the $Bi_{12}SiO_{20}$ crystals grown by the Czochralski method 134 (1993) 337
Xu, Y.-B., and S.-J. Fan, Accelerated crucible rotation technique: Bridgman growth of $Li_2B_4O_7$ single crystal and simulation of the flows in the crucible 133 (1993) 95
Xu, Z., C. Huo, P. Ge and Z. Zhu, Characteristics of crystal growth from solution: scaling laws 137 (1994) 538
Xu, Z.Y., see Chen 140 (1994) 287

Yadava, R.D.S., see Bagai 139 (1994) 259
Yakovlev, D.R., see Hellmann 138 (1994) 791
Yamada, A., H. Tamada and M. Saitoh, Liquid phase epitaxial growth of $LiNbO_3$ thin film using Li_2O–B_2O_3 flux system 132 (1993) 48
Yamada, A., see Okamoto 138 (1994) 204
Yamada, A., see Tojima 138 (1994) 408
Yamada, E., see Coleman 132 (1993) 129
Yamada, T., see Sugiura 136 (1994) 64
Yamada, T., see Mitsuhara 136 (1994) 195
Yamada, T., see Iga 136 (1994) 273
Yamada, Y., Y. Masumoto and T. Taguchi, Ultraviolet lasing and excitonic gain in $Cd_xZn_{1-x}S$–ZnS strained-layer multiple quantum wells 138 (1994) 570
Yamagishi, K., see Sugimoto 140 (1994) 349
Yamaguchi, M., T. Warabisako and H. Sugiura, Chemical beam epitaxy as a breakthrough technology for photovoltaic solar energy applications 136 (1994) 29
Yamaguchi, T., see Takakuwa 136 (1994) 328
Yamaguchi, T., see Horie 136 (1994) 344
Yamamoto, A., M. Tsujino, M. Ohkubo and A. Hashimoto, Nitridation effects of substrate surface on the metalorganic chemical vapor deposition growth of InN on Si and α-Al_2O_3 substrates 137 (1994) 415
Yamamoto, A., Y. Kanemitsu and Y. Masumoto, Structural characteristics and higher-order zone-folded phonon modes in ZnSe–ZnS strained-layer superlattices 138 (1994) 643
Yamamoto, Y., see Inoue 131 (1993) 347
Yamanari, T., see Kuwabara 138 (1994) 964
Yamano, Y., see Ohmi 138 (1994) 1061
Yamasaki, D., see Yanashima 138 (1994) 755
Yamauchi, S., see Hariu 136 (1994) 157
Yamawaki, K., see Ichikawa 138 (1994) 14
Yamazaki, S., see Mukai 137 (1994) 388
Yan, C., D. Sun, H. Guo, X. Li, S. Zu, Y. Huang, Y. Zheng and M. Kong, High-quality InGaP and InGaP/InAlP multiple quantum well growth by gas-source molecular beam epitaxy 136 (1994) 306
Yanashima, K., D. Yamasaki, S. Watabe, K. Hara, J. Yoshino and H. Kukimoto, Metalorganic vapor phase epitaxy growth of p-type ZnSSe and its application for blue-green lasers 138 (1994) 755
Yang, A.H., see Yang 138 (1994) 629
Yang, B.J., see Shen 138 (1994) 625
Yang, B.J., L.C. Chen, X.W. Fan, J.Y. Zhang, Z.H. Zheng, Y.M. Lu, Z.P. Guan, A.H. Yang and S.M. Wang, Growth and optical bistability of $Zn_{0.78}Cd_{0.22}Se$–ZnSe multiple quantum wells by metalorganic chemical vapor deposition 138 (1994) 629
Yang, B.J., see Zhang 138 (1994) 838
Yang, L., see Houng 136 (1994) 216
Yang, T.R., see Huang 135 (1994) 224
Yanka, R.W., see Meyer 138 (1994) 981
Yano, M., H. Furuse, Y. Iwai, K. Yoh and M. Inoue, Raman scattering analysis of InAs/GaSb ultrathin-layer superlattices grown by molecular beam epitaxy (E) 131 (1993) 620
Yano, M., see Kim 136 (1994) 310
Yao, T., see Sasaki 136 (1994) 162
Yao, T., T. Matsumoto, S. Sasaki, C.K. Chung, Z. Zhu and F. Nishiyama, Lattice location of N atoms in heavily N-doped ZnSe studied with ion beam analysis and its implication on deep level defects 138 (1994) 290
Yao, T., see Zhu 138 (1994) 397
Yao, T., see Zhu 138 (1994) 619
Yariv, A., see Hofmeister 131 (1993) 486
Yarmush, M., see Schall 135 (1994) 548
Yashchin, E., see Angert 137 (1994) 116
Yasuda, T., see Mochizuki 135 (1994) 318
Yeboah, Y.D., M.R. Saeed and A.K.K. Lee, Kinetics of strontium sulfate precipitation from aqueous electrolyte solutions 135 (1994) 323
Yew, T.R., see Chiang 135 (1994) 469
Yi, G.-J., see Radomsky 138 (1994) 99
Yi, G.-J., L. Radomsky and G.F. Neumark, Temperature dependence of luminescence in ZnSe and role of excitation transfer 138 (1994) 208
Yi, K.W., H.T. Chung, H.W. Lee and J.K. Yoon, The effects of pulling rates on the shape of crystal/melt interface in Si single crystal growth by the Czochralski method 132 (1993) 451
Yli-Juuti, E., see Prieur 132 (1993) 599
Yoda, Y., see Matsumoto 138 (1994) 403
Yoh, K., see Yano 131 (1993) 620
Yokogawa, T., P.D. Floyd, J.L. Merz, H. Luo and J.K. Furdyna, Optical confine-

ment in ZnSe-based quantum well structure using impurity induced disordering 138 (1994) 564
Yokohama, I., see Sugiyama 134 (1993) 255
Yokouchi, N., see Miyamoto 136 (1994) 210
Yokouchi, N., see Inaba 136 (1994) 297
Yokouchi, N., Y. Inaba, T. Uchida, T. Miyamoto, K. Mori, F. Koyama and K. Iga, Composition changes in $Ga_xIn_{1-x}As$/InP superlattice growth by chemical beam epitaxy 136 (1994) 302
Yokoyama, H., see Ikuta 136 (1994) 114
Yokoyama, M., see Li 137 (1994) 421
Yom, S.S., see Yoon 140 (1994) 355
Yonenaga, I., see Matsumoto 132 (1993) 348
Yoneta, M., H. Saito and M. Ohishi, Autodoping of Ga in ZnSe/GaAs layers grown at low temperatures by post-heated molecular beam epitaxy 138 (1994) 110
Yonezu, H., see Maruyama 131 (1993) 316
Yonezu, H., see Maruyama 139 (1994) 19
Yonezu, H., see Pak 140 (1994) 244
Yoo, J.-B., J.-S. Kim, D.-H. Jang, B.-H. Koak, D.-K. Oh, H.-M. Kim and Y.-T. Lee, Effects of the V/III ratio on Si doping in InGaAs lattice-matched to InP grown by organometallic vapor phase epitaxy 132 (1993) 43
Yoo, W.S., see Chien 137 (1994) 175
Yoon, J.K., see Yi 132 (1993) 451
Yoon, S.F., H.M. Li, K. Radhakrishnan and D.H. Zhang, The effect of growth interruption on the photoluminescence linewidth of GaAs/InGaAs quantum wells grown by molecular beam epitaxy 131 (1993) 1
Yoon, S.F., H.M. Li, K. Radhakrishnan and Z.Y. Han, Optical characterization of strained $In_xGa_{1-x}As$–$Al_{0.28}Ga_{0.72}As$ heterostructures grown by molecular beam epitaxy 134 (1993) 240
Yoon, S.F., see Zhang 135 (1994) 441
Yoon, Y.K., see Yoon 140 (1994) 355
Yoon, Y.S., Y.K. Yoon, W.N. Kang and S.S. Yom, Analysis of the formation of $BaTiO_3$ island deposited on (111) InSb by metalorganic chemical vapor deposition at low temperature 140 (1994) 355
Yoshida, K., see Inoue 138 (1994) 182
Yoshida, K., see Minami 138 (1994) 796
Yoshida, N. see Izumi 133 (1993) 123
Yoshida, S., and M. Sasaki, New damage-free patterning method of a GaAs oxide mask and GaAs selective growth using the metalorganic molecular beam epitaxy method 133 (1993) 201
Yoshida, S. and M. Sasaki, Catalytic decomposition of ammonia gas using aluminium oxide for GaN formation 135 (1994) 633
Yoshida, S., M. Sasaki and H. Kawanishi, Selective-area epitaxy of GaAs using a GaN mask in in-situ processes 136 (1994) 37
Yoshida, S., see Sasaki 136 (1994) 241
Yoshida, S., see Okumura 136 (1994) 361
Yoshida, T., see Kobayashi 138 (1994) 745
Yoshihara, H., see Zhu 138 (1994) 619
Yoshikawa, A., see Tokita 136 (1994) 376
Yoshikawa, A., see Kobayashi 138 (1994) 745
Yoshikawa, T., see Saito 134 (1993) 154
Yoshimoto, M., T. Hashimoto, P. Vaccaro and H. Matsunami, In-situ reflection high-energy electron diffraction observation of laser-triggered GaP growth in chemical beam epitaxy 136 (1994) 89
Yoshimura, Y., see Kaito 134 (1993) 157
Yoshino, J., see Yanashima 138 (1994) 755
Yoshinobu, T., see Hatayama 136 (1994) 333
Yoshioka, R.T., see Shirakashi 136 (1994) 186
Yu, E.T., see Wang 138 (1994) 508
Yu, F., U. Schanz and E. Schmidbauer, Single crystal growth of $FeWO_4$ and $CuWO_4$ 132 (1993) 606
Yu Wentao, see Hou 133 (1993) 71
Yu, Z., see Ren 138 (1994) 455
Yu, Z., see Eason 138 (1994) 703
Yuan Duorong, see Hou 133 (1993) 71
Yuan, L., see Chai 135 (1994) 639
Yugova, T.G., see Vdovin 132 (1993) 477

Zachariah, M.R., see Davis 132 (1993) 513
Zakrajšek, S., see Maček 132 (1993) 99
Zebib, A., see Zhou 135 (1994) 587
Zehnder, U., see Waag 138 (1994) 155
Zeinert, A., P. Benalloul, J. Benoit, C. Barthou and H.-E. Gumlich, Space charge and excitation efficiency in ZnS thin film electroluminescent devices 138 (1994) 1023
Zeitz, W.-D., see Schumann 138 (1994) 910
Zemke, D., P. Gerlach, W. Zulehner and K. Jacobs, Investigations on the correlation between growth rate and gate oxide integrity of Czochralski-grown silicon 139 (1994) 37
Zeng, H.C., T.C. Chong, L.C. Lim, H. Kumagai and M. Hirano, Pseudo-dendritic growth in lead molybdate single crystal by Czochralski technique 140 (1994) 148
Zerguine, D., see Alexandre 136 (1994) 235
Zerlauth, S., see Ullrich 138 (1994) 234
Zhang, D.H., see Yoon 131 (1993) 1
Zhang, D.H., K. Radhakrishnan and S.F. Yoon, The effect of As/Ga flux ratio on Si-doped GaAs layers grown by molecular beam epitaxy 135 (1994) 441
Zhang, G.F., X. Zheng and Z.T. Liu, Nucleation and growth behaviour of diamond

films deposited on chemically etched titanium alloy substrates 133 (1993) 117
Zhang, H.W., A.K. Batra and R.B. Lal, Growth of large methyl-(2,4-dinitrophenyl)-aminopropanoate : 2-methyl-4-nitroaniline for nonlinear optical applications 137 (1994) 141
Zhang, J., see Zhang 132 (1993) 331
Zhang, J.Y., see Yang 138 (1994) 629
Zhang, J.Y., X.W. Fan, B.J. Yang, Z.P. Guan, Y.M. Lu and D.Z. Shen, Excitonic emission in ZnCdSe–ZnSe multiple quantum wells 138 (1994) 838
Zhang Nan, see Hou 133 (1993) 71
Zhang, S., J. Cui, A. Tanaka and Y. Aoyagi, Short-pulse chemical beam epitaxy 136 (1994) 200
Zhang, W., Y. Someno, M. Sasaki and T. Hirai, Heteroepitaxy of AlN on α-Al_2O_3 by electron cyclotron resonance plasma-assisted chemical vapor deposition at low temperatures 132 (1993) 337
Zhang, X., D.W. Pashley, L. Hart, J.H. Neave, P.N. Fawcett and B.A. Joyce, The morphology and asymmetric strain relief behaviour of InAs films on GaAs(110) grown by molecular beam epitaxy 131 (1993) 300
Zhang, X., D.W. Pashley, J.H. Neave, P.N. Fawcett, J. Zhang and B.A. Joyce, Reflection high-energy electron diffraction/transmission electron microscopy observation of growth of InAs on GaAs (110) by molecular beam epitaxy 132 (1993) 331
Zhang, Y., W. Liu, B.J. Skromme, H. Cheng, S.M. Shibli and M.C. Tamargo, Systematic investigation of shallow acceptor levels in ZnSe 138 (1994) 310
Zhang, Z.M., H.M. Cheng, S.H. Li, Q.Y. Cai, D.L. Ling, S.J. Wang, Z.W. Hu, S.S. Jiang, C.Z. Ge and N.B. Ming, Morphologic study of (100) single crystal diamond films epitaxially grown by chemical vapor deposition 132 (1993) 200
Zhao, Z., see Li 138 (1994) 231
Zheng, J. and J.W. Allen, The hole diffusion length in epitaxial zinc selenide 138 (1994) 477
Zheng, J. and J.W. Allen, Photoionization of a deep centre in zinc selenide giving information about the conduction band structure 138 (1994) 504
Zheng, X., see Zhang 133 (1993) 117
Zheng, Y., see Yan 136 (1994) 306
Zheng, Z.H., see Yang 138 (1994) 629
Zhou, G.L., Z. Ma, M.E. Lin, T.C. Shen, L.H. Allen and H. Morkoç, Low temperature growth of single-crystalline cubic SiC on Si(111) by solid source molecular beam epitaxy 134 (1993) 167
Zhou, H. and A. Zebib, Oscillatory double diffusive convection in crystal growth 135 (1994) 587
Zhou, W., D.E. Bornside and R.A. Brown, Dynamic simulation of Czochralski crystal growth using an integrated thermal-capillary model 137 (1994) 26
Zhou, W., see Lin 140 (1994) 72
Zhou Yaohe, see Huang 134 (1993) 105
Zhu, Z., see Sasaki 136 (1994) 162
Zhu, Z., see Xu 137 (1994) 538
Zhu, Z., see Yao 138 (1994) 290
Zhu, Z., T. Ebisutani, K. Takebayashi, K. Tanaka and T. Yao, Molecular beam epitaxy of ZnSe doped with nitrogen on vicinal (100)-oriented and (211)-oriented GaAs substrates 138 (1994) 397
Zhu, Z., H. Yoshihara, K. Takebayashi and T. Yao, Characterization of alloy formation at the ZnSe/CdSe quantum-well interface by photoluminescence spectroscopy 138 (1994) 619
Zigone, M., see Haacke 138 (1994) 831
Zimmermann, H., R. Boyn, P. Rudolph, C. Albers, K.W. Benz, D. Sinerius, C. Eiche, B.K. Meyer and D.M. Hoffmann, State and distribution of point defects in doped and undoped Bridgman-grown CdTe single crystals (E) 131 (1992) 276
Zimmermann, H., see Meyer 135 (1994) 571
Zinck, J.J., see Rajavel 138 (1994) 19
Zlomanov, V., see Polity 131 (1993) 271
Zu, S., see Yan 136 (1994) 306
Zulehner, W., see Zemke 139 (1994) 37
Zumsteg, F.C., see Cheng 132 (1993) 289
Zweck, J., see Grün 138 (1994) 150
Zytkiewicz, Z.R., Influence of convection on the composition profiles of thick GaAlAs layers grown by liquid phase electroepitaxy 131 (1993) 426

ELSEVIER

Journal of Crystal Growth 140 (1994) 520–535

JOURNAL OF CRYSTAL GROWTH

Subject index to volumes 131–140

Adducts
– for aluminum gallium arsenide **136** (1994) 152
– for gallium arsenide **136** (1994) 127, 152; **137** (1994) 347
Agglomeration of crystals **135** (1993) 505
Alkali
– lead chlorides, ternary **131** (1993) 612
– titanyl arsenate **137** (1994) 107
– titanyl phosphate **137** (1994) 107, 535
Alloys
– binary **137** (1994) 623; **139** (1994) 134; **140** (1994) 139
– model of **134** (1993) 105
– of aluminum–iron **135** (1993) 561
– of copper **137** (1994) 91
– of copper (aluminum gallium) sulphur selenide **140** (1994) 388
– of gold **137** (1994) 91
– of magnesium–aluminum **137** (1994) 653
– organic **140** (1994) 115
Alumina **131** (1993) 457; **140** (1994) 79
Aluminum **132** (1993) 25, 592; **135** (1993) 285
– antimonide **136** (1994) 250, 310
– arsenide **132** (1993) 427; **134** (1993) 140; **135** (1993) 85, 365; **136** (1994) 50, 83; **137** (1994) 680; **140** (1994) 205
– copper iron quasicrystal **135** (1993) 297
– ferrite **135** (1993) 561
– gallium antimonide **136** (1994) 250
– gallium arsenide **131** (1993) 61, 426; **132** (1993) 166, 179; **133** (1993) 241, 281; **134** (1993) 140; **135** (1993) 85, 855; **136** (1994) 11, 152, 230; **138** (1994) 727; **139** (1994) 231, 344
– gallium indium arsenide **131** (1993) 419
– gallium indium phosphide **136** (1994) 306; **137** (1994) 240, 400
– indium arsenide **131** (1993) 419
– iron, alloy **135** (1993) 561
– nitride **133** (1993) 59
– organic **136** (1994) 11, 50, 152, 166, 235, 250; **137** (1994) 442
– oxide **132** (1993) 337
– phosphide **136** (1994) 268
Ammonium
– chloride **131** (1993) 111; **135** (1993) 594
– dihydrogen phosphate **137** (1994) 598
– triantimony decafluoride **137** (1994) 295
Antimony
– organic **139** (1994) 247
Apatite **140** (1994) 91
Apparatus
– for doping
– – of zinc selenide **138** (1994) 403
– for growth under microgravity **135** (1993) 513
– for melt growth
– – by Czochralski method
– – – automatic diameter control **132** (1993) 1
– – – of gallium indium antimonide **135** (1993) 269
– – – of silicon **131** (1993) 247
– – – segregation control **132** (1993) 461
– – – shaped crystal pulling **132** (1993) 467
– – – using nonwetted float, of tin **134** (1993) 287
– – by floating zone method
– – – of bismuth germanium oxide **134** (1993) 266
– – – of organic crystals **137** (1994) 663
– – by floating zone method, in microgravity
– – – of yttrium barium cuprate **139** (1994) 302
– – by focused ion beam
– – – of gallium arsenide **140** (1994) 244
– – by laser heated pedestal growth
– – – of bismuth silicon oxide **137** (1994) 528
– – – of bismuth titanium oxide **137** (1994) 528
– – – of strontium barium niobate **134** (1993) 255
– – by zone melting
– – – of gallium indium antimonide **139** (1994) 165
– for solution growth
– – by flux method
– – – of alkali titanyl arsenate **137** (1994) 107
– – – of alkali titanyl phosphate **137** (1994) 107
– – by low temperature method
– – – of organic crystals **137** (1994) 141
– – by yo-yo solute feeding method
– – – of indium gallium phosphide **137** (1994) 245
– for thin film growth
– – by gas source molecular beam epitaxy
– – – using microwave plasma source
– – – – of gallium nitride **136** (1994) 361
– – by metalorganic molecular beam epitaxy
– – – optimization of, by flow visualization **134** (1993) 302
– – – using short pulse
– – – – of gallium arsenide **136** (1994) 200
– – by molecular beam epitaxy **133** (1993) 241
– – – laser induced doping in zinc selenide **138** (1994) 357

– – by vapor phase epitaxy
– – – through chemical vapor deposition
– – – – of titanium silicide **134** (1993) 377
– – – through metalorganic chemical vapor deposition **135** (1993) 383
– – – – of mercury cadmium telluride **134** (1993) 90
– – – – research scale
– – – – – of barium titanate **137** (1994) 136
– – – – using improved gas switching
– – – – – of aluminum gallium arsenide **139** (1994) 344
– – – – using remote plasma assistance
– – – – – of indium phosphide **139** (1994) 15
– for vapor growth
– – by evaporation and condensation
– – – of cadmium telluride **139** (1994) 27
– for miscellaneous purposes
– – acoustic emission analysis during crystal growth **131** (1993) 395
– – ampoule failure sensor **140** (1994) 41
– – flow visualization of molten silicon **133** (1993) 23
– – growth in high magnetic fields **140** (1994) 435
– – growth of organic crystals, by new crystallizer **137** (1994) 141
– – high temperature carbon fiber spring **131** (1993) 470
– – in situ measurement of solubility and supersaturation using ATR IR spectroscopy **137** (1994) 561
– – magnetic stirring using electromagnetic rheocaster **137** (1994) 653
– – measurement of density and surface tension **137** (1994) 509
– – measurement of wafer thickness **137** (1994) 37
– – rotational electromagnetic stirring of Czochralski melt **139** (1994) 351
– – wetting measurement **131** (1993) 157
Aragonite **133** (1993) 13; **137** (1994) 577
L-Arginine
– phosphate **133** (1993) 132; **140** (1994) 336, 447
– phosphate, deuterated **140** (1994) 336
– phosphate (sulphate) **137** (1994) 598
Arsenic
– organic **136** (1994) 1, 78, 138, 162, 204; **137** (1994) 212, 347
Aspartame **133** (1993) 80

Barium
– borates **134** (1993) 219; **135** (1993) 279; **137** (1994) 123
– cuprate **132** (1993) 389
– fluoride **132** (1993) 241
– hexaferrite **131** (1993) 97
– metaborate **131** (1993) 199; **137** (1994) 123
– nitrate **137** (1994) 610
– organic **137** (1994) 136
– oxide–iron(III) oxide **139** (1994) 47
– titanate **137** (1994) 136; **140** (1994) 355
Benzil **137** (1994) 663
Beryllium
– aluminate **139** (1994) 327
Biological mineralization
– of calcium carbonate **137** (1994) 577
Bismuth **137** (1994) 605
– germanate **134** (1993) 266; **137** (1994) 509; **139** (1994) 67; **140** (1994) 361
– lead strontium calcium cuprate **135** (1993) 496
– silicate **133** (1993) 267; **134** (1993) 337; **137** (1994) 128, 132, 528; **140** (1994) 444
– strontium calcium cuprate **131** (1993) 105; **135** (1993) 481, 496; **137** (1994) 268, 472; **139** (1994) 86
– strontium calcium cuprate, rare earth substituted **139** (1994) 81
– strontium cuprate **140** (1994) 65
– telluride **140** (1994) 365
– titanate **137** (1994) 528; **139** (1994) 319
Borates **132** (1993) 173
Boron
– phosphide **132** (1993) 611
Bovine tooth enamel **137** (1994) 545
Buckminster fullerene **134** (1993) 157; **135** (1993) 154, 157

Cadmium
– magnesium selenide **135** (1993) 41; **138** (1994) 692
– magnesium telluride **131** (1993) 607; **138** (1994) 155, 437, 638
– manganese telluride **138** (1994) 437, 585, 652, 661, 791, 856, 900
– mercury telluride **134** (1993) 90; **138** (1994) 175, 486, 517, 917, 940, 944, 950, 956, 964, 981, 1040; **139** (1994) 6, 247
– selenide **135** (1993) 383; **138** (1994) 63, 150, 191, 545, 601, 619, 800, 849, 1004
– selenide telluride **138** (1994) 239
– sulphide **138** (1994) 150, 191, 213, 225, 231, 234, 559, 809, 976, 988, 993, 998
– sulphoselenide **134** (1993) 63; **135** (1993) 476
– telluride **131** (1993) 133; **132** (1993) 250, 351; **133** (1993) 230; **134** (1993) 281; **135** (1993) 53, 383, 409, 447; **137** (1994) 195, 201, 208, 435; **138** (1994) 8, 43, 86, 131, 161, 168, 244, 249, 274, 279, 285, 346, 437, 443, 493, 529, 538, 550, 580, 585, 590, 638, 652, 656, 791, 831, 856, 877, 900; **139** (1994) 27, 259; **140** (1994) 287, 327
– telluride selenide **138** (1994) 161, 529, 607
– zinc selenide **138** (1994) 1076
– zinc telluride **132** (1993) 250, 351; **137** (1994) 102, 195, 383; **138** (1994) 131, 168, 199, 244, 455, 529, 538, 607, 661, 826, 831, 950
Calcite **131** (1993) 533; **133** (1993) 13; **137** (1994) 577
Calcium
– apatite **137** (1994) 553
– cadmium sulphide **138** (1994) 1055
– carbonate **132** (1993) 115; **133** (1993) 13; **137** (1994) 577
– fluoride **132** (1993) 241
– hydrogen orthophosphate dihydrate **131** (1993) 331
– hydroxyapatite **137** (1994) 545
– (octa) phospate succinate **135** (1993) 533
– oxalate hydrates **132** (1993) 122; **133** (1993) 87, 189; **134** (1993) 211; **135** (1993) 235, 523

– phosphates **132** (1993) 215; **137** (1994) 553; **140** (1994) 91
– strontium gallate niobate **139** (1994) 54
– strontium sulphide **138** (1994) 1051
Carbon
– fiber spring **131** (1993) 470
– graphitic **134** (1993) 154
Cellular growth
– of binary mixture **139** (1994) 113
– of gallium arsenide **140** (1994) 264
– of γ-iron chromium carbide **133** (1993) 175
– of magnesium alloy **137** (1994) 653
– of succinonitrile–acetone alloy **134** (1993) 181
– of thermolysin **135** (1994) 199
– theory of **140** (1994) 398, 405
Cerium
– dioxide **131** (1993) 347
Cesium
– iodide **131** (1993) 230
– titanyl arsenate **131** (1993) 323; **132** (1993) 280, 289
Characterization
– by atomic force microscopy
– – of lead iodide **137** (1994) 299
– by quantitative IR imaging
– – of dopant in gallium arsenide **137** (1994) 249
– of barium borate **135** (1993) 279
– of bubbles in bismuth germanate **140** (1994) 361
– of cadmium sulphide **138** (1994) 809, 815
– of dislocations and microdefects
– – in gallium arsenide **135** (1993) 302
– – in nitrides **135** (1993) 309
– – theory of **135** (1993) 71
– of heteroepitaxial systems **140** (1994) 213
– of relaxation and mosaicity profiles in epitaxial layers **135** (1993) 41
– of solubility of oxalates **135** (1993) 135
– of solubility of octacalcium phosphate succinate **135** (1993) 533
– of strain in cadmium telluride layers **135** (1993) 53
– of zinc selenide **138** (1994) 805, 815
– optical properties
– – of cadmium sulphide **138** (1994) 225, 231
– – of zinc telluride **138** (1994) 187
– resonant Brillouin scattering
– – in zinc selenide **138** (1994) 195
– spectroscopy
– – of cadmium telluride **138** (1994) 244
– – of cadmium zinc telluride **138** (1994) 244
– theoretical calculations of properties
– – of II–VI ion implanted compounds **138** (1994) 910
– – of zinc manganese selenide **138** (1994) 905
– – of zinc selenium telluride **138** (1994) 499
– X-ray diffraction analysis of III–V compounds **140** (1994) 205
Chrysoberyl **139** (1994) 327
Citric acid **134** (1993) 196; **137** (1994) 561
Clusters
– formation in binary systems **132** (1993) 491
– of glycine **139** (1994) 104
– of interface in Bridgman furnace **131** (1993) 75
– of metals **132** (1993) 359
– of sodium chloride **139** (1994) 104
Cobalt **139** (1994) 363
Computer aided image analysis **137** (1994) 1
Computer simulation
– of ab initio study of molecular orbital calculations **136** (1994) 94
– of bismuth germanate growth **134** (1993) 266; **139** (1994) 67
– of calcite morphology **131** (1993) 533
– of chemical vapor deposition **140** (1994) 191
– of concentration profiles **140** (1994) 28
– of convection **135** (1993) 587
– of convection and transport mechanism **134** (1993) 266
– of crystal growth **135** (1993) 331
– of dendritic morphology **137** (1994) 1
– of diffusion coefficients **137** (1994) 91
– of dopant concentration in floating zone method **132** (1993) 578
– of floating zone growth **138** (1994) 161
– of floating zone growth under microgravity **133** (1993) 155, 309
– of floating zone growth of tube crystals **135** (1993) 606
– of flow in CVD reactor **132** (1993) 483, 513
– of flow in Czochralski growth **132** (1993) 551
– of garnets, Czochralski growth **139** (1994) 147
– of heteroepitaxial growth **138** (1994) 68
– of horizontal Bridgman growth **135** (1993) 341
– of indium gallium arsenide, in MBE **134** (1993) 51
– of integrated thermal capillary model **137** (1994) 26
– of magnetic induction model **137** (1994) 77
– of metalorganic chemical vapor deposition **131** (1993) 283; **133** (1993) 230
– of metalorganic molecular beam epitaxy **136** (1994) 83
– of molecular orbital calculation **135** (1993) 259
– of nucleation and growth **135** (1993) 571
– of nucleation rate **140** (1994) 128
– of oxide film growth **135** (1993) 145
– of oxygen concentration in Czochralski growth **132** (1993) 451
– of oxygen transport in melt **137** (1994) 427
– of particle photochemical degradation **138** (1994) 993
– of point defects **137** (1994) 12
– of silicon, Czochralski growth **139** (1994) 197
– of silicon nitride **140** (1994) 157
– of solidification interface in Czochralski growth **132** (1993) 451
– of stress **137** (1994) 667
– of surface morphology **139** (1994) 211
– of temperature field **131** (1993) 247
– – in Bridgman growth **132** (1993) 261
– – in Czochralski growth **132** (1993) 297, 451, 551
– – in floating zone growth **132** (1993) 578
– of temperature and velocity fields in floating zone **131** (1993) 83
– of II–VI diode lasers, modeling of **138** (1994) 697

– of vacancy concentrations **138** (1994) 94
Constitutional supercooling
– of calcium strontium gallate niobate **139** (1994) 54
– of solid solution **134** (1993) 342
– theory of **131** (1993) 209; **132** (1993) 405; **133** (1993) 132
Convection **131** (1993) 145, 165, 247, 431; **132** (1993) 226, 483; **133** (1993) 95, 155, 217, 261, 309; **134** (1993) 116; **135** (1993) 341, 587, 594, 619; **137** (1994) 41, 48, 64, 72, 91, 95, 427, 538, 653; **138** (1994) 161, 168; **139** (1994) 67, 134, 158, 266, 372; **140** (1994) 182, 237, 308, 315, 398, 406, 414, 435
Copper **139** (1994) 351
– alloy **137** (1994) 91
– (aluminum gallium) sulphur selenide **140** (1994) 388
– aluminum selenide **131** (1993) 551
– (gallium indium) sulphide **134** (1993) 174
– sulphoxinates **137** (1994) 585
– tungstate **132** (1993) 606

Dendritic growth
– of aluminum ferrite **135** (1993) 561
– of ammonium chloride **131** (1993) 111; **135** (1993) 594
– of binary alloy **139** (1994) 134
– of diamond **133** (1993) 329
– of iron iodide **132** (1993) 129
– of lead di-iodide **131** (1993) 453
– of lead molybdate **140** (1994) 148
– of organic alloys **140** (1994) 115
– of succinonitrile **132** (1993) 226; **137** (1994) 1
– of succinonitrile–acetone alloy **134** (1993) 181
– of succinonitrile–ethanol model alloy **134** (1993) 105
– theory of **140** (1994) 398, 406
Deuterated L-arginine phosphate **140** (1994) 336
Device characterization
– diodes **132** (1993) 191; **134** (1993) 35, 67; **135** (1993) 367; **136** (1994) 186, 230, 297, 355; **137** (1994) 161, 240, 400; **138** (1994) 367, 391, 455, 727, 917, 940, 1078; **139** (1994) 172, 251
– double heterostructures **136** (1994) 1, 11, 221, 225, 230, 235, 246, 287; **140** (1994) 277
– electroluminescent materials **137** (1994) 150; **138** (1994) 1010, 1017, 1023, 1061
– electronic materials **132** (1993) 191, 504; **136** (1994) 11, 50, 138, 143, 166, 230, 261, 293; **137** (1994) 155, 161, 181, 208, 249; **138** (1994) 99, 161, 175, 199, 208, 266, 285, 305, 331, 367, 391, 471, 477, 481, 486, 493, 504, 523, 607, 873, 924, 1034, 1046, 1051, 1055; **139** (1994) 238, 251; **140** (1994) 9, 308
– electro-optic switches **137** (1994) 116
– frequency doubler **137** (1994) 145
– heterojunction **132** (1993) 341; **134** (1993) 147; **135** (1993) 246; **137** (1994) 161, 240, 400; **138** (1994) 1, 391, 455, 464, 508, 538, 601, 607, 643, 692, 727, 944; **139** (1994) 238
– heterostructures **132** (1993) 166, 427, 435; **137** (1994) 680
– lasers **132** (1993) 289; **133** (1993) 281; **134** (1993) 1, 19; **135** (1993) 646; **136** (1994) 42, 56, 64, 195, 210, 216, 225; **138** (1994) 35, 63, 75, 105, 121, 131, 136, 140, 208, 219, 255, 367, 385, 391, 397, 418, 448, 464, 559, 564, 570, 585, 633, 667, 677, 686, 697, 714, 719, 737, 745, 750, 755, 759, 764, 768, 1076, 1077; **139** (1994) 309, 372; **140** (1994) 19, 277, 282, 287
– light emitting diodes **138** (1994) 692, 703, 768
– modulators **138** (1994) 709
– optical **138** (1994) 234
– optical parametric oscillator **137** (1994) 145
– optoelectronic materials **133** (1993) 108; **138** (1994) 204, 239, 338, 612, 800, 805, 1073
– photorefractive materials **137** (1994) 128
– pyroelectric materials **133** (1993) 212
– quantum dots **138** (1994) 976, 988, 998, 1004
– quantum wells **131** (1993) 1, 620; **132** (1993) 231, 435; **133** (1993) 281; **134** (1993) 140, 162; **135** (1993) 85, 455; **136** (1994) 56, 64, 78, 173, 195, 225, 273, 278, 293, 297, 302, 306, 315, 355; **137** (1994) 388; **138** (1994) 131, 155, 182, 191, 362, 391, 559, 564, 570, 575, 585, 590, 595, 601, 607, 619, 625, 629, 656, 661, 709, 719, 745, 759, 776, 791, 796, 826, 831, 838, 849, 856, 861, 884, 889, 1076; **139** (1994) 344
– quantum wires **132** (1993) 91, 179; **138** (1994) 638
– scintillators **131** (1993) 230
– second harmonic generation **137** (1994) 123
– solar cells **136** (1994) 29
– surface acoustic wave application **137** (1994) 319
– transistors **133** (1993) 123; **136** (1994) 1, 11, 50, 221, 230, 235, 256, 261
– wave guides **138** (1994) 843, 1076
– wavelength convector **137** (1994) 145
– theory **138** (1994) 709, 714
Diamond **132** (1993) 200; **133** (1993) 117, 329; **135** (1993) 165, 172, 370, 639; **137** (1994) 161, 676; **140** (1994) 441, 454
Diffusional control
– in solution crystal growth **138** (1994) 970
– in II–VI based semiconductors **138** (1994) 362
– of arsenic in gallium arsenide **140** (1994) 28
– of binary mixture **139** (1994) 113
– of cadmium telluride **137** (1994) 208
– of clusters **132** (1993) 419; **139** (1994) 104
– of crystal growth, theory of **140** (1994) 381
– of dopant transport **131** (1993) 165
– of doping **138** (1994) 140, 324
– of elements into cadmium telluride **138** (1994) 274, 279, 285
– of indium gallium arsenide **134** (1993) 51; **137** (1994) 388
– of interstitial vacancy **138** (1994) 940
– of segregation **137** (1994) 64, 623
– of solid systems **137** (1994) 91
– of vacancies **138** (1994) 94
Diodes, see Device characterization
Dissolution
– of alloys with semiconductors **137** (1994) 102
– of L-arginine phosphate monohydrate **140** (1994) 447
– of calcium hydroxyapatite **137** (1994) 545
– of oxygen in silicon melt **139** (1994) 357
– of potassium titanyl phosphate in polyphosphate fluxes **137** (1994) 535
– of pumpkin seed globulin **133** (1993) 29
– of sodium tungsten bronzes **131** (1993) 473
Double heterostructures, see Device characterization

Electroluminescent materials, see Device characterization
Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Erbium
– silicide **134** (1993) 247
Etching
– chemical **131** (1993) 32, 413, 565; **132** (1993) 179, 241, 250; **134** (1993) 35, 81, 219; **135** (1993) 61, 85, 367, 377; **136** (1994) 37, 166, 256; **137** (1994) 201, 289, 299, 653; **138** (1994) 638, 934; **139** (1994) 6, 27, 37, 211; **140** (1994) 45, 277, 336, 444, 447
– dry chemical **136** (1994) 42
– electron beam lithographic **138** (1994) 590, 638, 856
– ion beam **138** (1994) 940
– photolithographic **135** (1993) 85; **138** (1994) 8, 481
– thermal **137** (1994) 208
Eutectic growth
– of halogenated hydrocarbons **134** (1993) 353
– of γ-iron chromium carbide **133** (1993) 175
– of silver–copper **140** (1994) 175

Finite element model
– of gallium arsenide **137** (1994) 59
– of silicon **137** (1994) 26
Forsterite **139** (1994) 327
Fullerene **134** (1993) 157; **135** (1993) 154, 157

Gadolinium
– gallium garnet **139** (1994) 147
– molybdate **131** (1993) 598
Gallium **137** (1994) 41, 64
– antimonide **131** (1993) 157, 620; **132** (1993) 345; **133** (1993) 168; **135** (1993) 290; **136** (1994) 250; **139** (1994) 206; **140** (1994) 426
– arsenide **131** (1993) 1, 17, 61, 83, 176, 283; **132** (1993) 103, 166, 179, 209, 331, 364, 427, 477, 533, 599, 614; **133** (1993) 123, 201, 241, 296; **134** (1993) 14, 97, 140, 151; **135** (1993) 23, 31, 71, 78, 85, 259, 302, 367, 377, 423, 441, 455, 469, 623, 629; **136** (1994) 37, 69, 99, 104, 109, 114, 127, 133, 138, 143, 152, 162, 191, 200, 204, 221, 230, 235, 241, 256, 261; **137** (1994) 59, 102, 224, 249, 255, 335, 347, 375, 442, 667, 680; **138** (1994) 727; **139** (1994) 231, 344; **140** (1994) 9, 28, 205, 244, 264, 299
– arsenide phosphide **136** (1994) 282
– germanium **131** (1993) 75, 165
– indium aluminum phosphide **138** (1994) 768
– indium antimonide **135** (1993) 269; **139** (1994) 165
– indium arsenide **131** (1993) 1, 387; **132** (1993) 43, 61, 91, 231, 364, 435; **135** (1993) 11, 129; **136** (1994) 18, 133, 225, 302; **140** (1994) 33
– indium arsenide phosphide **131** (1993) 309, 387; **132** (1993) 231, 435; **136** (1994) 18, 210, 297; **138** (1994) 727
– indium phosphide **131** (1993) 387; **132** (1993) 364; **133** (1993) 207; **135** (1993) 123, 646; **136** (1994) 221, 261, 306
– nitride **135** (1993) 633; **136** (1994) 37, 361; **137** (1994) 161, 170
– organic **136** (1994) 11, 18, 37, 50, 64, 69, 78, 89, 99, 104, 109, 127, 133, 138, 143, 148, 162, 166, 173, 186, 195, 200, 204, 210, 221, 225, 230, 235, 241, 246, 250, 256, 261, 273, 297, 302; **137** (1994) 170, 212
– oxide **132** (1993) 335
– phosphide **131** (1993) 465; **132** (1993) 134, 364, 414; **135** (1993) 123; **136** (1994) 89, 268
– scandium aluminum garnet **131** (1993) 457
– selenide **135** (1993) 1; **138** (1994) 43
Garnets **131** (1993) 181, 457; **134** (1993) 43, 325; **135** (1993) 253; **139** (1994) 147, 372; **140** (1994) 84, 349
Germanium **131** (1993) 75; **137** (1994) 64; **138** (1994) 43; **139** (1994) 351
– silicide **137** (1994) 457
– silicon **139** (1994) 1
Globulin **133** (1993) 29
Glycine **139** (1994) 104
Gold **138** (1994) 1078
– alloys **137** (1994) 91
– silver telluride **131** (1993) 518
Graphite **135** (1993) 370
Gypsum **132** (1993) 99

Habit modification
– of sodium chlorate **139** (1994) 336
Halogenated hydrocarbons **134** (1993) 353
Heat flow control
– furnace design **137** (1994) 59
– measurement of **137** (1994) 54
– of Czochralski growth **132** (1993) 297; **137** (1994) 278; **139** (1994) 271, 286
– of edge-defined film-fed growth **137** (1994) 82
– of garnets, Czochralski growth **139** (1994) 147
– of liquid encapsulated Czochralski process **137** (1994) 41
– of melt convection **137** (1994) 48, 427
– of vapor growth method **132** (1993) 538
Heterojunction, see Device characterization
Huntite borate **133** (1993) 181
Hydrargillite **135** (1993) 505
Hydrocarbons, halogenated **134** (1993) 353
Hydrodynamics, see Convection
Hydroxyapatite **133** (1993) 1; **135** (1993) 229, 539

Ice **131** (1993) 153
Indium
– aluminum antimonide **137** (1994) 405
– aluminum arsenide **131** (1993) 186, 300, 465; **134** (1993) 147; **135** (1993) 365; **136** (1994) 166
– antimonide **131** (1993) 157; **132** (1993) 371; **135** (1993) 401, 434; **136** (1994) 157; **137** (1994) 64, 405; **140** (1994) 435
– antimonide arsenide **133** (1993) 108
– antimonide phosphide **133** (1993) 38
– arsenide **131** (1993) 300, 465, 620; **132** (1993) 331, 364; **135** (1993) 97; **136** (1994) 83, 157, 191, 278, 310; **137** (1994) 231, 381
– arsenide antimonide **137** (1994) 231
– arsenide bismuthide **134** (1993) 29
– arsenide phosphide **133** (1993) 185; **136** (1994) 273

- gallium aluminum arsenide **135** (1993) 463
- gallium aluminum phosphide **133** (1993) 303
- gallium arsenide **133** (1993) 289; **134** (1993) 51, 147, 162, 240; **136** (1994) 1, 50, 69, 78, 109, 166, 186, 191, 195, 216, 225, 246, 287, 293, 302; **137** (1994) 388, 667; **139** (1994) 238; **140** (1994) 277, 432
- gallium arsenide phosphide **134** (1993) 19; **136** (1994) 50, 56, 64, 148, 173, 195, 210, 246, 273, 297; **139** (1994) 251
- gallium phosphide **132** (1993) 231; **136** (1994) 1, 11, 221, 261; **137** (1994) 245; **138** (1994) 1
- nitride **137** (1994) 415
- organic **136** (1994) 18, 42, 64, 69, 78, 162, 166, 173, 179, 195, 210, 221, 225, 235, 246, 273, 278, 297, 302
- phosphide **131** (1993) 204, 465; **132** (1993) 91, 231, 348, 364, 435; **133** (1993) 185; **134** (1993) 81; **135** (1993) 11, 123; **136** (1994) 18, 42, 50, 162, 166, 173, 179, 195, 278, 287, 293, 297; **137** (1994) 224, 235, 313; **139** (1994) 15, 19; **140** (1994) 1, 19, 277, 291

Interferometry, using fiber optics
- for wafer characterization **137** (1994) 37

Iron
- chromium carbide (γ) **133** (1993) 175
- iodide **132** (1993) 129
- sulphide **131** (1993) 448
- tungstate **132** (1993) 606

Kinetics
- of adsorption **136** (1994) 322, 338
- of aggregation **133** (1993) 87, 196
- of complex formation **138** (1994) 285
- of decomposition **136** (1994) 338
- of deposition **137** (1994) 499
- of desupersaturation **132** (1993) 99
- of dissolution **132** (1993) 419
- of energy transfer **138** (1994) 889
- of excitons **138** (1994) 291
- of formation **135** (1993) 533
- of growth **131** (1993) 13, 17, 49, 283, 316, 387, 501, 560; **132** (1993) 25, 99, 122, 215, 405, 419, 533, 538, 614; **133** (1993) 13, 29, 80, 87, 202, 246, 322; **134** (1993) 43, 347, 377; **135** (1993) 11, 61, 85, 209, 323, 354, 434, 548, 623; **136** (1994) 18, 69, 109, 118, 127, 133, 200, 204, 246, 315, 322, 338, 344, 371, 376; **137** (1994) 82, 235, 335, 381, 452, 516, 538, 569, 610; **138** (1994) 8, 14, 19, 48, 367, 471, 970; **139** (1994) 19, 37, 47, 89, 95, 113, 120, 129, 179, 231, 332, 336; **140** (1994) 1, 33, 100, 167, 175, 191, 308, 315, 444
- of growth using Monte Carlo method **134** (1993) 369
- of inhibition of dissolution **137** (1994) 545
- of interface control **131** (1993) 17, 165, 239, 431; **133** (1993) 59; **134** (1993) 35; **135** (1993) 209; **136** (1994) 18, 118, 278, 287, 293, 310, 355; **137** (1994) 335, 388; **139** (1994) 47, 113; **140** (1994) 219
- of nucleation **131** (1993) 13, 49, 115; **132** (1993) 115, 134, 141, 491; **133** (1993) 29, 196, 246; **134** (1993) 211; **136** (1994) 18, 118; **137** (1994) 161, 181, 235, 381, 535, 671; **138** (1994) 373; **139** (1994) 120; **140** (1994) 128, 299
- of optical switching **138** (1994) 213
- of pair defects **138** (1994) 1040
- of precursor decomposition **135** (1993) 423
- of relaxation **131** (1993) 32
- of silicon incorporation in indium gallium arsenide **132** (1993) 43
- of steps **133** (1993) 141, 147
- of volume diffusion **133** (1993) 322

Lanthanum
- strontium cuprate **137** (1994) 479

L-arginine phosphate **133** (1993) 132; **137** (1994) 598; **140** (1994) 336, 447

Lasers, see Device characterization

Lasers, crystals for **132** (1993) 261, 435; **135** (1993) 373, 646
- β-barium borate **134** (1993) 219
- cadmium sulphide **138** (1994) 231
- frequency conversion **131** (1993) 199
- garnets **139** (1994) 382
- indium gallium arsenide phosphide **134** (1993) 19
- lead tin selenide **139** (1994) 172
- magnesium silicate **139** (1994) 327
- organic material **139** (1994) 309
- orthoaluminates **139** (1994) 372
- II–VI compounds **138** (1994) 786
- yttrium aluminum garnet **140** (1994) 349
- yttrium vanadate **134** (1993) 1
- zinc cobalt sulphide **138** (1994) 913

Lead
- bromide **134** (1993) 386; **135** (1993) 619; **139** (1994) 158
- chloride **131** (1993) 115, 612
- fluoride **132** (1993) 241
- germanium telluride **135** (1993) 565
- iodide **131** (1993) 453; **137** (1994) 299
- molybdate **140** (1994) 148
- selenide **131** (1993) 271
- strontium borate **132** (1993) 329
- sulphate **131** (1993) 115
- telluride **138** (1994) 1034
- telluride/manganese telluride alloys **132** (1993) 20
- tin selenide **131** (1993) 271; **139** (1994) 172

Light emitting diodes, see Device characterization

Lithium
- borate **140** (1994) 128
- calcium aluminum fluoride **132** (1993) 261
- niobate **131** (1993) 145; **132** (1993) 48; **133** (1993) 255; **134** (1993) 227; **140** (1994) 45, 57
- tetraborate **133** (1993) 95; **134** (1993) 235
- triborate **140** (1994) 343
- vanadate **135** (1993) 555

Lutetium
- orthoaluminate **139** (1994) 372

Lysozyme **133** (1993) 196, 246; **135** (1993) 548; **137** (1994) 671; **139** (1994) 89

Magnesium
- alloys **137** (1994) 653
- aluminate **134** (1993) 313

– alumino-silicate garnet **134** (1993) 325
– selenide **138** (1994) 295, 508
– silicate **139** (1994) 327
– sulphite trihydrate **137** (1994) 595
– telluride **131** (1993) 607; **138** (1994) 295, 877, 1079
Maleic anhydride **140** (1994) 370
Manganese
– chloride, tetrahydrate **139** (1994) 332
– selenide **138** (1994) 601
– telluride **135** (1993) 447; **138** (1994) 1028
Melt growth technique
– of bismuth **137** (1994) 605
– by Bridgman–Stockbarger method
– – of aluminum ferrite **135** (1993) 561
– – of ammonium chloride **135** (1993) 594
– – of bismuth silicon oxide **133** (1993) 267
– – of bismuth telluride **140** (1994) 365
– – of cadmium selenium telluride **138** (1994) 239, 529
– – of cadmium telluride **132** (1993) 250, 351; **134** (1993) 281; **137** (1994) 195; **138** (1994) 249, 529; **139** (1994) 259
– – of cadmium zinc telluride **132** (1993) 250, 351; **137** (1994) 195; **138** (1994) 529
– – of cesium iodide **131** (1993) 230
– – of gallium arsenide **137** (1994) 59, 255, 375
– – of gallium germanium **131** (1993) 165
– – of garnets **139** (1994) 372
– – of germanium **131** (1993) 75
– – of gold silver telluride **131** (1993) 518
– – of indium phosphide **132** (1993) 348
– – of lead bromide **135** (1993) 619; **139** (1994) 158
– – of lead chloride **131** (1993) 612
– – of lead telluride/manganese telluride **132** (1993) 20
– – of lithium calcium aluminum fluoride **132** (1993) 261
– – of lithium tetraborate **133** (1993) 95
– – of mercury cadmium telluride **138** (1994) 956
– – of organic crystals for nonlinear optical material **139** (1994) 309
– – of orthoaluminates **139** (1994) 372
– – of silver gallium sulphide **131** (1993) 41
– – of succinonitrile–acetone **134** (1993) 181
– – of ternary alkali lead chlorides **131** (1993) 612
– – of II–VI compounds **139** (1994) 6
– – of zinc manganese sulphide **138** (1994) 1066
– – theory of **137** (1994) 54; **139** (1994) 158
– – under magnetic field
– – – of cadmium telluride **137** (1994) 201
– – using submerged heater
– – – for steady state growth **137** (1994) 64
– by Czochralski method
– – of barium metaborate **131** (1993) 199
– – of bismuth germanate **139** (1994) 67
– – of bismuth silicate **137** (1994) 128, 132; **140** (1994) 444
– – of bismuth silicon oxide **134** (1993) 337
– – of calcium strontium gallate niobate **139** (1994) 54
– – of copper **139** (1994) 351
– – of gadolinium molybdate **131** (1993) 598
– – of gallium **137** (1994) 41
– – of gallium antimonide **132** (1993) 345; **135** (1993) 290; **140** (1994) 426
– – of gallium arsenide **132** (1993) 599, 614; **134** (1993) 97; **135** (1993) 623; **137** (1994) 255; **140** (1994) 264
– – of gallium indium antimonide **135** (1993) 269
– – of germanium **139** (1994) 351
– – of germanium silicon **139** (1994) 1
– – of indium phosphide **134** (1993) 81
– – of lead molybdate **140** (1994) 148
– – of lithium niobate **131** (1993) 145; **134** (1993) 227; **140** (1994) 45
– – of low aspect ratio melts **134** (1993) 115
– – of magnesium silicate **139** (1994) 327
– – of neodymium gallate **131** (1993) 413; **137** (1994) 278
– – of rare earth orthoaluminates **131** (1993) 616
– – of silicon **131** (1993) 247; **132** (1993) 31, 451; **133** (1993) 23; **137** (1994) 12, 26, 32, 326, 427, 642; **139** (1994) 37, 197, 225, 351, 357
– – of sodium nitrate **132** (1993) 461, 467; **135** (1993) 643
– – of strontium barium niobate **140** (1994) 439
– – of strontium lanthanum gallium oxide **132** (1993) 205
– – of strontium tetraborate **135** (1993) 373
– – of terbium molybdate **131** (1993) 598
– – of tin **134** (1993) 287
– – of (uranium cerium) ruthenium silicide **134** (1993) 342
– – of yttrium aluminum garnet **140** (1994) 349
– – theory of **131** (1993) 247, 481, 598; **132** (1993) 1, 31, 297, 523, 551, 614; **133** (1993) 273; **135** (1993) 359; **137** (1994) 41; **139** (1994) 147, 197, 271, 286
– – under magnetic field **137** (1994) 48
– by edge defined film fed growth
– – of rutile **137** (1994) 82, 516
– – of silicon **137** (1994) 77, 86
– by floating zone method
– – of bismuth germanium oxide **134** (1993) 266
– – of bismuth strontium calcium cuprate **135** (1993) 481; **137** (1994) 472
– – of gallium arsenide **131** (1993) 17, 83
– – of lanthanum strontium cuprate **137** (1994) 479
– – of lithium vanadate **135** (1993) 555
– – of magnesium aluminate **134** (1993) 313
– – of organic crystals **137** (1994) 663
– – of silicon **137** (1994) 12, 95; **139** (1994) 266
– – of sodium nitrate **132** (1993) 467; **137** (1994) 72
– – of titanium boride **140** (1994) 451
– – of yttrium aluminum garnet **140** (1994) 349
– – of yttrium barium cuprate **139** (1994) 302
– – theory of **131** (1994) 209, 481; **132** (1993) 467, 578; **133** (1994) 309; **135** (1993) 606; **139** (1994) 266
– by flux method
– – of aluminum copper iron quasicrystal **135** (1993) 297
– by Kyropoulos method
– – of gold silver telluride **131** (1993) 518
– – of lead strontium borate **132** (1993) 329
– – of zinc germanium diphosphide **137** (1994) 145
– by laser heated pedestal growth
– – of strontium barium niobate **134** (1993) 255

– by laser melting
– – of silicon **137** (1994) 355
– by miniature pedestal method
– – of alumina **131** (1993) 457
– – of gallium scandium aluminum garnet **131** (1993) 457
– by pedestal growth method
– – of alumina **140** (1994) 79
– by solidification using reinforcement and magnetic rotation
– – of magnesium alloy **137** (1994) 653
– by traveling heater method
– – of bismuth strontium calcium cuprate **137** (1994) 268
– – of cadmium telluride **138** (1994) 161, 168, 346
– – of cadmium telluride selenide **138** (1994) 161
– – of cadmium zinc telluride **138** (1994) 168
– – of lead iodide **137** (1994) 299
– – of mercury cadmium telluride **132** (1993) 191; **138** (1994) 175
– – of zinc telluride **138** (1994) 219
– by uniaxial solidification
– – of alloy, model **134** (1993) 105
– – of binary alloy **137** (1994) 623
– – of cadmium telluride **137** (1994) 208
– – of gallium **140** (1994) 414
– – of halogenated hydrocarbons **134** (1993) 353
– – of ice **131** (1993) 153
– – of γ-iron chromium carbide **133** (1993) 175
– – of organic alloys **140** (1994) 115
– – of ruthenium sesquigermanide **137** (1994) 283
– – theory of **137** (1994) 623; **140** (1994) 182
– by Verneuil method
– – review of **132** (1993) 315
– by vertical gradient freeze method
– – of indium antimonide **140** (1994) 435
– by zone melting
– – theory of **131** (1993) 209
– theory of **131** (1993) 431; **132** (1993) 141; **133** (1993) 261; **140** (1994) 237

Mercury
– (I) bromide **137** (1994) 155
– cadmium telluride **131** (1993) 124, 565; **132** (1993) 191; **134** (1993) 90; **135** (1993) 383; **138** (1994) 175, 486, 517, 917, 940, 944, 950, 956, 964, 981, 1040; **139** (1994) 6, 247
– cadmium manganese telluride **138** (1994) 481
– manganese telluride **139** (1994) 211
– selenide **138** (1994) 471, 1034
– telluride **135** (1993) 383; **138** (1994) 8, 964, 981
– zinc telluride **131** (1993) 574; **135** (1993) 383; **138** (1994) 538, 934

Metals
– clusters **132** (1993) 359
– transition **137** (1994) 633

Methyl-(2,4-dinitrophenyl)-aminopropanoate **137** (1994) 141
2-Methyl-4-nitroaniline **137** (1994) 141
Microgravity, growth under
– of ammonium chloride **135** (1993) 594
– of binary alloy **137** (1994) 623
– of cadmium telluride **138** (1994) 161
– of cadmium telluride selenide **138** (1994) 161
– of gallium arsenide **137** (1994) 255
– of gallium germanium **131** (1993) 165
– of organic crystals **137** (1994) 663
– of protein **135** (1993) 183, 513
– of silicon **133** (1993) 155; **137** (1994) 95; **139** (1994) 266
– of tin **140** (1994) 237
– of yttrium barium cuprate **139** (1994) 302
– theory of **132** (1993) 377, 578; **133** (1993) 155, 217, 273, 309

Molybdenum
– ditelluride **137** (1994) 209

Monte Carlo simulation
– of fcc crystal growth **139** (1994) 129
– of moving steps **134** (1993) 369

Morphological stability
– of aluminum nitride **133** (1993) 59
– of ammonium chloride dendrites **131** (1993) 111
– of binary alloy **139** (1994) 134; **140** (1994) 139
– of calcite **131** (1993) 533
– of calcium carbonate **132** (1993) 115
– of calcium hydrogen orthophosphate dihydrate **131** (1993) 331
– of gallium arsenide **131** (1993) 17; **140** (1994) 264
– of gallium indium arsenide phosphide **131** (1993) 309
– of gallium indium phosphide **133** (1993) 207; **135** (1993) 646
– of graphite **135** (1993) 370
– of growth face of gallium arsenide **131** (1992) 17
– of halogenated hydrocarbons **134** (1993) 353
– of polyethylene adipate **134** (1993) 347
– of spiral growth **137** (1993) 82, 516
– of succinonitrile **132** (1993) 226
– of tellurium–selenium–iodine **139** (1994) 120
– of thin film interfaces **137** (1994) 355
– of tin **140** (1994) 237
– of zinc telluride **138** (1994) 523
– control of, by additives **133** (1993) 1
– in physical vapor deposition **140** (1994) 219
– theory of **131** (1993) 209; **132** (1993) 141, 405, 538; **135** (1993) 331; **140** (1994) 381

Morphology
– of silicate garnets **134** (1993) 325

Neodymium
– barium borate **137** (1994) 521
– gallate **131** (1993) 138, 413; **137** (1994) 278
– gallium garnet **135** (1993) 253

Niobium
– diselenide **137** (1994) 289
– hafnium titanium alloy **137** (1994) 102
– nitride **135** (1993) 309

Nitrogen
– organic **136** (1994) 361

Nonlinear optics, crystal for
– alkali titanyl arsenate **137** (1994) 107
– alkali titanyl phosphate **137** (1994) 107, 535
– β-barium (meta) borate **137** (1994) 123
– organic material **137** (1994) 141; **139** (1994) 309

Nucleation
- of aluminum **132** (1993) 592
- of aspartame **133** (1993) 80
- of binary systems **132** (1993) 491
- of cadmium oxalate **134** (1993) 211
- of cadmium sulphide **138** (1994) 993
- of calcium oxalate hydrates **135** (1993) 235, 523
- of citric acid **134** (1993) 196
- of cluster **139** (1994) 104
- of diamond **133** (1993) 117; **140** (1994) 441
- of gallium antimonide **132** (1993) 168
- of indium phosphide **137** (1994) 235
- of lead chloride **131** (1993) 115
- of lead sulphate **131** (1993) 115
- of lithium borate **140** (1994) 128
- of lysozyme **137** (1994) 671
- of neodymium gallium garnet **135** (1993) 253
- of niobium diselenide **137** (1994) 289
- of palladium clusters **132** (1993) 359
- of potassium titanyl phosphate **137** (1994) 535
- of screw dislocations **137** (1994) 259
- of silicon carbide **131** (1993) 71
- of tellurium **140** (1994) 123
- of thermolysin **135** (1993) 199
- of zinc oxide tetrapod particles **134** (1994) 275
- of zinc selenide **138** (1994) 1

Numbers
- Biot **132** (1993) 523
- Grashof **131** (1993) 145; **132** (1993) 451, 483; **133** (1993) 132; **134** (1993) 116; **135** (1993) 587; **137** (1994) 48, 72; **139** (1994) 67; **140** (1994) 237, 414
- Hartmann **137** (1994) 32
- Marangoni **131** (1993) 145; **137** (1994) 72, 95
- Peclet **133** (1993) 132; **137** (1994) 623; **140** (1994) 237
- Prandtl **132** (1993) 132; **137** (1994) 538; **138** (1994) 168; **139** (1994) 67
- Rayleigh **131** (1993) 145; **132** (1993) 451; **133** (1993) 132, 261; **135** (1993) 618; **137** (1994) 538; **138** (1994) 168; **139** (1994) 147; **140** (1994) 237, 414
- Reynolds **132** (1993) 483; **133** (1993) 23; **137** (1994) 72; **139** (1994) 67, 197
- Rossby **139** (1994) 197
- Rossby, thermal **139** (1994) 197
- Schmidt **137** (1994) 538; **140** (1994) 237
- Taylor **139** (1994) 197

Numerical model
- for investigation of influence of stresses **137** (1994) 86
- of wave patterns in silicon melt **137** (1994) 326

Octacalcium
- phosphate **135** (1993) 229; **140** (1994) 91
- phosphate succinate **135** (1993) 533

Optoelectronic materials, see Device characterization
Organic alloys **140** (1994) 115
Organic crystals **137** (1994) 663; **139** (1994) 309
Orthoaluminates **139** (1994) 372
Oxalates **135** (1993) 135

Palladium **134** (1993) 75
- clusters **132** (1993) 359

Paraffins **131** (1993) 13; **135** (1993) 209; **139** (1994) 179
Periodic bond chain theory
- of copper sulphoxinates, hydrated **137** (1993) 585

Phase diagrams
- of barium metaborate/sodium oxide/sodium fluoride **131** (1993) 109
- of barium oxide/copper(II) oxide/copper(I) oxide **132** (1993) 444
- of barium oxide/neodymium oxide/boron oxide **137** (1994) 521
- of cadmium/tellurium **134** (1993) 281; **138** (1994) 249
- of carbon/hydrogen **135** (1993) 165
- of carbon/hydrogen/oxygen **135** (1993) 165
- of carbon/oxygen **135** (1993) 165
- of cesium iodide/tellurium iodide **131** (1993) 230
- of copper (gallium indium) sulphide **134** (1993) 174
- of gallium arsenide **134** (1993) 14
- of halogenated hydrocarbons **134** (1993) 353
- of lead telluride/manganese telluride **132** (1993) 20
- of magnesium aluminum alloy **137** (1994) 653
- of magnesium sulphite trihydrate **137** (1994) 595
- of potassium fluoride/yttrium aluminum garnet **131** (1993) 181
- of potassium lithium tantalate niobate **131** (1993) 486
- of potassium titanyl arsenate **137** (1994) 107
- of potassium yttrium tungstate/potassium tungstate **135** (1993) 636
- of ruthenium/germanium **137** (1994) 283
- of silver/copper **140** (1994) 175
- of silver gallium sulphide **131** (1993) 41
- of water **140** (1994) 51
- of yttrium barium copper oxide **137** (1994) 487
- of yttrium vanadate **134** (1993) 1; **135** (1993) 646
- of zinc arsenide/germanium **135** (1993) 601
- of zinc selenide **131** (1993) 277

Phosphorus
- organic **136** (1994) 1, 162; **137** (1994) 212

Platinum **133** (1933) 47
Polyethylene adipate **134** (1993) 347
Polymers **131** (1993) 501
Potassium
- beryllium borate fluoride **132** (1993) 609
- bromide **131** (1993) 395
- dihydrogen phosphate **133** (1993) 132; **137** (1994) 598
- lithium tantalate niobate **131** (1993) 486
- neodymium silicates **131** (1993) 352
- titanyl arsenate **137** (1994) 107
- titanyl phosphate **137** (1994) 107, 116, 535; **140** (1994) 51
- yttrium tungstate **135** (1993) 636

Precursor
- for aluminum arsenide **134** (1993) 140
- for aluminum film growth **135** (1994) 285
- for aluminum gallium arsenide **136** (1994) 11, 152
- for arsenides **137** (1994) 212
- for barium titanate **137** (1994) 136

– for bismuth lead strontium calcium cuprate **135** (1993) 496
– for cadmium telluride **140** (1994) 327
– for gallium arsenide **131** (1993) 176; **136** (1994) 69, 127, 133, 138, 152; **137** (1994) 347
– for gallium indium arsenide **140** (1994) 33
– for indium antimonide **132** (1993) 371; **135** (1993) 401
– for indium arsenide bismuthide **134** (1993) 29
– for indium gallium arsenide **136** (1994) 1, 69, 78, 133
– for indium gallium arsenide phosphide **136** (1994) 148
– for indium gallium phosphide **136** (1994) 1, 11
– for phosphides **137** (1994) 212
– for silicon nitride **137** (1994) 452
– for sulphur doping **135** (1993) 31
– for II–VI compounds **138** (1994) 425; **140** (1994) 327
– for zinc selenide **131** (1993) 49; **134** (1993) 293
– kinetics of reaction **137** (1994) 212
Proteins **135** (1993) 183, 513; **139** (1994) 95
Pumpkin seed globulin **133** (1993) 29
Purification of materials
– of lead chloride **131** (1993) 612
– of organic material **139** (1994) 309
– of silicon carbide **137** (1994) 181

Quantification of morphology **137** (1994) 1
Quantum dots, see Device characterization
Quantum wells, see Device characterization
Quantum wires, see Device characterization
Quartz **131** (1993) 560
Quasicrystals **135** (1993) 297

Rare earth
– aluminum garnets **139** (1994) 372
– garnets **140** (1994) 84
– orthoaluminates **131** (1993) 616
– rhombic aluminates **139** (1994) 372
Residual gas in silicon glas ampoule **131** (1993) 193
Rochelle salt **139** (1994) 332
Ruthenium
– sesquigermanide **137** (1994) 283
– telluride **135** (1993) 224
Rutile **137** (1994) 82, 516

Salol **137** (1994) 663
Selenium
– organic **136** (1994) 371
Silicate garnets **134** (1993) 325
Silicon **131** (1993) 247, 265, 316, 495, 589; **133** (1993) 23, 155; **134** (1993) 203; **135** (1993) 246, 273, 606; **136** (1994) 322, 328, 333, 338, 344, 349; **137** (1994) 12, 26, 32, 37, 48, 77, 86, 95, 326, 355, 427, 642; **139** (1994) 19, 37, 197, 225, 351, 357; **140** (1994) 191
– boron alloy **134** (1993) 203
– carbide **131** (1993) 5, 71; **132** (1993) 504; **135** (1993) 61; **137** (1994) 161, 175, 181
– dioxide **131** (1993) 560; **140** (1994) 308, 315
– germanium **131** (1993) 32; **134** (1993) 203; **136** (1994) 315, 355
– germanium boron alloy **134** (1993) 203
– nitride **137** (1994) 452; **140** (1994) 157
– organic **137** (1994) 400, 452
Silver
– copper **140** (1994) 175
– gallium sulphide **131** (1993) 41
Sodium
– chlorate **139** (1994) 336
– chloride **139** (1994) 104
– neodymium silicates **131** (1993) 373
– nitrate **132** (1993) 461, 467; **135** (1993) 643; **137** (1994) 72
– tungsten bronzes **131** (1993) 473
– yttrium silicates **131** (1993) 373
Solar cells, see Device characterization
Solid growth technique
– by recrystallization
– – of bismuth lead strontium calcium cuprate **135** (1993) 496
– – of cadmium telluride **138** (1994) 168
– – of cadmium zinc telluride **138** (1994) 168
– – of copper tungstate **132** (1993) 606
– – of diamond **140** (1994) 441
– – of erbium silicide **134** (1993) 247
– – of iron tungstate **132** (1993) 606
– – of mercury cadmium telluride **131** (1993) 565
– – of potassium bromide **131** (1993) 395
– – of tellurium–selenium–iodine **139** (1994) 120
– by sintering
– – of yttrium barium cuprate **135** (1993) 487
– by strain anneal
– – of mercury cadmium telluride **131** (1993) 565
– – theory of **139** (1994) 134
– theory of **131** (1993) 395
Solution growth technique
– by chemical reaction
– – of cadmium sulphide **138** (1994) 993
– by electrochemical deposition
– – of cadmium telluride **138** (1994) 86
– by electrocrystallization
– – of lead chloride **131** (1993) 115
– – of lead sulphate **131** (1993) 115
– by flux method
– – of alkali titanyl arsenate **137** (1994) 107
– – of alkali titanyl phosphate **137** (1994) 107
– – of β-barium borate **134** (1993) 219; **137** (1994) 123
– – of barium hexaferrite **131** (1993) 97
– – of bismuth strontium calcium cuprate **131** (1993) 105; **139** (1994) 86
– – of bismuth strontium calcium cuprate, rare earth substituted **139** (1994) 81
– – of borates **132** (1993) 173
– – of cadmium zinc telluride **138** (1994) 199
– – of calcium strontium sulphide **138** (1994) 1051
– – of cesium titanyl arsenate **131** (1993) 323; **132** (1993) 280, 289
– – of copper (gallium indium) sulphide **134** (1993) 174
– – of gallium oxide **132** (1993) 335
– – of huntite borate **133** (1993) 181

– – of iron sulphide **131** (1993) 448
– – of lithium triborate **140** (1994) 343
– – of neodymium barium borate **137** (1994) 521
– – of potassium beryllium borate fluoride **132** (1993) 609
– – of potassium titanyl phosphate **137** (1994) 116, 535
– – of potassium yttrium tungstate **135** (1993) 636
– – of strontium calcium cuprate **140** (1994) 72
– – of strontium hexaferrite **137** (1994) 493
– – of yttrium aluminum garnet **131** (1993) 181
– – of yttrium barium cuprate **132** (1993) 444; **137** (1994) 273, 487; **139** (1994) 190
– – of yttrium iron garnet **134** (1993) 43
– – of yttrium vanadate **134** (1993) 1; **135** (1993) 646
– by flux method, top seeded
– – of barium metaborate **131** (1993) 199
– by gel method
– – of cadmium sulphide **138** (1994) 998
– – of calcium carbonate **132** (1993) 115
– – of maleic anhydride **140** (1994) 370
– – of uric acid **132** (1993) 617
– by hydrostatic pressure
– – of lysozyme **135** (1993) 548
– by hydrothermal growth
– – of barium oxide–iron(III) oxide **139** (1994) 47
– – of bismuth silicate **137** (1994) 128
– – of potassium neodymium silicates **131** (1993) 352
– – of potassium titanyl phosphate **140** (1994) 51
– – of quartz **131** (1993) 560
– – of sodium neodymium silicates **131** (1993) 373
– – of sodium yttrium silicates **131** (1993) 373
– by isothermal method at high supersaturation
– – of sucrose **137** (1994) 304
– by local growth in solution
– – of zinc hexacyanoferrates **137** (1994) 569
– by low temperature method
– – of ammonium dihydrogen phosphate **137** (1994) 598
– – of ammonium triantimony decafluoride **137** (1994) 295
– – of barium nitrate **137** (1994) 610
– – of calcium carbonate **132** (1993) 23; **137** (1994) 577
– – of calcium oxalate **132** (1993) 122; **133** (1993) 87, 189
– – of calcium oxalate hydrates **135** (1993) 235
– – of calcium oxalate hydrate in presence of membrane vesicles **134** (1993) 211
– – of copper sulphoxinates, hydrated **137** (1994) 585
– – of deuterated L-arginine phosphate **140** (1994) 336
– – of gypsum **132** (1993) 99
– – of hydrargillite **135** (1993) 505
– – of hydroxyapatite **133** (1993) 1; **135** (1993) 229, 539
– – of L-arginine phosphate **133** (1993) 132; **137** (1994) 598; **140** (1994) 336, 447
– – of lysozyme **133** (1993) 196, 246; **139** (1994) 89
– – of magnesium sulphite trihydrate **137** (1994) 595
– – of manganese chloride, tetrahydrate **139** (1994) 332
– – of octacalcium phosphate **132** (1993) 215; **135** (1993) 229; **137** (1994) 553; **140** (1994) 91
– – of organic crystals **137** (1994) 141
– – of paraffins **135** (1993) 209
– – of potassium dihydrogen phosphate **133** (1993) 132; **137** (1994) 598
– – of protein **135** (1993) 183; **139** (1994) 95
– – of pumpkin seed globulin **133** (1993) 29
– – of Rochelle salt **139** (1994) 332
– – of sodium chlorate **139** (1994) 336
– – of strontium sulphate **135** (1993) 323
– – of tetrathiofulvalene–tetracyanoquinodimethane **135** (1993) 196
– – of thermylysin **135** (1993) 199
– – of triallylthiourea mercury bromide **133** (1993) 71
– – of triglycine sulphate **133** (1993) 212; **140** (1994) 100
– – of triglycine sulpho-phosphate **133** (1993) 212
– – of zinc sulphide **138** (1994) 970
– – theory of **137** (1994) 585
– by room temperature method
– – of calcium hydrogen orthophosphate dihydrate **131** (1993) 331
– by solvent evaporation
– – of polyethylene adipate **134** (1993) 347
– by top seeded solution growth
– – of potassium lithium tantalate niobate **131** (1993) 486
– – of yttrium vanadate **134** (1993) 1; **135** (1993) 646
– by yo-yo solute feeding method
– – of indium gallium phosphide **137** (1994) 245
– cluster formation, theory of **139** (1994) 104
– theory of **131** (1993) 560; **132** (1993) 405; **137** (1994) 538; **140** (1994) 107
Spinel **134** (1993) 313
Statistical mechanics, molecular theory
– of defects **137** (1993) 12
– of interfaces **135** (1993) 209
– of roughening transition **139** (1994) 179
Stefan problem or moving boundary problem
– of binary alloy **139** (1994) 134; **140** (1994) 139
– of binary mixture **139** (1994) 113
– of cell formation **140** (1994) 264
– of silicon **137** (1994) 26
– of tube crystals **135** (1993) 606
– theory **131** (1993) 209; **132** (1993) 551, 578
Strontium
– barium niobate **134** (1993) 255; **140** (1994) 439
– calcium cuprate **140** (1994) 72
– hexaferrite **137** (1994) 493
– lanthanum gallium oxide **132** (1993) 205
– sulphate **135** (1993) 323
– sulphide **137** (1994) 150; **138** (1994) 1010, 1017, 1061, 1075
– tetraborate **135** (1993) 373
– titanate **135** (1993) 145
Succinonitrile **132** (1993) 226; **137** (1994) 304
Succinonitrile–acetone alloy **134** (1993) 181
Succinonitrile–ethanol model alloy **134** (1993) 105
Sucrose **137** (1994) 304
Superconductivity materials, high T_c
– bulk
– – of BSCCO **131** (1993) 105; **135** (1993) 481, 496; **137** (1994) 268, 472; **139** (1994) 86

– – of BSCCO, rare earth substituted **139** (1994) 81
– – of LaSCO **137** (1994) 479
– – of YBCO **132** (1993) 82, 396, 444; **137** (1994) 273, 487; **139** (1994) 302
– – of YBCO, tantalum doped **139** (1994) 190
– film
– – of YBCO **135** (1993) 145, 487; **137** (1994) 259
– substrate application for **139** (1994) 54
Superconductivity materials, low T_c
– bulk
– – of niobium diselenide **137** (1994) 289
Superlattices, multilayers
– of close-packed metals **137** (1994) 633
– of IV compounds **134** (1993) 203
– of III–V compounds **131** (1993) 1; **132** (1993) 341, 435; **134** (1993) 240; **135** (1993) 123; **136** (1994) 18, 56, 210, 268, 273, 287, 293, 297, 302, 310; **137** (1994) 231, 405; **138** (1994) 776; **140** (1994) 205
– of II–VI compounds **135** (1993) 447; **138** (1994) 35, 63, 121, 140, 150, 182, 191, 513, 534, 550, 559, 564, 580, 590, 601, 612, 633, 643, 647, 652, 656, 661, 750, 776, 786, 796, 826, 868, 877, 884, 889, 900, 981, 1028
Surface energy, determination
– of calcite **131** (1993) 533
– of gallium antimonide **131** (1993) 157
– of garnets **134** (1993) 325
– of indium antimonide **131** (1993) 157
– of paraffins **135** (1993) 209
– of polymers **131** (1993) 501
– of potassium titanyl phosphate **137** (1994) 535
– of silicon nitride **140** (1994) 157
– of triglycine sulphate **140** (1994) 100
Surface morphology
– of aluminum nitride **133** (1993) 59
– of yttrium barium cuprate **132** (1993) 82
Surface processes, theory of **133** (1993) 141, 147
Surface structure
– of aspartame **133** (1993) 80
– of barium nitrate **137** (1994) 610
– of cadmium selenide **138** (1994) 545
– of calcite **131** (1993) 533
– of cerium dioxide **131** (1993) 347
– of diamond film **135** (1994) 172
– of gallium arsenide **136** (1994) 114; **137** (1994) 335
– of garnets **134** (1993) 325
– of indium antimonide **135** (1993) 401
– of indium arsenide **135** (1993) 97
– of indium phosphide **133** (1993) 185
– of lead iodide **137** (1994) 299
– of mercury cadmium telluride **138** (1994) 517
– of mercury zinc telluride **138** (1994) 934
– of metalorganic molecular beam epitaxy interface **136** (1994) 118
– of palladium catalyst **134** (1993) 75
– of paraffins **135** (1993) 209
– of silicon nitride **140** (1994) 157
– of III–V compounds **136** (1994) 18
– of yttrium barium cuprate **132** (1993) 396; **137** (1994) 259
– of zinc selenide **131** (1993) 277; **133** (1993) 75; **138** (1994) 55, 59

Tellurium **140** (1994) 123
– organic **136** (1994) 256
– selenium–iodine **139** (1994) 120
Terbium
– molybdate **131** (1993) 598
Ternary alkali lead chlorides **131** (1993) 612
Tetrathiofulvalene–tetracyanoquinodimethane **135** (1993) 196
Thermolysin **135** (1993) 199; **139** (1994) 95
Thin film growth, epitaxy
– by atomic layer epitaxy
– – of cadmium selenide **138** (1994) 63
– – of cadmium telluride **135** (1993) 447
– – of gallium arsenide **131** (1993) 61
– – of gallium nitride **135** (1993) 633
– – of manganese telluride **135** (1994) 447
– – of zinc selenide **138** (1994) 63, 136
– – of zinc telluride **135** (1993) 447
– by chemical beam epitaxy
– – of gallium indium arsenide **131** (1993) 387
– – of gallium indium phosphide **131** (1993) 387
– – theory of **131** (1993) 387; **137** (1994) 212
– by chemical reaction
– – of silicon carbide **131** (1993) 5
– by focused ion beam
– – of gallium arsenide **140** (1994) 244
– by gas source molecular beam epitaxy
– – of aluminum antimonide **136** (1994) 310
– – of aluminum gallium indium phosphide **136** (1994) 306
– – of aluminum phosphide **136** (1994) 268
– – of gallium arsenide phosphide **131** (1993) 309; **136** (1994) 282
– – of gallium indium phosphide **136** (1994) 306
– – of gallium nitride **136** (1994) 361
– – of gallium phosphide **136** (1994) 268
– – of indium arsenide **136** (1994) 310
– – of indium gallium arsenide **136** (1994) 216, 287
– – of indium phosphide **136** (1994) 287
– – of silicon **136** (1994) 322, 328, 333, 338, 344
– – of silicon germanium **136** (1994) 315, 355
– – of zinc selenide **136** (1994) 366
– by hot wall epitaxy
– – of cadmium selenide **138** (1994) 150, 191
– – of cadmium sulphide **138** (1994) 150, 191
– – of cadmium telluride **138** (1994) 131
– – of cadmium zinc telluride **138** (1994) 131
– – of strontium sulphide **138** (1994) 1010, 1061
– – of zinc sulphide **138** (1994) 1010, 1061
– – of zinc telluride **138** (1994) 81
– by laser ablation
– – of silicon **137** (1994) 355
– – of yttrium barium cuprate **132** (1993) 396
– by laser-assisted metalorganic molecular beam epitaxy
– – of indium gallium arsenide phosphide **136** (1994) 273

– by liquid phase electroepitaxy
– – of aluminum gallium arsenide **131** (1993) 426
– – of gallium antimonide **139** (1994) 206
– by liquid phase epitaxy
– – of aluminum gallium arsenide **131** (1993) 426
– – of aluminum gallium indium phosphide **137** (1994) 240
– – of cadmium zinc telluride **138** (1994) 950
– – of gallium arsenide **131** (1993) 17; **133** (1993) 123; **134** (1993) 14; **135** (1993) 367; **137** (1994) 335; **140** (1994) 28
– – of germanium silicide **137** (1994) 457
– – of indium antimonide arsenide **133** (1993) 108
– – of indium gallium arsenide **139** (1994) 238
– – of indium gallium arsenide phosphide **139** (1994) 251
– – of lithium niobate **132** (1993) 48
– – of mercury cadmium telluride **138** (1994) 517, 944, 950; **139** (1994) 6
– – of rare earth garnets **140** (1994) 84
– – of silicon **135** (1993) 273
– – theory of **135** (1993) 145
– by magnetron sputtering
– – of indium aluminum antimonide **137** (1994) 405
– – of indium antimonide **137** (1994) 405
– – of nitrides **135** (1993) 309
– – of zinc oxide **137** (1994) 319
– by metalorganic molecular epitaxy
– – of aluminum **132** (1993) 592
– – of aluminum antimonide **136** (1994) 250
– – of aluminum arsenide **136** (1994) 50
– – of aluminum gallium antimonide **136** (1994) 250
– – of aluminum gallium arsenide **136** (1994) 11, 152
– – of gallium antimonide **136** (1994) 250
– – of gallium arsenide **133** (1993) 296; **136** (1994) 37, 69, 99, 104, 109, 114, 127, 133, 138, 143, 152, 162, 200, 221, 230, 235, 241, 256, 261
– – of gallium indium arsenide **131** (1993) 387; **132** (1993) 91
– – of gallium indium arsenide phosphide **131** (1993) 387
– – of gallium indium phosphide **131** (1993) 387
– – of gallium nitride **136** (1994) 37
– – of gallium phosphide **136** (1994) 89
– – of indium aluminum arsenide **136** (1994) 166
– – of indium arsenide **136** (1994) 278
– – of indium gallium arsenide **136** (1994) 1, 50, 69, 78, 109, 133, 166, 186, 195, 225, 293, 302; **140** (1994) 277
– – of indium gallium arsenide phosphide **136** (1994) 50, 56, 64, 148, 173, 195, 210, 246, 297
– – of indium gallium phosphide **136** (1994) 1, 11, 221, 261
– – of indium phosphide **132** (1993) 91; **136** (1994) 42, 50, 162, 166, 173, 179, 195, 278, 293, 297; **140** (1994) 277
– – of III–V compounds **136** (1994) 18, 29
– – of zinc selenide **131** (1993) 49; **136** (1994) 371, 376; **138** (1994) 19, 391, 425
– – of zinc sulphoselenide **138** (1994) 391
– – of zinc telluride **133** (1993) 101
– – theory of **131** (1993) 387; **136** (1994) 69, 83, 109, 127; **137** (1994) 224
– – theory of precursor design **136** (1994) 118
– by migration enhanced epitaxy
– – of silicon **139** (1994) 19
– – of zinc cadmium selenide **137** (1994) 187
– – of zinc sulphoselenide **137** (1994) 187
– by molecular beam epitaxy
– – of aluminum arsenide **132** (1993) 427; **135** (1993) 85; **137** (1994) 680
– – of aluminum gallium arsenide **132** (1993) 166; **133** (1993) 241; **135** (1993) 85, 455
– – of aluminum gallium indium arsenide **131** (1993) 419
– – of aluminum indium arsenide **131** (1993) 419
– – of barium fluoride **132** (1993) 241
– – of bismuth telluride **140** (1994) 365
– – of cadmium magnesium selenide **138** (1994) 692
– – of cadmium magnesium telluride **138** (1994) 155, 437
– – of cadmium manganese telluride **138** (1994) 437, 652, 661, 856
– – of cadmium selenide **138** (1994) 601, 619
– – of cadmium sulphide **138** (1994) 559
– – of cadmium telluride **131** (1993) 607; **135** (1993) 53; **137** (1994) 435; **138** (1994) 8, 437, 443, 550, 590, 607, 652, 856; **140** (1994) 287
– – of cadmium zinc telluride **137** (1994) 393; **138** (1994) 607, 661
– – of calcium fluoride **132** (1993) 241
– – of cobalt **139** (1994) 363
– – of gallium antimonide **131** (1993) 620
– – of gallium arsenide **132** (1993) 103, 209, 331, 427, 533; **133** (1993) 241; **134** (1993) 151; **135** (1993) 31, 78, 85, 377, 441, 455, 469; **136** (1994) 114, 191; **137** (1994) 680
– – of gallium arsenide/gallium indium arsenide **131** (1993) 1
– – of gallium phosphide **131** (1993) 465; **135** (1993) 123
– – of gallium selenide **135** (1993) 1; **138** (1994) 204
– – of indium aluminum arsenide **134** (1993) 147
– – of indium arsenide **131** (1993) 300, 465, 620; **132** (1993) 331; **135** (1993) 97; **137** (1994) 381
– – of indium gallium arsenide **134** (1993) 51, 147, 162, 240; **136** (1994) 191
– – of indium gallium phosphide **138** (1994) 1
– – of indium phosphide **131** (1993) 465; **135** (1993) 123; **139** (1994) 19
– – of lead fluoride **132** (1993) 241
– – of magnesium selenide **138** (1994) 508
– – of magnesium telluride **131** (1993) 607
– – of manganese selenide **138** (1994) 601
– – of manganese telluride **138** (1994) 1028
– – of mercury selenide **138** (1994) 471
– – of mercury telluride **138** (1994) 8
– – of palladium **134** (1993) 75
– – of platinum **133** (1993) 47
– – of silicon **131** (1993) 316; **134** (1993) 203; **135** (1993) 246
– – of silicon germanium **134** (1993) 203
– – of transition metals **137** (1994) 633
– – of zinc cadmium selenide **137** (1994) 187; **138** (1994) 391, 455, 564, 647, 686, 745, 861
– – of zinc cadmium sulphoselenide **138** (1994) 28, 703
– – of zinc magnesium sulphoselenide **138** (1994) 367, 686

– – of zinc selenide **131** (1993) 277; **133** (1993) 75; **135** (1993) 41; **138** (1994) 1, 14, 48, 55, 59, 94, 110, 182, 266, 290, 331, 352, 357, 373, 391, 397, 403, 408, 455, 464, 564, 601, 619, 633, 647, 745, 861, 1073
– – of zinc sulphide **138** (1994) 28, 145, 559
– – of zinc sulphoselenide **137** (1994) 187; **138** (1994) 28, 182, 331, 367, 391, 455, 686, 745
– – of zinc sulphoselenide telluride **138** (1994) 703
– – of zinc telluride **138** (1994) 8, 81, 523, 550, 590, 633, 692; **140** (1994) 282
– – strain limits in **135** (1993) 36
– – theory of **135** (1993) 354; **137** (1994) 212
– by molecular beam epitaxy, photo-assisted
– – of zinc selenide **132** (1993) 575
– of molecular beam epitaxy, through plasma source
– – of zinc selenide **138** (1994) 430
– by radio frequency sputtering
– – of neodymium gallium oxide **131** (1993) 138
– – of zinc oxide **131** (1993) 546
– by solid source molecular beam epitaxy
– – of silicon germanium **136** (1994) 355
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of aluminum nitride **133** (1993) 59
– – – of boron phosphide **132** (1993) 611
– – – of diamond **132** (1993) 200; **133** (1993) 117, 329; **135** (1993) 165, 172, 639; **137** (1994) 161, 676; **140** (1994) 454
– – – of gallium arsenide **135** (1993) 259
– – – of gallium indium arsenide **135** (1993) 11
– – – of gallium nitride **137** (1994) 161
– – – of indium phosphide **135** (1993) 11; **140** (1994) 291
– – – of silicon **131** (1993) 495, 589; **136** (1994) 349
– – – of silicon carbide **137** (1994) 161, 175
– – – of silicon germanium **131** (1993) 32
– – – of titanium silicide **134** (1993) 377
– – – of zinc selenide **138** (1994) 75
– – – theory of **131** (1993) 589; **132** (1993) 483, 513; **135** (1993) 11, 172; **140** (1994) 191, 308
– – through chemical vapor deposition, plasma-assisted
– – – of aluminum oxide **132** (1993) 337
– – through co-deposition methods
– – – of yttrium barium cuprate **137** (1994) 259
– – through evaporation and condensation
– – – of bismuth strontium cuprate **140** (1994) 65
– – – of cerium dioxide **131** (1993) 347
– – – of mercury cadmium telluride **138** (1994) 964
– – – of mercury telluride **138** (1994) 964
– – – of n-paraffin **131** (1993) 13
– – – of silicon carbide **131** (1993) 71
– – – of yttrium barium cuprate **132** (1993) 82
– – – of zinc selenide **138** (1994) 255
– – through metalorganic chemical vapor deposition
– – – of aluminum **132** (1993) 25; **135** (1993) 285
– – – of aluminum arsenide **134** (1993) 140; **135** (1993) 365
– – – of aluminum gallium arsenide **132** (1993) 179; **133** (1993) 281; **134** (1993) 140; **139** (1994) 231, 344
– – – of aluminum gallium indium phosphide **137** (1994) 400
– – – of aluminum nitride **133** (1993) 59
– – – of barium titanate **137** (1994) 136; **140** (1994) 355
– – – of bismuth titanium oxide **139** (1994) 319
– – – of cadmium mercury telluride **138** (1994) 917
– – – of cadmium selenide **135** (1993) 383
– – – of cadmium sulphide **138** (1994) 140
– – – of cadmium telluride **131** (1993) 133; **133** (1993) 230; **135** (1993) 383, 409; **138** (1994) 43, 538; **140** (1994) 327
– – – of cadmium zinc sulphide **138** (1994) 538, 570
– – – of cadmium zinc telluride **138** (1994) 538
– – – of copper aluminum selenide **131** (1993) 176, 283
– – – of gallium antimonide **133** (1993) 168
– – – of gallium arsenide **131** (1993) 176, 283; **132** (1993) 179, 364, 477; **133** (1993) 201, 296; **134** (1993) 35, 140; **135** (1993) 423, 629; **137** (1994) 347, 442; **139** (1994) 231, 344; **140** (1994) 299
– – – of gallium indium aluminum phosphide **138** (1994) 768
– – – of gallium indium arsenide **132** (1993) 43, 61, 231, 364, 435; **135** (1994) 129; **140** (1994) 33
– – – of gallium indium arsenide phosphide **132** (1993) 231, 435
– – – of gallium indium phosphide **132** (1993) 364; **133** (1993) 207; **135** (1993) 646
– – – of gallium nitride **137** (1994) 170
– – – of gallium phosphide **132** (1993) 132, 354, 414
– – – of germanium **138** (1994) 43
– – – of indium aluminum arsenide **131** (1993) 186; **135** (1993) 365
– – – of indium antimonide **132** (1993) 371; **135** (1993) 401, 434
– – – of indium antimonide phosphide **133** (1993) 38
– – – of indium arsenide **137** (1994) 231
– – – of indium arsenide antimonide **137** (1994) 231
– – – of indium arsenide bismuthide **134** (1993) 29
– – – of indium gallium aluminum arsenide **135** (1993) 463
– – – of indium gallium aluminum phosphide **133** (1993) 303
– – – of indium gallium arsenide **133** (1993) 289; **140** (1994) 432
– – – of indium gallium arsenide phosphide **134** (1993) 19; **136** (1994) 56
– – – of indium nitride **137** (1994) 415
– – – of indium phosphide **131** (1993) 204; **132** (1993) 231, 364, 435; **133** (1993) 185; **137** (1994) 313; **140** (1994) 1, 19
– – – of lithium niobate **140** (1994) 57
– – – of mercury cadmium telluride **131** (1993) 124; **134** (1993) 90; **135** (1993) 383; **139** (1994) 247
– – – of mercury manganese telluride **139** (1994) 211
– – – of mercury telluride **135** (1993) 383
– – – of mercury zinc telluride **135** (1993) 383; **138** (1994) 538
– – – of semiconductors (III–V) **132** (1993) 305
– – – of silicon dioxide **140** (1994) 308, 315
– – – of titanium dioxide **134** (1993) 302
– – – of zinc cadmium selenide **138** (1994) 629
– – – of zinc selenide **131** (1993) 49; **133** (1993) 101; **134** (1993) 293; **135** (1993) 383; **138** (1994) 35, 105, 114, 121, 127, 182, 208, 266, 324, 338, 379, 412, 448, 513, 534, 595, 612, 629, 750; **140** (1994) 429

– – – of zinc selenide telluride **138** (1994) 595
– – – of zinc sulphide **137** (1994) 421; **138** (1994) 121, 140, 418, 534, 578
– – – of zinc sulphoselenide **134** (1993) 293; **138** (1994) 35
– – – of zinc telluride **135** (1993) 113, 383; **138** (1994) 412, 513, 538
– – – optimization of, by flow visualization **134** (1993) 302
– – – theory of **131** (1993) 283; **132** (1993) 364; **133** (1993) 289; **135** (1993) 354, 629; **137** (1994) 212, 224; **140** (1994) 33, 249
– – through metalorganic chemical vapor deposition, photo-assisted
– – – of gallium arsenide **135** (1993) 23
– – – of indium phosphide **139** (1994) 15
– – – of zinc aluminum selenide **138** (1994) 737
– – – of zinc selenide **138** (1994) 737, 1071
– – through plasma-assisted epitaxy
– – – of indium antimonide **136** (1994) 157
– – – of indium arsenide **136** (1994) 157
– – – of zinc selenide **136** (1994) 157
– – theory of **135** (1993) 259; **137** (1994) 235
– theory of **138** (1994) 68
Three–five (III–V) compounds **136** (1994) 18, 83
Thulium
– orthoaluminate **139** (1994) 372
Tin **134** (1993) 287; **140** (1994) 237
– disulphide **131** (1993) 268
Titanium
– boride **140** (1994) 451
– dioxide **134** (1993) 302; **137** (1994) 82, 516
– nitride **135** (1993) 309
– organic **137** (1994) 136
– silicide **134** (1993) 377
– zirconium molybdenum alloy **137** (1994) 102
Transistors, see Device characterization
Triallylthiourea mercury bromide **133** (1993) 71
Triglycine
– sulphate **133** (1993) 212; **140** (1994) 100
– sulpho-phosphate **133** (1993) 212
Tungsten **131** (1993) 439; **135** (1993) 606
– dioxide **137** (1994) 499
Twinning
– of neodymium gallate **137** (1994) 278
– of ruthenium sesquigermanate **137** (1994) 283
– of zinc oxide **134** (1993) 275
Two–six (II–VI) compounds **139** (1994) 6
– doping and impurities in **138** (1994) 290, 310, 318, 324, 338, 352, 357, 379, 385, 391, 397, 403, 408, 418, 425, 437, 443, 448, 607, 737, 745, 750
– theory of **138** (1994) 295, 301, 305, 820, 895

Uranium
– cerium ruthenium silicide **135** (1993) 342
Uric acid **132** (1993) 617

Vanadium
– nitride **135** (1993) 309
Vapor growth technique
– by chemical transport
– – of cadmium sulphoselenide **134** (1993) 63
– – of copper (aluminum gallium) sulphur selenide **140** (1994) 388
– – of copper tungstate **132** (1993) 606
– – of iron iodide **132** (1993) 129
– – of iron tungstate **132** (1993) 606
– – of mercury zinc telluride **131** (1993) 574
– – of molybdenum ditelluride **137** (1994) 309
– – of niobium diselenide **137** (1994) 289
– – of ruthenium telluride **135** (1993) 224
– – of tungsten dioxide **137** (1994) 499
– – of zinc germanium diphosphide **137** (1994) 145
– – of zinc oxide **134** (1993) 275
– – of zinc sulphide **134** (1993) 67
– – theory of **131** (1993) 574
– by evaporation and condensation
– – of cadmium sulphide selenide **135** (1993) 476
– – of cadmium telluride **139** (1994) 27
– – of carbon, graphitic **134** (1993) 154
– – of fullerene **134** (1993) 157; **135** (1993) 154
– – of lead di-iodide **131** (1993) 453
– – of lead germanium telluride **135** (1993) 565
– – of lead tin selenide **139** (1994) 172
– – of mercury(I) bromide **137** (1994) 155
– – of protein **135** (1993) 183
– – of silicon carbide **132** (1993) 504; **135** (1993) 61; **137** (1994) 181
– – of silicon nitride **137** (1994) 452
– – of strontium sulphide **137** (1994) 150; **138** (1994) 1075
– – of succinonitrile **132** (1993) 226
– – of tellurium **140** (1994) 123
– – of tin disulphide **131** (1993) 268
– – of tungsten **131** (1993) 439
– – of ytterbium **132** (1993) 71
– – of ytterbium oxide **132** (1993) 71
– – of zinc selenide **135** (1993) 318; **138** (1994) 260
– – of zinc telluride **138** (1994) 219
– – theory of **132** (1993) 538; **135** (1993) 578; **140** (1994) 219
– by plasma in arc discharge
– – of fullerene **135** (1993) 157
– theory of **133** (1993) 217
Vapor–liquid–solid growth
– of succinonitrile–acetone alloy **134** (1993) 181
Vaterite **133** (1993) 13; **137** (1994) 577

Wave guides, see Device characterization
Whisker growth
– of carbon, graphitic **134** (1993) 154
– of sodium tungsten bronzes **131** (1993) 473
– of zinc oxide **134** (1993) 275

Ytterbium **132** (1993) 71
– orthoaluminate **139** (1994) 372
– oxide **132** (1993) 71
Yttrium

- aluminum garnet **131** (1993) 181; **139** (1994) 147, 372; **140** (1994) 349
- barium cuprate **132** (1993) 82, 396, 444; **135** (1993) 145, 487; **137** (1994) 259, 273, 487; **139** (1994) 302
- iron garnet **134** (1993) 43
- orthoaluminate **139** (1994) 372
- vanadate **134** (1993) 1; **135** (1993) 646

Zinc
- cadmium selenide **137** (1994) 187; **138** (1994) 391, 508, 564, 625, 629, 647, 667, 677, 686, 709, 714, 719, 745, 759, 764, 838, 861, 1077
- cadmium sulphide **138** (1994) 538, 570
- cadmium sulphoselenide **138** (1994) 28, 391, 703
- cobalt sulphide **138** (1994) 913
- germanium arsenide **135** (1993) 601
- germanium diphosphide **137** (1994) 145
- hexacyanoferrates **137** (1994) 569
- magnesium sulphoselenide **138** (1994) 367, 667, 677, 686, 709, 719, 1077
- magnesium sulphoselenide telluride **138** (1994) 1079
- manganese selenide **138** (1994) 575, 905
- manganese sulphide **138** (1994) 1066
- organic **136** (1994) 371, 376; **137** (1994) 400, 421
- oxide **131** (1993) 546; **134** (1993) 275; **137** (1994) 319; **138** (1994) 924
- selenide **131** (1993) 49, 277; **132** (1993) 575; **133** (1993) 75; **134** (1993) 293; **135** (1993) 41, 318, 383; **136** (1994) 157, 366, 371, 376; **138** (1994) 1, 14, 19, 35, 48, 55, 59, 63, 75, 94, 99, 105, 110, 114, 127, 136, 195, 255, 260, 295, 301, 305, 310, 318, 324, 331, 338, 352, 357, 373, 379, 385, 391, 397, 403, 408, 412, 425, 430, 448, 455, 464, 477, 504, 534, 564, 575, 595, 601, 619, 625, 629, 633, 643, 647, 677, 714, 727, 745, 750, 759, 764, 796, 805, 820, 838, 849, 861, 868, 924, 1071, 1073, 1076, 1078; **140** (1994) 429
- selenide telluride **138** (1994) 595
- sulphide **134** (1993) 67; **137** (1994) 421; **138** (1994) 28, 140, 145, 418, 534, 559, 570, 643, 796, 873, 970, 1010, 1023, 1061
- sulphoselenide **134** (1993) 293; **137** (1994) 187; **138** (1994) 28, 35, 324, 331, 367, 455, 667, 686, 709, 714, 719, 745, 750, 755, 1046, 1076, 1077
- sulphoselenide telluride **138** (1994) 703
- telluride **133** (1993) 101; **135** (1993) 113, 383, 447; **138** (1994) 8, 81, 187, 219, 295, 412, 523, 538, 550, 580, 590, 633, 692, 826, 868; **140** (1994) 282

Control of Semiconductor Interfaces

Proceedings of the First International Symposium, Karuizawa, Japan, 8-12 November 1993

Edited by **I. Ohdomari**, **M. Oshima** and **A. Hiraki**

©1994 600 pages Price: Dfl. 325.00 (US$185.75) ISBN 0-444-81889-8

This book focuses exclusively on control of interfacial properties and structures for semiconductor device applications from the point of view of improving and developing novel electrical properties. The following topics are covered: metal-semiconductors, semiconductor hetero-interfaces, characterization, semiconducting new materials, insulator-semiconductor, interfaces in device, control of interface formation, control of interface properties, contact metallization.

A variety of up-to-date research topics such as atomic layer epitaxy, atomic layer passivation, atomic scale characterization including STM and SR techniques, single ion implementation, self-organization crystal growth, in situ measurements for process control and extremely high-spatial resolution analysis techniques, are also included. Furthermore it bridges the macroscopic, mesoscopic, and atomic-scale regimes of semicondutor interfaces, describing the state of the art in forming, controlling and characterizating unique semiconductor interfaces, which will be of practical importance in advanced devices. Intended for both technologists who require an up-to-date assessment of methods for interface formation, processing and characterization, and solid state researchers who desire the latest developments in understanding the basic mechanisms of interface physics, chemistry and electronics, this book will be a welcome addition to the existing literature.

Contents: (*Please contact the publisher for a complete list of contents.*) Preface. Parts 1. Plenary (*2 papers*). 2. Metal/silicon (*8 papers*). 3. Semiconductor hetero-interface (*8 papers*). 4. Characterization (I) (*4 papers*). 5. Semiconducting new materials (*6 papers*). 6. Metal/compound semiconductor (*7 papers*). 7. SiO_2/Si (*6 papers*). 8. Characterization (II) (*4 papers*). 9. Insulator/semiconductor (*8 papers*). 10. Characterization (III) (*6 papers*). 11. Interface in device (*4 papers*). 12. Control of interface formation: Si (*7 papers*). 13. Control of interface properties: Si (*3 papers*). 14. Contact metallization: Si (*2 papers*). 15. Characterization: Si (*5 papers*). 16. Control of interface formation: compound semiconductors (*5 papers*). 17. Control of interface properties: compound semiconductors (*5 papers*). 18. Contact metallization: compound semiconductors (*8 papers*). 19. Characterization: compound semiconductors (*8 papers*). Subject index.

ELSEVIER
An imprint of Elsevier Science

TO ORDER

Contact your regular supplier or:

ELSEVIER SCIENCE B.V.

attn. C. Ryan
P.O. Box 103
1000 AC Amsterdam
The Netherlands
Fax: (+31) 20 5862580

Customers in the USA and Canada:

ELSEVIER SCIENCE INC.

attn. J. Weislogel
P.O. Box 882
Madison Square Station
New York, NY 10159, USA
Fax: (212) 633 3680

No postage will be added to prepaid book orders. Dutch Guilder price(s) quoted applies worldwide US Dollar price(s) quoted may be subject to exchange rate fluctuations. Customers in the European Union should add the appropriate VAT rate applicable in their country to the price(s). In New York State please add applicable sales tax. All prices are subject to change without prior notice.

Resonant Anomalous X-Ray Scattering

Theory and Applications

Edited by **G. Materlik, C.J. Sparks** and **K. Fischer**

©1994 688 pages Price: Dfl. 350.00 (US$200.00) ISBN 0-444-82025-6

The collected articles in this book written by recognized experts in the field explore the theoretical and experimental insights and applications of the rapidly expanding science of x-ray resonant interactions. The variety of papers presented reflects the theoretical and experimental progress made possible with tunable, polarized and highly brilliant synchrotron radiation sources. In a rapidly changing field this book provides a single selected reference source on the present understanding of x-ray resonance scattering and its many applications. A detailed subject index provides easy access to the many topics covered by the authors who list over 1000 references.

Contents: Preface. **Part I: X-Ray Scattering Factors.** X-ray resonance, then and now *(D.H. Templeton)*. New relativistic S-matrix results for scattering-beyond the usual anomalous factors/beyond impulse approximation *(R.H. Pratt, L. Kissel, P.M. Bergstrom, Jr.)*. Experimental determination of the dispersion correction f'(E) to the atomic scattering factor *(B. Lengeler)*. Towards improved form factor tables *(C.T. Chantler)*. Optical constants and scattering factors from reflectivity measurements: 50 eV to 5 keV *(R.L. Blake et al.)*. Resonant x-ray diffraction and polarization analysis at the iron K-edge *(K.D. Finkelstein, M. Hamrick, Q. Shen)*. Electrical quadrupole contributions to x-ray absorption and anomalous scattering *(G. Dräger, W. Czolbe)*. Polarizing x-ray optics and anomalous dispersion in chiral systems *(M. Hart)*. **Part II: Crystal Structures.** X-ray standing waves in noncentrosymmetric crystals and the phase problem in crystallography (B.N. Dev, G. Materlik). Developments in anomalous scattering for structure determination *(J. Karle)*. MAD phasing for macromolecular crystal structures *(W.A. Hendrickson)*. Anomalous dispersion of X-ray scattering from low-z elements *(H.B. Stuhrmann, M.S. Lehmann)*. Powder diffraction studies using anomalous dispersion *(D.E. Cox, A.P. Wilkinson)*. Phase and sign determination from multiple wavelength powder diffraction data using anomalous scattering techniques and synchrotron radiation *(W. Limper, W. Prandl)*. Anisotropy of anomalous scattering in single crystals *(A. Kirfel)*. Computing kinematic diffraction intensities with anisotropic anomalous scatterers - "forbidden" axial reflections in space groups up to orthorhombic symmetry *(W. Morgenroth, A. Kirfel, K. Fischer)*. **Part III: Short-Range Correlations.** Chemical and displacement atomic pair correlations in crystalline solid solutions recovered by resonant (anomalous) x-ray scattering *(G.E. Ice, C.J. Sparks, L.B. Shaffer)*. Structural characterization of compositional and density inhomogeneities by ASAXS *(H.-G. Haubold et al.)*. Anomalous small angle x-ray scattering in materials science *(J.P. Simon, O. Lyon)*. Short- and medium-range order in noncrystalline materials by using anomalous scattering at large angles *(D. Raoux)*. Structural studies of oxide thin films, solutions and quasicrystals by anomalous x-ray scattering method *(E. Matsubara, Y. Waseda)*. Anomalous crystal truncation rod intensity: a chemical and structural probe *(F.J. Walker, E.D. Specht)*. Diffraction anomalous fine structure: unifying x-ray diffraction and x-ray absorption with DAFS *(L.B. Sorensen et al.)*. Anomalous reflectivity methods for determining the density profiles of thin films *(S.K. Sinha et al.)* **Part IV: Resonant Raman Scattering.** Radiative and radiationless resonant Raman scattering *(T. Aberg, B. Crasemann)*. Resonant x-ray Raman scattering from atoms and molecules *(P.L. Cowan)*. Experimental study of non-radiative resonant Raman scattering at the L_3-edge of 4d-transition metals *(W. Drube, A. Lessmann, G. Materlik)*. High resolution near edge x-ray spectroscopy *(K. Hämäläinen et al.)*. **Part V: Magnetic X-Ray Scattering.** Magnetic effects in anomalous dispersion *(M. Blume)*. Resonant magnetic x-ray scattering *(C. Vettier)*. Magnetic form factor measurements using x-rays *(D. Laundy, S.P. Collins)*. X-ray magnetic circular dichroism and its relation to local magnetic structures *(G. Schütz, M. Knülle, H. Ebert)*. First measurement of site-specific normal and magnetic XANES by using a standing wave field *(H. Kawata et al.)* **Part IV: Nuclear Resonant Scattering.** Resonant γ-ray scattering and coherent excitations of nuclei *(J.P. Hannon, G.T. Trammell)*. Nuclear resonant diffraction of synchrotron radiation - on the way from an exotic experiment to established spectroscopy *(E. Gerdau, U. van Bürck)*. Nuclear resonant scattering with conventional sources *(G.V. Smirnov, A.I. Chumakov)*. Suppression of charge scattering in Mössbauer experiments using synchrotron radiation *(U. Bergmann, D.P. Siddons, J.B. Hastings)*. Nuclear resonant scattering using synchtrotron radiation from an x-ray undulator *(S. Kikuta)*. Development of neV scattering spectroscopy using resonant nuclear Bragg scattering *(J.Z. Tischler et al.)*. Guide to some crystallographic symbols and definitions with discussions on short-range correlations *(C.J. Sparks, J.L. Robertson)*. Subject index. Substance index.

TO ORDER

Contact your regular supplier or:

ELSEVIER SCIENCE B.V.

attn. C. Ryan
P.O. Box 103
1000 AC Amsterdam
The Netherlands
Fax: (+31) 20 5862580

Customers in the USA and Canada:

ELSEVIER SCIENCE INC.

attn. J. Weislogel
P.O. Box 945
New York, NY 10159-0945, USA
Fax: (212) 633 3680

No postage will be added to prepaid book orders. US $ book prices are valid only in the USA and Canada. Dutch guilder (Dfl.) price(s) quoted applies worldwide. US Dollar price(s) quoted may be subject to exchange rate fluctuations. Customers in the European Union should add the appropriate VAT rate applicable in their country to the price(s). In New York State please add applicable sales tax. All prices are subject to change without prior notice.

NORTH-HOLLAND

(AN IMPRINT OF ELSEVIER SCIENCE)

Scope of the Journal of Crystal Growth

Experimental and theoretical contributions are invited in the following fields:
- Theory of nucleation and growth, molecular kinetics and transport phenomena, crystallization in viscous media such as polymers and glasses.
- Crystal growth of metals, minerals, semiconductors, magnetics, inorganic, organic and biological substances in bulk or as thin films.
- Apparatus, instrumentation and techniques for crystal growth, and purification methods.
- Characterization of single crystals by physical and chemical methods.

Instructions to Authors

Contributions may be written in English, French or German. They should have an abstract in English. They should be submitted in triplicate to a Member of the Editorial Board or preferably to an appropriate subject Associate Editor. The authors will receive the final answer of acceptance or rejection from the Office of the Principal Editor. The submission of a paper will be taken to imply that the author has satisfied himself that no copyright will thereby be infringed. Upon acceptance of an article by the journal, the author(s) will be asked to transfer copyright of the article to the publisher. This transfer will ensure the widest possible dissemination of information.

Rapid publication: Short manuscripts (up to 5 typewritten pages) which have been entitled "Letter to the Editors" by the author may be published directly, without sending proofs to the author.
Short manuscripts (up to 5 typewritten pages and up to 3 figures and/or tables) which have been entitled "Priority communication" by the author may also be published directly, without sending proofs to the author. These manuscripts should be submitted to D. Elwell.

Manuscripts should be concisely written, stressing the novel aspects of the work. Experimental papers should not be longer the 16 typed (double-spaced, regular size characters) pages, including list of references and figure captions, and 7 figures + tables. For theoretical papers, a maximum of 20 pages and 10 figures + tables will be applied. In any case the number of figures and tables should be kept to the **absolute minimum** needed to effectively present the results of the study. The manuscripts should be typewritten or word-processed with **double spacing and sufficiently large letters.** Failure to observe these guidelines will cause delay in processing the paper and invites its rejection.

All *acronyms* should be spelled out the first time they occur. No acronyms should be used in the title.

Displayed formulae should be numbered and typed.
Vectors will be printed in bold-face italics (heavy, slanting type), and should be indicated by a wavy underlining in the typescript. Otherwise no symbols should be underlined. If necessary, unusual symbols should be explained in pencil in the margin.

Each table should be typed on a separate sheet, and should have a title in addition to its serial number, typed above the table.

Line drawings for the figures should be originals, drawn in black Indian ink and carefully lettered (letter height 3–6 mm). **The lettering as well as the details should have proportionate dimensions** so as not to become illegible or unclear after the usual reduction by the printers; in general, the figures should be designed for a reduction factor of two to three. Glossy prints or xerographic copies of these figures can be accepted only if they are of good quality.

Photographs should be originals, with somewhat more contrast than is desired in the printed version. They should be unmounted unless they form part of a composite figure. Where necessary the top edge should be identified on the back. Figures are in general reduced to the width of one column – the parts that may be cropped should be marked on the back. Photographs should not be stapled to each other.

For information on colour illustrations, please contact publisher.
Original ink drawings and photographs will be returned after publication of the paper.
Each figure should have a number and a caption. The captions should be collected on a separate sheet.

References to other papers should be consecutively numbered in the text: "Woods and Lang [1] have reported that ...", and listed at the end of the typescript as in the following examples:
[1] G.S. Woods and A.R. Lang, J. Crystal Growth 28 (1975) 215.
[2] J.C. Brice, The Growth of Crystals from Liquids (North-Holland, Amsterdam, 1973) ch. 3, p. 55.
[3] D.T.J. Hurle and J.B. Mullin, in: Crystal Growth, Ed. H.S. Peiser (Pergamon, Oxford, 1967) p. 27.

IMPORTANT: When page proofs of the accepted manuscript are made and sent out to authors, this is in order to check that no undetected errors have arisen in the typesetting (or file conversion) process. At the proof stage only printer's errors may be corrected. No changes in, or additions to, the edited manuscript will be accepted.

Page charge and reprints: There will be no page charge. Reprints may be ordered from the publisher (50 reprints will be supplied free of charge). An order form will be sent to contributors together with the proofs.

News or announcements should be submitted through the Principal Editor; a duplicate should be sent directly to Mrs. F.Y. Verploegh Chassé, Elsevier Science B.V., P.O. Box 103, 1000 AC Amsterdam, Netherlands.

Subscriptions and Advertising Orders

Subscriptions should be sent to the Publishers, Elsevier Science B.V., Journals Department, P.O. Box 211, 1000 AE Amsterdam, Netherlands, or to any subscription agent. Subscription price is available upon request. For 1994, 11 volumes have been announced.

Claims for issues not received should be made within six months, following the date of publication. The Publisher expects to supply missing numbers free only when losses have been sustained in transit and when the reserve stock will permit.

Advertising orders and enquiries should be submitted to the Advertising Manager, Elsevier Science B.V., Journals Department, P.O. Box 211, 1000 AE Amsterdam, Netherlands.

JOURNAL OF
CRYSTAL GROWTH

CONTENTS

Author index to volumes 131–140 467

Subject index to volumes 131–140 520

0022-0248(1994)131/140*;1-$